bq40z50-R3

Technical Reference

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Preface

Read this First

This manual discusses the bq40z50-R3 device's modules and peripherals, and how each is used to build a complete battery pack gas gauge and protection solution. See the *bq40z50-R2 1-Series to 4-Series Li-Ion Battery Pack Manager* data sheet (SLUSCS4) for bq40z50-R3 electrical specifications, and the *bq40z50-R2 to bq40z50-R3 Change List* (SLUA874) to see the new bq40z50-R3 features and performance improvements.

Notational Conventions

The following notation is used if SBS commands and data flash values are mentioned within a text block:

- SBS commands: *italics* with parentheses and no breaking spaces; for example, *RemainingCapacity()*
- Data flash: *italics*, **bold**, and breaking spaces; for example, ***Design capacity***
- Register bits and flags: *italics* and brackets; for example, *[TDA]*
- Data flash bits: *italics* and **bold**; for example, ***[LED1]***
- Modes and states: ALL CAPITALS; for example, UNSEALED

The reference format for SBS commands is: SBS:Command Name(Command No.): Manufacturer Access(MA No.)[Flag]; for example:

SBS:Voltage(0x09) or SBS:ManufacturerAccess(0x00): Seal Device(0x0020)

Trademarks

Impedance Track is a trademark of Texas Instruments.
All other trademarks are the property of their respective owners.

Glossary

TI Glossary **—**This glossary lists and explains terms, acronyms, and definitions.

Introduction

The bq40z50-R3 device provides a feature-rich battery management solution for 1-series cell to 4-series cell battery-pack applications. The bq40z50-R3 device has extended capabilities, including:

- Fully Integrated 1-Series, 2-Series, 3-Series, and 4-Series Li-Ion or Li-Polymer Cell Battery Pack Manager and Protection
- Next-Generation Patented Impedance Track™ Technology Accurately Measures Available Charge in Li-Ion and Li-Polymer Batteries
- High-Side N-CH Protection FET Drive
- Integrated Cell Balancing While Charging or At Rest
- Low Power Modes
  - LOW POWER
  - SLEEP
- Full Array of Programmable Protection Features
  - Voltage
  - Current
  - Temperature
  - Charge Timeout
  - CHG/DSG FETs
  - Cell Imbalance
- Sophisticated Charge Algorithms
  - JEITA
  - Advanced Charging Algorithm
- Diagnostic Lifetime Data Monitor
- Black Box Event Recorder
- Supports Two-Wire SMBus v1.1 Interface
- SHA-1 Authentication
- Ultra-Compact Package: 32-Lead QFN

Protections

2.1 Introduction

The bq40z50-R3 provides recoverable protection. When the protection is triggered, charging and/or discharging is disabled. This is indicated by the *OperationStatus()[XCHG]* = 1 when charging is disabled, and/or the *OperationStatus()[XDSG]* = 1 when discharging is disabled. Once the protection is recovered, charging and discharging resume. All protection items can be enabled or disabled under ***Settings:Enabled Protections A***, ***Settings:Enabled Protections B***, ***Settings:Enabled Protections C***, and ***Settings:Enabled Protections D***.

When the protections and permanent fails are triggered, the *BatteryStatus()[TCA][TDA][FD][OCA][OTA]* is set according to the type of safety protections. Section 4.8 provides a summary of the various alarms flags' set conditions.

NOTE: Delay settings with 1-s granularity can have an average trigger delay equal to the delay setting plus 1.5 s.

2.2 Cell Undervoltage Protection

The bq40z50-R3 device can detect cell undervoltage in batteries and protect cells from damage by preventing further discharge.

Status	Condition	Action
Normal	Min cell voltage1..4 > ***CUV:Threshold***	*SafetyAlert()[CUV]* = 0 *BatteryStatus()[TDA]* = 0
Alert	Min cell voltage1..4 ≤ ***CUV:Threshold***	*SafetyAlert()[CUV]* = 1 *BatteryStatus()[TDA]* = 1
Trip	Min cell voltage1..4 ≤ ***CUV:Threshold*** for ***CUV:Delay*** duration	*SafetyAlert()[CUV]* = 0 *SafetyStatus()[CUV]* = 1 *BatteryStatus()[FD]* = 1, *[TDA]* = 0 *OperationStatus()[XDSG]* = 1
Recovery	Condition 1: *SafetyStatus()[CUV]* = 1 AND Min cell voltage1..4 ≥ ***CUV:Recovery*** AND ***Protection Configuration[CUV_RECOV_CHG]*** = 0	*SafetyStatus()[CUV]* = 0 *BatteryStatus()[FD]* = 0, *[TDA]* = 0 *OperationStatus()[XDSG]* = 0
	OR Condition 2: *SafetyStatus()[CUV]* = 1 AND Min cell voltage1..4 ≥ ***CUV:Recovery*** AND ***Protection Configuration[CUV_RECOV_CHG]*** = 1 AND Charging detected (that is, *BatteryStatus()[DSG]* = 0)	

2.3 Cell Undervoltage Compensated Protection

The bq40z50-R3 device can detect cell undervoltage in batteries and protect cells from damage by preventing further discharge. The protection is compensated by the *Current()* × cell resistance1..4.

Status	Condition	Action
Normal	Min cell voltage1..4 – *Current()* × cell resistance > ***CUVC: Threshold***	*SafetyAlert()[CUVC]* = 0 *BatteryStatus()[TDA]* = 0
Alert	Min cell voltage1..4 – *Current()* × cell resistance ≤ ***CUVC: Threshold***	*SafetyAlert()[CUVC]* = 1 *BatteryStatus()[TDA]* = 1

Status	Condition	Action
Trip	Min cell voltage1..4 – *Current()* × cell resistance ≤ ***CUVC: Threshold*** for ***CUVC:Delay*** duration	*SafetyAlert()[CUVC]* = 0 *SafetyStatus()[CUVC]* = 1 *BatteryStatus()[FD]* = 1, *[TDA]* = 0 *OperationStatus()[XDSG]* = 1
Recovery	Condition 1: *SafetyAlert()[CUVC]* = 1 AND Min cell voltage1..4 – *Current()* × cell resistance > ***CUVC: Recovery*** AND ***Protection Configuration[CUV_RECOV_CHG]*** = 0	*SafetyStatus()[CUVC]* = 0 *BatteryStatus()[FD]* = 0, *[TDA]* = 0 *OperationStatus()[XDSG]* = 0
	OR Condition 2: *SafetyAlert()[CUVC]* = 1 AND Min cell voltage1..4 – *Current()* × cell resistance > ***CUVC: Recovery*** AND ***Protection Configuration[CUV_RECOV_CHG]*** = 1 AND Charging detected (that is, *BatteryStatus()[DSG]* = 0)	

2.4 Cell Overvoltage Protection

The bq40z50-R3 device can detect cell overvoltage in batteries and protect cells from damage by preventing further charging.

NOTE: The protection detection threshold may be influenced by the temperature settings of the advanced charging algorithm and the measured temperature. Additionally, this protection feature can be enabled to create a PF by setting the ***[COVL]*** bit in the ***Enabled PF A*** register.

Status	Condition	Action
Normal, *ChargingStatus()[UT] or [LT]* = 1	Max cell voltage1..4 < ***COV:Threshold Low Temp***	*SafetyAlert()[COV]* = 0 *PFAlert()[COVL]* = 0 Decrement COVL counter by one after each ***COV:Counter Dec Delay*** period if COVL counter > 0
Normal, *ChargingStatus()[STL]* = 1	Max cell voltage1..4 < ***COV:Threshold Standard Temp Low***	
Normal, *ChargingStatus()[STH]* = 1	Max cell voltage1..4 < ***COV:Threshold Standard Temp High***	
Normal, *ChargingStatus()[RT]* = 1	Max cell voltage1..4 < ***COV:Threshold Rec Temp***	
Normal, *ChargingStatus()[HT] or [OT]* = 1	Max cell voltage1..4 < ***COV:Threshold High Temp***	
Alert, *ChargingStatus()[UT] or [LT]* = 1	Max cell voltage1..4 ≥ ***COV:Threshold Low Temp***	*SafetyAlert()[COV]* = 1 *BatteryStatus()[TCA]* = 1
Alert, *ChargingStatus()[STL]* = 1	Max cell voltage1..4 ≥ ***COV:Threshold Standard Temp Low***	
Alert, *ChargingStatus()[STH]* = 1	Max cell voltage1..4 ≥ ***COV:Threshold Standard Temp High***	
Alert, *ChargingStatus()[RT]* = 1	Max cell voltage1..4 ≥ ***COV:Threshold Rec Temp***	
Alert, *ChargingStatus()[HT] or [OT]* = 1	Max cell voltage1..4 ≥ ***COV:Threshold High Temp***	
Trip, *ChargingStatus()[UT] or [LT]* = 1	Max cell voltage1..4 ≥ ***COV:Threshold Low Temp*** for ***COV:Delay*** duration	*SafetyAlert()[COV]* = 0 *SafetyStatus()[COV]* = 1 *BatteryStatus()[TCA]* = 0 *OperationStatus()[XCHG]* = 1 Increment COVL counter
Trip, *ChargingStatus()[STL]* = 1	Max cell voltage1..4 ≥ ***COV:Threshold Standard Temp Low*** for ***COV:Delay*** duration	
Trip, *ChargingStatus()[STH]* = 1	Max cell voltage1..4 ≥ ***COV:Threshold Standard Temp High*** for ***COV:Delay*** duration	
Trip, *ChargingStatus()[RT]* = 1	Max cell voltage1..4 ≥ ***COV:Threshold Rec Temp*** for ***COV:Delay*** duration	
Trip, *ChargingStatus()[HT] or [OT]* = 1	Max cell voltage1..4 ≥ ***COV:Threshold High Temp*** for ***COV:Delay*** duration	

Status	Condition	Action
Recovery, *ChargingStatus()[UT] or [LT]* = 1	*SafetyStatus()[COV]* = 1 AND Max cell voltage1..4 ≤ ***COV:Recovery Low Temp***	*SafetyStatus()[COV]* = 0 *BatteryStatus()[TCA]* = 0 *OperationStatus()[XCHG]* = 0
Recovery, *ChargingStatus()[STL]* = 1	*SafetyStatus()[COV]* = 1 AND Max cell voltage1..4 ≤ ***COV:Recovery Standard Temp Low***	
Recovery, *ChargingStatus()[STH]* = 1	*SafetyStatus()[COV]* = 1 AND Max cell voltage1..4 ≤ ***COV:Recovery Standard Temp High***	
Recovery, *ChargingStatus()[RT]* = 1	*SafetyStatus()[COV]* = 1 AND Max cell voltage1..4 ≤ ***COV:Recovery Rec Temp***	
Recovery, *ChargingStatus()[HT] or [OT]* = 1	*SafetyStatus()[COV]* = 1 AND Max cell voltage1..4 ≤ ***COV:Recovery High Temp***	
Latch Alert	COVL counter > 0	*SafetyAlert()[COVL]* = 1 if *EnabledProtections[COVL]* is set. *PFAlert()[COVL]* = 1 if *EnabledPF[COVL]* is set
Latch Trip	COVL counter ≥ COV:Latch limit	*SafetyStatus()[COVL]* = 1 if *EnabledProtections[COVL]* is set *PFStatus()[COVL]* = 1 if *EnabledPF[COVL]* is set. *PFAlert()[COVL]* = 0 *SafetyAlert()[COVL]* = 0 *OperationStatus()[XCHG]* = 1
Latch Reset(***[NR]***=0)	*SafetyStatus()[COVL]* = 1 AND ***DA Configuration[NR]*** = 0 AND Low-high-low transition on $\overline{\text{PRES}}$ pin	*SafetyStatus()[COVL]* = 0 Reset COVL counter. *OperationStatus[XCHG]* = 0 if *SafetyStatus()[COV]* = 0
Latch Reset(***[NR]***=1)	(*SafetyStatus()[COVL]* = 1 AND ***DA Configuration[NR]***=1 for COV:Reset time	*SafetyStatus()[COVL]* = 0 Reset COVL counter. *OperationStatus[XCHG]* = 0 if *SafetyStatus()[COV]* = 0

2.5 Overcurrent in Charge Protection

The bq40z50-R3 device has two independent overcurrent in charge protections that can be set to different current and delay thresholds to accommodate different charging behaviors.

Status	Condition	Action
Normal	*Current()* < ***OCC1:Threshold***	*SafetyAlert()[OCC1]* = 0
Normal	*Current()* < ***OCC2:Threshold***	*SafetyAlert()[OCC2]* = 0
Alert	*Current()* ≥ ***OCC1:Threshold***	*SafetyAlert()[OCC1]* = 1 *BatteryStatus()[TCA]* = 1
Alert	*Current()* ≥ ***OCC2:Threshold***	*SafetyAlert()[OCC2]* = 1 *BatteryStatus()[TCA]* = 1
Trip	*Current()* ≥ ***OCC1:Threshold*** for ***OCC1:Delay*** duration	*SafetyAlert()[OCC1]* = 0 *SafetyStatus()[OCC1]* = 1 *BatteryStatus()[TCA]* = 0 Charging is not allowed. *OperationStatus()[XCHG]* = 1
Trip	*Current()* ≥ ***OCC2:Threshold*** for ***OCC2:Delay*** duration	*SafetyAlert()[OCC2]* = 0 *SafetyStatus()[OCC2]* = 1 *BatteryStatus()[TCA]* = 0 *OperationStatus()[XCHG]* = 1
Recovery	*SafetyStatus()[OCC1]* = 1 AND *Current()* ≤ ***OCC:Recovery Threshold*** for ***OCC:Recovery Delay*** time	*SafetyStatus()[OCC1]* = 0 *BatteryStatus()[TCA]* = 0 *OperationStatus()[XCHG]* = 0
Recovery	*SafetyStatus()[OCC2]* = 1 AND *Current()* ≤ ***OCC:Recovery Threshold*** for ***OCC:Recovery Delay*** time	*SafetyStatus()[OCC2]* = 0 *BatteryStatus()[TCA]* = 0 *OperationStatus()[XCHG]* = 0

2.6 Overcurrent in Discharge Protection

The bq40z50-R3 device has two independent overcurrent in discharge protections that can be set to current and delay thresholds to accommodate different load behaviors. Additionally, this protection feature can be enabled to create a PF by setting the ***[OCDL]*** bit in ***Enabled PF C*** register.

Status	Condition	Action
Normal	*Current()* > ***OCD1:Threshold***	*SafetyAlert()[OCD1]* = 0 *SafetyAlert()[OCDL]* = 0 *PFAlert()[SOCDL]* = 0 Decrement OCDL1 counter by one after each ***OCD:Counter Dec Delay*** period, if OCDL1 counter > 0
Normal	*Current()* > ***OCD2:Threshold***	*SafetyAlert()[OCD2]* = 0 *SafetyAlert()[OCDL]* = 0 *PFAlert()[SOCDL]* = 0 Decrement OCDL2 counter by one after each ***OCD:Counter Dec Delay*** period if OCDL2 counter > 0
Alert	*Current()* ≤ ***OCD1:Threshold***	*SafetyAlert()[OCD1]* = 1 *BatteryStatus()[TDA]* = 1
Alert	*Current()* ≤ ***OCD2:Threshold***	*SafetyAlert()[OCD2]* = 1 *BatteryStatus()[TDA]* = 1
Trip	*Current()* ≤ ***OCD1:Threshold*** for ***OCD1:Delay*** duration	*SafetyAlert()[OCD1]* = 0 *SafetyStatus()[OCD1]* = 1 *BatteryStatus()[TDA]* = 0 *OperationStatus()[XDSG]* = 1 Increment OCDL1 counter
Trip	*Current()* ≤ ***OCD2:Threshold*** for ***OCD2:Delay*** duration	*SafetyAlert()[OCD2]* = 0 *SafetyStatus()[OCD2]* = 1 *BatteryStatus()[TDA]* = 0 *OperationStatus()[XDSG]* = 1 Increment OCDL2 counter
Recovery	*SafetyStatus()[OCD1]* = 1 AND *Current()* ≥ ***OCD:Recovery Threshold*** for ***OCD:Recovery Delay*** time	*SafetyStatus()[OCD1]* = 0 *BatteryStatus()[TDA]* = 0 *OperationStatus()[XDSG]* = 0
Recovery	*SafetyStatus()[OCD2]* = 1 AND *Current()* ≥ ***OCD:Recovery Threshold*** for ***OCD:Recovery Delay*** time	*SafetyStatus()[OCD2]* = 0 *BatteryStatus()[TDA]* = 0 *OperationStatus()[XDSG]* = 0
Recovery	*SafetyStatus()[OCD2]* = 1 AND *Current()* ≥ ***OCD:Recovery Threshold*** for ***OCD:Recovery Delay*** time	*SafetyStatus()[OCD2]*=0 *OperationStatus()[XDSG]*=0 *BatteryStatus()[TDA]* = 0
Latch Alert	OCDL counter > 0	*SafetyAlert()[OCDL]* = 1 if *SafetyEnable[OCDL]* is set. *PFAlert()[SOCDL]* = 1 if *PFEnable()[AOCDL]* is set.
Latch Trip	OCDL counter ≥ ***OCD:Latch limit***	*SafetyStatus()[OCDL]* = 1 if *SafetyEnable[OCDL]* is set. *PFStatus()[SOCDL]* = 1 if *PFEnable()[SCOV]* is set. *SafetyAlert()[OCDL]* = *PFAlert()[SOCDL]* = 0
Latch Reset(***[NR]*** = 0)	*SafetyStatus()[OCDL]* = 1 AND ***DA Configuration[NR]*** = 0 AND Low-high-low transition on $\overline{\text{PRES}}$ pin	*SafetyStatus()[OCDL]* = 0 Reset OCDL counter. OperationStatus[XDSG] = 0 if *SafetyStatus()[OCD1]* = 0 and *SafetyStatus()[OCD2]* = 0
Latch Reset(***[NR]*** = 1)	*SafetyStatus()[OCDL]* = 1 AND ***DA Configuration[NR]*** = 1 for ***OCD:Reset time***	*SafetyStatus()[OCDL]* = 0 Reset OCDL counter. *OperationStatus[XDSG]* = 0 if *SafetyStatus()[OCD1]* = 0 and *SafetyStatus()[OCD2]* = 0

2.7 Hardware-Based Protection

The bq40z50-R3 device has three main hardware-based protections—AOLD, ASCC, and ASCD1,2—with adjustable current and delay time. Setting ***AFE Protection Configuration[RSNS]*** divides the threshold value in half. The ***Threshold*** settings are in mV; therefore, the actual current that triggers the protection is based on the R_{SENSE} used in the schematic design.

In addition, setting the ***AFE Protection Configuration[SCDDx2]*** bit provides an option to double all of the SCD1,2 delay times for maximum flexibility towards the application's needs.

For details on how to configure the AFE hardware protection, refer to the tables in *Appendix A*.

All of the hardware-based protections provide a Trip/Latch Alert/Recovery protection. The latch feature stops the FETs from toggling on and off continuously on a persistent faulty condition.

In general, when a fault is detected after the ***Delay*** time, the CHG and DSG FETs will be disabled (Trip stage), and an internal fault counter will be incremented (Alert stage). Since both FETs are off, the current will drop to 0 mA. After ***Recovery*** time, the CHG and DSG FETs will be turned on again (Recovery stage).

If the alert is caused by a current spike, the fault count will be decremented after ***Counter Dec Delay*** time. If this is a persistent faulty condition, the device will enter the Trip stage after ***Delay*** time, and repeat the Trip/Latch Alert/Recovery cycle. The internal fault counter is incremented every time the device goes through the Trip/Latch Alert/Recovery cycle. Once the internal fault counter hits the ***Latch Limit***, the protection enters a Latch stage and the fault will only be cleared through the Latch Reset condition.

The Trip/Latch Alert/Recovery/Latch stages are documented in each of the following hardware-based protection sections.

The recovery condition for the removable pack (***[NR]*** = 0) is based on the transition on the $\overline{\text{PRES}}$ pin, while the recovery condition for the embedded pack (***[NR]*** = 1) is based on the ***Reset*** time.

2.7.1 Overload in Discharge Protection

The bq40z50-R3 device has a hardware-based overload in discharge protection with adjustable current and delay time. Additionally, this protection feature can be enabled to create a PF by setting the ***[AOLDL]*** bit in the ***Enabled PF B*** register.

Status	Condition	Action
Normal	*Current()* > (***OLD Threshold[3:0]***/R_{SENSE})	*SafetyAlert()[AOLDL]* = 0, if OLDL counter = 0 *PFAlert()[SAOLDL]* = 0 Decrement AOLDL counter by one after each ***OLD:Counter Dec Delay*** period, if AOLDL counter > 0
Trip	*Current()* ≤ (***OLD Threshold[3:0]***/R_{SENSE}) for ***OLD Threshold[7:4]*** duration	*SafetyStatus()[AOLD]* = 1 *OperationStatus()[XDSG]* = 1 Increment AOLDL counter
Recovery	*SafetyStatus()[AOLD]* = 1 for ***OLD:Recovery*** time	*SafetyStatus()[AOLD]* = 0 *OperationStatus()[XDSG]* = 0 if *SafetyStatus()[AOLDL]* = 0.
Latch Alert	AOLDL counter > 0	*SafetyAlert()[AOLDL]* = 1 *PFAlert()[SAOLDL]* = 1, if *PFEnable()[SAOLDL]* is set.
Latch Trip	AOLDL counter ≥ ***OLD:Latch Limit***	*SafetyAlert()[AOLDL]* = 0 *SafetyStatus()[AOLDL]* = 1 *OperationStatus()[XDSG]* = 1 *PFAlert()[AOLDL]* = 0 *PFStatus()[AOLDL]* = 1, if *PFEnable()[AOLDL]* is set.
Latch Reset (***[NR]*** = 0)	*SafetyStatus()[AOLDL]* = 1 AND ***DA Configuration[NR]*** = 0 AND Low-high-low transition on $\overline{\text{PRES}}$ pin	*SafetyStatus()[AOLDL]* = 0 *OperationStatus()[XDSG]* = 0 if *SafetyStatus()[AOLD]* = 0.
Latch Reset (***[NR]*** = 1)	*SafetyStatus()[AOLDL]* = 1 AND ***DA Configuration[NR]*** = 1 for ***OLD:Reset*** time	*SafetyStatus()[AOLDL]* = 0 *OperationStatus()[XDSG]* = 0 if *SafetyStatus()[AOLD]* = 0.

2.7.2 Short Circuit in Charge Protection

The bq40z50-R3 device has a hardware-based short circuit in charge protection with adjustable current and delay time. Additionally, this protection feature can be enabled to create a PF by setting the ***[ASCCL]*** bit in the ***Enabled PF B*** register.

Status	Condition	Action
Normal	*Current()* < (***SCC Threshold[2:0]***/R_{SENSE})	*SafetyAlert()[ASCCL]* = 0, if ASCCL counter = 0 *PFAlert()[ASCCL]* = 0 Decrement ASCCL counter by one after each ***SCC:Counter Dec Delay*** period, if ASCCL counter > 0
Trip	*Current()* ≥ (***SCC Threshold[2:0]***/R_{SENSE}) for ***SCC Threshold[7:4]*** duration	*SafetyStatus()[ASCC]* = 1 *BatteryStatus()[TCA]* = 1 *OperationStatus()[XCHG]* = 1 increment ASCCL counter
Recovery	*SafetyStatus()[ASCC]* = 1 for ***SCC:Recovery*** time	*SafetyStatus()[ASCC]* = 0 *BatteryStatus()[TCA]* = 0 *OperationStatus()[XCHG]* = 0 if *SafetyStatus()[ASCCL]* = 0.
Latch Alert	ASCCL counter > 0	*SafetyAlert()[ASCCL]* = 1 *PFAlert()[ASCCL]* = 1, if *PFEnable()[ASCCL]* is set.
Latch Trip	ASCCL counter ≥ ***SCC:Latch Limit***	*SafetyAlert()[ASCCL]* = 0 *SafetyStatus()[ASCCL]* = 1 *OperationStatus()[XCHG]* = 1 *PFAlert()[ASCCL]* = 0 *PFStatus()[ASCCL]* = 1, if *PFEnable()[ASCCL]* is set.

Status	Condition	Action
Latch Reset (***[NR]*** = 0)	*SafetyStatus()[ASCCL]* = 1 AND ***DA Configuration[NR]*** = 0 AND Low-high-low transition on PRES pin	*SafetyStatus()[ASCCL]* = 0 *OperationStatus()[XCHG]* = 0 if *SafetyStatus()[ASCC]* = 0
Latch Reset (***[NR]*** = 1)	*SafetyStatus()[ASCCL]* = 1 AND ***DA Configuration[NR]*** = 1 for ***SCC:Reset*** time	*SafetyStatus()[ASCCL]* = 0 *OperationStatus()[XCHG]* = 0 if *SafetyStatus()[ASCC]* = 0

2.7.3 Short Circuit in Discharge Protection

The bq40z50-R3 device has a hardware-based short circuit in discharge protection with adjustable current and delay time. Additionally, this protection feature can be enabled to create a PF by setting the ***[ASCDL]*** bit in the ***Enabled PF B*** register.

Status	Condition	Action
Normal	*Current()* > (***SCD1 Threshold[2:0]***/R_{SENSE}) AND *Current()* > (***SCD2 Threshold[2:0]***/R_{SENSE})	*SafetyAlert()[ASCDL]* = 0 if ASCDL counter = 0 *PFAlert()[ASCDL]* = 0 Decrement ASCDL counter by one after each ***SCD:Counter Dec Delay*** period, if ASCDL counter > 0
Trip	*Current()* ≤ (***SCD1 Threshold[2:0]***/R_{SENSE}) for ***SCD1 Threshold[7:4]*** duration OR *Current()* ≤ (***SCD2 Threshold[2:0]***/R_{SENSE}) for ***SCD2 Threshold[7:4]*** duration	*SafetyStatus()[ASCD]* = 1 *OperationStatus()[XDSG]* = 1 Increment ASCDL counter
Recovery	*SafetyStatus()[ASCD]* = 1 for ***SCD:Recovery*** time	*SafetyStatus()[ASCD]* = 0 *OperationStatus()[XDSG]* = 0 if *SafetyStatus()[ASCDL]* = 0.
Latch Alert	ASCDL counter > 0	*SafetyAlert()[ASCDL]* = 1 *PFAlert()[ASCDL]* = 1, if *PFEnable()[ASCDL]* is set.
Latch Trip	SCD counter ≥ ***SCD:Latch Limit***	*SafetyStatus()[ASCD]* = 0 *SafetyStatus()[ASCDL]* = 1 *OperationStatus()[XDSG]* = 1 *SafetyAlert()[ASCDL]* = 0 *PFAlert()[ASCDL]* = 0 *PFStatus()[ASCDL]* = 1, if *PFEnable()[ASCDL]* is set.
Latch Reset (***[NR]*** = 0)	*SafetyStatus()[ASCDL]* = 1 AND ***DA Configuration[NR]*** = 0 AND Low-high-low transition on PRES pin	*SafetyStatus()[ASCDL]* = 0 *OperationStatus()[XDSG]* = 0 if *SafetyStatus()[ASCD]* = 0
Latch Reset (***[NR]*** = 1)	*SafetyStatus()[ASCCL]* = 1 AND ***DA Configuration[NR]*** = 1 for ***SCD:Reset*** time	*SafetyStatus()[ASCDL]* = 0 *OperationStatus()[XDSG]* = 0 if *SafetyStatus()[ASCD]* = 0

2.8 Temperature Protections

The bq40z50-R3 device provides overtemperature and undertemperature protections, based on cell and FET temperature measurements. The cell temperature-based protections are further divided into CHARGE and DISCHARGE conditions. This section describes in detail each of the protection functions.

The device supports four external thermistors and one internal temperature sensor for measuring temperature. Unused temperature sensors must be disabled by clearing the corresponding flag in ***Settings:Temperature Enable[TS4][TS3][TS2][TS1][TSInt]***.

Each of the temperature sensors can be used as a source for cell or FET temperature measurement. Setting the corresponding flag in ***Settings:Temperature Mode[TS4 Mode][TS3 Mode][TS2 Mode][TS1 Mode][TSInt Mode]*** configures the sensor to measure FET temperature. Clearing the corresponding flag configures the sensor to measure cell temperature.

The average temperature among the sensors set for FET measurement is used when ***Settings:DA Configuration[FTEMP]*** is set. The maximum temperature is used when ***[FTEMP]*** is cleared.

Under cell temperature protections use the minimum cell temperature sensor. Over cell temperature protections use the maximum cell temperature sensor.

The *Temperature()* command returns the cell temperature measurement. Setting ***Settings:DA Configuration[CTEMP1][CTEMP0]*** to 1, 0 uses the lowest cell temperature sensor. Setting ***[CTEMP1][CTEMP0]*** to 0, 1 uses the average of the sensors. A setting of 0, 0 uses the maximum cell temperature sensor.

ManufacturerBlockAccess() command *DAStatus2()* returns all the temperature measurements.

The ***Settings:SBS Configuration[SMB_CELL_TEMP]*** bit enables the host to override the value used for cell temperature with the MAC command *WriteTemp()*. On power up, if ***[SMB_CELL_TEMP]*** = 1, the temperature register is written to 293 K (20°C). When this feature is used, the temperature must be written in 0.1 K. This feature is helpful on PCBs that do not have the area or height to include thermistors, but do have a host that is capable of using its own onboard measurement of cell temperature.

The cell-based overtemperature and undertemperature safety provides protections in CHARGE and DISCHARGE conditions. The battery pack is in CHARGE mode when *Current()* > ***Chg Current Threshold*** and *BatteryStatus()[DSG]* = 0. The overtemperature and undertemperature in CHARGE protections are active in this mode. *BatteryStatus()[DSG]* is set to 1 in a non-CHARGE mode condition, which includes RELAX and DISCHARGE modes. The overtemperature and undertemperature in discharge protections are active in these two modes. See Section 6.3 for detailed descriptions of the gas gauge modes.

2.9 Overtemperature in Charge Protection

The bq40z50-R3 device has an overtemperature protection for cells under charge.

Status	Condition	Action
Normal	Max Cell Temp TS1..4 < ***OTC:Threshold*** OR not charging	*SafetyAlert()[OTC]* = 0
Alert	Max Cell Temp TS1..4 ≥ ***OTC:Threshold*** AND charging	*SafetyAlert()[OTC]* = 1 *BatteryStatus()[TCA]* = 1
Trip	Max Cell Temp TS1..4 ≥ ***OTC:Threshold*** AND Charging for ***OTC:Delay*** duration	*SafetyAlert()[OTC]* = 0 *SafetyStatus()[OTC]* = 1 *BatteryStatus()[OTA]* = 1 *BatteryStatus()[TCA]* = 0 *OperationStatus()[XCHG]* = 1 if ***FET Options[OTFET]*** = 1
Recovery	*SafetyStatus()[OTC]* AND Max Cell Temp TS1..4 ≤ ***OTC:Recovery***	*SafetyStatus()[OTC]* = 0 *BatteryStatus()[OTA]* = 0 *BatteryStatus()[TCA]* = 0 *OperationStatus()[XCHG]* = 0

2.10 Overtemperature in Discharge Protection

The bq40z50-R3 device has an overtemperature protection for cells in the DISCHARGE or RELAX state (that is, non-charging state with *BatteryStatus[DSG]* = 1).

Status	Condition	Action
Normal	Max Cell Temp TS1..4 < ***OTD:Threshold*** OR charging	*SafetyAlert()[OTD]* = 0
Alert	Max Cell Temp TS1..4 ≥ ***OTD:Threshold*** AND Not charging (that is, *BatteryStatus[DSG]* = 1)	*SafetyAlert()[OTD]* = 1 *BatteryStatus()[TDA]* = 1
Trip	Max Cell Temp TS1..4 ≥ ***OTD:Threshold*** AND Not charging (that is, *BatteryStatus[DSG]* = 1) for ***OTD:Delay*** duration	*SafetyAlert()[OTD]* = 0 *SafetyStatus()[OTD]* = 1 *BatteryStatus()[OTA]* = 1 *OperationStatus()[XDSG]* = 1 if ***FET Options[OTFET]*** = 1 *BatteryStatus()[TDA]* = 0
Recovery	*SafetyStatus()[OTD]* AND Max Cell Temp TS1..4 ≤ ***OTD:Recovery***	*SafetyStatus()[OTD]* = 0 *BatteryStatus()[OTA]* = 0 *OperationStatus()[XDSG]* = 0 *BatteryStatus()[TDA]* = 0

2.11 Overtemperature FET Protection

The bq40z50-R3 device has an overtemperature protection to limit the FET temperature.

Status	Condition	Action
Normal	FET Temperature in *DAStatus2()* < ***OTF:Threshold***	*SafetyAlert()[OTF]* = 0
Alert	FET Temperature in *DAStatus2()* ≥ ***OTF:Threshold***	*SafetyAlert()[OTF]* = 1 *BatteryStatus()[TDA]* = 1, *[TCA]* = 1
Trip	FET Temperature in *DAStatus2()* ≥ ***OTF:Threshold*** for ***OTF:Delay*** duration	*SafetyAlert()[OTF]* = 0 *SafetyStatus()[OTF]* = 1 *BatteryStatus()[OTA]* = 1 *BatteryStatus()[TDA]* = 0, *[TCA]* = 0 *OperationStatus()[XCHG][XDSG]* = 1,1 if ***FET Options[OTFET]*** = 1
Recovery	*SafetyStatus()[OTF]* AND FET Temperature in *DAStatus2()* ≤ ***OTF:Recovery***	*SafetyStatus()[OTF* = 0 *BatteryStatus()[OTA]* = 0 *BatteryStatus()[TDA]* = 0, *[TCA]* = 0 *OperationStatus()[XCHG][XDSG]* = 0,0

2.12 Undertemperature in Charge Protection

The bq40z50-R3 device has an undertemperature protection for cells in charge direction.

Status	Condition	Action
Normal	Min Cell Temp TS1..4 > ***UTC:Threshold*** OR not charging	*SafetyAlert()[UTC]* = 0
Alert	Min Cell Temp TS1..4 ≤ ***UTC:Threshold*** AND charging	*SafetyAlert()[UTC]* = 1 *BatteryStatus()[TCA]* = 1
Trip	Min Cell Temp TS1..4 ≤ ***UTC:Threshold*** AND Charging for ***UTC:Delay*** duration	*SafetyAlert()[UTC]* = 0 *SafetyStatus()[UTC]* = 1 *OperationStatus()[XCHG]* = 1
Recovery	*SafetyStatus()[UTC]* AND Min Cell Temp TS1..4 ≥ ***UTC:Recovery***	*SafetyStatus()[UTC]* = 0 *OperationStatus()[XCHG]* = 0

2.13 Undertemperature in Discharge Protection

The bq40z50-R3 device has an undertemperature protection for cells in the DISCHARGE or RELAX state (that is, non-charging state with *BatteryStatus[DSG]* = 1).

Status	Condition	Action
Normal	Min Cell Temp TS1..4 > ***UTD:Threshold*** OR charging	*SafetyAlert()[UTD]* = 0
Alert	Min Cell Temp TS1..4 ≤ ***UTD:Threshold*** AND Not charging (that is, *BatteryStatus[DSG]* = 1)	*SafetyAlert()[UTD]* = 1
Trip	Min Cell Temp TS1..4 ≤ ***UTD:Threshold*** AND Not charging (that is, *BatteryStatus[DSG]* = 1) for ***UTD:Delay*** duration	*SafetyAlert()[UTD]* = 0 *SafetyStatus()[UTD]* = 1 *OperationStatus()[XDSG]* = 1 *BatteryStatus()[TDA]* = 1
Recovery	*SafetyStatus()[UTD]* AND Min Cell Temp TS1..4 ≥ ***UTD:Recovery***	*SafetyStatus()[UTD]* = 0 *OperationStatus()[XDSG]* = 0

2.14 SBS Host Watchdog Protection

The bq40z50-R3 device can check periodic communication over SBS and prevent usage of the battery pack if no valid communication is detected.

Status	Condition	Action
Trip	No valid SBS transaction for ***HWD:Delay*** duration	*SafetyStatus()[HWD]* = 1 *OperationStatus()[XCHG]* = 1
Recovery	Valid SBS transaction detected	*SafetyStatus()[HWD]* = 0 *OperationStatus()[XCHG]* = 0

2.15 Precharge Timeout Protection

The bq40z50-R3 device can measure the precharge time and stop charging if it exceeds the adjustable period.

Status	Condition	Action
Enable	*Current()* > ***PTO:Charge Threshold*** AND *ChargingStatus()[PV]* = 1	Start PTO timer *SafetyAlert()[PTOS]* = 0
Suspend or Recovery	*Current()* < ***PTO:Suspend Threshold***	Stop PTO timer *SafetyAlert()[PTOS]* = 1 *BatteryStatus()[TCA]* = 1
Trip	PTO timer > ***PTO:Delay***	Stop PTO timer *SafetyStatus()[PTO]* = 1 *OperationStatus()[XCHG]* = 1
Reset	*SafetyStatus()[PTO]* = 1 AND ***DA Configuration[NR]*** = 0 AND (Discharge by an amount of ***PTO:Reset*** OR low-high-low transition on $\overline{\text{PRES}}$)	Stop and reset PTO timer *SafetyAlert()[PTOS]* = 0 *SafetyStatus()[PTO]* = 0 *BatteryStatus()[TCA]* = 0 *OperationStatus()[XCHG]* = 0
Reset	*SafetyStatus()[PTO]* = 1 AND ***DA Configuration[NR]*** = 1 AND Discharge by an amount of ***PTO:Reset***	Stop and reset PTO timer *SafetyAlert()[PTOS]* = 0 *SafetyStatus()[PTO]* = 0 *BatteryStatus()[TCA]* = 0 *OperationStatus()[XCHG]* = 0

2.16 Fast Charge Timeout Protection

The bq40z50-R3 device can measure the charge time and stop charging if it exceeds the adjustable period.

Status	Condition	Action
Enable	*Current()* > ***CTO:Charge Threshold*** AND (*ChargingStatus()[LV]* = 1 OR *ChargingStatus()[MV]* = 1 OR *ChargingStatus()[HV]* = 1)	Start CTO timer *SafetyAlert()[CTOS]* = 0
Suspend or Recovery	*Current()* < ***CTO:Suspend Threshold***	Stop CTO timer *SafetyAlert()[CTOS]* = 1
Trip	CTO time > ***CTO:Delay***	Stop CTO timer *SafetyStatus()[CTO]* = 1 *OperationStatus()[XCHG]* = 1
Reset	*SafetyStatus()[CTO]* = 1 AND ***DA Configuration[NR]*** = 0 AND (Discharge by an amount of ***CTO:Reset*** OR low-high-low transition on $\overline{\text{PRES}}$)	Stop and reset CTO timer *SafetyAlert()[CTOS]* = 0 *SafetyStatus()[CTO]* = 0 *OperationStatus()[XCHG]* = 0
Reset	*SafetyStatus()[CTO]* = 1 AND ***DA Configuration[NR]*** = 1 AND Discharge by an amount of ***CTO:Reset***	Stop and reset CTO timer *SafetyAlert()[CTOS]* = 0 *SafetyStatus()[CTO]* = 0 *OperationStatus()[XCHG]* = 0

2.17 Overcharge Protection

The bq40z50-R3 device can prevent continued charging if the pack is charged in excess over *FullChargeCapacity()*.

Status	Condition	Action
Normal	*RelativeStateOfCharge()* < 100%	*SafetyAlert()[OC]* = 0
Alert	*RelativeStateOfCharge()* ≥ 100% AND Internal charge counter > 0	*SafetyAlert()[OC]* = 1 *BatteryStatus()[TCA]* = 1
Trip	*RelativeStateOfCharge()* ≥ 100% AND Internal charge counter ≥ ***OC:Threshold***	*SafetyAlert()[OC]* = 0 *SafetyStatus()[OC]* = 1 *BatteryStatus()[TCA]* = 0, *[OCA]* = 1 if the device is in the CHARGE state (that is, *BatteryStatus[DSG]* = 0). *OperationStatus()[XCHG]* = 1
Recovery, ***DA Configuration[NR]*** = 0	*SafetyStatus()[OC]* = 1 AND Low-high-low transition on $\overline{\text{PRES}}$ pin	*SafetyStatus()[OC]* = 0 *BatteryStatus()[TCA]* = 0, *[OCA]* = 0 *OperationStatus()[XCHG]* = 0

Status	Condition	Action
Recovery ***DA Configuration[NR]*** = 1	Condition 1: *SafetyStatus()[OC]* = 1 AND discharge of ***Recovery***	*SafetyStatus()[OC]* = 0 *BatteryStatus()[TCA]* = 0, *[OCA]* = 0 *OperationStatus()[XCHG]* = 0
	OR Condition 2: *SafetyStatus()[OC]* = 1 AND ***DA Configuration[NR]*** = 1 AND *RelativeStateOfCharge()* < ***OC:RSOC Recovery***	

2.18 OverCharging Voltage Protection

The bq40z50-R3 device can stop charging if it measures a difference between the requested *ChargingVoltage()* and the delivered voltage from the charger. This feature only operates when the device is in CHARGE mode.

NOTE: *ChargingVoltage()* will be set to 0 mV when the protection is tripped. The *ChargingVoltage()* for the recovery is the intended or targeted charging voltage, not the 0 mV that was set due to the trip of protection.

Status	Condition	Action
Normal	PACK voltage in *DAStatus1()* < *ChargingVoltage()* + ***CHGV:Threshold*** × Number of series cells	*SafetyAlert()[CHGV]* = 0
Alert	PACK voltage in *DAStatus1()* ≥ *ChargingVoltage()* + ***CHGV:Threshold*** × Number of series cells	*SafetyAlert()[CHGV]* = 1 *BatteryStatus()[TCA]* = 1
Trip	PACK voltage in *DAStatus1()* ≥ *ChargingVoltage()* + ***CHGV:Threshold*** × Number of series cells for ***CHGV:Delay*** period	*SafetyAlert()[CHGV]* = 0 *SafetyStatus()[CHGV]* = 1 *BatteryStatus()[TCA]* = 0 *OperationStatus()[XCHG]* = 1
Recovery	*SafetyStatus()[CHGV]* = 1 AND PACK voltage in *DAStatus1()* ≤ intended *ChargingVoltage()* + ***CHGV Recovery*** × Number of series cells	*SafetyStatus()[CHGV]* = 0 *BatteryStatus()[TCA]* = 0 *OperationStatus()[XCHG]* = 0

2.19 OverCharging Current Protection

The bq40z50-R3 device can stop charging if it measures a difference between the requested *ChargingCurrent()* and the delivered current from the charger. This protection is designed to recover by a discharge event; therefore, ***CHGC:Recovery*** should be set to a negative value in data flash.

Status	Condition	Action
Normal	*Current()* < *ChargingCurrent()* + ***CHGC:Threshold***	*SafetyAlert()[CHGC]* = 0
Alert	*Current()* ≥ *ChargingCurrent()* + ***CHGC:Threshold***	*SafetyAlert()[CHGC]* = 1 *BatteryStatus()[TCA]* = 1
Trip	*Current()* ≥ *ChargingCurrent()* + ***CHGC:Threshold*** for ***CHGC:Delay*** period	*SafetyAlert()[CHGC]* = 0 *SafetyStatus()[CHGC]* = 1 *BatteryStatus()[TCA]* = 0 *OperationStatus()[XCHG]* = 1
Recovery	*SafetyStatus()[CHGC]* = 1 AND *Current()* ≤ ***CHGC:Recovery Threshold*** for ***CHGC:Recovery Delay*** time	*SafetyStatus()[CHGC]* = 0 *BatteryStatus()[TCA]* = 0 *OperationStatus()[XCHG]* = 0

2.20 OverPrecharging Current Protection

The bq40z50-R3 device can stop charging if it measures a difference between the requested *ChargingCurrent()* and the delivered current from the charger during precharge. This protection is designed to recover by a discharge event; therefore, ***PCHGC:Recovery*** should be set to a negative value in data flash.

Status	Condition	Action
Normal	*Current()* < *ChargingCurrent()* + ***PCHGC:Threshold*** AND *ChargingStatus()[PV]* = 1	*SafetyAlert()[PCHGC]* = 0
Alert	*Current()* ≥ *ChargingCurrent()* + ***PCHGC:Threshold*** AND *ChargingStatus()[PV]* = 1	*SafetyAlert()[PCHGC]* = 1 *BatteryStatus()[TCA]* = 1
Trip	*Current()* ≥ *ChargingCurrent()* + ***PCHGC:Threshold*** for ***PCHGC:Delay*** period AND *ChargingStatus()[PV]* = 1	*SafetyAlert()[PCHGC]* = 0 *SafetyStatus()[PCHGC]* = 1 If charging, *BatteryStatus()[TCA]* = 0 *OperationStatus()[XCHG]* = 1
Recovery	*SafetyStatus()[PCHGC]* = 1 AND *Current()* ≤ ***PCHGC:Recovery Threshold*** for ***PCHGC:Recovery Delay*** time	*SafetyStatus()[PCHGC]* = 0 *BatteryStatus()[TCA]* = 0 *OperationStatus()[XCHG]* = 0

Permanent Fail

3.1 Introduction

The bq40z50-R3 device can permanently disable the use of the battery pack in case of a significant failure. The permanent failure checks, except for IFC and DFW, can be enabled or disabled individually by setting the appropriate bit in ***Settings:Enabled PF A***, ***Settings:Enabled PF B***, ***Settings:Enabled PF C***, and ***Settings:Enabled PF D***. All permanent failure checks, except for IFC and DFW, are disabled until *ManufacturingStatus()[PF]* is set. When any *PFStatus()* bit is set, the device enters PERMANENT FAIL mode and the following actions are taken in sequence:

1. Precharge, charge, and discharge FETs are turned off.
2. *OperationStatus()[PF]* = 1, *[XCHG]* = 1, *[XDSG]* = 1
3. The following SBS data is changed: *BatteryStatus()[TCA]* = 1, *BatteryStatus()[TDA]* = 1, *ChargingCurrent()* = 0, and *ChargingVoltage()* = 0.
4. A backup of the internal AFE hardware registers are written to data flash: ***AFE Interrupt Status***, ***AFE FET Status***, ***AFE RXIN***, ***AFE Latch Status***, ***AFE Interrupt Enable***, ***AFE FET Control***, ***AFE RXIEN***, ***AFE RLOUT***, ***AFE RHOUT***, ***AFE RHINT***, ***AFE Cell Balance***, ***AFE AD/CC Control***, ***AFE ADC Mux***, ***AFE LED Output***, ***AFE State Control***, ***AFE LED/Wake Control***, ***AFE Protection Control***, ***AFE OCD***, ***AFE SCC***, ***AFE SCD1***, and ***AFE SCD2***.
5. The black box data of the last three *SafetyStatus()* changes leading up to PF with the time difference is written into the black box data flash along with the 1st *PFStatus()* value.
6. The following SBS values are preserved in data flash for failure analysis:
   - *SafetyAlert()*
   - *SafetyStatus()*
   - *PFAlert()*
   - *PFStatus()*
   - *OperationStatus()*
   - *ChargingStatus()*
   - *GaugingStatus()*
   - Voltages in *DAStatus1()*
   - *Current()*
   - TSINT, TS1, TS2, TS3, and TS4 from *DAStatus2()*
   - Cell DOD0 and passed charge
7. Data flash writing is disabled (except to store subsequent *PFStatus()* flags).
8. The FUSE pin is driven high if configured for specific failures and *Voltage()* is above ***Min Blow Fuse Voltage*** or there is a CHG FET (CFETF) or DSG FET (DFETF) failure. The FUSE pin will remain asserted until the ***Fuse Blow Timeout*** expires.

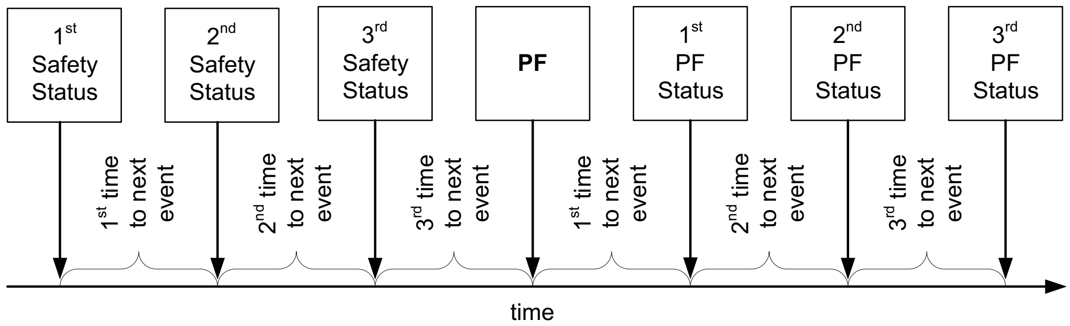
NOTE: If ***[PACK_FUSE]*** = 0, *Voltage()* is used to check for ***Min Blow Fuse Voltage***, indicating the fuse is connected to the BAT side.

If ***[PACK_FUSE]*** = 1 (that is, the fuse is connected to the PACK side and is required to have a charger connected in order to blow the fuse), then the PACK voltage is used to check for ***Min Blow Fuse Voltage*** threshold.

While the device is in PERMANENT FAIL mode, any new *SafetyAlert()*, *SafetyStatus()*, *PFAlert()*, and *PFStatus()* flags that are set are added to the permanent fail log. Any new *PFStatus()* flags that occur during PERMANENT FAIL mode can trigger the FUSE pin. In addition, new *PFStatus()* flags are recorded in the Black Box Recorder 2nd and 3rd PF Status entries.

3.1.1 Black Box Recorder

The Black Box Recorder maintains the last three updates of *SafetyStatus()* in memory. When entering PERMANENT FAIL mode, this information is written to data flash together with the first three updates of *PFStatus()* after the PF event.



NOTE: This information is useful in failure analysis, and can provide a full recording of the events and conditions leading up to the permanent failure.

If there were less than three safety events before PF, then some information will be left blank.

3.1.2 GPIO Control During Permanent Failure

The device includes a feature to toggle a GPIO pin if the FUSE signal is asserted. It is enabled by setting ***[GPIO_PF]*** and clearing ***[LED_EN]***. After the FUSE signal is asserted in PERMANENT FAILURE mode, the LEDCNTLC pin will be driven high for ***GPIO_Timeout*** seconds. If ***GPIO_Timeout*** = 0, the pin is held high indefinitely.

3.2 Safety Cell Undervoltage Permanent Fail

The device can permanently disable the battery in the case of significant undervoltage in any of the cells.

Status	Condition	Action
Normal	Min cell voltage1..4 > ***SUV:Threshold***	*PFAlert()[SUV]* = 0 *BatteryStatus()[TDA]* = 0
Alert	Min cell voltage1..4 ≤ ***SUV:Threshold***	*PFAlert()[SUV]* = 1 *BatteryStatus()[TDA]* = 1
Trip	Min cell voltage1..4 ≤ ***SUV:Threshold*** for ***SUV:Delay*** duration	*PFAlert()[SUV]* = 0 *PFStatus()[SUV]* = 1 *BatteryStatus()[FD]* = 1

3.2.1 SUV Check Option

When ***Protection Configuration[SUV_MODE]*** is set, the SUV PF check only applies when the gauge wakes up from shutdown. The CHG and DSG FETs are disabled for the duration of the test (***SUV:Delay***) to prevent an applied charge voltage from masking a copper deposition condition.

3.3 Safety Cell Overvoltage Permanent Fail

The bq40z50-R3 device can permanently disable the battery in the case of significant overvoltage in any of the cells.

Status	Condition	Action
Normal	Max cell voltage1..4 < ***SOV:Threshold***	*PFAlert()[SOV]* = 0
Alert	Max cell voltage1..4 ≥ ***SOV:Threshold***	*PFAlert()[SOV]* = 1 *BatteryStatus()[TCA]* = 1
Trip	Max cell voltage1..4 ≥ ***SOV:Threshold*** for ***SOV:Delay*** duration	*PFAlert()[SOV]* = 0 *PFStatus()[SOV]* = 1

3.4 Safety Overcurrent in Charge Permanent Fail

The bq40z50-R3 device can permanently disable the battery in the case of significant overcurrent in the CHARGE state.

Status	Condition	Action
Normal	*Current()* < ***SOCC:Threshold***	*PFAlert()[SOCC]* = 0
Alert	*Current()* ≥ ***SOCC:Threshold***	*PFAlert()[SOCC]* = 1 *BatteryStatus()[TCA]* = 1
Trip	*Current()* ≥ ***SOCC:Threshold*** for ***SOCC:Delay*** duration	*PFAlert()[SOCC]* = 1 *PFStatus()[SOCC]* = 1

3.5 Safety Overcurrent in Discharge Permanent Fail

The bq40z50-R3 device can permanently disable the battery in the case of significant overcurrent in the DISCHARGE or RELAX state.

Status	Condition	Action
Normal	*Current()* > ***SOCD:Threshold***	*PFAlert()[SOCD]* = 0
Alert	*Current()* ≤ ***SOCD:Threshold***	*PFAlert()[SOCD]* = 1 *BatteryStatus()[TDA]* = 1
Trip	*Current()* ≤ ***SOCD:Threshold*** for ***SOCD:Delay*** duration	*PFAlert()[SOCD]* = 1 *PFStatus()[SOCD]* = 1

3.6 Safety Overtemperature Cell Permanent Fail

The bq40z50-R3 device can permanently disable the battery pack in case of significant overtemperature of the cells detected using the external TS1..4 temperature sensor(s), which are configured to report as cell temperature, *Temperature()*. For ***Safety Overtemperature Cell Permanent Fail***, the temperature sensor with the highest temperature is used.

Status	Condition	Action
Normal	All *CellVoltageN()* < ***SOT:Threshold***	*PFAlert()[SOT]* = 0
Alert	A *CellVoltageN()* ≥ ***SOT:Threshold***	*PFAlert()[SOT]* = 1 *BatteryStatus()[OTA]* = 0
Trip	A *CellVoltageN()* ≥ ***SOT:Threshold*** for ***SOT:Delay*** duration	*PFAlert()[SOT]* = 0 *PFStatus()[SOT]* = 1 *BatteryStatus()[OTA]* = 1

3.7 Safety Overtemperature FET Permanent Fail

The bq40z50-R3 device can permanently disable the battery pack in case of significant overtemperature on the power FET. The temperature sensor(s) can be configured to report as FET temperature in *DAStatus2()* by setting the corresponding flag in ***Temperature Mode*** and ***DA Configuration[FTEMP]***.

Status	Condition	Action
Normal	FET Temperature in *DAStatus2()* < ***SOTF:Threshold***	*PFAlert()[SOTF]* = 0
Alert	FET Temperature in *DAStatus2()* ≥ ***SOTF:Threshold***	*PFAlert()[SOTF]* = 1 *BatteryStatus()[OTA]* = 0

Status	Condition	Action
Trip	FET Temperature in *DAStatus2()* ≥ ***SOTF:Threshold*** for ***SOTF:Delay*** duration	*PFAlert()[SOTF]* = 0 *PFStatus()[SOTF]* = 1 *BatteryStatus()[OTA]* = 1

3.8 QMax Imbalance Permanent Fail

The bq40z50-R3 device can permanently disable the battery pack in case the capacity of one of the cells is much lower than the others.

Status	Condition	Action
Normal	***[Max(QMax Cell 1..4) – Min(QMax1..4)]/Qmax Pack*** × 100 < ***QIM:Delta Threshold***	*PFAlert()[QIM]* = 0
Alert	***[Max(QMax Cell 1..4) – Min(QMax1..4)]/Qmax Pack*** × 100 > ***QIM:Delta Threshold***	*PFAlert()[QIM]* = 1
Trip	***[Max(QMax Cell 1..4) – Min(QMax1..4)]/Qmax Pack*** × 100 ≥ ***QIM:Delta Threshold*** for number of ***QIM:Delay***[(1)] updates	*PFAlert()[QIM]* = 0 *PFStatus()[QIM]* = 1

(1) The delay for this check is counted each time ***QMax Cycle Count*** is updated.

3.9 Cell Balancing Permanent Fail

The bq40z50-R3 device can permanently disable the battery pack in case one of the cells in the stack is cell-balanced much more than the others.

Status	Condition	Action
Normal	∆(***CB Time Cell 1..4***) < ***CB:Delta Threshold***	*PFAlert()[CB]* = 0
Alert	∆(***CB Time Cell 1..4***) ≥ ***CB:Delta Threshold***	*PFAlert()[CB]* = 1
Trip	∆(***CB Time Cell 1..4***) ≥ ***CB:Delta Threshold*** for ***CB:Delay***[(1)] cycles	*PFAlert()[CB]* = 0 *PFStatus()[CB]* = 1 *BatteryStatus()[TCA]* = 1 *BatteryStatus()[TDA]* = 1
Trip	Max (***CB Time Cell 1..4***) ≥ ***CB:Max Threshold***	*PFAlert()[CB]* = 0 *PFStatus()[CB]* = 1

(1) The delay for this check is counted each time ***QMax Cycle Count*** is updated.

3.10 Impedance Permanent Fail

The bq40z50-R3 device can permanently disable the battery pack in case the impedance of one of the cells is much higher than the others.

NOTE: ***Reference Grid*** is configurable from 0 (resistance at fully charged cell) to 14 (resistance at fully discharged cell). The default setting of ***Reference Grid*** = 4 is a good typical value to use because it is close to the average in the range of 20% to 100% SOC. ***Design Resistance*** is automatically calculated and updated during the learning cycle and is part of the golden image).

This check is only performed when the gauge updates the ***Ra*** data for the ***Reference Grid*** directly. If a selected grid point is typically being scaled rather than directly updated by the gauge (for example, grid point 0 or grid point 14), this check is effectively disabled. It is recommended to use the default ***Design Resistance*** setting.

Status	Condition	Action
Normal	Δ(***Cell 1..4 R_a*** at ***IT Cfg:Reference Grid***) < (***IMP:Delta Threshold*** × ***IT Cfg:Design Resistance***)	*PFAlert()[IMP]* = 0
Alert	Δ(***Cell 1..4 R_a*** at ***IT Cfg:Reference Grid***) ≥ (***IMP:Delta Threshold*** × ***IT Cfg:Design Resistance***)	*PFAlert()[IMP]* = 1
Trip	Δ(***Cell 1..4 R_a*** at ***IT Cfg:Reference Grid***) ≥ (***IMP:Delta Threshold*** × ***IT Cfg:Design Resistance***) for ***IMP:Ra Update Counts***	*PFAlert()[IMP]* = 0 *PFStatus()[IMP]* = 1 *BatteryStatus()[TCA]* = 1 *BatteryStatus()[TDA]* = 1
Trip	Δ(***Cell 1..4 R_a*** at ***IT Cfg:Reference Grid***) ≥ (***IMP:Max Threshold*** × ***IT Cfg:Design Resistance***)	*PFAlert()[IMP]* = 0 *PFStatus()[IMP]* = 1

3.11 Capacity Degradation Permanent Fail

The bq40z50-R3 device can permanently disable the battery pack in case the capacity of the battery is degraded below a threshold.

Status	Condition	Action
Normal	QMax pack > ***CD:Threshold***	*PFAlert()[CD]* = 0
Alert	QMax pack ≤ ***CD:Threshold***	*PFAlert()[CD]* = 1
Trip	QMax pack ≤ ***CD:Threshold*** for ***CD:Delay***(1) cycles	*PFAlert()[CD]* = 0 *PFStatus()[CD]* = 1

(1) The delay for this check is counted each time ***QMax Cycle Count*** is updated.

3.12 Voltage Imbalance At Rest Permanent Fail

The bq40z50-R3 device can permanently disable the battery pack in case of a voltage difference between the cells in a stack while at rest.

Status	Condition	Action
Normal	Max cell voltage1..4 < ***VIMR:Check Voltage*** OR |*Current()*| > ***VIMR:Check Current*** OR Max cell voltage1..4 – Min cell voltage1..4 < ***VIMR:Delta Threshold***	*PFAlert()[VIMR]* = 0
Alert	(Max cell voltage1..4 ≥ ***VIMR:Check Voltage*** AND |*Current()*| < ***VIMR:Check Current)*** for ***VIMR:Duration*** AND Max cell voltage1..4 – Min cell voltage1..4 ≥ ***VIMR:Delta Threshold***	*PFAlert()[VIMR]* = 1
Trip	(Max cell voltage1..4 ≥ ***VIMR:Check Voltage*** AND |*Current()*| < ***VIMR:Check Current***) for ***VIMR:Duration*** AND Max cell voltage1..4 – Min cell voltage1..4 ≥ ***VIMR:Delta Threshold*** for ***VIMR:Delta Delay***	*PFAlert()[VIMR]* = 0 *PFStatus()[VIMR]* = 1

3.13 Voltage Imbalance Active Permanent Fail

The bq40z50-R3 device can permanently disable the battery pack in case of a voltage difference between the cells in a stack while active.

Status	Condition	Action
Normal	Max cell voltage1..4 < ***VIMA:Check Voltage*** OR *Current()* < ***VIMA:Check Current*** OR Max cell voltage1..4 – Min cell voltage1..4 < ***VIMA:Delta Threshold***	*PFAlert()[VIMA]* = 0
Alert	Max Cell voltage ≥ ***VIMA:Check Voltage*** AND *Current()* > ***VIMA:Check Current*** AND Max cell voltage1..4 – Min cell voltage1..4 ≥ ***VIMA:Delta Threshold***	*PFAlert()[VIMA]* = 1

Status	Condition	Action
Trip	(Max cell voltage1..4 ≥ ***VIMA:Check Voltage*** AND *Current()* > ***VIMA:Check Current*** AND Max cell voltage1..4 – Min cell voltage1..4 ≥ ***VIMA:Delta Threshold)*** for ***VIMA:Delay***	*PFAlert()[VIMA]* = 0 *PFStatus()[VIMA]* = 1

3.14 Charge FET Permanent Fail

The bq40z50-R3 device can permanently disable the battery pack in case the charge FET is not working properly.

Status	Condition	Action
Normal	CHG FET off AND *Current()* < ***CFET:OFF Threshold***	*PFAlert()[CFETF]* = 0
Alert	CHG FET off AND *Current()* ≥ ***CFET:OFF Threshold***	*PFAlert()[CFETF]* = 1
Trip	CHG FET off AND *Current()* ≥ ***CFET:OFF Threshold*** for ***CFET:OFF Delay*** duration	*PFAlert()[CFETF]* = 0 *PFStatus()[CFETF]* = 1

3.15 Discharge FET Permanent Fail

The bq40z50-R3 device can permanently disable the battery pack in case the discharge FET is not working properly.

Status	Condition	Action
Normal	DSG FET off AND *Current()* > ***DFET:OFF Threshold***	*PFAlert()[DFETF]* = 0
Alert	DSG FET off AND *Current()* ≤ ***DFET:OFF Threshold***	*PFAlert()[DFETF]* = 1
Trip	DSG FET off AND *Current()* ≤ ***DFET:OFF Threshold*** for ***DFET:OFF Delay*** duration	*PFAlert()[DFETF]* = 0 *PFStatus()[DFETF]* = 1

3.16 Chemical Fuse Permanent Fail

The bq40z50-R3 device can detect a non-working fuse. It cannot disable the battery pack permanently, but can record this event for analysis.

Status	Condition	Action
Normal	FUSE pin = high AND |*Current()*| < ***FUSE:Threshold***	*PFAlert()[FUSE]* = 0
Alert	FUSE pin = high AND |*Current()*| ≥ ***FUSE:Threshold***	*PFAlert()[FUSE]* = 1
Trip	FUSE pin = high AND |*Current()*| ≥ ***FUSE:Threshold*** for ***FUSE:Delay*** duration	*PFAlert()[FUSE]* = 0 *PFStatus()[FUSE]* = 1

3.17 AFE Register Permanent Fail

The bq40z50-R3 device compares the AFE hardware register periodically with a RAM backup and corrects any errors. If any errors are found during the check, the device increments the AFE register fail counter. If the comparison fails too many times, the device disables the pack permanently.

Status	Condition	Action
Normal	AFE register fail counter = 0	*PFAlert()[AFER]* = 0 Compare AFE register and RAM backup every ***AFER:Compare Period***
Alert	AFE register fail counter > 0	*PFAlert()[AFER]* = 1 Decrement AFE register fail counter by one after each ***AFER:Delay Period*** Compare AFE register and RAM backup every ***AFER:Compare Period***
Trip	AFE register fail counter ≥ ***AFER:Threshold***	*PFAlert()[AFER]* = 0 *PFStatus()[AFER]* = 1

3.18 AFE Communication Permanent Fail

The bq40z50-R3 device monitors the internal communication to the AFE hardware and increments the AFE read/write fail counter on any communication error. If the read or write fails exceed a limit within a configurable timeframe, the device disables the pack permanently.

Status	Condition	Action
Normal	AFE read/write fail counter = 0	*PFAlert()[AFEC]* = 0
Alert	AFE read/write fail counter > 0	*PFAlert()[AFEC]* = 1 Decrement AFE read/write fail counter by one after each ***AFEC:Delay Period***
Trip	Read and Write Fail counter ≥ ***AFEC:Threshold***	*PFAlert()[AFEC]* = 0 *PFStatus()[AFEC]* = 1

3.19 PTC Permanent Fail

The bq40z50-R3 device can detect overtemperature using a positive temperature coefficient (PTC) resistor connected to the PTC pin. This protection also works in SHUTDOWN mode.

If the device detects a PTC pin high state, the CHG and DSG FETs are turned off, and the pack is disabled permanently. For manufacturer testing, the fault state can be reset by a full power cycle of the device.

This is a hardware controlled feature. To enable this feature, the PTCEN pin should be tied to BAT. To disable this feature, connect the PTCEN pin to ground.

Status	Condition	Action
Normal	Reset AFE and PTC pin = high	*PFStatus()[PTC]* = 0
Trip	PTC pin = low	*PFStatus()[PTC]* = 1 FUSE = high *BatteryStatus()[TCA]* = 1 *BatteryStatus()[TDA]* = 1

3.20 Second Level Protection Permanent Fail

The bq40z50-R3 device can detect an external trigger of the chemical fuse by an external protection circuit such as a 2nd-level protector by monitoring the FUSE pin state.

If the device detects a FUSE pin high state, the CHG and DSG FETs are turned off.

Clearing ***Enabled PF C[2LVL]*** does not prevent the second-level protector from triggering and blowing the fuse: Clearing ***Enabled PF C[2LVL]*** only prevents the gauge from detecting the FUSE state.

Status	Condition	Action
Normal	Reset AFE and FUSE pin = low AND No FUSE trigger by firmware	*PFAlert()[2LVL]* = 0
Alert	FUSE pin = high AND No FUSE trigger by firmware	*PFAlert()[2LVL]* = 1 Reset AFE FUSE bit
Trip	FUSE pin high for ***2LVL:Delay*** period AND No FUSE trigger by firmware	*PFAlert()[2LVL]* = 0 *PFStatus()[2LVL]* = 1

3.21 Instruction Flash (IF) Checksum Permanent Fail

The bq40z50-R3 device can permanently disable the battery if it detects a difference between the stored and calculated IF checksum following a device reset.

Status	Condition	Action
Normal	The stored and calculated IF checksum matches.	—
Trip	The stored and calculated IF checksum after a reset does not match.	*PFStatus()[IFC]* = 1

3.22 Data Flash (DF) Permanent Fail

The bq40z50-R3 device can permanently disable the battery in case a data flash write fails.

NOTE: A DF write failure causes the gauge to disable further DF writes.

Status	Condition	Action
Normal	The data flash write is successful.	—
Trip	The data flash write is not successful.	*PFStatus()[DFW]* = 1

3.23 Open Thermistor Permanent Fail (TS1, TS2, TS3, TS4)

The bq40z50-R3 device can permanently disable the battery if it detects an open thermistor on TS1, TS2, TS3, or TS4. The state of TS1..4 and the internal temperature sensor is available in *DAStatus2()*.

Status	Condition	Action
Normal, TS1	TS1 Temperature > ***Open Thermistor:Threshold*** OR Internal Temperature ≤ TS1 Temperature + ***Cell Delta*** if ***Temperature Mode[TS1 Mode]*** = 0 OR Internal Temperature ≤ TS1 Temperature + ***FET Delta*** if ***Temperature Mode[TS1 Mode]*** = 1	*PFAlert()[TS1]* = 0
Normal, TS2	TS2 Temperature > ***Open Thermistor:Threshold*** OR Internal Temperature ≤ TS2 Temperature + ***Cell Delta*** if ***Temperature Mode[TS2 Mode]*** = 0 OR Internal Temperature ≤ TS2 Temperature + ***FET Delta*** if ***Temperature Mode[TS2 Mode] = 1***	*PFAlert()[TS2]* = 0
Normal, TS3	TS3 Temperature > ***Open Thermistor:Threshold*** OR Internal Temperature ≤ TS3 Temperature + ***Cell Delta*** if ***Temperature Mode[TS3 Mode]*** = 0 OR Internal Temperature ≤ TS3 Temperature + ***FET Delta*** if ***Temperature Mode[TS3 Mode] = 1***	*PFAlert()[TS3]* = 0
Normal, TS4	TS4 Temperature > ***Open Thermistor:Threshold*** OR Internal Temperature ≤ TS4 Temperature + ***Cell Delta*** if ***Temperature Mode[TS4 Mode]*** = 0 OR Internal Temperature ≤ TS4 Temperature + ***FET Delta*** if ***Temperature Mode[TS4 Mode] = 1***	*PFAlert()[TS4]* = 0
Alert, TS1	Condition 1: TS1 Temperature ≤ ***Open Thermistor:Threshold*** AND Internal Temperature > TS1 Temperature + ***Cell Delta*** if ***Temperature Mode[TS1 Mode]*** = 0	*PFAlert()[TS1]* = 1
	OR Condition 2: TS1 Temperature ≤ ***Open Thermistor:Threshold*** AND Internal Temperature > TS1 Temperature + ***FET Delta*** if ***Temperature Mode[TS1 Mode]*** = 1	

Status	Condition	Action
Alert, TS2	Condition 1: TS2 Temperature ≤ ***Open Thermistor:Threshold*** AND Internal Temperature > TS2 Temperature + ***Cell Delta*** if ***Temperature Mode[TS2 Mode]*** = 0	*PFAlert()[TS1]* = 1
	OR Condition 2: TS2 Temperature ≤ ***Open Thermistor:Threshold*** AND Internal Temperature > TS2 Temperature + ***FET Delta*** if ***Temperature Mode[TS2 Mode]*** = 1	
Alert, TS3	Condition 1: TS3 Temperature ≤ ***Open Thermistor:Threshold*** AND Internal Temperature > TS3 Temperature + ***Cell Delta*** if ***Temperature Mode[TS3 Mode]*** = 0	*PFAlert()[TS1]* = 1
	OR Condition 2: TS3 Temperature ≤ ***Open Thermistor:Threshold*** AND Internal Temperature > TS3 Temperature + ***FET Delta*** if ***Temperature Mode[TS3 Mode]*** = 1	
Alert, TS4	Condition 1: TS4 Temperature ≤ ***Open Thermistor:Threshold*** AND Internal Temperature > TS4 Temperature + ***Cell Delta*** if ***Temperature Mode[TS4 Mode]*** = 0	*PFAlert()[TS1]* = 1
	OR Condition 2: TS4 Temperature ≤ ***Open Thermistor:Threshold*** AND Internal Temperature > TS4 Temperature + ***FET Delta*** if ***Temperature Mode[TS4 Mode]*** = 1	
Trip, TS1	Condition 1: TS1 Temperature ≤ ***Open Thermistor:Threshold*** AND Internal Temperature > TS1 Temperature + ***Cell Delta*** for ***Open Thermistor:Delay*** duration if ***Temperature Mode[TS1 Mode]*** = 0	*PFAlert()[TS1]* = 0 *PFStatus()[TS1]* = 1
	OR Condition 2: TS1 Temperature ≤ ***Open Thermistor:Threshold*** AND Internal Temperature > TS1 Temperature + ***FET Delta*** for ***OpenThermistor:Delay*** duration if ***Temperature Mode[TS1 Mode]*** = 1	
Trip, TS2	Condition 1: TS2 Temperature ≤ ***Open Thermistor:Threshold*** AND Internal Temperature > TS2 Temperature + ***Cell Delta*** for ***Open Thermistor:Delay*** duration if ***Temperature Mode[TS2 Mode] = 0***	*PFAlert()[TS2]* = 0 *PFStatus()[TS2]* = 1
	OR Condition 2: TS2 Temperature ≤ ***Open Thermistor:Threshold*** AND Internal Temperature > TS2 Temperature + ***FET Delta*** for ***OpenThermistor:Delay*** duration if ***Temperature Mode[TS2 Mode]*** = 1	
Trip, TS3	Condition 1: TS3 Temperature ≤ ***Open Thermistor:Threshold*** AND Internal Temperature > TS3 Temperature + ***Cell Delta*** for ***Open Thermistor:Delay*** duration if ***Temperature Mode[TS3 Mode]*** = 0	*PFAlert()[TS3]* = 0 *PFStatus()[TS3]* = 1
	OR Condition 2: TS3 Temperature ≤ ***Open Thermistor:Threshold*** AND Internal Temperature > TS3 Temperature + ***FET Delta*** for ***OpenThermistor:Delay*** duration if ***Temperature Mode[TS3 Mode]*** = 1	
Trip, TS4	Condition 1: TS4 Temperature ≤ ***Open Thermistor:Threshold*** AND Internal Temperature > TS4 Temperature + ***Cell Delta*** for ***Open Thermistor:Delay*** duration if ***Temperature Mode[TS4 Mode]*** = 0	*PFAlert()[TS4]* = 0 *PFStatus()[TS4]* = 1
	OR Condition 2: TS4 Temperature ≤ ***Open Thermistor:Threshold*** AND Internal Temperature > TS4 Temperature + ***FET Delta*** for ***OpenThermistor:Delay*** duration if ***Temperature Mode[TS4 Mode]*** = 1	

3.24 Cell Overvoltage Latch Permanent Failure

The bq40z50-R3 device can permanently disable the battery in the case of repeated cell overvoltage events. *PFAlert()[COVL]* and *PFStatus()[COVL]* use the same logic and data flash settings as *SafetyAlert()[COVL]* and *SafetyStatus()[COVL]* with the exception of there being no recovery mechanism. It is recommended to not have both *PFStatus()[COVL]* and *SafetyStatus()[COVL]* enabled at the same time.

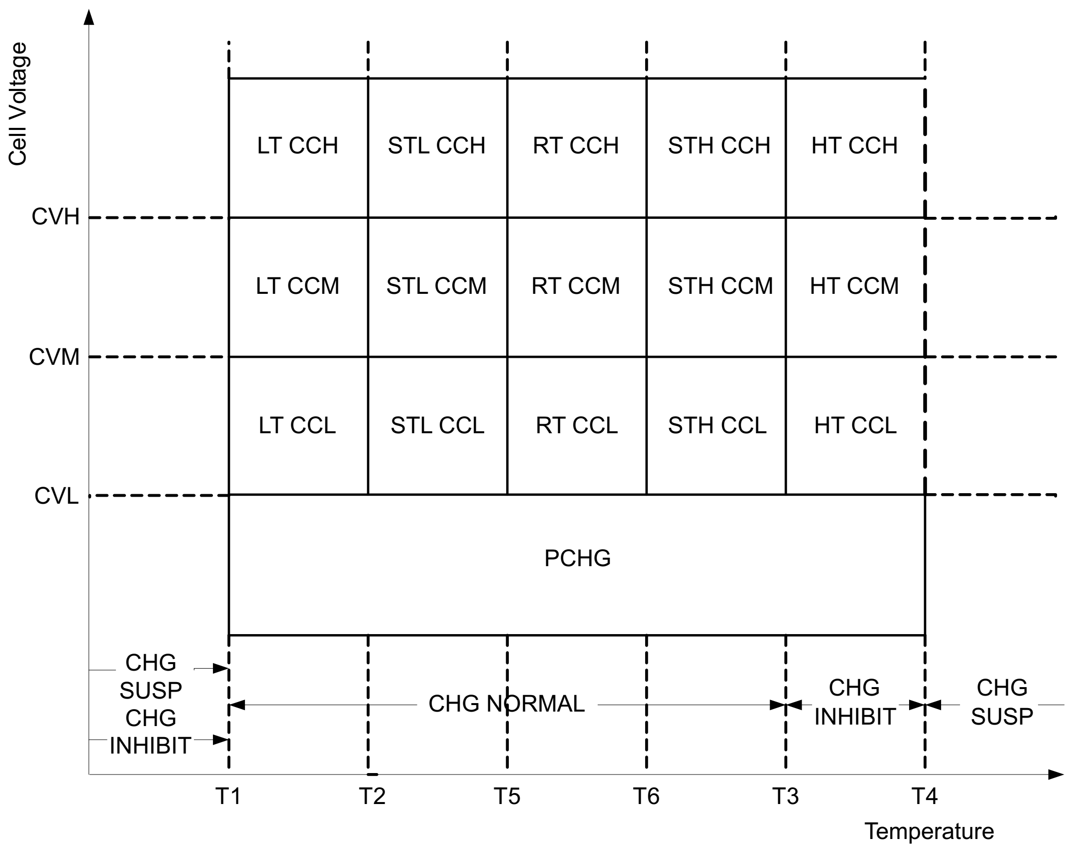
3.25 Manual Permanent Failure

The bq40z50-R3 device can permanently disable the battery upon receipt of a two-word MAC sequence. The two-word key is programmable via *ManufacturerAccess()* 0x0035 security keys. Both keys must be sent within 4 s of each other for *[PFFORCE]* to activate.

Advanced Charge Algorithm

4.1 Introduction

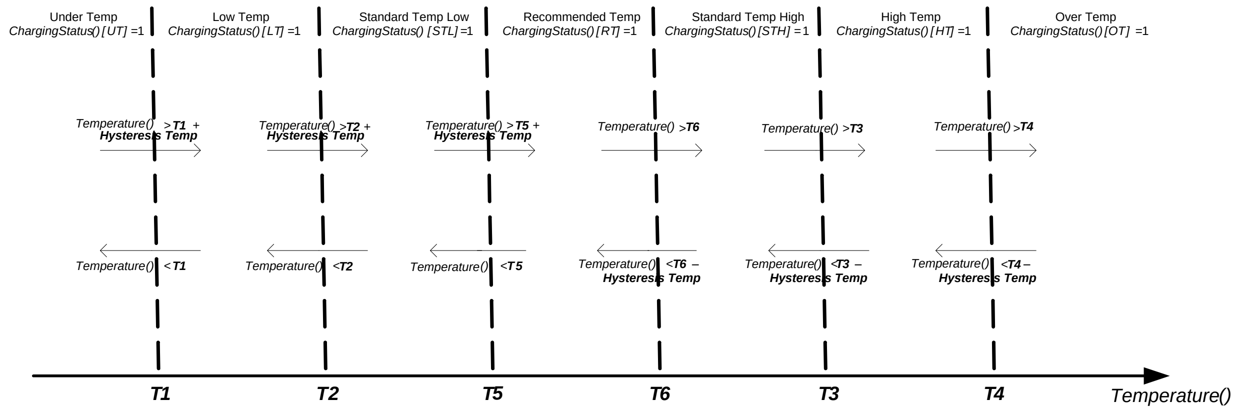
The bq40z50-R3 device can change the values of *ChargingVoltage()* and *ChargingCurrent()* based on *Temperature()* and cell voltage1..4 or *RelativeStateofCharge()*. Its flexible charging algorithm is JEITA compatible and can also meet other specific cell manufacturer charge requirements. The *ChargingStatus()* register shows the state of the charging algorithm.



4.2 Charge Temperature Ranges

The measured temperature is segmented into several temperature ranges. The charging algorithm adjusts *ChargingCurrent()* and *ChargingVoltage()* according to the temperature range. The temperature ranges set in data flash should adhere to the following format:

T1 ≤ ***T2*** ≤ ***T5*** ≤ ***T6*** ≤ ***T3*** ≤ ***T4***.

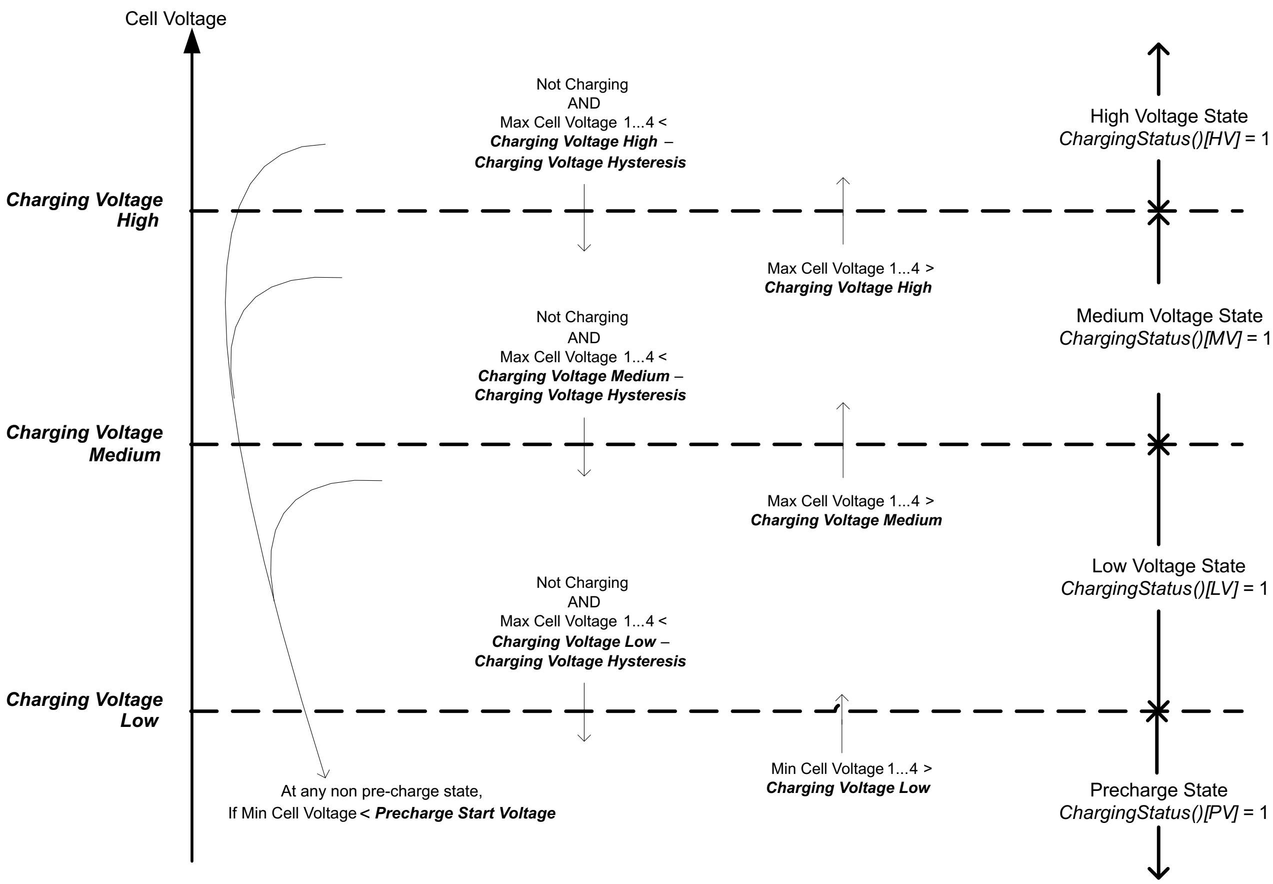


4.3 Voltage Range

The measured cell voltage is segmented into several voltage ranges. The charging algorithm adjusts *ChargingCurrent()* according to the temperature and voltage range. The voltage ranges set in data flash need to adhere to the following format:

Charging Voltage Low ≤ Charging Voltage Med ≤ Charging Voltage High ≤ × Temp Charging:Voltage

where × is standard or recommended. Depending on the specific charging profile, the ***Low Temp Charging:Voltage*** and ***High Temp Charging:Voltage*** settings do not necessarily have the highest setting values.



4.3.1 *RelativeStateofCharge()* Range

If ***[SOC_CHARGE]*** in ***Charging Configuration*** is set, then the voltage threshold control, as described in Section 4.3, is replaced with the *RelativeStateOfCharge()* control.

With this method, the following changes in control transitions occur:

a. [LV] state and *RelativeStateOfCharge()* > ***Charging SOC Mid***; move to [MV].
b. [MV] state and *RelativeStateOfCharge()* > ***Charging SOC High***; move to [HV].
c. [MV] state [DSG] = 1, and *RelativeStateOfCharge()* < ***Charging SOC Mid*** – ***SOC Hysteresis***; move to [LV].
d. [HV] state [DSG] = 1, and *RelativeStateOfCharge()* < ***Charging SOC High*** – ***Charging SOC Hysteresis***; move to [MV].

Table 4-1. *RelativeStateofCharge()* Range

Class	Subclass	Name	Type	Min Value	Max Value	Default Value	Unit
Advanced Charge Algorithm	SOC Range	Charging SOC Mid	U1	0	100	50	%
Advanced Charge Algorithm	SOC Range	Charging SOC High	U1	0	100	75	%
Advanced Charge Algorithm	SOC Range	Charging SOC Hysteresis	U1	0	100	1	%

4.4 Charging Current

The *ChargingCurrent()* value changes depending on the detected temperature and voltage per the charging algorithm.

The ***Charging Configuration[CRATE]*** flag provides an option to adjust the *ChargingCurrent()* based on *FullChargeCapacity()/DesignCapacity()*.

For example, with ***[CRATE]*** = 1, if *FullChargeCapacity()*/*DesignCapacity()* = 90% and ***Rec Temp Charging: Current Med*** is active per the charging algorithm, then *ChargeCurrent()* = ***Rec Temp Charging: Current Med*** × 90%.

NOTE: Table priority is top to bottom.

Temp Range	Voltage Range	Condition	Action
Any	Any	*OperationStatus()[XCHG]* = 1	*ChargingCurrent()* = 0
UT or OT	Any	—	*ChargingCurrent()* = 0
Any	PV	—	*ChargingCurrent()* = ***Pre-Charging:Current***
Any	LV, MV, or HV	*ChargingStatus()[MCHG]* = 1	*ChargingCurrent()* = ***Maintenance Charging:Current***
LT	LV	—	*ChargingCurrent()* = ***Low Temp Charging:Current Low***
	MV	—	*ChargingCurrent()* = ***Low Temp Charging:Current Med***
	HV	—	*ChargingCurrent()* = ***Low Temp Charging:Current High***
STL	LV	—	*ChargingCurrent()* = ***Standard Temp Low Charging:Current Low***
	MV	—	*ChargingCurrent()* = ***Standard Temp Low Charging:Current Med***
	HV	—	*ChargingCurrent()* = ***Standard Temp Low Charging:Current High***

Temp Range	Voltage Range	Condition	Action
STH	LV	—	*ChargingCurrent()* = ***Standard Temp High Charging:Current Low***
	MV	—	*ChargingCurrent()* = ***Standard Temp High Charging:Current Med***
	HV	—	*ChargingCurrent()* = ***Standard Temp High Charging:Current High***
RT	LV	—	*ChargingCurrent()* = ***Rec Temp Charging:Current Low***
	MV	—	*ChargingCurrent()* = ***Rec Temp Charging:Current Med***
	HV	—	*ChargingCurrent()* = ***Rec Temp Charging:Current High***
HT	LV	—	*ChargingCurrent()* = ***High Temp Charging:Current Low***
	MV	—	*ChargingCurrent()* = ***High Temp Charging:Current Med***
	HV	—	*ChargingCurrent()* = ***High Temp Charging:Current High***

4.5 Charging Voltage

ChargingVoltage() is dependent on cell temperature per the charge algorithm. If cell temperature reduces *ChargingVoltage()* below the stack voltage, it can be held unchanged while *ChargingCurrent()* is held at 0 by setting ***[HIBAT_CHG]***. This action continues until the desired *ChargingVoltage()* is above the stack voltage.

NOTE: Table priority is top to bottom.

Temp Range	Condition	Action
Any	*OperationStatus()[XCHG]* = 1	*ChargingVoltage()* = 0
UT or OT	—	*ChargingVoltage()* = 0
LT	—	*ChargingVoltage()* = ***Low Temp Charging:Voltage*** × (***DA Configuration[CC1:CC0]*** + 1)
STL	—	*ChargingVoltage()* = ***STL:Voltage*** × (***DA Configuration[CC1:CC0]*** + 1)
STH	—	*ChargingVoltage()* = ***STH:Voltage*** × (***DA Configuration[CC1:CC0]*** + 1)
RT	—	*ChargingVoltage()* = ***Rec Temp Charging:Voltage*** × (***DA Configuration[CC1:CC0]*** + 1)
HT	—	*ChargingVoltage()* = ***High Temp Charging:Voltage*** × (***DA Configuration[CC1:CC0]*** + 1)

4.6 Valid Charge Termination

The charge termination condition must be met to enable valid charge termination. The bq40z50-R3 device has the following actions at charge termination, based on the flags settings:

- If ***SBS Gauging Configuration[CSYNC]*** = 1, *RemainingCapacity()* = *FullChargeCapacity()*.
- If ***SBS Gauging Configuration[RSOCL]*** = 1, *RelativeStateOfCharge()* and *RemainingCapacity()* are held at 99% until charge termination occurs. Only on entering charge termination is 100% displayed.
- If ***SBS Gauging Configuration[RSOCL]*** = 0, *RelativeStateOfCharge()* and *RemainingCapacity()* are not held at 99% until charge termination occurs. Fractions of % greater than 99% are rounded up to display 100%.

Status	Condition	Action
Charging	*GaugingStatus()[DSG]* = 0	Charge Algorithm active
Valid Charge Termination	All of the following conditions must occur for two consecutive 40-s periods: Charging (that is, *BatteryStatus[DSG]* = 0) AND *AverageCurrent()* < ***Charge Term Taper Current*** AND Max cell voltage1..4 + ***Charge Term Voltage*** ≥ *ChargingVoltage()* / number of cells in series AND ***[TAPER_VOLT]*** = 0 AND The accumulated change in capacity > 0.25 mAh.	*ChargingStatus()[VCT]* = 1 *ChargingStatus()[MCHG]* = 1 *ChargingVoltage()* = Charging Algorithm *ChargingCurrent()* = Charging Algorithm *BatteryStatus()[FC]* = 1 and *GaugingStatus()[FC]* = 1 if ***SOCFlagConfig A[FCSETVCT]*** = 1 *BatteryStatus()[TCA]* = 1 and *GaugingStatus()[TCA]* = 1 if ***SOCFlagConfig B[TCASETVCT]*** = 1

NOTE: Setting ***[TAPER_VOLT]*** causes ***Charge Term Charging Voltage*** to be used in place of *ChargingVoltage()* / the number of cells in series for a valid charge termination condition.

4.7 Charge and Discharge Termination Flags

The *[TC]* and *[FC]* bits in *GaugingStatus()* can be set at charge termination, as well as based on RSOC or cell voltages. If multiple set and clear conditions are selected, then the corresponding flag will be set whenever a valid set or clear condition is met. If both set and clear conditions are true at the same time, the flag will clear. The same functionality is applied to the *[TD]* and *[FD]* bits in *GaugingStatus()*.

NOTE: *GaugingStatus()[TC][TD][FC][FD]* are the status flags based on the gauging conditions only. These flags are set and cleared based on ***SOC Flag Config A*** and ***SOC Flag Config B***.

The *BatteryStatus()[TAC][FC][TDA][FD]* flags will be set and cleared according to the *GaugingStatus()[TC][FC][TD][FD]* flags, as well as the safety and permanent failure protections status. For more information, see Section 4.8.

When *GaugingStatus()[TC]* is set AND ***FET Options[CHGFET]*** = 1, the CHG FET turns off.

The *[FC]* flag is identical between gauging status and battery status, but not *[TD]*. The tables below summarize the options to set and clear the *[TC]* and *[FC]* flags in *GaugingStatus()*.

Flag	Set Criteria	Set Condition	Enable
[TC]	cell voltage	Max cell voltage1..4 ≥ ***TC: Set Voltage Threshold***	***SOC Flag Config A[TCSetV]*** = 1
	RSOC	*RelativeStateOfCharge()* ≥ ***TC: Set % RSOC Threshold***	***SOC Flag Config A[TCSetRSOC]*** = 1
	Valid Charge Termination (enabled by default)	When *ChargingStatus[VCT]* = 1	***SOC Flag Config A[TCSetVCT]*** = 1
[FC]	cell voltage	Max cell voltage1..4 ≥ ***FC: Set Voltage Threshold***	***SOC Flag Config B[FCSetV]*** = 1
	RSOC	*RelativeStateOfCharge()* ≥ ***FC: Set % RSOC Threshold***	***SOC Flag Config B[FCSetRSOC]*** = 1
	Valid Charge Termination (enabled by default)	When *ChargingStatus[VCT]* = 1	***SOC Flag Config A[FCSetVCT]*** = 1

Flag	Clear Criteria	Clear Condition	Enable
[TC]	cell voltage	Max cell voltage1..4 ≤ ***TC: Clear Voltage Threshold***	***SOC Flag Config A[TCClearV]*** = 1
	RSOC (enabled by default)	*RelativeStateOfCharge()* ≤ ***TC: Clear % RSOC Threshold***	***SOC Flag Config A[TCClearRSOC]*** = 1

Flag	Clear Criteria	Clear Condition	Enable
[FC]	cell voltage	Max cell voltage1..4 ≤ ***FC: Clear Voltage Threshold***	***SOC Flag Config B[FCClearV]*** = 1
	RSOC (enabled by default)	*RelativeStateOfCharge()* ≤ ***FC: Clear % RSOC Threshold***	***SOC Flag Config B[FCClearRSOC]*** = 1

[TD] and *[FD]* both have extra conditions. If gauging status *[FD]* is set, then battery status is always set, but clearing also depends on some safety conditions (CUV, SUV, and so on).

The tables below summarize the various options to set and clear the *[TD]* and *[FD]* flags in *GaugingStatus()*.

Flag	Set Criteria	Set Condition	Enable
[TD]	cell voltage	Min cell voltage1..4 ≤ ***TD: Set Voltage Threshold***	***SOC Flag Config A[TDSetV]*** = 1
	RSOC (enabled by default)	*RelativeStateOfCharge()* ≤ ***TD: Set % RSOC Threshold***	***SOC Flag Config A[TDSetRSOC]*** = 1
[FD]	cell voltage	Min cell voltage1..4 ≤ ***FD: Set Voltage Threshold***	***SOC Flag Config B[FDSetV]*** = 1
	RSOC (enabled by default)	*RelativeStateOfCharge()* ≤ ***FD: Set % RSOC Threshold***	***SOC Flag Config B[FDSetRSOC]*** = 1

Flag	Clear Criteria	Clear Condition	Enable
[TD]	cell voltage	Min cell voltage1..4 ≥ ***TD: Clear Voltage Threshold***	***SOC Flag Config A[TDClearV]*** = 1
	RSOC (enabled by default)	*RelativeStateOfCharge()* ≥ ***TD: Clear % RSOC Threshold***	***SOC Flag Config A[TDClearRSOC]*** = 1
[FD]	cell voltage	Min cell voltage1..4 ≥ ***FD: Clear Voltage Threshold***	***SOC Flag Config B[FDClearV***] = 1
	RSOC (enabled by default)	*RelativeStateOfCharge()* ≥ ***FD: Clear % RSOC Threshold***	***SOC Flag Config B[FDClearRSOC]*** = 1

4.8 Terminate Charge and Discharge Alarms

When the protections and permanent fails are triggered, *BatteryStatus()[TCA][TDA][FD][OCA][OTA][FC]* will be set according to the type of safety protections. Here is a summary of the set conditions of the various alarms flags.

[TCA] = 1 if

- *SafetyAlert()[OCC1]*, *[OCC2]*, *[COV]*, *[OTC]*, *[OTF]*, *[OC]*, *[CHGC]*, *[CHGV]*, or *[PCHGC]* = 1 OR
- *PFAlert()[SOV]* or *[SOCC]* = 1 OR
- Any *PFStatus()* = 1 OR
- *OperationStatus()[PRES]* = 0 OR
- *GaugingStatus()[TC]* = 1 AND in CHARGE mode

[FC] = 1

- if *GaugingStatus()[FC]* = 1

[OCA] = 1 if

- *SafetyStatus()[OC]* = 1 AND in CHARGE mode

[TDA] = 1 if

- *SafetyAlert()[OCD1]*, *[OCD2]*, *[CUV]*, *[CUVC]*, *[OTD]*, or *[OTF]* = 1 OR
- *PFAlert()[SUV]* or *[SOCD]* = 1 OR
- Any *PFStatus()* = 1 OR

- *OperationStatus()[PRES]* = 0
- *GaugingStatus()[TD]* = 1 AND in DISCHARGE mode

[FD] = 1 if

- *SafetyStatus()[CUV]* = 1 OR
- *PFStatus()[SUV]* = 1 OR
- *GaugingStatus()[FD]*

[OTA] = 1 if

- *SafetyStatus()[OTC]*, *[OTD]*, or *[OTF]* = 1 OR
- *PFStatus()[SOT]* or *[SOTF]* = 1

4.9 Precharge

The gauge enters PRECHARGE mode if,

1. Min cell voltage1..4 < ***Precharge Start Voltage*** OR
2. Max cell voltage1..4 < ***Charging Voltage Low – Charging Voltage Hysteresis*** and not in CHARGE mode

Depending on the ***FET Options[PCHG_COMM]*** settings, the external precharge FET or CHG FET can be used in PRECHARGE mode. Setting ***Precharge Start Voltage*** and ***Charging Voltage Low*** = 0 mV disables the precharge function.

***[PCHG_COMM]* = 0**	***[PCHG_COMM]* = 1**
FET USED: external precharge FET	FET USED: CHG FET

The bq40z50-R3 device also supports 0-V charging using either an external precharge FET or CHG FET. If ***[PCHG_COMM]*** = 1, the gauge enables the hardware 0-V charging circuit automatically when the battery stack voltage is below the minimum operation voltage of the device (see the *bq40z50-R2 1-Series to 4-Series Li-Ion Battery Pack Manager* data sheet [SLUSCS4] for bq40z50-R3 electrical specifications).

4.10 Maintenance Charge

Maintenance charge can be configured to provide charge current after charge termination is reached.

If overcharge protection is enabled, ***Enabled Protections C[OC]*** = 1, an extra margin may be needed for ***OC:Threshold*** to prevent triggering the OC protection by the maintenance charging.

Status	Condition	Action
Set	*ChargingStatus()[IN]* = 0 AND *ChargingStatus()[SU]* = 0 AND *ChargingStatus()[PV]* = 0 AND *GaugingStatus()[TCA]* = 1	*ChargingStatus()[MCHG]* = 1 *ChargingVoltage()* = Charging Algorithm *ChargingCurrent()* = Charging Algorithm
Clear	*ChargingStatus()[IN]* = 1 OR *ChargingStatus()[SU]* = 1 OR *ChargingStatus()[PV]* = 1 OR *GaugingStatus()[TCA]* = 0	*ChargingStatus()[MCHG]* = 0 *ChargingVoltage()* = Charging Algorithm *ChargingCurrent()* = Charging Algorithm

4.11 Charge Control SMBus Broadcasts

If the ***[HPE]*** bit is enabled, MASTER mode broadcasts to the host address are PEC enabled. If the ***[CPE]*** bit is enabled, MASTER mode broadcasts to the smart-charger address are PEC enabled. The ***[BCAST]*** bit enables all broadcasts to a host or a smart charger. When the ***[BCAST]*** bit is enabled, the following broadcasts are sent:

- *ChargingVoltage()* and *ChargingCurrent()* broadcasts are sent to the smart-charger device address (0x12) every 10 s to 60 s.

- If any of the *[OCA]*, *[TCA]*, *[OTA]*, *[TDA]*, *[RCA]*, *[RTA]* flags are set, the *AlarmWarning()* broadcast is sent to the host device address (0x14) every 10 s. Broadcasts stop when all flags above have been cleared.
- If any of the *[OCA]*, *[TCA]*, *[OTA]*, *[TDA]* flags are set, the *AlarmWarning()* broadcast is sent to a smart-charger device address every 10 s. Broadcasts stop when all flags above have been cleared.

4.12 Charge Disabled

The bq40z50-R3 device disables charging by opening the charge FET when certain safety conditions are detected. In this case the FW will set *OperationStatus()[XCHG]* = 1.

Status	Condition	Action
Normal	*ALL PFStatus()* = 0 AND *SafetyStatus()[COV]* = 0 AND *SafetyStatus()[OCC1][OCC2]* = 0,0 AND *SafetyStatus()[ASCC]* = 0 AND *SafetyStatus()[ASCCL]* = 0 AND *SafetyStatus()[CTO]* = 0 AND *SafetyStatus()[PTO]* = 0 AND *OperationStatus()[PRES]* = 1 AND *GaugingStatus()[TCA]* = 0 if ***FET Options[CHGFET]*** = 1	*ChargingVoltage()* = Charging Algorithm *ChargingCurrent()* = Charging Algorithm *OperationStatus()[XCHG]* = 0
Trip	*ManufacturingStatus()[FET_EN]* = 0 OR *ANY PFStatus()[]* = 1 OR *SafetyStatus()[COV]* = 1 OR *SafetyStatus()[OCC1]* = 1 OR *SafetyStatus()[OCC2]* = 1 OR *SafetyStatus()[ASCC]* = 1 OR *SafetyStatus()[ASCCL]* = 1 OR *SafetyStatus()[CTO]* = 1 OR *SafetyStatus()[PTO]* = 1 OR *SafetyStatus()[HWDF]* = 1 OR *SafetyStatus()[OC]* = 1 OR *SafetyStatus()[CHGC]* = 1 OR *SafetyStatus()[CHGV]* = 1 OR *SafetyStatus()[PCHGC]* = 1 OR *SafetyStatus()[UTC]* = 1 OR *SafetyStatus()[OTC]* = 1 if ***[OTFET]*** = 1 OR *ChargingStatus()[IN]* = 1 if ***[CHGIN]*** = 1 OR *ChargingStatus()[SU]* = 1 if ***[CHGSU]*** = 1 OR *OperationStatus()[SLEEP]* = 1 if ***[NR]*** = 1 AND ***[SLEEPCHG]*** = 0 OR *OperationStatus()[EMSHUT]* = 1 OR *OperationStatus()[PRES]* = 0 OR *GaugingStatus()[TCA]* = 1 if ***FET Options[CHGFET]*** = 1	*ChargingVoltage()* = 0 *ChargingCurrent()* = 0 *OperationStatus()[XCHG]* = 1

Similarly, the device can disable discharge if any of the following conditions are detected, setting the *OperationStatus()[XDSG]* = 1.

- *ManufacturingStatus()[FET_EN]* = 0 OR
- Any *PFStatus()* set OR
- *SafetyStatus()[OCD1]* or *[OCD2]* or *[CUV]* or *[CUVC]* or *[AOLD]* or *[AOLDL]* or *[ASCD]* or *[ASCDL]* or *[UTD]* = 1 OR
- *SafetyStatus()[OTD]* or *[OTF]* = 1 if ***[OTFET]*** = 1 OR
- *OperationStatus()[PRES]* = 0 OR
- *OperationStatus()[EMSHUT]* = 1 OR
- *OperationStatus()[SDM]* = 1 AND delay time > ***FET Off Time*** OR
- *OperationStatus()[SDV]* = 1 AND low voltage time ≥ ***Shutdown Time***

4.13 Charge Inhibit

The bq40z50-R3 device can inhibit the start of charging at high and low temperatures to prevent damage of the cells. This feature prevents the start of charging when the temperature is at the inhibit range; therefore, if the device is already in the charging state when the temperature reaches the inhibit range, a FET action will not take place even if ***FET Options[CHGIN]*** = 1. High Temperature charge inhibit can be disabled by setting ***[HT_INHIB_DIS]***.

Status	Condition	Action
Normal	*ChargingStatus()[LT]* = 1 OR *ChargingStatus()[STL]* = 1 OR *ChargingStatus()[RT]* = 1 OR *ChargingStatus()[STH]* = 1	*ChargingStatus()[IN]* = 0 *ChargingVoltage()* = charging algorithm *ChargingCurrent()* = charging algorithm
Trip	Not charging AND (*ChargingStatus()[HT]* = 1 OR (*ChargingStatus()[OT]* = 1 AND ***[HT_INHIB_DIS]*** = 0) OR *ChargingStatus()[UT]* = 1	*ChargingStatus()[IN]* = 1 *ChargingStatus()[SU]* = 0 *ChargingVoltage()* = 0 *ChargingCurrent()* = 0 *OperationStatus()[XCHG]* = 1 if ***FET Options[CHGIN]*** = 1

4.14 Charge Suspend

The bq40z50-R3 device can stop charging at high and low temperatures to prevent damage of the cells. The *ChargingStatus()[SU]* condition is only active in the CHARGING mode. Once CHARGE SUSPEND is triggered, the gauge will exit CHARGING mode after ***Chg Relax Time*** and the CHARGE SUSPEND will change to CHARGE INHIBIT.

Status	Condition	Action
Normal	*ChargingStatus()[LT]* = 1 OR *ChargingStatus()[STL]* = 1 OR *ChargingStatus()[RT]* = 1 OR *ChargingStatus[STH]* = 1 OR *ChargingStatus()[HT]* = 1	*ChargingStatus()[SU]* = 0 *ChargingVoltage()* = charging algorithm *ChargingCurrent()* = charging algorithm
Trip	*ChargingStatus()[UT]* = 1 OR *ChargingStatus()[OT]* = 1	*ChargingStatus()[SU]* = 1 *ChargingVoltage()* = 0 *ChargingCurrent()* = 0 *OperationStatus()[XCHG]* = 1 if ***FET Options[CHGSU]*** = 1

4.15 ChargingVoltage() Rate of Change

The bq40z50-R3 device can slope the value changes from one range to another to avoid jumping between different voltage ranges. Setting the ***Voltage Rate*** to 1 disables this feature, because the *ChargingVoltage()* changes in one step. The gauge will not apply any voltage stepping if ***Voltage Rate*** is set to 1.

NOTE: The host needs to read *ChargingVoltage()* at least once a second during charging to adjust the charger accordingly.

Status	Condition	Action
Trip	*ChargingVoltage()* Change	*ChargingStatus()[CVR]* = 1 *ChargingVoltage()* = Old + n × (New – Old)/***Voltage Rat***e, where Old = present *ChargingVoltage()* New = the target *ChargingVoltage()* that the device will change to n = 1..***Voltage Rate***, increments in steps of one per second.

4.16 ChargingCurrent() Rate of Change

The bq40z50-R3 device can slope the value changes from one range to another to avoid jumping between different current ranges. Setting the ***Current Rate*** to 1 disables this feature because the *ChargingCurrent()* changes in one step. The gauge will not do any current stepping if ***Current Rate*** is set to 1.

NOTE: The host needs to read *ChargingCurrent()* at least once a second during charging to adjust the charger accordingly.

Status	Condition	Action
Trip	*ChargingCurrent()* Change	*ChargingStatus()[CCR]* = 1 *ChargingCurrent()* = Old + n × (New – Old)/***Current Rate***, where Old = present *ChargingCurrent()* New = the target *ChargingCurrent()* that the device will change to n = 1..***Current Rate***, increment in steps of 1 per second.

4.17 Charging Loss Compensation

The bq40z50-R3 device can modify *ChargingVoltage()* and *ChargingCurrent()* to compensate losses caused by the FETs, the fuse, and the sense resistor by measuring the cell voltages directly and adjusting *ChargingCurrent()* and *ChargingVoltage()* accordingly.

In CONSTANT CURRENT mode, the device can increase the *ChargingVoltage()* value to compensate the drop losses. This feature can be enabled by setting ***Configuration[CCC]*** = 1 and configuring the ***CCC Current Threshold***.

NOTE: The host must read *ChargingVoltage()* and/or *ChargingCurrent()* at least once a second during charging to adjust the charger accordingly.

Status	Condition	Action
Normal	*Current()* > ***CCC Current Threshold*** AND *Voltage()* = Charging algorithm voltage	*ChargingStatus()[CCC]* = 0 *ChargingVoltage()* = Charging Algorithm
Active	*Current()* > ***CCC Current Threshold*** AND *Voltage()* < Charging algorithm voltage	*ChargingStatus()[CCC]* = 1 *ChargingVoltage()* = Charging Algorithm + (PACK voltage – *Voltage()*)
Limit	(PACK voltage in *DAStatus1()* – *Voltage()*) > ***CCC Voltage Threshold***	*ChargingVoltage()* = Charging Algorithm + ***CCC Voltage Threshold***

4.18 Cycle Count/SOH Based Degradation of Charging Voltage and Current

This feature, if enabled by setting either ***[Cycle_Based_Degrade]*** or ***[SOH_Based_Degrade]*** in the charging configuration register, reduces the *ChargingVoltage()* and/or *ChargingCurrent()* levels based on cycle count or SOH. This helps to reduce the *ChargingVoltage()* and/or *ChargingCurrent()* as the battery pack ages in order to increase the longevity of the battery pack. These degradations are at the cell level. Additionally, these degradations can be selected to trigger off either specific cycle counts or specific SOH values.

4.18.1 Cycle Count Based Degradation

There are four programmable stages/levels entered using ***Cycle Count*** (when enabled by setting ***[Cycle_Degrade]***).

NORMAL mode (***Cycle Count*** is equal to or more than ***Cycle Threshold*** for Mode 1.)

Cycle Count Mode 1 (***Cycle Threshold*** for Mode 1 with default 50 cycles is reached.)

Cycle Count Mode 2 (***Cycle Threshold*** for Mode 2 with default 150 cycles is reached.)

Cycle Count Mode 3 (***Cycle Threshold*** for Mode 3 with default 350 cycles is reached.)

4.18.2 SOH Based Degradation

In addition, when using the configuration bit ***[SOH_Degrade]***, SOH can be used as a selector (like ***Cycle Count***) for voltage degradation. There are four programmable stages/levels of SOH entered:

NORMAL mode (SOH is equal to or lower than ***SOH Threshold*** for Mode 1.)

SOH Mode 1 (***SOH Threshold*** for Mode 1 with SOH of default 95%)

SOH Mode 2 (***SOH Threshold*** for Mode 2 with SOH of default 80%)

SOH Mode 3 (***SOH Threshold*** for Mode 3 with SOH of default 60%)

4.18.3 Runtime Based Degradation

In addition, when using the configuration bit ***[RUNTIME_DEGRADE]***, runtime counted when ***Cycle Count*** is above ***Cycle Count Start Runtime*** can be used as a selector (for example, ***Cycle Count***) for voltage degradation. There are four programmable stages/levels entered:

NORMAL mode (Runtime is equal to or lower than ***Runtime Threshold*** for Mode 1.)

Runtime Mode 1 (***Runtime Threshold*** for Mode 1 with Runtime of default 8760 hrs)

Runtime Mode 2 (***Runtime Threshold*** for Mode 2 with Runtime of default 17520 hrs)

Runtime Mode 3 (***Runtime Threshold*** for Mode 3 with Runtime of default 26280 hrs)

When the configuration bits ***[RUNTIME_DEGRADE]***, ***[CYCLE_DEGRADE]***, and ***[RTORCC]*** are all set, then degradation occurs according to the runtime or cycle count criteria first met.

4.18.3.1 Charging Voltage Degradation Process

The following is the charging voltage degradation process (using ***Cycle Count*** as an example, although it would be the same for SOH):

In NORMAL mode, no *ChargingVoltage()* adjustment, moving to Cycle Count Mode 1, *ChargingVoltage()* is reduced by CV Degradation Mode 1 (assuming the Cycle Count 1 entry conditions are met), then moving to Cycle Count Mode 2, *ChargingVoltage()* is further reduced by ***CV Degradation*** Mode 2 (assuming Cycle Count 2 entry conditions are met). It is similar for Cycle Count Mode 3. The charging voltage mode transition is a one-way transition. The gauge only goes from Normal → Lvl1 → Lvl2 → Lvl3. The three degradation points each occur one time when that level is reached with the amount of voltage degradation based on the related register.

- Charging voltage degradation on reaching CC/SOH Mode 1 (Degrade Mode 1:***Voltage Degradation*** with default 10 mV / cell)
- Charging voltage degradation on reaching CC/SOH Mode 2 (Degrade Mode 2:***Voltage Degradation*** with default 40 mV / cell)
- Charging voltage degradation on reaching CC/SOH Mode 3 (Degrade Mode 3:***Voltage Degradation*** with default 70 mV / cell)

This charging voltage degradation scheme (if enabled) works in conjunction with any other existing degradation/increments (such as charging loss compensation).

4.18.3.2 Optional Charging Current Degradation

Optionally (with cycle count and SOH based degradations), by setting the configuration bit ***[Degrade_CC]***, charging current can also be degraded (in addition to charging voltage degrading). The level of degradation can be programmed using the following data flash:

- Charging current degradation on reaching CC/SOH Mode 1 (Degrade Mode 1:***Current Degradation*** with default 10%)
- Charging Current degradation on reaching CC/SOH Mode 2 (Degrade Mode 2:***Current Degradation*** with default 20%)
- Charging Current degradation on reaching CC/SOH Mode 3 (Degrade Mode 3:***Current Degradation*** with default 40%)

4.18.3.3 Charging Current Degradation Process

The following is the charging current degradation process (using ***Cycle Count*** as an example, although it would be the same for SOH).

In NORMAL mode (no *ChargingCurrent()* adjustment), *ChargingCurrent()* is reduced by CC Degradation Mode 1 (assuming the Cycle Count 1 entry conditions are met), then moving to Cycle Count Mode 2, *ChargingCurrent()* is further reduced by CC Degradation Mode 2 (assuming Cycle Count 2 entry conditions are met). This is similar for Cycle Count Mode 3.

The charging current mode transition is a one-way transition. The gauge only goes from Normal → Lvl1 → Lvl2 → Lvl3. The three degradation points each occur one time when that level is reached, with the amount of voltage degradation based on the related register.

This charging current degradation scheme (if enabled) must work in conjunction with any other existing degradation/increments (such as charge loss compensation).

The following table shows how charging voltage and charging current are degraded at different points:

Cycle Count (in counts)/SOH (in %) (One or the other must be enabled.[(1)])	Charging Voltage (CV) (CV degradation is available by default.)	Charging Current (CC) (CC degradation is available if enabled *[Degrade_CC]*.[(2)])
Normal	***No CV Degradation***	***No CC Degradation***
Mode 1	***CV Degradation*** (default 10 mV / cell)	***CC Degradation*** (default 10%)
Mode 2	***CV Degradation*** (default 40 mV / cell)	***CC Degradation*** (default 20%)
Mode 3	***CV Degradation*** (default 70 mV / cell)	***CC Degradation*** (default 40%)

(1) Only SOH or ***Cycle Count*** can be used at a time. Both must not be enabled together.
(2) Only [Degrade CC] or [CRATE] can be used at a time. Both must not be enabled together.

4.19 Elevated Charge Degradation

The bq40z50-R3 includes a monitoring scheme that notifies the host when the battery spends a prolonged period of time at an elevated RSOC level with or without respect to temperature, depending on the configuration. The temperature used for this feature is the maximum temperature source configured for cell temperature. This feature uses the counter ***Accumulated ERM Time*** that is incremented once for every hour that *RelativeStateOfCharge()* ≥ ***ERM RSoC Threshold***. For periods where ***ERM Reset RSoC Threshold*** < *RelativeStateOfCharge()* < ***ERM RSoC Threshold***, the ***Accumulated ERM Time*** is held unchanged at its present value.

When the ***Accumulated ERM Time*** ≥ ***ERM Time Threshold***, an *[ERM]* flag is set, signaling to the host that ELEVATED RSOC mode has been entered.

Recovery occurs if *RelativeStateOfCharge()* < ***ERM Reset RSoC Threshold***, at which point ***Accumulated ERM Time*** and *[ERM]* are cleared to their default state of 0.

To use voltage-based thresholds (***ERM Voltage Threshold*** and ***ERM Reset Voltage Threshold***) in place of RSOC-based ones for this mode, the configuration bit ***[ERM_MODE]*** must be set (the default value is 0).

The separate counter ***Accumulated ERETM Time*** is used to track time at the elevated temperature, as well as *RelativeStateOfCharge()*, and can be used to reduce *ChargingVoltage()*. This counter is incremented once for every hour that *RelativeStateOfCharge()* ≥ ***ERETM RSoC Threshold***, and ***ERETM Temperature Threshold*** < temperature < ***ERETM Temperature Max Threshold***. For periods where *RelativeStateOfCharge()* < ***ERETM RSoC Threshold*** or *RelativeStateOfCharge()* ≥ ***ERETM RSoC Threshold*** and temperature < ***ERETM Temperature Threshold***, the ***Accumulated ERETM Time*** is held unchanged at its present value.

When the ***Accumulated ERETM Time*** ≥ ***ERETM Time Threshold***, an *[ERETM_ACTIVE]* flag is set, signaling to the host that ***Elevated RSOC and Temperature Mode*** has been entered, and *ChargingVoltage()* for all temperature ranges is permanently set to ***ERETM Charging Voltage***, starting from the next charge cycle along with the flag ***[ERETM_DEGRADE]*** setting.

If at any point *RelativeStateOfCharge()* > ***ERETM RSoC Threshold*** and temperature > ***ERETM Temperature Max Threshold***, the *[ERETM_ACTIVE]* flag is immediately set, bypassing the counter threshold. Once active, exit from this mode is prohibited and the gauge stays in this mode for the remaining life of the pack. This ***ERETM Temperature Max Threshold*** related trigger can be disabled by clearing the ***[ERETM_MAX_T]*** configuration bit.

Since ***Elevated RSOC and Temperature Mode*** supersedes ELEVATED RSOC mode, the latter and its associated *[ERM]* flag are deactivated once the former is triggered.

To use voltage-based thresholds (***ERETM Voltage Threshold***) in place of *RelativeStateOfCharge()*-based ones for this mode, the configuration bit ***[ERETM_MODE]*** must be set (default is cleared).

To disable each mode, clear its respective enable bit (***[ERM TIME]*** and/or ***[ERETM TIME]***).

4.20 Charge Voltage Compensation for System Impedance

The design of some battery charging systems may have a not insignificant impedance between the charger and battery terminals. In this case a voltage compensation feature handles system level IR drops to ensure the correct charging voltage is supplied at the battery terminals. Program the ***System Resistance*** register with the measured resistance in milliohms (mΩ) between the battery terminals and charger terminals. This feature is enabled by setting the configuration bit ***[COMP_IR]*** in (default 0) the ***Charging Configuration*** register.

This feature works as follows:

SBS.ChargingVoltage = Charging_Voltage + *SBS.ChargingCurrent()* × ***System Resistance***

where Charging_Voltage has been computed as a result of a selected configuration.

4.21 Cell Swelling Control (via Charging Voltage Degradation)

Cell swelling can occur when the cell temperature and cell voltage are above certain thresholds. In these situations, the charging voltage can be stepped down gradually until the cell temperature moves back down.

This scheme works (as shown in Figure 4-1) when enabled by setting ***[CS_CV]*** (default is cleared) in the ***Charging Configuration*** register. When the max cell voltage1..4 and cell temperature are above the ***Voltage Threshold*** and ***Temperature Threshold***, respectively, for the period defined by ***Time Interval***, then the charging voltage is stepped down by ***Delta Voltage***. This step down continues until either the max cell voltage1..4 and cell temperature conditions go away (that is, cell swelling reduces) or the step down reaches ***Min CV***.

The charging voltage reduction/degradation resulting from this feature is reset when exiting CHARGE mode.

NOTE: This degradation works in conjunction with other degradation features; therefore, use with care.

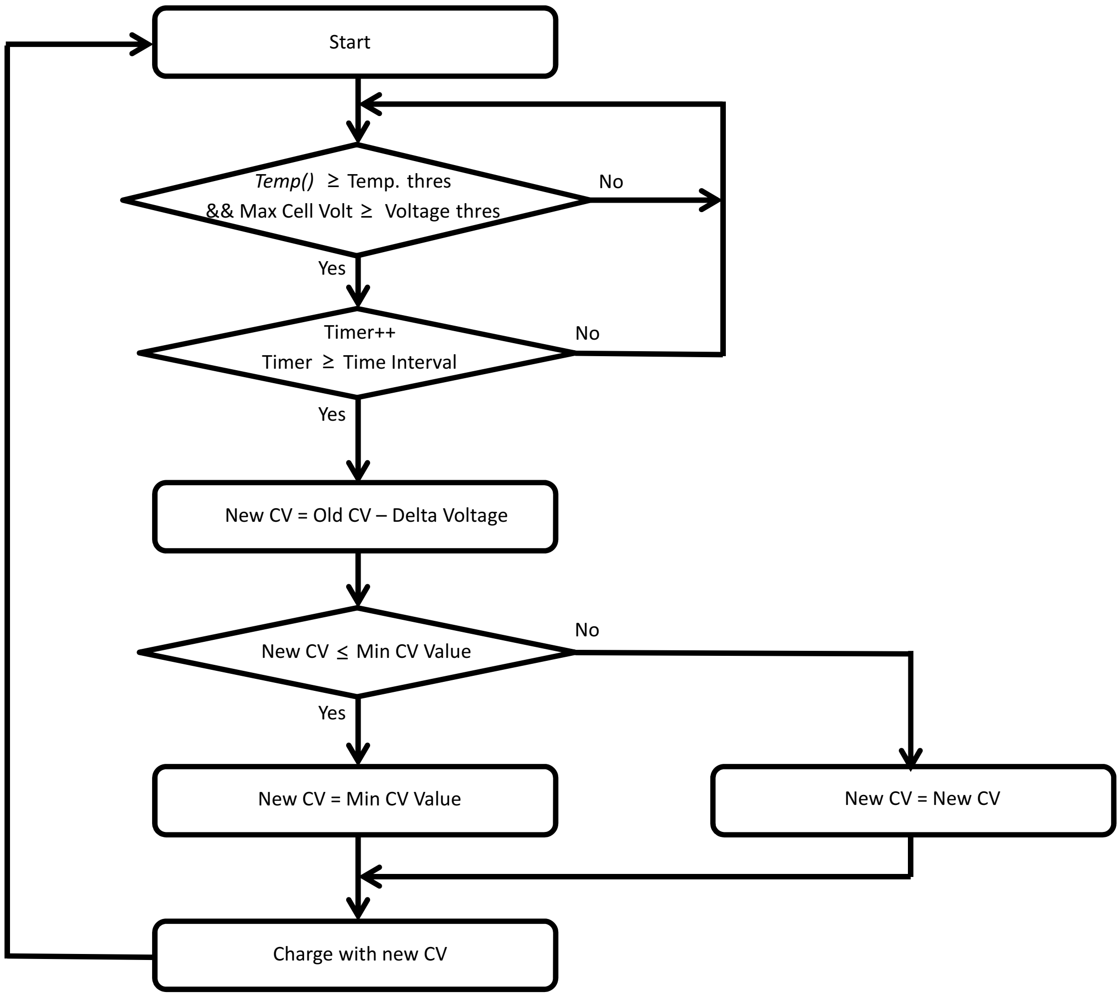
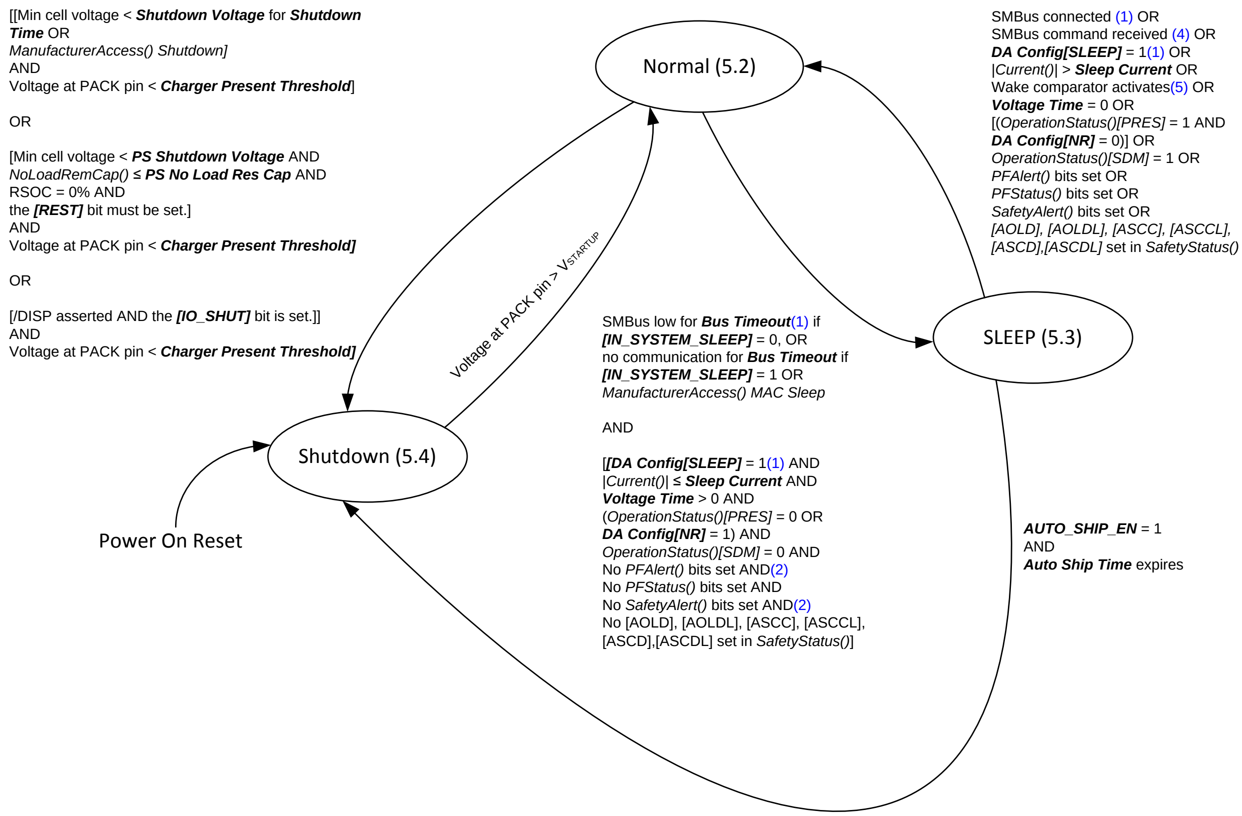


Figure 4-1. Cell Swelling Control

Power Modes

5.1 Introduction

To enhance battery life, the bq40z50-R3 device supports several power modes to minimize power consumption during operation. Figure 5-1 shows a summary of the power modes.



(1) ***DA Config[SLEEP]*** and SMBus low are not checked if the *ManufacturerAccess()* SLEEP mode command is used to enter SLEEP mode.
(2) *SafetyAlert()[PTO]*, *[PTOS]*, *[CTO]*, *[CTOS]*, or *PFAlert()[QIM]*, *[OC]*, *[IMP]*, *[CB]* will not prevent the gauge to enter SLEEP mode.
(3) For ***[NR]*** = 0, the CHG FET and PCHG FET remains on in SLEEP mode if ***[SLEEPCHG]*** = 1, but if the battery pack is removed from the system, the CHG FET is off because the system present takes higher priority than ***[SLEEPCHG]***.
(4) Wake on SMBus command is only possible when the gas gauge is put to sleep using the *ManufacturerAccess()* SLEEP mode command or ***[IN_SYSTEM_SLEEP]*** is enabled with ***Bus Timeout*** = 0. Otherwise, the gas gauge wakes on an SMBus connection (clock or data high).
(5) The wake comparator threshold is set through ***Power.WakeComparator[WK1,WK0]***.

Figure 5-1. Power Modes Summary Diagram

5.2 NORMAL Mode

In NORMAL mode, the device takes voltage, current, and temperature readings every 250 ms, performs protection and gauging calculations, updates SBS data, and makes status decisions at 1-s intervals. Between these periods of activity, the device is in a reduced power state.

5.2.1 BATTERY PACK REMOVED Mode/System Present Detection

Pack removal and system present detection should be disabled for non-removable packs by setting the ***DA Configuration[NR]*** bit.

If the ***[NR]*** bit is set, the PRES input is not monitored. If ***[NR]*** is set and ***[EMSHUT_EN]*** is cleared, the PRES pin should be tied to VSS. If ***[NR]*** and ***[EMSHUT_EN]*** are set, then the PRES input must be configured correctly for that function.

5.2.1.1 System Present

PRES is sampled four times per second, and if PRES is high for 4 samples (one second), the *OperationStatus[PRES]* flag is cleared. If PRES is low for 4 samples (one second), the *OperationStatus [PRES]* flag is set, indicating the system is present (the battery is inserted).

5.2.1.2 Battery Pack Removed

The bq40z50-R3 device detects the BATTERY PACK REMOVED mode if the ***[NR]*** bit is cleared AND the PRES input is high (*[PRES]* = 0).

On entry to the BATTERY PACK REMOVED mode, the *[TCA]* and *[TDA]* flags are set, *ChargingCurrent()* and *ChargingVoltage()* are set to 0, the CHG and DSG FETs are turned off, and the precharge FET is turned off (if used).

Polling of the PRES pin continues at a rate of once every 1 s.

The bq40z50-R3 exits the BATTERY PACK REMOVED state if the PRES input is low (*[PRES]* = 1). When this occurs, the *[TCA]* and *[TDA]* flags are reset.

5.3 SLEEP Mode

5.3.1 Device Sleep

When the sleep conditions are met, the device goes into SLEEP mode with periodic wakeups for voltage, temperature, and current measurements to reduce power consumption.

OperationStatus()[SLPAD] is set when the gauge wakes to measure voltage and temperature. Similarly, the *[SLPCC]* is set when the gauge wakes for current measurement. In general, it is not possible to read these flags because an SMBus communication will wake up the gauge.

The bq40z50-R3 device returns to NORMAL mode if any exit sleep condition is met.

Status	Condition	Action
Activate	SMBus low for ***Bus Timeout***[(1)] if ***[IN_SYSTEM_SLEEP]*** = 0, or no communication for ***Bus Timeout*** if ***[IN_SYSTEM_SLEEP]*** = 1 AND ***DA Config[SLEEP]*** = 1[(1)] AND |*Current()*| ≤ ***Sleep Current*** AND ***Voltage Time*** > 0 AND (*OperationStatus()[PRES]* = 0 OR ***DA Config[NR]*** = 1) AND *OperationStatus()[SDM]* = 0 AND No *PFAlert()* bits set AND[(2)] No *PFStatus()* bits set AND No *SafetyAlert()* bits set AND[(2)] No [AOLD], [AOLDL], [ASCC], [ASCCL], [ASCD], [ASCDL] set in *SafetyStatus()*	Turn off CHG FET and PCHG FET if ***FET Options[SLEEPCHG]*** = 0.[(3)] The device goes to sleep. The device wakes up every ***Sleep:Voltage Time*** period to measure voltage and temperature. The device wakes up every ***Sleep:Current Time*** period to measure current.

(1) ***DA Config[SLEEP]*** and SMBus low are not checked if the *ManufacturerAccess()* SLEEP mode command is used to enter SLEEP mode.

(2) *SafetyAlert()[PTO]*, *[PTOS]*, *[CTO]*, *[CTOS]* or *PFAlert()[QIM]*, *[OC]*, *[IMP]*, *[CB]* will not prevent the gauge to enter SLEEP mode.

(3) For ***[NR]*** = 0, the CHG FET and PCHG FET remains on in SLEEP mode if ***[SLEEPCHG]*** = 1, but if the battery pack is removed from the system, the CHG FET is off because the system present takes higher priority than ***[SLEEPCHG]***.

Status	Condition	Action
Exit	SMBus connected [1] OR SMBus command received [4] OR ***DA Config[SLEEP]*** = 1 [1] OR *|Current()|* > ***Sleep Current*** OR Wake comparator activates [5] OR ***Voltage Time*** = 0 OR (*OperationStatus()[PRES]* = 1 AND ***DA Config[NR]*** = 0) OR *OperationStatus()[SDM]* = 1 OR *PFAlert()* bits set OR *PFStatus()* bits set OR *SafetyAlert()* bits set OR *[AOLD], [AOLDL], [ASCC], [ASCCL], [ASCD], [ASCDL]* set in *SafetyStatus()*	Return to NORMAL mode SLEEPWKCHG estimates an accumulated charge on exit from SLEEP mode for the duration of ***Current Time*** preceding the last current measurement when ***Current Time*** is greater than 2 s. The current read upon exit of SLEEP mode is assumed to have been present for half of the ***Current Time*** interval, when enabled. This feature does not have any effect when ***Current Time*** is less than or equal to 2.

(4) Wake on SMBus command is only possible when the gas gauge is put to sleep using the *ManufacturerAccess()* SLEEP mode command or ***[IN_SYSTEM_SLEEP]*** is enabled with ***Bus Timeout*** = 0. Otherwise, the gas gauge wakes on an SMBus connection (clock or data high).

(5) The wake comparator threshold is set through ***Power.WakeComparator[WK1,WK0]*** (see Section 5.3.4).

5.3.2 IN SYSTEM SLEEP Mode

The bq40z50-R3 device provides an option for removable packs (that is, ***DA Config[NR]*** = 0) to enter SLEEP mode in-system. When the ***DA Config[IN_SYSTEM_SLEEP]*** = 1, the device will enter SLEEP mode even if the *OperationStatus()[PRES]* = 1. This option ignores the $\overline{\text{PRES}}$ pin status only. Additionally, in this option, the SMBus low state is not a condition to enter SLEEP mode (instead, communication must not occur for ***Bus Timeout*** to enter SLEEP). All the other sleep conditions must be met for the device to enter SLEEP mode.

In IN SYSTEM SLEEP mode, it is possible to read the *[SLPAC]* and *[SLPCC]* flags if ***[IN_SYSTEM_SLEEP]*** = 1 and ***Bus Timeout*** = 0. This setting allows the gauge to enter SLEEP mode with active communication in progress.

NOTE: Setting the ***Bus Timeout*** = 0 with ***[IN_SYTEM_SLEEP]*** can be used for testing purposes, but it is not recommended to set the ***Bus Timeout*** = 0 in the field. If ***Bus Timeout*** = 0, the device's sleep and wake conditions are strictly controlled by current detection. If the host system performs a low load operation periodically (for example, wireless detection in a tablet application), this small load current may be missed, introducing an error into remaining capacity tracking. Having a non-zero ***Bus Timeout*** setting enables the gauge to wake up by a communication and capture the current measurement.

5.3.3 ManufacturerAccess() MAC Sleep

The SLEEP MAC command can override the requirement for bus low to enter sleep. In this case, the bq40z50-R3 clock and data high condition is ignored for sleep to exit, though sleep will also exit if there is any further SMBus communication. The bq40z50-R3 device can be sent to sleep with *ManufacturerAccess()* if specific sleep entry conditions are met.

5.3.4 Wake Function

The bq40z50-R3 device can exit SLEEP mode if enabled by the presence of a voltage across SRP and SRN. The voltage threshold needed for the device to wake from SLEEP mode is programmed in ***Power:Wake Comparator***. This allows the gauge to wake up quickly in response to a higher current detection. Otherwise, the gauge only wakes up every ***Sleep Current Time*** to detect if |*Current()*| is greater than Sleep Current.

Reserved (Bits 7–4, 1–0): Reserved. Do not use.

WK1,0 (Bits 3–2): Wake Comparator Threshold

WK1	WK0	Voltage
0	0	±0.625 mV
0	1	±1.25 mV
1	0	±2.5 mV
1	1	±5 mV

5.4 SHUTDOWN Mode

5.4.1 VOLTAGE BASED SHUTDOWN

To minimize power consumption and to avoid draining the battery, the device can be configured to shut down at a programmable stack voltage threshold. This function also works in PERMANENT FAILURE mode. When the device is in PERMANENT FAILURE mode, the parameters ***PF Shutdown Voltage*** and ***PF Shutdown Time*** configure the shutdown threshold.

Status	Condition	Action
Enable	Min cell voltage < ***Shutdown Voltage***	*OperationStatus()[SDV]* = 1
Trip	Min cell voltage < ***Shutdown Voltage*** for ***Shutdown Time***	Turn DSG FET off
Shutdown	Voltage at PACK pin < ***Charger Present Threshold***	Send device into SHUTDOWN mode
Exit	Voltage at PACK pin > $V_{STARTUP}$	*OperationStatus()[SDV]* = 0 Return to NORMAL mode

Table 5-1. PF Shutdown Voltage

Class	Subclass	Name	Format	Size in Bytes	Min Value	Max Value	Default Value	Unit
Power	Shutdown	PF Shutdown Voltage	Int	2	0	32767	1750	mV

Table 5-2. PF Shutdown Time

Class	Subclass	Name	Format	Size in Bytes	Min Value	Max Value	Default Value	Unit
Power	Shutdown	PF Shutdown Time	Unsigned Int	1	0	255	10	s

NOTE: The bq40z50-R3 device goes through a full reset when exiting from SHUTDOWN mode, which means the device will reinitialize. On power up, the gauge will check some special memory locations. If the memory checksum is incorrect, or if the gauge or the AFE watchdog has been triggered, the gauge will do a full reset.

If the memory checksum is good, for example, in a case of a short power glitch, the gauge will do a partial reset. The initialization is faster in a partial reset, and certain memory data will not be reinitialized (for example, all SBS registers, last known FET state, last ADC and CC readings, and so on), and so a partial reset is usually transparent to the host.

5.4.2 ManufacturerAccess() MAC Shutdown

In SHUTDOWN mode, the device turns off the FETs after ***FET Off Time***, and then shuts down to minimize power consumption after ***Delay*** time. ***FET Off Time*** and ***Delay*** time are referenced to the time the gauge receives the command. Thus, the ***Delay*** time must be set longer than ***FET Off Time***. The bq40z50-R3 device returns to NORMAL mode when the voltage at the PACK pin > $V_{STARTUP}$. The bq40z50-R3 device can be sent to this mode with the *ManufacturerAccess() Shutdown* command. Charger voltage must not be present for the device to enter SHIP SHUTDOWN mode.

NOTE: If the gauge is sealed and the MAC *Shutdown()* command is sent twice in a row, the gauge will execute the shutdown sequence immediately and skip the normal delay sequence.

5.4.3 Time-Based Shutdown

The bq40z50-R3 device can be configured to shut down after staying in SLEEP mode without communication for a preset time interval specified in ***Auto Ship Time***. Setting***PowerConfig[AUTO_SHIP_EN]*** enables this feature. Any communication to the device restarts the timer. When the timer reaches ***Auto Ship Time***, the time-based shutdown effectively triggers the MAC shutdown command to start the shutdown sequence. The bq40z50-R3 device returns to NORMAL mode when voltage at PACK pin > $V_{STARTUP}$.

5.4.4 Power Save Shutdown

Power Save Shutdown is enabled when ***[PWR_SAVE_VSHUT]*** is set. The bq40z50-R3 enters ***Power Save Shutdown*** when the lowest cell voltage is below ***PS Shutdown Voltage*** and: *NoLoadRemCap()* ≤ ***PS NoLoadResCapThreshold***.

Status	Condition	Action
Enable	Min cell voltage < ***PS Shutdown Voltage***	*OperationStatus()[PSSHUT]* = 1
Trip	Min cell voltage < ***PS Shutdown Voltage*** AND *NoLoadRemCap()* ≤ ***PS No Load Res Cap*** AND RSOC = 0% AND the ***[REST]*** bit must be set.	Turn DSG FET off
Shutdown	Voltage at PACK pin < ***Charger Present Threshold***	Send device into SHUTDOWN mode.
Exit	Voltage at PACK pin > $V_{STARTUP}$	*OperationStatus()[PSSHUT]* = 0 Return to NORMAL mode

Table 5-3. PS Shutdown Voltage

Class	Subclass	Name	Format	Size in Bytes	Min Value	Max Value	Default Value	Unit
Power	Shutdown	PS Shutdown Voltage	Int	2	0	32767	2500	mV

Table 5-4. PS No Load Res Cap

Class	Subclass	Name	Format	Size in Bytes	Min Value	Max Value	Default Value	Unit
Power	Shutdown	PS No Load Res Cap	Unsigned Int	2	0	32767	0	mAh

5.4.5 IO Based Shutdown

The bq40z50-R3 device can shut down upon the assertion of the DISP pin when the configuration bits ***[IO_SHUT]*** = 1 and ***[LED_EN]*** = 0. This feature is disabled when the LED display is enabled. When the pin is asserted for ***IO Shutdown Delay***, the gas gauge opens its DSG FET, then shuts down once PACK voltage < ***Charger Present Threshold***. If the pin is deasserted or ***[IO_TIMEOUT]*** is set and ***IO Shutdown Timeout*** expires following activation before PACK voltage < ***Charger Present Threshold***, then the shutdown is stopped and the DSG FET turns back on and returns to the state it was in before the pin was asserted. An active low signal is detected when ***[IO_POL]*** = 0. An active high signal is detected when ***[IO_POL]*** = 1. An internal pullup is enabled when ***[IO_PUL_DIS]*** = 0. The pullup is disabled when ***[IO_PUL_DIS]*** = 1. The pin is sampled every 250 ms.

Status	Condition	Action
Trip	DISP asserted AND the ***[IO_SHUT]*** bit is set.	Turn DSG FET off
Shutdown	Voltage at PACK pin < ***Charger Present Threshold***	Send device into SHUTDOWN mode.
Exit	Voltage at PACK pin > $V_{STARTUP}$	*OperationStatus()[IOSHUT]* = 0 Return to NORMAL mode.

5.5 Option to Manage Unintended Wakeup from Shutdown

In some user systems, there can be glitches on the supply line during mass production. This can result in a glitch getting to the PACK pin (V_{PACK}), which can then unintentionally wake up a device that was in shutdown.

The feature to manage an unintended wakeup from shutdown, if enabled (with the ***[CHECK_WAKE]*** bit), manages a shutdown of the gauge by any allowed shutdown process (except for VOLTAGE BASED SHUTDOWN and POWER SAVE SHUTDOWN, both of which are excluded from this feature). This feature does not function on a wake/start up from a reset.

When this feature is active on wake up from shutdown, the gauge starts a ***Delay*** timer (with the default of 2 s) and looks for communication to the gauge during this time—with CHG and DSG FETs remaining off. If during the ***Delay*** timer period there is no valid communication with the device, then the device goes back into shutdown (with FETs turned off). If there is valid communication within the ***Delay*** timer period, then the device stays in wake and continues like a normal wakeup. Valid communication means the gauge receives a valid address and a command. (It does not matter if the command is invalid. Invalid commands are OK with a valid address.)

One variant to this is the wake up from an IATA shutdown. In this case, each time the gauge wakes up, the IATA function will be called as usual. However, if the gauge then goes back into shutdown (because it was an unintended wakeup from shutdown), then the ***[IATA_SHUT]*** bit will be set before going into shutdown again and the FCC and RemCap stored during the original IATA shutdown will still be kept for the next wakeup.

Additionally, the number of times the gauge wakes up from shutdown unintentionally is recorded. This "unintentional wakeup" counter is reset when the gauge wakes up and sees valid communication. If this count exceeds a threshold (***Count***, with the default of 3), then the next time the gauge wakes up from shutdown, it will execute a normal wakeup without looking for valid communication (and the counter recording wakeup will be reset). If the ***Count*** is set to 0, then no threshold exists and the gauge will only wake up with valid communications.

NOTE: If this feature is enabled (***[CHECK_WAKE]*** set high), then by default the CHG and DSG FETs are off on wake up from SHUTDOWN (during the ***Delay*** timer period); thus, the FETs will turn on only if the gauge enters a normal wakeup. However, if the ***[CHECK_WAKE_FET]*** bit is set (default is cleared), then the FETs will not be forced off during the ***Delay*** timer period.

5.6 Emergency FET Shutdown (EMSHUT)

The Emergency FET Shutdown function provides an option to disable the battery power to the system by opening up the CHG and DSG FETs before removing an embedded battery pack. There are two ways to enter the EMERGENCY FET SHUTDOWN state:

a. Use an external signal (for example, a push-button switch) to detect a low-level threshold signal on the $\overline{\text{SHUTDN}}$ pin.

b. Send a Manual FET Control (MFC) sequence to *ManufacturerAccess()*.

When the gauge is in the EMERGENCY FET SHUTDOWN state, the *OperationStatus()[EMSHUT]* = 1.

5.6.1 Enter Emergency FET Shutdown Through $\overline{\text{SHUTDN}}$

When a high-to-low transition on the $\overline{\text{SHUTDN}}$ pin is detected with a debounce delay of about 1 s for the low level threshold, the gauge will turn off the CHG and DSG FETs immediately. This entry method only applies if ***[NR]*** = 1 and ***DA Configuration[EMSHUT]*** = 1. If ***[NR]*** = 0, the $\overline{\text{SHUTDN}}$ pin will restore to the regular system present detection.

5.6.2 Enter Emergency FET Shutdown Through MFC

Alternatively, sending a manual FET control (MFC) sequence using the steps below also puts the gauge to the EMERGENCY FET SHUTDOWN state. This entry method applies to ***[NR]*** = 0 and ***[NR]*** = 1.

a. Send word 0x270C to *ManufacturerAccess()* (0x00) to enable the MFC.

b. Within 4 s, send word 0x043D to *ManufacturerAccess()* (0x00) to turn off CHG and DSG FETs.

c. The CHG and DSG FETs will be off after ***Manual FET Control Delay***.

5.6.3 Exit Emergency FET Shutdown

Regardless of which EMSHUT entry method is used, the gauge can exit the EMSHUT mode by turning on the CHG and DSG FETs with any one of the following conditions:

- A high-to-low transition on the $\overline{\text{SHUTDN}}$ pin is detected with a debounce delay of 1 s for the low level threshold. For example, a push button is pressed again. This exit condition can be disabled by setting the ***[EMSHUT_PEXIT_DIS]*** bit in the ***DA Configuration*** register.
- Send word 0x23A7 to *ManufacturerAccess()* (0x00).
- PACK voltage > ***Charger Present Threshold*** for two sample periods (that is, ~500 ms). This exit condition requires the ***[EMSHUT_EXIT_VPACK]*** bit to be set.
- Valid SMBus communication is received. Valid SMBus communication means a valid gauge address and any command is received (that is, an invalid command with a valid address is OK). This exit condition requires the ***[EMSHUT_EXIT_COMM]*** bit to be set. When using this exit option, the ***Manual FET Control (MFC) Delay*** should be set to a minimum of 4 seconds.

In addition to these exit conditions, if the gauge enters EMSHUT (via a push button, for example), it can exit the EMSHUT mode after a shutdown restore timeout defined by the ***Timeout*** parameter. When the timeout is equal to 0, it will not exit EMSHUT mode.

For the case of ***[NR]*** = 0, a battery insertion will also exit the EMERGENCY FET SHUTDOWN mode.

In EMSHUT mode, to detect the voltage level at the PACK pin quickly (even while in SLEEP), the AD conversion will occur every second.

5.7 System Disconnect

The system can signal the gas gauge via the $\overline{\text{PRES}}$ pin to open the CFET and DFET, disconnecting the battery power to the host. This feature will only be enabled for an embedded pack configuration (that is, ***[NR]*** = 1). For a removable battery pack configuration (that is, ***[NR]*** = 0), the original $\overline{\text{PRES}}$ pin function remains as a system-present detection. The internal pullup of the $\overline{\text{PRES}}$ pin is enabled for this feature. Entry to the SYSTEM DISCONNECT mode occurs when the gas gauge detects a high-to-low transition of the $\overline{\text{PRES}}$ pin (default $\overline{\text{PRES}}$ pin debounce of ~1 s is used). The gauge opens the CFET and DFET in SYSTEM DISCONNECT mode. The *OperationStatus()[DISCONN]* = 1.

NOTE: Because the system is shutdown in this mode, the gas gauge enters SLEEP mode after a bus timeout. Regardless if the ***[SLEEPCHG]*** flag sets, the CFET and DFET will remain off in the SYSTEM DISCONNECT mode.

The $\overline{\text{PRES}}$ pin state is sampled in 250-ms intervals. A “low” is detected by receiving four consecutive low samples. The debounce time ranges from 750 ms (if the pin state is changed just before a sample is taken) to 1 s (if the pin state is changed just after a sample is taken). It exits from the SYSTEM DISCONNECT mode when:

- It detects a charger is present AND
- The $\overline{\text{PRES}}$ pin is high.

The gauge then returns to NORMAL mode and closes the CFET and DFET.

Gauging

6.1 Introduction

The bq40z50-R3 measures individual cell voltages, pack voltage, temperature, and current. It determines battery state-of-charge by analyzing individual cell voltages when a certain relax time has passed since the last charge or discharge activity of the battery.

The bq40z50-R3 measures charge and discharge activity by monitoring the voltage across a small-value series sense resistor (1-mΩ typical) between the negative terminal of the cell stack and the negative terminal of the battery pack. The battery state-of-charge is subsequently adjusted during a load or charger application using the integrated charge passed through the battery. The bq40z50-R3 device is capable of supporting a maximum battery pack capacity of 32 Ah. See the *Theory and Implementation of Impedance Track™ Battery Fuel-Gauging Algorithm in bq20zxx Product Family* (SLUA364) for further details.

The default for Impedance Track gauging is *off*. To enable the gauging function, set ***Manufacturing Status[GAUGE_EN]*** = 1. The gauging function will be enabled after a reset or a seal command is set. Alternatively, the *Gauging()* MAC command can be used to turn on and off the gauging function. The *Gauging()* command will take effect immediately and the ***[GAUGE_EN]*** will be updated accordingly.

The *GaugeStatus1()*, *GaugeStatus2()*, and *GaugeStatus3()* commands return various gauging related information that is useful for problem analysis.

6.2 Impedance Track Configuration

Load Mode — During normal operation, the battery-impedance profile compensation of the Impedance Track algorithm can provide more accurate full-charge and remaining state-of-charge information if the typical load type is known. The two selectable options are constant current (***Load Mode*** = 0) and constant power (***Load Mode*** = 1).

Load Select — To compensate for the I × R drop near the end of discharge, the bq40z50-R3 must be configured for the current (or power) that will flow in the future. While it cannot be exactly known, the bq40z50-R3 can use load history, such as the average current of the present discharge, to make a sufficiently accurate prediction.

The bq40z50-R3 can be configured to use several methods of this prediction by setting the ***Load Select*** value. Because this estimate has only a second-order effect on remaining capacity accuracy, different measurement-based methods (methods 0–3 and method 7) result in only minor differences in accuracy. However, methods 4–6, where an estimate is arbitrarily user-assigned, can result in a significant error if a fixed estimate is far from the actual load. For highly variable loads, selection 7 provides the most conservative estimate and is preferable.

	Constant Current (***Load Mode*** = 0)	Constant Power (***Load Mode*** = 1)
0 =	***Avg I Last Run***	***Avg P Last Run***
1 =	Present average discharge current	Present average discharge power
2 =	*Current()*	*Current()* × *Voltage()*
3 =	*AverageCurrent()*	*AverageCurrent()* × average *Voltage()*
4 =	***Design Capacity***/5	***Design Capacity cWh***/5
5 =	*AtRate()* (mA)	*AtRate()* (cW)
6 =	***User Rate-mA***	***User Rate-mW***
7 =	***Max Avg I Last Run*** (default)	***Max Avg P Last Run***

Pulsed Load Compensation and Termination Voltage — To take into account pulsed loads while calculating remaining capacity until ***Term Voltage*** threshold is reached, the bq40z50-R3 monitors not only the average load but also the short load spikes. The maximum voltage deviation during a load spike is continuously updated during discharge and stored in ***Delta Voltage***.

Reserve Battery Capacity — The bq40z50-R3 allows an amount of capacity to be reserved in either mAh (***Reserve Cap-mAh***, ***Load Mode*** = 0) or cWh (***Reserve Cap-cWh***, ***Load Mode*** = 1) units between the point where the *RemainingCapacity()* function reports zero capacity and the absolute minimum battery stack voltage, ***Term Voltage***. This enables a system to report zero energy, but still have enough reserve energy to perform a controlled shutdown or provide an extended sleep period for the host system.

The reserve capacity is compensated at the present discharge rate as selected by ***Load Select***.

No Load Reserve Capacity — The ***PS No Load Res Cap*** threshold is programmed to a value in mAh based on how much capacity to reserve for powering the RTC for a period of time after RSOC is 0%.

Table 6-1. PS No Load Res Cap

Class	Subclass	Name	Format	Size in Bytes	Min	Max	Default	Unit
Power	Shutdown	PS No Load Res Cap	Unsigned Int	2	0	32767	0	mAh

NOTE: There is no requirement to change ***Term Voltage***, and this can remain set to the minimum system operation voltage.

Stack Based and Cell Based Termination — The bq40z50-R3 forces *RemainingCapacity()* to 0 mAh when the battery stack voltage reaches the ***Term Voltage*** for a period of ***Term V Hold Time***. If ***IT Gauging Configuration[CELL_TERM]*** = 1, the battery can terminate based on cell voltage or battery stack voltage. When the cell-based termination is used, the ***Term Min Cell V*** threshold is checked for the termination condition. The cell-based termination can provide an option to enable the gauge to reach 0% before the device triggers CUV for a pack imbalance.

Table 6-2. Term V Hold Time

Class	Subclass	Name	Format	Size in Bytes	Min Value	Max Value	Default Value	Unit
Gas Gauging	IT Cfg	Term V Hold Time	Unsigned Int	1	0	255	1	s

6.3 Gas Gauge Modes

Resistance updates take place only in DISCHARGE mode, while open circuit voltage (OCV) and QMax updates only take place in RELAX mode. If ***Fast Qmax*** is enabled, the Qmax also updates at the end of discharge given a minimum of 37% delta change of charge. Entry and exit of each mode is controlled by data flash parameters in the subclass ***Gas Gauging: Current Thresholds*** section. When the device is determined to be in RELAX mode and OCV is taken, the *GaugingStatus()[REST]* flag is set. In RELAX or DISCHARGE mode, the DSG flag in *BatteryStatus()* is set.

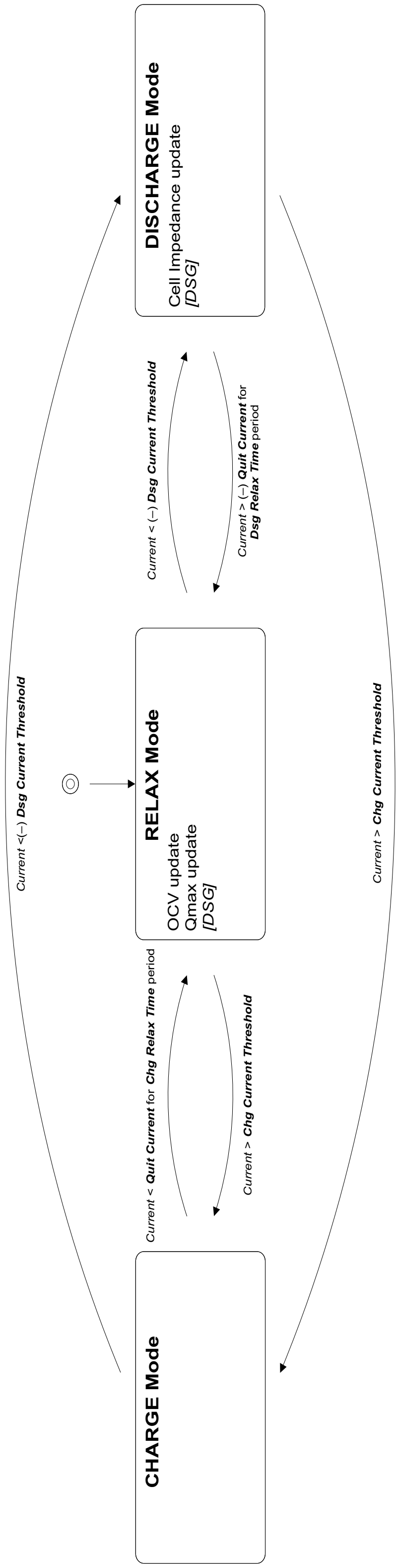


Figure 6-1. Gas Gauge Operating Modes

- CHARGE mode is exited and RELAX mode is entered when current goes below ***Quit Current*** for a period of ***Chg Relax Time***.
- DISCHARGE mode is entered when current goes below ***(–)Dsg Current Threshold***.

- DISCHARGE mode is exited and RELAX mode is entered when current goes above ***(–)Quit Current*** threshold for a period of ***Dsg Relax Time***.
- CHARGE mode is entered when current goes above ***Chg Current Threshold***.

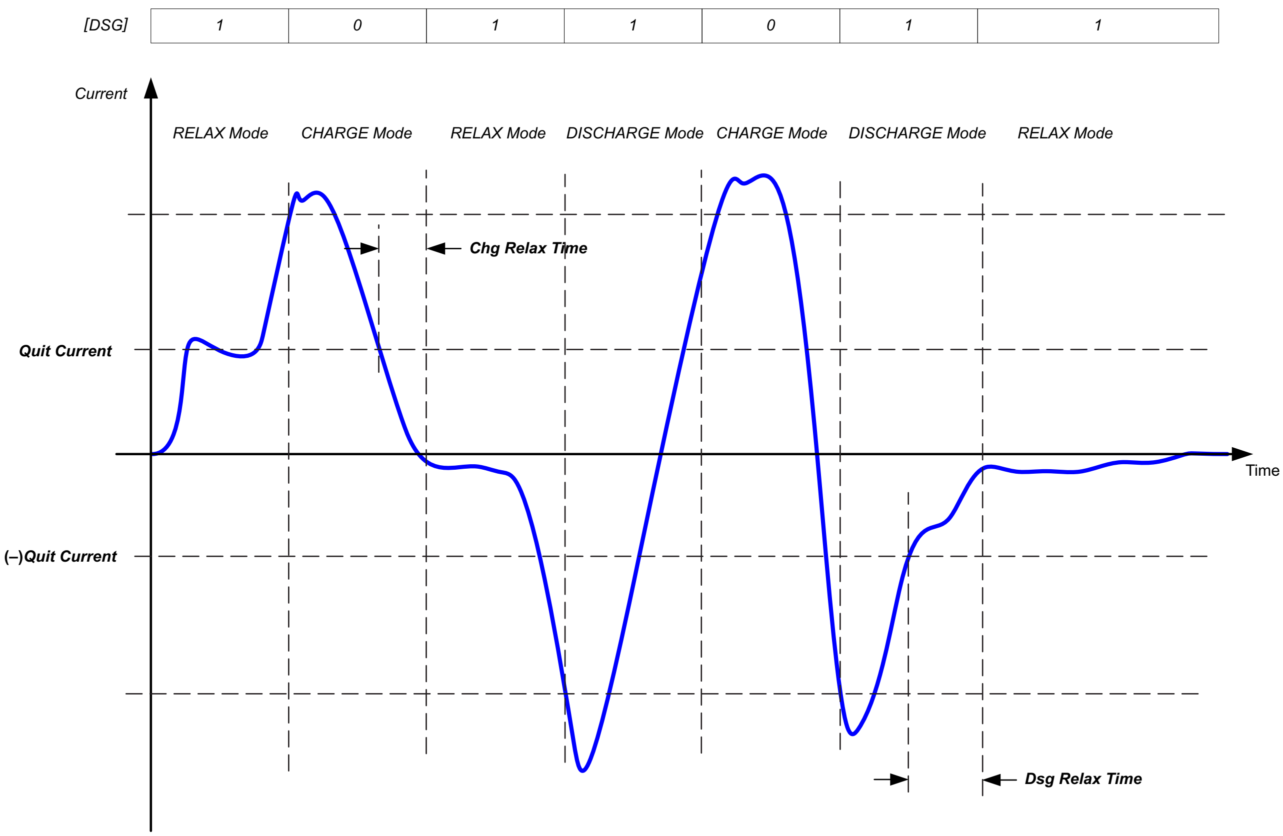


Figure 6-2. Gas Gauge Operating Mode Example

6.4 QMax and Ra

The total battery capacity is found by comparing states of charge before and after charge and discharge with the amount of charge passed. When an applications load is applied, the impedance of each cell is measured by comparing the open circuit voltage (OCV) obtained from a predefined function for present state-of-charge with the measured voltage under load.

Measurements of OCV and charge integration determine chemical state-of-charge and chemical capacity (*QMax*).

The bq40z50-R3 acquires and updates the battery-impedance profile during normal battery usage. It uses this profile, along with state-of-charge and the *QMax* values, to determine *FullChargeCapacity* and *RelativeStateOfCharge* specifically for the present load and temperature. *FullChargeCapacity* reports a capacity or energy available from a fully charged battery reduced by ***Reserve Cap-mAh*** or ***Reserve Cap-cWh*** under the present load and present temperature until voltage reaches the ***Term Voltage***.

6.4.1 QMax Initial Values

The initial ***QMax Pack***, ***QMax Cell 0***, ***QMax Cell 1***, ***QMax Cell 2***, and ***QMax Cell 3*** values should be taken from the cell manufacturers' data sheet multiplied by the number of parallel cells, and are also used for the *DesignCapacity* function value in the ***Design Capacity*** data flash value.

See the *Theory and Implementation of Impedance Track Battery Fuel-Gauging Algorithm in bq20zxx Product Family Application Report* (SLUA364) for further details.

6.4.2 QMax Update Conditions

A QMax update is enabled when gauging is enabled. This is indicated by the *GaugingStatus()[QEN]* flag. The bq40z50-R3 updates the no-load full capacity (QMax) when two open circuit voltage (OCV) readings are taken. These OCV readings are taken when the battery is in a relaxed state before and after charge or discharge activity. A relaxed state is achieved if the battery voltage has a dV/dt of < 4 µV/s. Typically, it takes two hours in a charged state and five hours in a discharged state to ensure that the dV/dt condition is satisfied. If five hours is exceeded, a reading is taken even if the dV/dt condition was not satisfied. The *GaugingStatus()[REST]* flag is set when a valid OCV reading occurs. If a valid DOD0 (taken at the previous QMax update) is available, then QMax will also be updated when a valid charge termination is detected.

The flag is cleared at the exit of a relaxed state. A QMax update is disqualified under the following conditions:

Temperature — If *Temperature()* is outside of the range 10°C to 40°C.

Delta Capacity — If the capacity change between suitable battery rest periods is less than 37%.

Voltage — If *CellVoltage4..1()* is inside a flat voltage region. (See the *Support of Multiple Li-Ion Chemistries with Impedance Track Gas Gauges Application Report* (SLUA372) for the voltage ranges of other chemistries.) This flat region is different with different chemistry. The *GaugingStatus()[OCVFR]* flag indicates if the cell voltage is inside this flat region.

Offset Error — If offset error accumulated during time passed from previous OCV reading exceeds 1% of *Design Capacity*, update is disqualified. Offset error current is calculated as ***CC Deadband*** / sense resistor value.

Several flags in *GaugingStatus()* are helpful to track for QMax update conditions. The *[REST]* flag indicates an OCV is taken in RELAX mode. The *[VOK]* flag indicates the last OCV reading is qualified for the QMax update. The *[VOK]* is set when charge or discharge starts. It clears when the QMax update occurs, when the offset error for a QMax disqualification is met, or when there is a full reset. The *[QMax]* flag will be toggled when the QMax update occurs. *GaugeStatus3()* returns the QMax and DOD (depth of discharge, corresponding to the OCV reading) data.

The bq40z50-R3 device includes a check in which, during discharge, there must be a minimum change in *Voltage()* programmed in ***Min Delta Voltage***. There is also a maximum change set in ***Max Delta Voltage***.

Table 6-3. Min DeltaV

Class	Subclass	Name	Format	Size in Bytes	Min Value	Max Value	Default Value	Unit
Gas Gauging	IT Cfg	Min Delta Voltage	Int	2	–32768	32767	0	mV

Table 6-4. Max DeltaV

Class	Subclass	Name	Format	Min Value	Max Value	Default Value	Unit
Gas Gauging	IT Cfg	Max Delta Voltage	I2	–32768	32767	200	mV

6.4.3 Fast Qmax Update Conditions

The Fast Qmax update conditions are very similar to the QMax update conditions with the following differences:

- Instead of taking two OCV readings for QMax update, a Fast Qmax update requires only one OCV reading AND
- The battery pack should discharge below 10% RSOC.

The differences in requirements allow the Fast Qmax feature to have a QMax update at the end of discharge (given one OCV reading is already available and discharge below 10% RSOC) without a longer relax time after a discharge event. Typically, it can take up to 5 hours in a DISCHARGE state to ensure the dV/dt < 4 µV/s condition is satisfied. The temperature, delta capacity, voltage, and offset error requirements for QMax update are still required for the Fast Qmax update.

This feature is particularly useful for reducing production QMax learning cycle time or for an application that is mostly in charge or discharge stage with infrequent relaxation. Setting ***IT Gauging Configuration[FAST_QMAX_LRN]*** = 1 enables Fast Qmax during production learning only (that is, ***Update Status*** = 6). When setting ***IT Gauging Configuration[FAST_QMAX_FLD]*** = 1, Fast Qmax is enabled when Impedance Track is enabled and ***Update Status*** ≥ 6.

6.4.4 QMax and Fast Qmax Update Boundary Check

The bq40z50-R3 implements a QMax and Fast Qmax check prior to saving the value to data flash. This improves the robustness of the QMax update in case of potential QMax corruption during the update process.

The verifications are as follows:

1. Verify that the updating QMax or Fast Qmax value is within ***Qmax Delta Percent***, which is the maximum allowed QMax change for each update. If the updating value is outside of this data flash parameter, the bq40z50-R3 caps the change to ***Qmax Delta Percent*** of the ***Design Capacity***.
2. Bound the absolute QMax value, ***Qmax Upper Bound***. This is the maximum allowed QMax value over the lifetime of the pack.
3. Ensure that QMax is greater than 0 before saving to data flash.

6.4.5 Ra Table Initial Values

The Ra table is part of the impedance profile that updates during discharge when gauging is enabled. The initial ***Cell 0 R_a0...14***, ***Cell 1 R_a0...14***, ***Cell 2 R_a0...14***, ***Cell 3 R_a0...14*** values should be programmed by selecting the correct chemistry data during data flash configuration. A chemistry database is constantly updating, and can be downloaded from the Gas Gauge Chemistry Updater product web page (http://www.ti.com/tool/gasgaugechem-sw). The initial ***xCell 0 R_a0...14***, ***xCell 1 R_a0...14***, ***xCell 2 R_a0...14***, ***xCell 3 R_a0...14*** values are a copy of the non-x data set. Two sets of Ra tables are used alternatively when gauging is enabled to prevent wearing out the data flash.

The ***Cell 0 R_a Flag***, ***Cell 1 R_a Flag***, ***Cell 2 R_a Flag***, ***Cell 3 R_a Flag*** and the ***xCell 0 R_a Flag***, ***xCell 1 R_a Flag***, ***xCell 2 R_a Flag***, ***xCell 3 R_a Flag*** indicate the validity of the cell impedance table for each cell.

NOTE: FW updates these values: It is not recommended to change them manually.

High Byte		Low Byte	
0x00	Cell impedance and QMax updated	0x00	The table is not used and QMax updated.
0x05	RELAX mode and QMax update in progress	0x05	RSVD
0x55	DISCHARGE mode and cell impedance updated	0x55	The table is used.
0xFF	Cell impedance never updated	0xFF	A Fast Qmax update without OCV read will also clear the R_DIS flag. The table is never used, no QMax or cell impedance update.

6.4.6 Ra Table Update Conditions

The impedance is different across different DOD states. Each cell has 15 Ra grid points presenting the impedance from 0%–100% DOD. In general, the Ra table is updated during discharge. The *GaugingStatus()[RX]* flag will toggle when the Ra grid point is updated. The Ra update is disabled if any of the following conditions are met. The *GaugingStatus()[R_DIS]* is set to indicate the Ra update is disabled.

- During the optimization cycle, the Ra update is disabled until QMax is updated (that is, Ra will not be updated if ***Update Status*** = 4) OR
- Ra update is disabled if the charge accumulation error > 2% of ***Design Capacity*** OR
- During a discharge, a bad Ra value is calculated:
  - A negative Ra is calculated or
  - A bad RaScale value is calculated.

A valid OCV reading during RELAX mode or a Fast Qmax update without an OCV read will clear the *[R_DIS]* flag.

6.4.7 Application of Resistance Scaling

As a part of the Impedance Track algorithm, the bq40z50-R3 calculates an RScale value. The RScale value can be applied in two ways:

- When DOD_RSCALE_EN = 0 in ***IT Gauging Configuration*** and when the new RScale is calculated, it is applied across all DODs.
- When DOD_RSCALE_EN = 1 in ***IT Gauging Configuration***, the new RScale is only applied to DODs higher than the DOD where the new RScale was calculated.

This can prevent early termination of certain simulations, as the RScale will not be applied in computing voltages at DODs below RScale DOD. As a result, sensitivity to passed charge error is drastically decreased for low resistance and high resistance cells.

6.5 FullChargeCapacity(FCC), RemainingCapacity(RemCap), and RelativeStateOfCharge(RSOC)

The Impedance Track algorithm applies QMax, impedance, temperature, voltage, and current data to predict the runtime *FullChargeCapacity()*, *RemainingCapacity()*, and *RelativeStateOfCharge()*. These values are updated if any of the following conditions are met, reflecting the battery capacity at real time.

- QMax update occurs
- Ra update occurs
- At onset of charge and discharge
- At exit of discharge
- Every 5 hours in RELAX mode
- If temperature changes more than 5°C

6.6 Impedance Track Configuration Options

The bq40z50-R3 provides several Impedance Track (IT) configuration options to fine-tune the gauging performance. These configurations can be turned on or off through the corresponding flags in ***SBS Gauging Configuration*** or ***IT Gauging Configuration***.

[LOCK0]: After a discharge event, cell voltage will usually recover to a slightly higher voltage during RELAX state. A new OCV reading during this time can result in a slightly higher state-of-charge. This flag provides an option to keep *RemainingCapacity()* and *RelativeStateOfCharge()* from jumping back during relaxation after 0% and FD are reached during discharge.

[RSOC_HOLD]: An IT simulation will run at the onset of discharge. If charge terminates at a low temperature and a discharge occurs at a higher temperature, the difference in temperature could cause a small rise of RSOC for a short period of time at the beginning of discharge. This flag option prevents RSOC rises during discharge. RSOC will be held until the calculated value falls below the actual state.

[RSOC_HOLD] should not be used when ***[SMOOTH]*** is set.

[RSOCL]: When set, RSOC will be held at 99% until charge termination is detected. When the device exits reset and ***[RSOCL]*** = 1, then even if the battery is fully charged (***[FC]*** = 1), only a value of ≤ 99% is reported by *RelativeStateOfCharge()* until a valid charge termination is detected. See Section 4.6 for more details.

[RFACTSTEP]: The gauge keeps track of an Ra factor of the (old Ra)/(new Ra) during the Ra update. This factor is used for Ra scaling. It is limited to three max. During an Ra update, if (old Ra)/(new Ra) is > 3, the gauge can take on two different actions based on the setting of this flag.

If this flag is set (default), the gauge allows Ra to update once using the max factor of 3, then disables the Ra update. If this flag is set to 0, the gauge will not update Ra and also disables the Ra update. It is recommended to keep the default setting.

[OCVFR]: An OCV reading is taken when a dV/dt condition is met. This is not the case if charging stops within the flat voltage region.

By default, this flag is set. The bq40z50-R3 device will take a 48-hour wait before taking an OCV reading if charge stops below the FlatVoltMax. A discharge will not cancel this 48-hour wait. The 48-hour wait will only be cleared if charging stops above the FlatVoltMax level. Setting this flag to 0 removes the 48-hour wait requirement, and OCV is taken when the dV/dt condition is met. Removing the 48-hour requirement can be useful sometimes to reduce test time during evaluation.

[DOD0EW]: DOD0 readings have an associated error based on the elapsed time since the reading, the conditions at the time of the reading (reset, charge termination, and so on), the temperature, and the amount of relax time at the time of the reading, among others. This flag provides an option to take into account both the previous and new calculated DOD0, which are weighted according to their respective accuracies. This can result in improved accuracy and in a reduction of RSOC jumps after relaxation.

[LFP_RELAX]: This is an option for LiFePO4 chemistry. This flag can be enabled even if non-LiFePO4 chemistry is programmed. The bq40z50-R3 device will check for the chemistry ID (that is, ChemID = 4xx series) before activating this function.

LiFePO4 chemistry has a unique slow relaxation time near full charge. Detailed, in-house test data suggests that the relaxation after a full charge takes a few days to settle. The slow decaying voltage causes RSOC to continue to drop every 5 hours. Depending on the full charge taper current, the fully relaxed voltage could be close to or even below FlatVoltMax. For the chemID 4xx (LiFePO4) series, the condition to exit the long RELAX mode is if the pack had previously charged to full or near full state, and then either a significant long relaxation or a non-trivial discharge has happened, such that when in relaxation, the OCV < ***FlatVoltMax***.

The QMax update is disabled because DOD will not be taken as long as it is in LFP_relax mode. By the time the gas gauge exits the LFP_relax mode, the OCV is already in the flat zone. Therefore, the QMax update takes an alternative approach: Once full charge occurs (***[FC]*** bit set), DOD0=Dod_at_EOC is automatically assigned and valid for a QMax update. ***[VOK]*** is set if there is no QMax update. If QMax is updated, ***[VOK]*** is cleared. The DOD error as a result of this action is zero or negligible because in the LiFePO4 table, OCV voltage corresponding to DOD= 0 is much lower.

[Fast_QMAX_LRN] and ***[Fast_QMAX_FLD]***: The first flag enables Fast Qmax during the learning cycle when ***Update Status*** = 06. The second flag enables Fast Qmax in the field when ***Update Status*** ≥ 06. See Section 6.4.3 for more details.

[RSOC_CONV]: This function is also called fast scaling. It is an option to address the convergence of RSOC to 0% at a low temperature and a very high rate of discharge. Under such conditions, it is possible to have a drop of RSOC to 0%, especially if the termination voltage is reached at the DOD region with a higher Ra grid interval. To account for the error caused by the high granularity of the impedance grid interval, the ***[RSOC_CONV]***, when enabled, applies a scale factor to impedance, allowing more frequent impedance data updates used for RemCap simulation leading up to 0% RSOC.

If ***[RSOC_CONV]*** is enabled, it is recommended to start this function around the knee region of the discharge curve. This is usually around 10% of RSOC or around 3.3 V–3.5 V. This function will check for the cell voltage and RSOC status and start the function when either condition is met. The RSOC and cell voltage setting can be configured through ***Fast Scale Start SOC*** or ***Term Voltage Delta***.

[FF_NEAR_EDV]: Fast Filter Near EDV. If this flag is set, the gauge applies an alternative filter, ***Near EDV Ra Param Filter***, for an Ra update in the fast scaling region (starting around 10% RSOC). This flag should be kept to 1 as default. When this flag is 0, the gauge uses the regular Ra filter, ***Resistance Parameter Filter***. Both of the DF filters should not be changed from the default.

[SMOOTH]: A change in temperature or current rate can cause a significant change in remaining capacity (RemCap) and full charge capacity (FCC), resulting in a jump or drop in the Relative State-of-Charge (RSOC). This function provides an option to prevent an RSOC jump or drop during charge and discharge.

If a jump or drop of RSOC occurs, the device examines the amount of RSOC jump or drop versus the expected end point (that is, the charge termination for the charging condition or the EDV for the discharge condition) and automatically smooths the change of RSOC, and always converges with the filtered (or smoothed) value to the actual charge termination or EDV point. The actual and filtered values are always available. The ***[SMOOTH]*** flag selects whether actual or filtered values are returned by the SBS commands.

[RELAX_JUMP_OK] and ***[RELAX_SMOOTH_OK]***: When the battery enters RELAX mode from CHARGE or DISCHARGE mode, the transient voltage may change to RSOC as the battery goes into its RELAX state. Once the battery is in RELAX mode, a change in temperature or self-discharge may also cause a change in RSOC.

If ***[RELAX_JUMP_OK]*** = 1, this allows the RSOC jump to occur during RELAX mode. Otherwise, RSOC holds constant during RELAX mode and any RSOC jump will be passed into the onset of the charge or discharge phase.

If ***[RELAX_SMOOTH_OK]*** = 1, this allows the amount of the RSOC jump to be smoothed out over a period of ***Smooth Relax Time***. Otherwise, the additional RSOC jump amount will be passed into the onset of charge or discharge phase.

If both flags are set, the ***[RELAX_JUMP_OK]*** = 1 takes higher priority and the RSOC jump is allowed during RELAX mode.

[TDELAV]: This flag determines how the ***Delta Voltage*** is calculated. By setting this flag, the gauge will calculate ***Delta Voltage*** that corresponds to the power spike defined in ***Min Turbo Power***. This flag must be set to 1 if TURBO BOOST mode is used. Otherwise, leaving this flag cleared as default enables the gauge to calculate ***Delta Voltage*** by using the maximal difference between instantaneous and average voltage.

[CELL_TERM]: This flag provides an option to have a cell voltage based discharge termination. If the minimum cell voltage reaches ***Term Min Cell V***, *RemainingCapacity()* will be forced to 0 mAh. For more details, see the *Pack Based and Cell Based Termination* section in Section 6.2.

[CSYNC]: This flag, if set, will synchronize *RemainingCapacity()* to *FullChargeCapacity()* at valid charge termination.

[CCT]: This flag provides an option to use *FullChargeCapacity()* (***[CCT]*** = 1) or *DesignCapacity()* (***[CCT]*** = 0) for cycle count threshold calculation. If *FullChargeCapacity()* is selected for cycle count threshold calculation, the minimum cycle count threshold is always 10% of ***Design Capacity***. This is to avoid any erroneous cycle count increment caused by extremely low *FullChargeCapacity()*.

[CHG_100_SMOOTH_OK]: This handles smoothing in the charge direction to 100%. For jumps to 100% during charge, this feature uses the taper termination detection logic to predict when charge termination will occur. The taper termination logic requires two consecutive 40-s windows that meet all taper conditions. After the first 40-s window is satisfied, time-based smoothing will be initiated, smoothing RemCap to smoothed FCC over the next 40-s window. It is important to note that smoothed RemCap will converge to smoothed FCC and not True RemCap.

[TS1, TS0]: These two flags together provide an option to select which one of the individual temperature sensors (TS 1…4) is used by the IT algorithm.

[DSG_0_SMOOTH_OK]: Allows smoothing in the discharge direction when there is a jump to 0%. Set this flag to prevent jumps to 0% during discharge, two DF parameters are used: ***Term Smooth Start Cell V Delta*** and ***Term Smooth Time***. Once battery stack voltage is below ***Term Smooth Start Cell V Delta*** and discharging, time-based smoothing is initiated. This smooths RemCap to 0 mAh over the next ***Term Smooth Time*** seconds. ***Term Smooth Start Cell V Delta*** is a per cell voltage delta. This value is multiplied by the number of cells, added to ***Terminate Voltage***, and checked against *Voltage()*. Smoothing will continue to 0% unless charging starts (even in RELAX mode).

To assure that the gauge reports 0% in low voltage situations, the DF ***Term Smooth Final Cell V Delta*** is used. This value is multiplied by the number of cells, subtracted from ***Terminate Voltage***, and checked against *Voltage()*. Once voltage passes this threshold, 0% will be forced even if smoothing was not completed.

NOTE: ***Term Smooth Final Cell V Delta*** can be disabled by setting to 0 and is typically expected to be set low enough to enable the system to shut down properly (without brownout).

6.7 State of Health

The bq40z50-R3 implements a new state-of-health (SOH) function. Previously, the SOH of a battery was typically represented by the actual runtime ***FullChargeCapacity***/***Design Capacity*** (or FCC/DC). Using the runtime FCC, however, was not a very good representation for the state-of-health because the runtime FCC reflects the usable capacity under load. A high current load reduces the runtime FCC. If using just the FCC/DC calculation for SOH, the SOH under high load will be worse than the SOH under typical load. However, a smaller usable capacity at high load does not mean the SOH of a battery is degraded. This is the same when FCC is reduced at a lower temperature.

The bq40z50-R3 implementation of state-of-health addresses these issues. It provides the SOH of the battery through an SBS command, *SOH()*. The *SOH()* is calculated using the FCC simulated at 25°C with current specified by ***SOH Load Rate***. The ***SOH Load Rate*** can be set to the typical current of the application, and it is specified in hour-rate (that is, ***Design Capacity***/***SOH Load Rate*** will be the current used for the SOH simulation). This data flash setting is used for *SOH()* calculation only. This SOH FCC is updated at the same time ASOC and RSOC are updated. Since this implementation removes the variation of current or temperature, it is a better representation of a battery's state-of-health. The SOH FCC is available on MAC *StateofHealth()*.

6.8 TURBO Mode 3.0

A system with TURBO Mode 3.0 applies short high-power load pulses (for example, up to 4 C-rate for as long as 10 ms). In addition, 10-s load pulses of 2 C-rate can occur in some cases prior to 10-ms pulses, resulting in a combined effect during the turbo boost operation. The 10-s pulse support is new in TURBO Mode 3.0 (relative to TURBO Mode 1.0). Additionally, TURBO Mode 3.0 provides Rhf effective and Vload parameters for the host to use to make power-level decisions.

These high-power pulses may drop down battery voltage. If the battery voltage drops below the ***Shutdown Voltage***, the system will shut down. To avoid shutting down the system during turbo boost operation, the system should never apply a pulse that would cause the system voltage to drop below the termination voltage (or exceed the recommended current threshold) that could result in a shutdown, reducing the total available run time.

The bq40z50-R3 TURBO Mode 3.0 helps the system to adjust the power level by providing information about maximal power, depending on the battery state-of-charge, temperature, and present battery impedance. In particular, the gauge informs the system about the power level above which would cause the system voltage to drop below termination after the 10-s pulse, called the sustained peak power (SPP). In addition, the gauge also reports the maximum power for the combined 10-s and 10-ms pulses called the maximum peak power (MPP).

The SPP is computed using a 10-s effective resistance that is temperature- and DOD-dependent. The computation of MPP uses the high-frequency resistance along with the 10-s effective resistance. Both of these resistances are chemistry-specific. In addition, the ***Pack Resistance*** and ***System Resistance*** are important parameters used in the calculation of these two powers. The computed TURBO mode currents, the sustained peak current, and the maximum peak current are capped to their respective maximum discharge rates. Depending on how often the system polls the peak power data and how fast the system can switch to a lower power mode, it is possible to exceed the reported peak power levels during the present power consumption. To avoid any system shutdown, the gauge provides a *Reserve Energy %* setting that can serve as a buffer to ensure there is available energy at the present average discharge rate. These calculations occur on the cell level using ***Term Min Cell V***, on the pack level using ***Term Voltage***, and on the system level using ***Min System Voltage***, ***Pack Resistance***, and ***System Resistance***—with the most conservative prediction reported.

NOTE: ***Min System Voltage*** should be set lower than ***Term Voltage***.

6.9 Battery Trip Point (BTP)

Required for WIN8 OS, the battery trip point (BTP) feature indicates when the RSOC of a battery pack has depleted to a certain value set in a DF register.

The BTP feature allows a host to program two capacity-based thresholds that govern the triggering of a BTP interrupt on the BTP_INT pin and the setting or clearing of the *OperationStatus()[BTP_INT]* on the basis of *RemainingCapacity()*. The interrupt is enabled or disabled via ***Settings.Configuration.IO Config[BTP_EN]***. Similarly, the polarity of the interrupt is configurable based on the value set in ***Settings.Configuration.IO Config[BTP_POL]***.

- *OperationStatus()[BTP_INT]* is set when:
  - Current > 0 and RemCap > “clear” threshold (“charge set threshold”). This threshold is initialized at reset from ***Settings.BTP.Init Charge Set***.
  - Current ≤ 0 and RemCap < “set” threshold (“discharge set threshold”). This threshold is initialized at reset from ***Settings.BTP.Init Discharge Set***.
- When *OperationStatus()[BTP_INT]* is set, if ***Settings.Configuration.IO Config[BTP_EN]*** is set, then the BTP_INT pin output is asserted.
  - If ***Settings.Configuration.IO Config[BTP_POL]*** is set, it will assert high; otherwise, it will assert low.
- When either *BTPDischargeSet()* or *BTPChargeSet()* commands are received, *OperationStatus()[BTP_INT]* will clear and the pin will be deasserted. The new threshold is written to either *BTPDischargeSet()* or *BTPChargeSet()*.
- At reset, the pin is set to the deasserted state.
  - If ***[BTP_POL]*** is changed, one of the BTP commands must be reset or sent to “clear" the state.

6.10 Cell Interconnect IR Compensation

The ***Cell 1..4 Interconnect Resistance*** settings (user-measured values) compensate cell voltages for the related IR drop of the cell interconnect wire resistance.

6.11 RSOC Rounding Option

By default, if there is an RSOC of 20.1 through 20.9, then the RSOC becomes 21 (ceiling function). However, the following shows how the RSOC rounding feature works when enabled by setting ***[RSOC_RND_OFF]*** = 1 (default is 0) in the ***SBS Gauging Configuration*** register:

Round-off applies to charging and discharging between an RSOC 0% to 99% if, for example:

There is an RSOC of 20.1 through 20.4, then the RSOC becomes 20 (round off).

There is an RSOC of 20.5 through 20.9, then the RSOC becomes 21 (round off).

Round-down applies for charging and discharging between an RSOC of 99% to 99.9% if:

There is an RSOC of 99.1 or 99.9, then the RSOC becomes 99 (round down).

In charge, RSOC is set to 100% only when FC is set.

6.12 RSOC 1% Hold

When ***[1PERCENT_HOLD]*** is set, RSOC is prevented from going below 1% until ***Terminate Voltage*** is detected.

6.13 Accumulated Charge Measurement

The bq40z50-R3 device includes an accumulated charge function that measures the integrated current passed in or out of the battery. This function can be used to generate an alert to the host when a programmable threshold of accumulated charge is achieved.

The device also integrates the elapsed time since the current integration began, assuming the timer has not been interrupted by a power cycle or put into SHUTDOWN mode. This time is read using the command *AccumulatedTimeCharge()*. If an event has occurred that interrupted the timer, the value of *AccumulatedTimeCharge()* will be fixed unchanging at 0 until the integration is reset.

The current and time integration is started at initial power up or upon issue of the *AccumulationStart()* command. The current and time integration is stopped upon issue of the *AccumulationStop()* command. The current and time integration is reset at initial power up or upon issue of the *AccumulationReset()* command.

While the battery is DISCHARGING, then the current integration counter decreases. If the battery starts CHARGING then the current integration counter increases. The integrated charge value in mAh (or cWh if *BatteryMode()[CAPM]* = 1) and the elapsed time (which does not decrease in value) can be read by the host using the command *AccumulatedTimeCharge()*.

The Accumulated Charge calculation uses the current measured across the sense resistor and, similar to the coulomb counter integration, ignores currents below a programmed level controlled by ***CC Deadband***. In periods when the bq40z50-R3 device is in SLEEP mode, the Accumulated Charge integration includes an estimate of the charge integrated based on analysis of the periodic measured current if ***[SLP_ACCUM]*** is enabled.

The current integration can also be limited to only include positive (charging) currents, only negative (discharging) currents, or both, through setting the ***[ACCHG_EN]*** and ***[ACDSG_EN]*** configuration bits. If both ***[ACCHG_EN]*** and ***[ACDSG_EN]*** are cleared, then the timer is halted. These bits can be set using the *AccumulationChargeEnable()* and *AccumulationDischargeEnable()* commands.

The user can set thresholds to alert the host when accumulated charge reaches a particular level in both the charge (positive) and discharge (negative) directions. These thresholds are set by ***AccumulationChargeThreshold*** and ***AccumulationDischargeThreshold***, which can be changed in SEALED mode with *AccumulationChargeThreshold()* and *AccumulationDischargeThreshold()*. Setting one or both of these to zero will disable the associated threshold.

AccumulatedTimeCharge() does not reset when a threshold is reached, the data is only reset by the host using the *AccumulationReset()* command. When a threshold is passed, a flag is set in *OperationStatus()[ACTHR]*.

Due to the current integration and timer information being stored in RAM, any power cycle of the device or putting the device into SHUTDOWN will result in the loss of *AccumulatedTimeCharge()* data.

Cell Balancing

7.1 Introduction

The bq40z50-R3 can determine the chemical state-of-charge of each cell using the Impedance Track algorithm. The cell balancing algorithm used in the device decreases the differences in imbalanced cells in a fully charged state gradually, which prevents fully charged cells from becoming overcharged, causing excessive degradation. This increases overall pack energy by preventing premature charge termination.

The algorithm determines the amount of charge needed to fully charge each cell. There is a bypass FET in parallel with each cell connected to the gas gauge. The FET is enabled for each cell with a charge greater than the lowest charged cell to reduce charge current through those cells. Each FET is enabled for a precalculated time as calculated by the cell balancing algorithm. When any bypass FET is turned on, then the *OperationStatus()[CB]* operation status flag is set; otherwise, the *[CB]* flag is cleared.

The gas gauge balances the cells by balancing the SOC difference. Thus, a field updated QMax (***Update Status*** = 0E) is required prior to any attempt of cell balance time calculation. This ensures the accurate SOC delta is calculated for the cell balancing operation. If the Qmax update has only occurred once (***Update Status*** = 06), then the gauge will only attempt to calculate the cell balance time if a fully charged state is reached, *GaugingStatus()[FC]* = 1.

The cell balancing is enabled if ***Settings:Balancing Configuration [CB]*** = 1. The cell balancing at rest can be enabled separately by setting ***Balancing Configuration [CBR]*** = 1. If ***Settings:Balancing Configuration [CB]*** = 0, both cell balancing at charging and at rest are disabled.

The cell balancing at rest can be configured by determining the data flash ***Min Start Balance Delta***, ***Relax Balance Interval***, and ***Min RSOC for Balancing***. For the data flash setting description, see Section 16.5.13. The gas gauge balances cells by bypassing the energy. It is recommended to perform cell balancing at rest when there is capacity in the battery pack.

7.2 Cell Balancing Setup

The bq40z50-R3 is required to be in RELAX mode before it can determine if the cells are unbalanced and how much balancing is required. The bq40z50-R3 enters RELAX mode when:

|*Current()*|< ***Quit Current*** for at least ***Dsg Relax Time*** when coming from DISCHARGE mode or ***Chg Relax Time*** when coming from CHARGE mode.

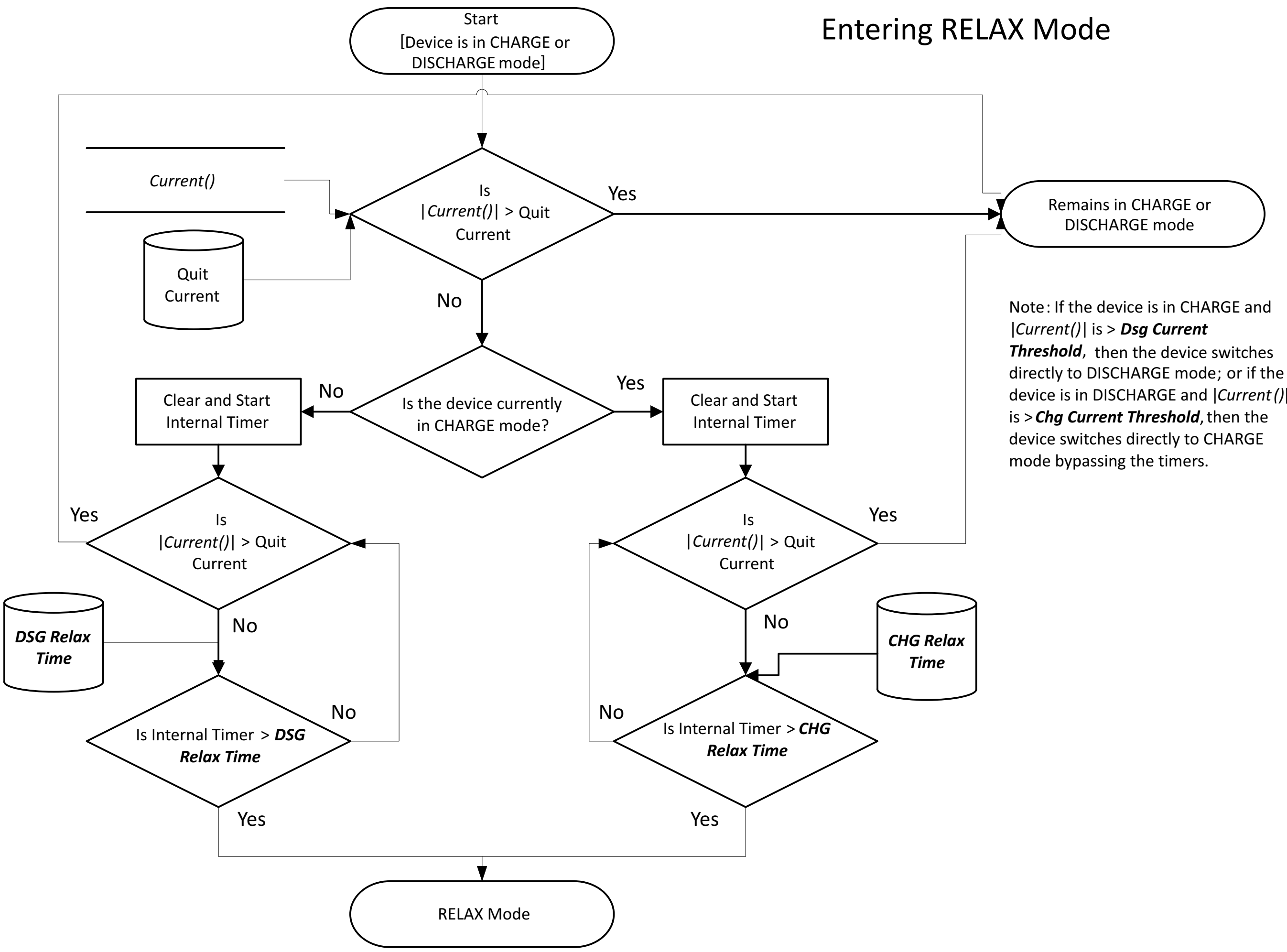


Figure 7-1. Entering CHARGE or RELAX Mode

Once in RELAX mode, the bq40z50-R3 will take an OCV measurement after one of the following events occurs:

1. A dV/dt condition of < 4 µV/s is satisfied,
2. Five hours from when |*Current()*| < ***Quit Current***,
3. Upon gas gauge reset,
4. An IT Enable command is issued.

The determination of when to update the OCV data is part of the normal Impedance Track algorithm and is not specific to the cell balancing algorithm.

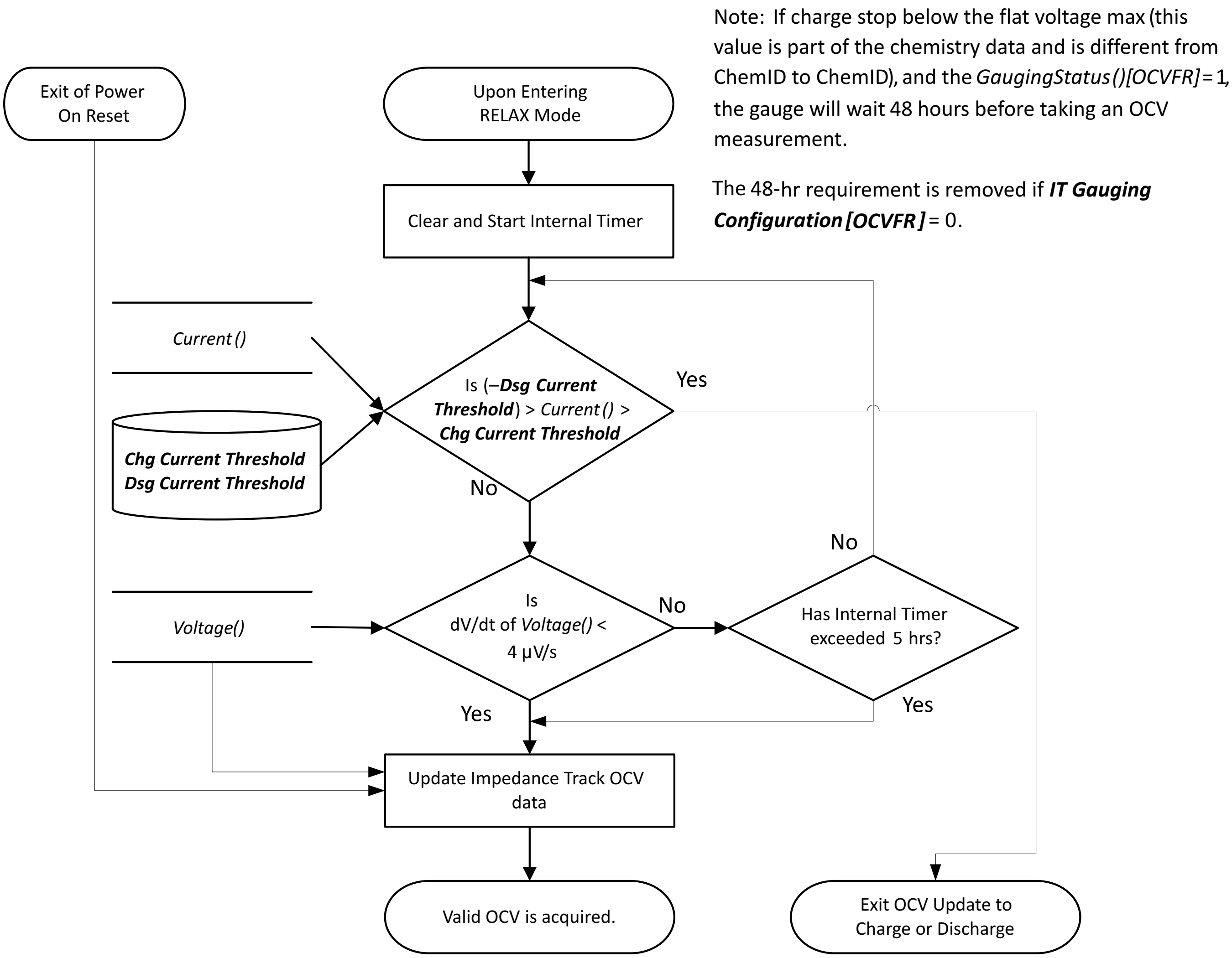


Figure 7-2. OCV Measurement

The bq40z50-R3 then calculates the amount of charge difference between cells with a higher state-of-charge than the lowest cell SOC. The value, dQ, is determined for each cell based by converting the measured OCV to Depth-of-Discharge (DOD) percentages using a temperature-compensated DOD versus OCV table lookup table. If the measured OCV does not coincide with a specific table entry, then the DOD value is linearly interpolated from the two adjacent DODs of the respective table adjacent OCVs.

The delta in DOD% between each cell and the cell of lowest SOC is multiplied by the respective cells QMax to create dQ: for example, dQ = CellnDOD – CellLOWEST_SOC DOD × CellnQMax (mAh).

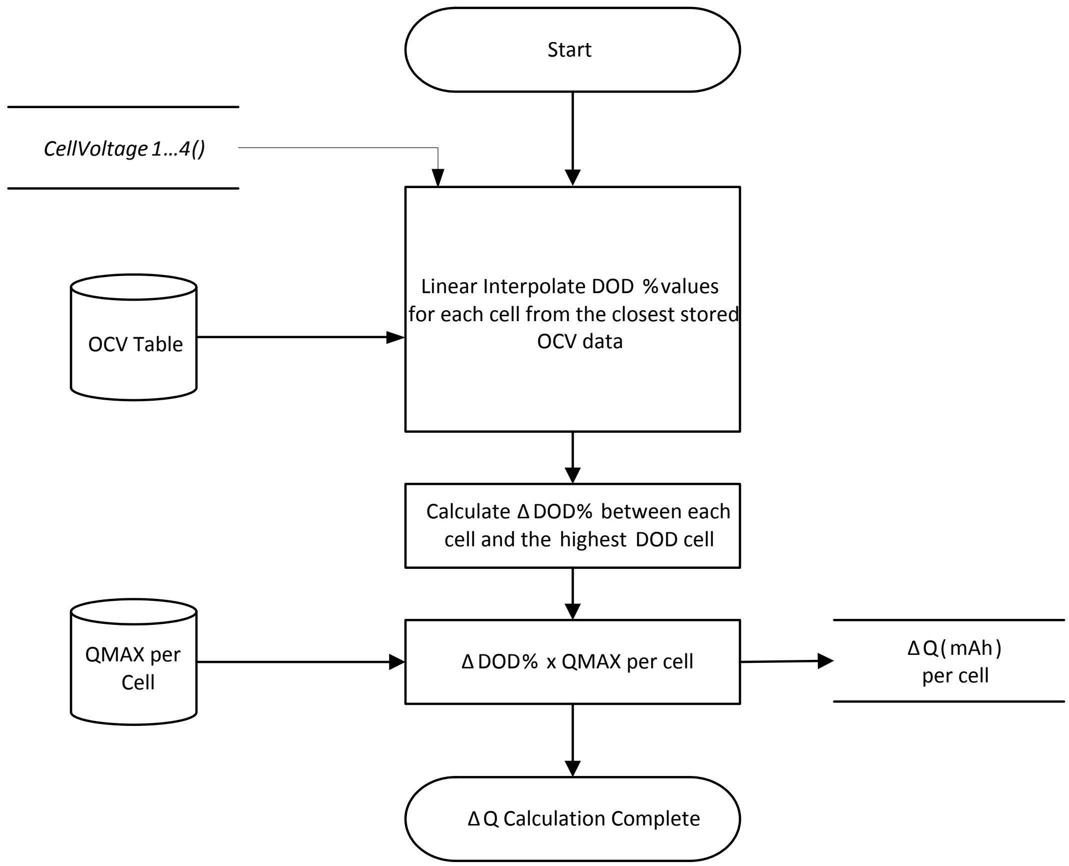


Figure 7-3. ΔQ Calculation

The bq40z50-R3 calculates the required balancing time using dQ and ***Bal Time/mAh Cell 1*** (for Cell 1) or Bal Time/mAh Cell 2–4 (for cells 2–4). The values of ***Bal Time/mAh Cell 1*** and ***Bal Time/mAh Cell 2–4*** are fixed values determined based on key system factors and are calculated by:

Internal Cell Balancing:

$$\textit{Balance Time per mAh Cell } 1 = \frac{3600 \textit{ mAs} \times (\textit{RVCx} + \textit{Rcb})}{\textit{Vcell} \times \textit{Duty}}$$

$$\textit{Balance Time per mAh Cell } 2-4 = \frac{3600 \textit{ mAs} \times (2 \times \textit{RVCx} + \textit{Rcb})}{\textit{Vcell} \times \textit{Duty}}$$

External Cell Balancing:

$$\textit{Balance Time per mAh Cell } 1 = \frac{3600 \textit{ mAs} \times (\textit{RVCx} + \textit{Rcb}) \,||\, \textit{Rext}}{\textit{Vcell} \times \textit{Duty}}$$

$$\textit{Balance Time per mAh Cell } 2-4 = \frac{3600 \textit{ mAs} \times (2 \times \textit{RVCx} + \textit{Rcb}) \,||\, \textit{Rext}}{\textit{Vcell} \times \textit{Duty}}$$

Where:

V_{CELL} = average cell voltage (for example, 3700 mV for most chemistries)

RVCx = resistor value in series to VCx input (for example, 100 Ω, based on the reference schematic)

R_{cb} = cell balancing FET R_{dson}, which is 200 Ω (Max)

DUTY = cell balancing duty cycle, which is 75% typ

The cell balancing time for each cell to be balanced is calculated by: dQCelln × ***Bal Time/mAh Cell 1*** for Cell 1 or and dQCelln × ***Bal Time/mAh Cell 2–4*** for Cell 2–4. The cell balancing time is stored in the 16-bit RAM register ***CellnBalanceTimer***, providing a maximum calculated time of 65535 s (or 18.2 hrs). This update only occurs if a valid QMax update has been made; otherwise, they are all set to 0.

7.3 Balancing Multiple Cells

The bq40z50-R3 can balance multiple cells simultaneously if internal cell balancing is selected, ***Balancing Configuration[CBM]*** = 0.

If external cell balancing is selected, ***[CBM]*** = 1, the gauge will perform a rotation of cell balancing with only one cell to be balanced at a time, starting on the cell with highest dQ. For example, at time 0, Cell 1 has the highest dQ while Cell 2 has the second highest dQ on a 3-series pack. Cell balancing will start to balance Cell 1 first. As time progresses, the dQ in the Cell 1 reduces, and Cell 2 becomes the cell with the highest dQ. The gauge then switches to balance Cell 2. The cell balancing rotation between Cell 1 and Cell 2 continues until all the cells are balanced.

7.4 Cell Balancing Operation

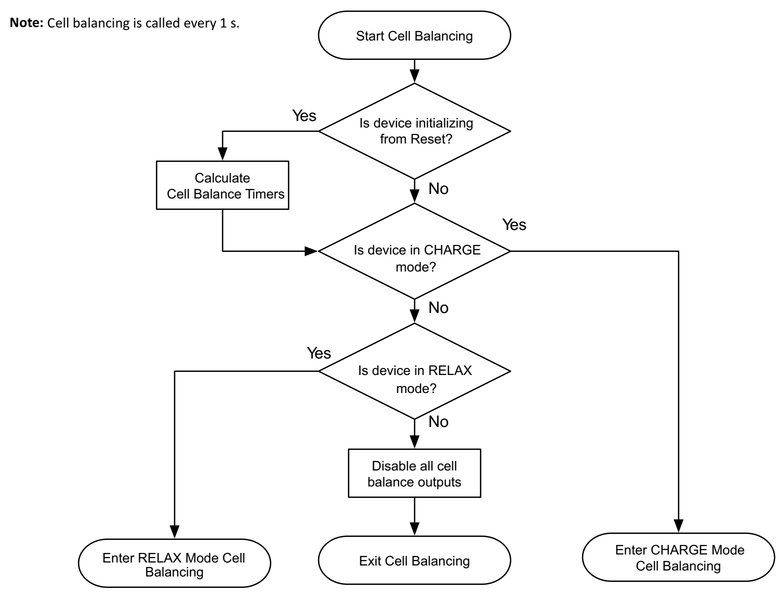


Figure 7-4. Cell Balance Mode Detection

The bq40z50-R3 calls the cell balancing algorithm every 1 s during normal operation. Cell balancing is not called when the device is in SLEEP mode. All algorithm decisions are made on this same 1-s timer.

In RELAX mode, if cell balancing at rest is enabled, ***Balancing Configuration[CBR]*** = 1, the gauge will verify if the dv/dt condition is met at the entry of the RELAX mode. If so, then the cell balance at rest will start when all of the conditions below are met:

- Any of the precalculated cell balance timer is non-zero AND
- *RelativeStateofCharge()* > ***Min RSOC for Balancing***

The gauge will attempt to recalculate the cell balancing time in RELAX mode every ***Relax Balance Interval***. The cell balancing time is updated if the conditions below are met:

- The Relax Balance Interval has passed AND
- A OCV measurement is taken AND
- The max cell voltage delta > ***Min Start Balance Delta***

On exit of the RELAX mode, cell balancing time is recalculated as long as a valid OCV update is available.

NOTE: Cell balancing is paused during OCV measurement.

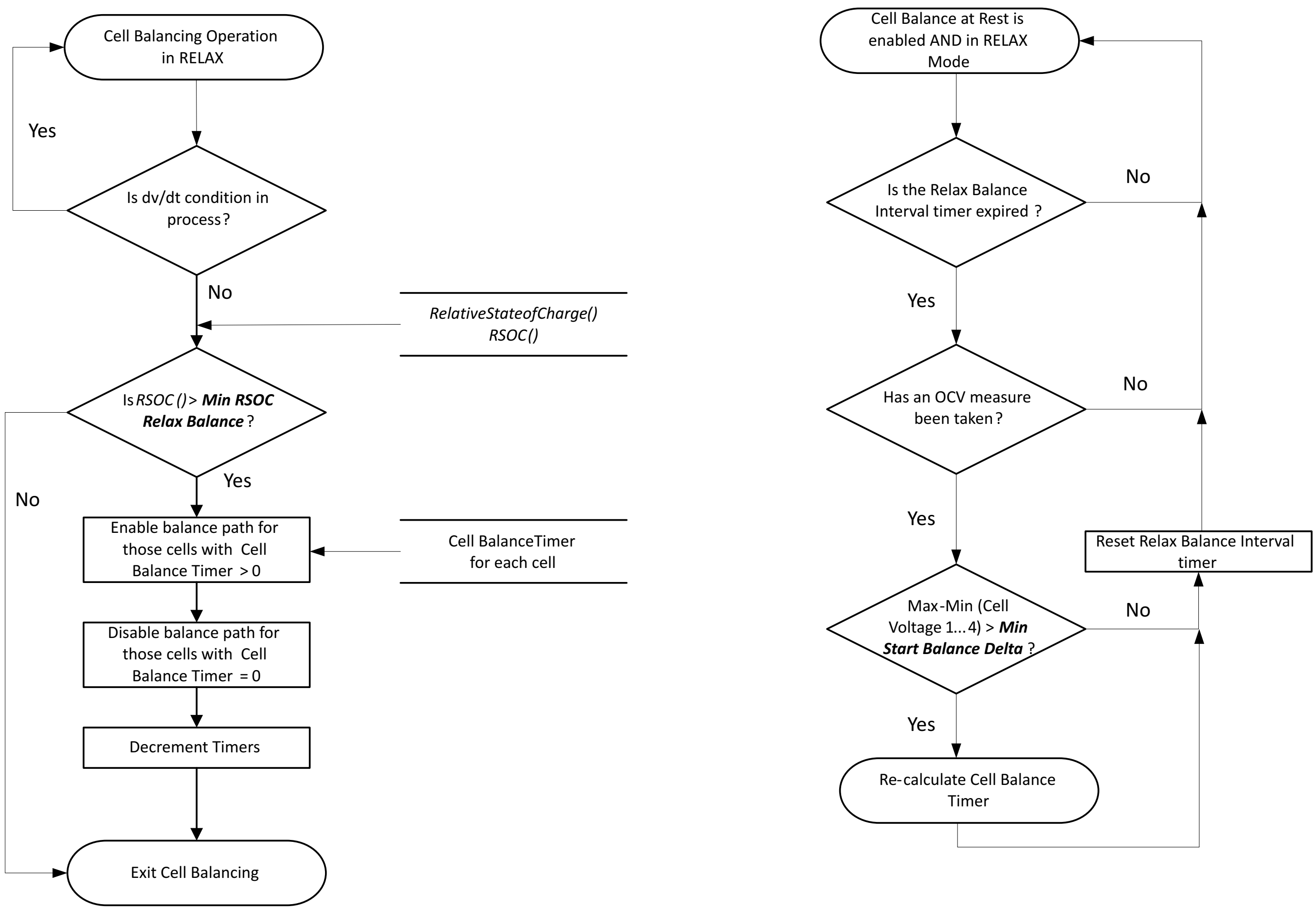


Figure 7-5. Cell Balance Operation in RELAX Mode

When the bq40z50-R3 is in CHARGE mode, it follows these steps during cell balancing:

a. Check if any of the precalculated cell balance timers are > 0.

b. The cell balance FETs are turned ON for the corresponding cell balance timers that are ≠ 0.

NOTE: There are no SOC restrictions controlling the enabling of cell balancing in CHARGE mode.

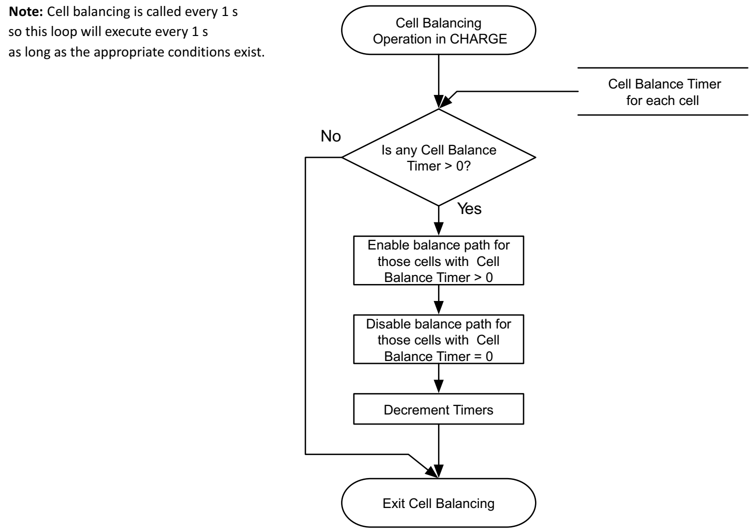


Figure 7-6. Cell Balance Operation in CHARGE Mode

Cell balancing in sleep can be enabled, by setting ***Balancing Configuration[CBS]***.

Once enabled, cell balancing in sleep will start under the following conditions:

A. The bq40z50-R3 device has been in SLEEP for a duration > ***Start Time for Bal in Sleep*** (default 100 hrs) AND
B. The value of RSOC > ***Start Rsoc for Bal in Sleep*** (default 95%).

Once the cell balancing in sleep is started, it will end when The value of RSOC < ***End Rsoc for Bal in Sleep*** (default 60%).

LED Display

8.1 Introduction

The bq40z50-R3 device has an LED display that shows various status information when a high-to-low transition of the $\overline{DISP}$ pin is detected. The LED display is available in SLEEP mode, but is disabled during device shutdown or under CUV conditions (assuming neither charging nor PFs are active). However, under PF conditions, if ***[LEDPFON]*** is set, then LED functionality is available. Additionally, even under CUV conditions, if the charger is connected and charging is active, then the LED functionality is allowed.

8.2 LED Display of State-of-Charge

When the $\overline{DISP}$ pin is pressed and a high-to-low transition of the pin is detected, the LED display shows the state-of-charge for ***LED Hold Time***. The state-of-charge can display the *RelativeStateOfCharge()* or *AbsoluteStateOfCharge()*, based on the ***[LEDMODE]*** setting.

The state-of-charge threshold can be set according to the number of LEDs available. The following table shows an example for data flash setting with 5-LED display.

	State-of-Charge (1) (2)	
	Current() > 0	*Current()* ≤ 0
LED1	***CHG Thresh 1*** to 100%	***DSG Thresh 1*** to 100%
LED2	***CHG Thresh 2*** to 100%	***DSG Thresh 2*** to 100%
LED3	***CHG Thresh 3*** to 100%	***DSG Thresh 3*** to 100%
LED4	***CHG Thresh 4*** to 100%	***DSG Thresh 4*** to 100%
LED5	***CHG Thresh 5*** to 100%	***DSG Thresh 5*** to 100%

(1) If ***[LEDCHG]*** = 1, then the LED display will stay on (that is, no $\overline{DISP}$ pin press is needed), showing the state-of-charge during charging while *Current()* > ***Charge Current Threshold***.

(2) Typically, once full charge (FC) is achieved, the LEDs are turned-off. If the ***[LEDONFC]*** bit is set, then the LEDs will be allowed to remain on after FC is achieved, if the charger remains connected. The LEDs will remain on after FC for a period defined by ***LED FC Time***. It is not recommended to leave the LED on for extended periods after FC because of the potential for short charge / discharge cycling.

If SOC drops below the flash alarm thresholds in charge or discharge, then the LED display will also flash with ***LED Flash Period*** per the ***CHG Flash Alarm*** or ***DSG Flash Alarm*** setting shown below.

	State-of-Charge (1)	
	Current() > 0	*Current()* ≤ 0
Flash Alert	0% to ***CHG Flash Alarm***	0% to ***DSG Flash Alarm***

(1) If ***[LEDRCA]*** = 1, then the LED will also flash at ***LED Flash Period*** when remaining capacity < *RemainingCapacityAlarm()* while in DISCHARGE or RELAX mode (that is, the RCA bit is set).

8.3 LED Display of PF Error Code

If ***[LEDPF1, LEDPF0]*** = 0,1, then the LED display shows each PF code for 2 × the ***LED Hold Time*** after showing the state-of-charge information.

The following table shows each PF error code. Each code is shown with the lowest to highest priority order.

PF Flag	Priority	LED3	LED2	LED1
No PF	0	***LED Blink Period***	off	off
SUV	0	***LED Blink Period***	on	off
SOV	1	***LED Blink Period***	***LED Flash Period***	off
SOCC	2	***LED Blink Period***	off	on
SOCD	3	***LED Blink Period***	on	on
SOT	4	***LED Blink Period***	***LED Flash Period***	on
COVL	5	***LED Blink Period***	off	***LED Flash Period***
SOTF	6	***LED Blink Period***	on	***LED Flash Period***
QIM	7	***LED Blink Period***	***LED Flash Period***	***LED Flash Period***
CB	8	***LED Blink Period***	off	***LED Blink Period***
IMP	9	***LED Blink Period***	on	***LED Blink Period***
CD	10	***LED Flash Period***	***LED Blink Period***	off
VIMR	11	off	***LED Blink Period***	off
VIMA	12	on	***LED Blink Period***	off
OLDL	13	***LED Flash Period***	***LED Blink Period***	on
SCCL	14	off	***LED Blink Period***	on
SCDL	15	on	***LED Blink Period***	on
CFETF	16	***LED Flash Period***	***LED Blink Period***	***LED Flash Period***
DFETF	17	off	***LED Blink Period***	***LED Flash Period***
OCDL	18	on	***LED Blink Period***	***LED Flash Period***
FUSE	19	***LED Flash Period***	***LED Blink Period***	***LED Blink Period***
AFER	20	off	***LED Blink Period***	***LED Blink Period***
AFEC	21	on	off	***LED Blink Period***
2LVL	22	***LED Flash Period***	off	***LED Blink Period***
PTC	23	off	off	***LED Blink Period***
IFC	24	on	on	***LED Blink Period***
FORCE	25	***LED Flash Period***	on	***LED Blink Period***
DF	26	off	on	***LED Blink Period***
Reserved	27	on	***LED Flash Period***	***LED Blink Period***
Open Therm TS1	28	***LED Flash Period***	***LED Flash Period***	***LED Blink Period***
Open Therm TS2	29	off	***LED Flash Period***	***LED Blink Period***
Open Therm TS3	30	on	***LED Blink Period***	***LED Blink Period***
Open Therm TS4	31	***LED Flash Period***	***LED Blink Period***	***LED Blink Period***

If ***[LEDPF1, LEDPF0]*** = 1,0, then under PF conditions, if the $\overline{\text{DISP}}$ button is pressed (high-to-low transition of the $\overline{\text{DISP}}$ pin is detected), the LED display immediately shows each PF code for 2 × the ***LED Hold Time*** (without showing the state-of-charge information).

8.4 LED Display on Exit of a Reset

If the ***[LEDR]*** = 1 and a reset occurs, then on exit from reset, the LED display shows the state-of-charge for ***LED Hold Time***. Additionally, if ***[LEDPF1, LEDPF0]*** = 0,1, the LED display also shows each of the PF error code for 2 × of the ***LED Hold Time*** afterward.

8.5 LED Display Control Through ManufacturerAccess()

The gauge provides the *ManufacturerAccess()* command (MAC) for testing purposes. The MAC *LED Toggle()* command can toggle the LED display on and off. The MAC *LED Display Press()* command can trigger the LED display and simulate 100% RSOC to demonstrate with all LEDs in actions.

8.6 LED Operation Under CUV Conditions

Typically under CUV (Cell Undervoltage) conditions, the LED operation is not allowed to preserve remaining battery charge. However, under certain situations even under CUV conditions, the LED operation will be allowed; that is, either with PF active with the ***[LEDPFON]*** bit set or with the charger connected with charging active. Additionally, an option is provided to turn on the LED even under CUV without the charger present by setting the ***[LEDIFCUV]*** bit in the LED configuration register. This option must be used with care so as to not run the battery too low.

8.7 LED Blinking Option for State of Charge

This LED feature enables LED blinking until the midpoint of each LED segment. The blinking occurs between the bottom and the midway point of each programmed segment level; thus, providing more granularity as to where the charge level is within that LED segment. If the LED configuration bit ***[BLINKMIDPT]*** is set, then this blinking feature will work as indicated below:

With this feature disabled, as the charging or discharging occurs (assuming the segments programmed are 0%, 20%, 40%, 60%, and 80% of SOC), the LED display of state-of-charge ranges are as follows:

80 to 100%	LED5 on solid, else LED 5 off, if SOC is lower %.
60 to 80%	LED4 on solid, else LED 4 off, if SOC is lower %.
40 to 60%	LED3 on solid, else LED 3 off, if SOC is lower %.
20 to 40%	LED2 on solid, else LED 2 off, if SOC is lower %.
0 to 20%	LED1 on solid

With the blinking feature enabled, as either charge or discharge occurs (assuming the segments programmed are 0%, 20%, 40%, 60%, and 80% of RSOC), the state-of-charge ranges are as follows:

90 to 100%	LED5 on solid
80 to 90%	LED5 on Blink, else LED5 off, if SOC is lower %.
70 to 80%	LED4 on solid
60 to 70%	LED4 on Blink, else LED4 off, if SOC is lower %.
50 to 60%	LED3 on solid
40 to 50%	LED3 on Blink, else LED3 off, if SOC is lower %.
30 to 40%	LED2 on solid
20 to 30%	LED2 on Blink, else LED2 off, if SOC is lower %.
10 to 20%	LED1 on solid
0 to 10%	LED1 on Blink

The blinking occurs between the bottom and the midway point of each of the programmed segments during charge or discharge. In this example, the segments programmed are 0%, 20%, 40%, 60%, and 80%; the midway points are 10%, 30%, 50%, 70%, and 90%. If the range is defined differently, then the midpoint where the blinking occurs is accordingly different. If the segments are programmed such that the midway point is a decimal point, then it rounds down to get to the next whole number. The blinking follows the ***LED Blink Period***. If this feature is enabled, it will work when ***[LEDCHG]*** is set or cleared. When the LED is operating due to the $\overline{\text{DISP}}$ being pressed, the LEDs are on for ***LED Hold Time*** (default is 4 s, so at a default a blink rate of ~500 ms, there would be at least 7 to 8 blinks in the 4 s—if ***[BLINKMIDPT]*** is set).

IATA Support

The gauge provides International Air Transport Association (IATA) support with the following commands and procedures.

9.1 Initiating IATA Shutdown (Before Shipping)

1. Initiate IATA shutdown through either a) a separate *IATA_SHUTDOWN()* MAC command, or b) the standard *ShutdownMode()* MAC command (works in SEALED and UNSEALED modes):
   a. With the *IATA_SHUTDOWN()* MAC command, the device sets the ***[IATA_SHUT]*** bit.
   b. With the standard *ShutdownMode()* MAC command, the ***[IATA_SHUT]*** bit must be set to enable ***IATA_SHUTDOWN***.
   c. The *IATA_SHUTDOWN()* MAC command is ignored if ***IATA Delay Time*** has not expired.
2. Check if true RSOC is below (less than or equal to) a certain ***IATA RSOC Threshold***, then continue to Step 3. If not, then stop shutdown and clear the ***[IATA_SHUT]*** bit.
   a. If ***IATA RSOC Threshold*** = 0%, then the gauge will not check or care about the condition of the true RSOC. It clears the ***[IATA_SHUT]*** bit and enters the normal command shutdown (Step 4).
3. Store the true remaining capacity and FCC in the data flash registers ***IATA RM*** and ***IATA FCC***, respectively.
4. Enter the device command shutdown procedure.
5. Shut down the gauge (same as before).

9.2 After Wakeup (Charging Is Connected for a Short Period to Wake)

1. Check if the ***[IATA_SHUT]*** bit is set. If it is, continue with Step 2. If not, then True FCC and RC are used.
   1. The ***[IATA_SHUT]*** bit should always be cleared in this step.
2. Check the following conditions: If all are true (AND), continue with Step 3. If ANY are NOT True, then True FCC and RC are used.
   a. The delta cell voltage difference between max cell voltage and min cell voltage is within an ***IATA DeltaV Threshold*** (The default is 50 mV. If this threshold is set to 0 V, this delta cell voltage check is disabled.) AND
   b. The temperature is greater than or equal to (≥) ***IATA MIN Temperature*** (default 10C) and less than or equal to (≤) ***IATA MAX Temperature*** (default 40C) AND
   c. Min cell voltage is greater than or equal to (≥) ***IATA Min Voltage*** (default 3000 mV) and less than or equal to (≤) ***IATA MAX Voltage*** (default 3600 mV).
3. Display the remaining capacity and FCC from the DF registers ***IATA RM*** and ***IATA FCC***, respectively (***[ISTORE_FCC]***, ***[ISTORE_RM]*** bits are set [the default]). Must be ready before the INIT (battery status) is ready. The ***[ISTORE_FCC]*** and ***[ISTORE_RM]*** configuration bits, when set, define whether the stored value or true value is displayed during the ***IATA Delay Time*** period. However, the ***IATA Delay Time*** can be set to zero OR to a value greater than zero.
   a. If ***IATA Delay Time*** > 0:
      - On wake up from IATA shutdown, the remaining capacity and FCC will be displayed from ***IATA RM*** and ***IATA FCC***, respectively, for the duration programmed in ***IATA Delay Time***. At the end of this period, the displayed values will be transitioned from stored value to the true value of remaining capacity and FCC using the smoothing engine. Smoothing must be enabled. If it is not, the display will jump to the true values immediately.

b. If ***IATA Delay Time*** = 0:
   - On wake up from IATA shutdown, if true RSOC ≤ ***IATA Wake AbsRSOC*** (default 10%), then the true value of remaining capacity and FCC will only be displayed.
   - On wake up from IATA shutdown, if true RSOC > ***IATA Wake AbsRSOC*** (default 10%), then the remaining capacity and FCC will be displayed from ***IATA RM*** and ***IATA FCC***. Subsequently, the Delta true RSOC (change in true RSOC from wakeup) is monitored. The display will switch from the ***IATA RM*** and ***IATA FCC*** values to the true value of remaining capacity and FCC only if Delta true RSOC ≥ ***IATA Delta RSOC*** (default 3%).

   At this point, if smoothing is not enabled, the display will jump to the true values immediately. However, if smoothing is enabled, the displayed values will transition from the stored value to the true value of remaining capacity and FCC using the smoothing engine.

4. There are two additional MAC commands, *IATA_RM()* and *IATA_FCC()*, that read ***IATA RM*** and ***IATA FCC***, respectively, and that work in SEALED and UNSEALED modes.

General Purpose Input Output (GPIO) Capability

10.1 Description

The bq40z50-R3 supports GPIO capability on the three LED pins and the $\overline{DISP}$ pin when they are not used for LED operation.

NOTE: GPIO and LED functionality cannot coexist: It is not possible for some pins to function for the gauge LED operation, while others are used as GPIOs. However, when the pins are used as GPIOs, the user can attach an LED and control the pin manually using the commands described below.

When *ManufacturingStatus()[LED_EN]* = 0 and *IO Config()[GPIO_EN]* = 1, then the LED and $\overline{DISP}$ pins can be used as GPIOs.

The DF byte ***GPIO Sealed Access Config*** is provided to determine whether the GPIO can be controlled or read when the gauge is SEALED. In some cases, they will be preferred controllable while SEALED, and not in other cases.

A GPIO that is configured as an output can also be read. A GPIO that is configured as an input cannot be written to drive high or low. The DF byte ***Flag Map Set Up*** holds the default configuration for the four GPIO pins.

When the read-only subcommand *GPIORead()* is sent by the host, the level of the GPIO pins is reflected in the data read back. When GPIO mode is selected and the write-only subcommand *GPIOWrite()* is sent by the host, the pins may be configured as outputs driven low, outputs driven high, or hi-Z (which is the setting that will generally be used if the pins are intended to be used as inputs).

NOTE: The LED pins and the $\overline{DISP}$ pin are different, in that when driving high, the LED pin will provide a level = BAT. The $\overline{DISP}$ pin can only provide a weak pullup with maximum ~6 V and a minimum of 1.8 V while sourcing 10 µA.

When the gauge goes into SHUTDOWN mode, these pins will be set to hi-Z.

In addition, assertion of pins can be controlled via the ***Flag Map Set Up*** scheme to assert upon particular status bits in the device. There are four such configurations for use described in ***Flag Map Set Up 1..4***.

Lifetime Data Collection

11.1 Description

Useful for analysis, the device has extensive capabilities for logging events over the life of the battery. The ***Lifetime Data Collection*** is enabled by setting *ManufacturingStatus()LF_EN]*. The data is collected in RAM and only written to DF under the following conditions to avoid wear out of the data flash:

- Every 10 hours if RAM content is different from flash.
- In permanent fail, before data flash updates are disabled.
- A reset counter increments. The lifetime RAM data is reset; therefore, only the reset counters are updated to data flash.
- Before scheduled shutdown.
- Before low voltage shutdown and the voltage is above the ***Valid Update Voltage***.

The Lifetime Data stops collecting under following conditions:

- After permanent fail.
- ***Lifetime Data Collection*** is disabled by setting *ManufacturingStatus()[LF_EN]* = 0.

When the gauge is unsealed, the following *ManufacturingStatus()* can be used for testing Lifetime Data.

- *Lifetime Data Reset()* can be used to reset the Lifetime Data.
- *Lifetime Data Flush()* can be used to flush out RAM Lifetime Data to data flash.
- *Lifetime Data Speedup Mode()* can be used to increase the rate the Lifetime Data is incremented.

The collection of the following data starts when ***[LF_EN]*** is set.

- Total firmware runtime
- Voltage
  - Maximum/Minimum Cell Voltage for each cell
  - ***Maximum Delta Cell Voltage*** at any given time (that is, the max cell imbalance voltage)
- Current
  - Maximum charge/discharge current
  - Maximum average discharge current
  - Maximum average discharge power
- For safety events that trigger the *SafetyStatus()*
  - Number of safety events
  - Cycle count at last safety event(s)
- Charging Events
  - Number of valid charge terminations (That is, the number of times *[VCT]* is set.)
  - Cycle Count at Last Charge Termination
- Gauging Events
  - Number of QMax updates
  - Cycle Count at Last QMax update
  - Number of RA updates and disable

  - Cycle Count at Last RA update and disable
- Power Events
  - Number of resets, partial resets, and watchdog resets
  - Number of shutdowns
- Cell balancing (This data is stored with a resolution of 1 second up to over 100 years.)
  - Cell balancing time for each cell
- Temperature
  - Max/Min Cell Temp
  - Delta Cell Temp (max delta cell temperature across the thermistors that are used to report cell temperature)
  - Max/Min Int Temp Sensor
  - Max FET Temp
- Time (This data is stored with a resolution of 1 second up to over 100 years.)
  - Total runtime
  - Time spent in different *RelativeStateOfCharge() – Temperature()* ranges
    - Eight *RelativeStateOfCharge()* ranges for each of the seven charge temperature ranges
    - 56 *RelativeStateOfCharge() – Temperature()* runtime values

Table 11-1. Time Spent in *RelativeStateOfCharge()* – *Temperature()* Ranges

	RSOC ≥ 95% [default]	RSOC ≥ 90%	RSOC ≥ 80%	RSOC ≥ 60%	RSOC ≥ 40%	RSOC ≥ 20%	RSOC ≥ 10%	RSOC ≥ 0%
Undertemperature								
Low Temperature								
Standard Temperature Low								
Recommended Temperature								
Standard Temperature High								
High Temperature								
Over Temperature								

11.2 Reset

In addition to the *ManufacturerAccess() 0x0028 Lifetime Data Reset*, ***Lifetime Data Collection*** can also be reset when ***[SEALED_RESET]*** is set using a two-word MAC sequence available in SEALED and UNSEALED modes. The two-word key is programmable using *ManufacturerAccess() 0x0035 Security Keys*. Both keys must be sent within 4 seconds of each other for ***LIfetimes*** data to reset.

Device Security

12.1 Introduction

There are three levels of secured operation within the device. To switch between the levels, different operations are needed with different keys. The three levels are SEALED, UNSEALED, and FULL ACCESS. The bq40z50-R3 device also supports SHA-1 HMAC authentication with the host system.

12.2 SHA-1 Description

As of March 2012, the latest revision is FIPS 180-4. SHA-1, or secure hash algorithm, is used to compute a condensed representation of a message or data also known as hash. For messages < 2^{64}, the SHA-1 algorithm produces a 160-bit output called a digest.

In a SHA-1 one-way hash function, there is no known mathematical method of computing the input given, only the output. The specification of SHA-1, as defined by FIPS 180-4, states that the input consists of 512-bit blocks with a total input length less than 264 bits. Inputs that do not conform to integer multiples of 512-bit blocks are padded before any block is input to the hash function. The SHA-1 algorithm outputs the 160-bit digest.

The bq40z50-R3 device generates a SHA-1 input block of 288 bits (total input = 160-bit message + 128-bit key). To complete the 512-bit block size requirement of the SHA-1 function, the device pads the key and message with a 1, followed by 159 0s, followed by the 64 bit value for 288 (000...00100100000), which conforms to the pad requirements specified by FIPS 180-4.

Detailed information about the SHA-1 algorithm can be found here:

1. http://www.nist.gov/itl/
2. http://csrc.nist.gov/publications/fips
3. www.faqs.org/rfcs/rfc3174.html

12.3 HMAC Description

The SHA-1 engine calculates a modified HMAC value. Using a public message and a secret key, the HMAC output is considered to be a secure fingerprint that authenticates the device used to generate the HMAC.

To compute the HMAC: Let H designate the SHA-1 hash function, M designate the message transmitted to the device, and KD designate the unique 128-bit Authentication key of the device. HMAC(M) is defined as:

H[KD || H(KD || M)], where || symbolizes an append operation.

The message, M, is appended to the authentication key, KD, and padded to become the input to the SHA-1 hash. The output of this first calculation is then appended to the authentication key, KD, padded again, and cycled through the SHA-1 hash a second time. The output is the HMAC digest value.

12.4 Authentication

1. Generate 160-bit message M using a random number generator that meets approved random number generators described in FIPS PUB 140–2.
2. Generate SHA-1 input block B1 of 512 bits (total input = 128-bit authentication key KD + 160-bit message M + 1 + 159 0s + 100100000).
3. Generate SHA-1 hash HMAC1 using B1.
4. Generate SHA-1 input block B2 of 512 bits (total input = 128-bit authentication key KD + 160-bit hash

HMAC1 + 1 + 159 0s + 100100000).

5. Generate SHA-1 hash HMAC2 using B2.
6. With no active *Authenticate()* data waiting, write 160-bit message M to *Authenticate()* in the format: 0xAABBCCDDEEFFGGHHIIJJKKLLMMNNOOPPQQRRSSTT, where AA is LSB.
7. Wait 250 ms, then read *Authenticate()* for HMAC3.
8. Compare host HMAC2 with device HMAC3. If it matches, both host and device have the same key KD and the device is authenticated.

12.5 Security Modes

12.5.1 FULL ACCESS or UNSEALED to SEALED

The MAC *Seal Device()* command instructs the device to limit access to the SBS functions and data flash space, and sets the *[SEC1][SEC0]* flags. In SEALED mode, standard SBS functions have access (per the *Smart Battery Data Specification*). Most of the extended SBS functions and data flash are not accessible. Refer to Chapter 15 where each command has documented the accessibility information. Once in SEALED mode, the gauge can never permanently return to UNSEALED or FULL ACCESS modes.

12.5.2 SEALED to UNSEALED

SEALED to UNSEALED instructs the device to extend access to the SBS and data flash space and clears the *[SEC1][SEC0]* flags. In UNSEALED mode, all data, SBS, and DF have read/write access. Note that although writing to most of the SBS commands are accepted by the gauge, the written data will be immediately overwritten by the gauge and the write action is ignored. Unsealing is a two-step command performed by writing the first word of the unseal key to *ManufacturerAccess() (MAC)*, followed by the second word of the unseal key to *ManufacturerAccess()*. The two words must be sent within 4 s. The unseal key can be read and changed via the *MAC SecurityKey()* command when in the FULL ACCESS mode. To return to the SEALED mode, either a hardware reset is needed or the *MAC Seal Device()* command is needed to transit from FULL ACCESS or UNSEALED to SEALED.

The default UNSEAL key is 0x0414 and 0x3672. To go from SEALED to UNSEALED, these two words must be sent to *ManufacturerAccess() (MAC)*, first 0x0414 followed by 0x3672, both sent sequentially with the second word sent within 4 seconds of the first.

12.5.3 UNSEALED to FULL ACCESS

UNSEALED to FULL ACCESS instructs the device to allow full access to all SBS commands and data flash. The bq40z50-R3 device is shipped from TI in this mode. The keys for UNSEALED to FULL ACCESS can be read and changed via the *SecurityKey()* MAC command when in FULL ACCESS mode. Changing from UNSEALED to FULL ACCESS is performed by using the *ManufacturerAccess()* command, by writing the first word of the Full Access Key to *ManufacturerAccess()*, followed by the second word of the Full Access Key to *ManufacturerAccess()*. The two words must be sent within 4 s. In FULL ACCESS mode, the command to go to boot ROM can be sent.

NOTE: If the gauge is sealed, it will always return to the SEALED state after POR even if the gauge is unsealed prior to a POR. If the SREC of a sealed gauge is extracted and then programmed into another gauge, the other gauge will also power up in the SEALED state. The only way to permanently restore the UNSEALED state is to reflash the gauge with an unsealed SREC.

Manufacture Production

13.1 Manufacture Testing

To improve the manufacture testing flow, the gas gauge device allows certain features to be toggled on or off through *ManufacturerAccess()* commands; for example, the *PCHG FET()*, *CHG FET()*, *DSG FET()*, *Lifetime Data Collection()*, *Calibration()*, among others. Enabling only the feature under test can simplify the test flow in production by avoiding any feature interference. The *ManufacturerAccess()* commands that toggle the *ManufacturingStatus()[CAL_EN]*, *[LT_TEST]*, *[DSG_TEST]*, *[CHG_TEST]*, and *[PCHG_TEST]* will only set the RAM data, meaning the conditions set by these commands will be cleared if a reset or seal is issued to the gauge. The *ManufacturerAccess()* commands that toggle the *ManufacturingStatus()[LED_EN]*, *[FUSE_EN]*, *[BBR_EN]*, *[PF_EN]*, and *[LF_EN], [FET_EN], [GAUGE_EN]* will be updated to data flash and synchronized between *ManufacturingStatus()* and ***Mfg Status Init***. The *ManufacturingStatus()* keeps track of the status (enabled or disabled) of each feature.

The ***Mfg Status Init*** provides the option to enable or disable individual features for normal operation. Upon a reset or a seal command, *ManufacturingStatus()* will be reloaded from data flash ***Mfg Status Init***. This means if an update is made to ***Mfg Status Init*** to enable or disable a feature, the gauge will only take the new setting if a reset or seal command is sent.

13.2 Calibration

Refer to the *bq40zxx Manufacture, Production, and Calibration Application Note* (SLUA734) for the detailed calibration procedure.

The bq40z50-R3 device has integrated routines that support calibration of current, voltage, and temperature readings, accessible after writing 0xF081 or 0xF082 to *ManufacturerAccess()* when the *ManufacturingStatus()[CAL]* bit is ON. While the calibration is active, the raw ADC data is available on *ManufacturerData()*. The bq40z50-R3 device stops reporting calibration data on *ManufacturerData()* if any other MAC commands are sent or the device is reset or sealed.

NOTE: The *ManufacturingStatus()[CAL]* bit must be turned OFF after calibration is completed. The *ManufacturingStatus()[CAL]* bit is set by default when the ***Manufacturing Status Init*** is cleared This bit is cleared at reset or after sealing.

ManufacturerAccess()	Description
0x002D	Enables/Disables *ManufacturingStatus()[CAL]*
0xF080	Disables raw ADC data output on *ManufacturerData()*
0xF081	Outputs raw ADC data of voltage, current, and temperature on *ManufacturerData()*
0xF082	Outputs raw ADC data of voltage, current, and temperature on *ManufacturerData()*. This mode enables an internal short on the coulomb counter inputs (SRP, SRN).

The *ManufacturerData()* output format is: ZZYYaaAAbbBBccCCddDDeeEEffFFggGGhhHHiiIIjjJJkkKK,

where:

Value	Format	Description
ZZ	byte	8-bit counter, increments when raw ADC values are refreshed (every 250 ms)
YY	byte	Output status *ManufacturerAccess()* = 0xF081: 1 *ManufacturerAccess()* = 0xF082: 2
AAaa	2's comp	Current (coulomb counter)

Value	Format	Description
BBbb	2's comp	Cell Voltage 1
CCcc	2's comp	Cell Voltage 2
DDdd	2's comp	Cell Voltage 3
EEee	2's comp	Cell Voltage 4
FFff	2's comp	PACK Voltage
GGgg	2's comp	BAT Voltage
HHhh	2's comp	Cell Current 1
IIii	2's comp	Cell Current 2
JJjj	2's comp	Cell Current 3
KKkk	2's comp	Cell Current 4

13.2.1 Calibration Data Flash

13.2.1.1 Voltage

Class	Subclass	Name	Type	Min	Max	Default	Unit	Description
Calibration	Voltage	Cell Gain	I2	–32767	32767	12101 [(1)]	—	VC[n]–VC[n–1] gain
Calibration	Voltage	PACK Gain	U2	0	65535	49669 [(1)]	—	PACK–VSS gain
Calibration	Voltage	BAT Gain	U2	0	65535	48936 [(1)]	—	BAT–VSS gain

(1) Clearing this value causes the gauge to use the internal factory calibration default.

13.2.1.2 Current

Class	Subclass	Name	Type	Min	Max	Default	Description
Calibration	Current	CC Gain	F4	1.00E–001	4.00E+000	3.58422	Coulomb counter gain
Calibration	Current	Capacity Gain	F4	2.98E+004	1.19E+006	1069035.256	Capacity gain

13.2.1.3 Current Offset

13.2.1.3.1 CC Offset

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	Current Offset	CC Offset	I2	–32767	32767	0	—

Description: This is the sum of samples when the coulomb counter inputs are internally shorted. This offset is used for *Current()* measurement.

13.2.1.3.2 Coulomb Counter Offset Samples

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	Current Offset	Coulomb Counter Offset Samples	U2	0	65535	64	—

Description: ***Coulomb Counter Offset Samples*** is used for averaging.

13.2.1.3.3 Board Offset

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	Current Offset	Board Offset	I2	–32768	32767	0	—

Description: This is the sum of coulomb counts when zero current is flowing across the sense resistor.

13.2.1.4 CC Auto Config

Class	Subclass	Name	Type	Min	Max	Default	Units
Calibration	Current Offset	CC Auto Config	H1	0x00	0x07	0x03	Hex

7	6	5	4	3	2	1	0
RSVD	RSVD	RSVD	RSVD	RSVD	OFFSET_TAKEN	AUTO_NESTON	AUTO_CAL_EN

SpecificationInformation() values

RSVD (Bits 7–3): Reserved. Do not use.

OFFSET_TAKEN (Bit 2): ***CC Auto Offset*** is taken.

1 = ***CC Auto Offset*** has been measured.

0 = ***CC Auto Offset*** has not been measured.

AUTO_NESTON (Bit 1): NEST Circuit ON

1 = When ***[OFFSET_TAKEN]*** = 1, FW automatically controls the HW NEST circuit for best current and cell current measurements.

0 = HW NEST circuit is always on. Individual cell current measurement may have error relative to *Current()*, but the *Current()* accuracy is not impacted.

AUTO_CAL_EN (Bit 0): ***CC Auto Offset*** calibration enable

1 = FW performs auto CC calibration on entry into SLEEP mode. A min auto CC calibration interval is set to 10 hours to prevent flash wear out. The result is saved to ***CC Auto Offset***.

0 = ***CC Auto Offset*** calibration is disabled.

13.2.1.5 CC Auto Offset

Class	Subclass	Name	Type	Min	Max	Default
Calibration	Current Offset	CC Auto Offset	I2	–10000	10000	0

Description: ***CC Offset*** collected via ***CC Auto Offset Calibration***. This offset is used for cell current measurement and is different than ***CC Offset***.

13.2.1.6 Temperature

13.2.1.6.1 Internal Temp Offset

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	Temperature	Internal Temp Offset	I1	–128	127	0	0.1°C

Description: Internal temperature sensor reading offset

13.2.1.6.2 External 1 Temp Offset

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	Temperature	External 1 Temp Offset	I1	–128	127	0	0.1°C

Description: TS1 temperature sensor reading offset

13.2.1.6.3 External 2 Temp Offset

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	Temperature	External 2 Temp Offset	I1	–128	127	0	0.1°C

Description: TS2 temperature sensor reading offset

13.2.1.6.4 External 3 Temp Offset

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	Temperature	External 3 Temp Offset	I1	–128	127	0	0.1°C

Description: TS3 temperature sensor reading offset

13.2.1.6.5 External 4 Temp Offset

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	Temperature	External 4 Temp Offset	I1	–128	127	0	0.1°C

Description: TS4 temperature sensor reading offset

13.2.1.7 Internal Temp Model

13.2.1.7.1 Int Gain

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	Internal Temp Model	Int Gain	I2	–32768	32767	–12143	—

Description: Internal temperature gain

13.2.1.7.2 Int Base Offset

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	Internal Temp Model	Int Base Offset	I2	–32768	32767	6232	—

Description: Internal temperature base offset

13.2.1.7.3 Int Minimum AD

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	Internal Temp Model	Int Minimum AD	I2	–32768	32767	0	—

Description: Minimum AD count used for calculation

13.2.1.7.4 Int Maximum Temp

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	Internal Temp Model	Int Maximum Temp	I2	–32768	32767	6232	0.1 K

Description: Maximum Temperature boundary

13.2.1.8 External Thermistor Cell Temp Model

Translation of resistance measurement to temperature for NTC thermistors is computed using two polynomials (denoted as "a" and "b"). The default coefficients are optimized for a 10-KΩ at 25°C thermistor.

13.2.1.8.1 Coefficient a1

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	Cell Temp Model	Coefficient a1	I2	–32768	32767	–11130	—

Description: Cell temperature calculation polynomial a1

13.2.1.8.2 Coefficient a2

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	Cell Temp Model	Coefficient a2	I2	–32768	32767	19142	—

Description: Cell temperature calculation polynomial a2

13.2.1.8.3 Coefficient a3

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	Cell Temp Model	Coefficient a3	I2	–32768	32767	–19262	—

Description: Cell temperature calculation polynomial a3

13.2.1.8.4 Coefficient a4

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	Cell Temp Model	Coefficient a4	I2	–32768	32767	28203	—

Description: Cell temperature calculation polynomial a4

13.2.1.8.5 Coefficient a5

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	Cell Temp Model	Coefficient a5	I2	–32768	32767	892	—

Description: Cell temperature calculation polynomial a5

13.2.1.8.6 Coefficient b1

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	Cell Temp Model	Coefficient b1	I2	–32768	32767	328	—

Description: Cell temperature calculation polynomial b1

13.2.1.8.7 Coefficient b2

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	Cell Temp Model	Coefficient b2	I2	–32768	32767	–605	—

Description: Cell temperature calculation polynomial b2

13.2.1.8.8 Coefficient b3

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	Cell Temp Model	Coefficient b3	I2	–32768	32767	–2443	—

Description: Cell temperature calculation polynomial b3

13.2.1.8.9 Coefficient b4

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	Cell Temp Model	Coefficient b4	I2	–32768	32767	4969	—

Description: Cell temperature calculation polynomial b4

13.2.1.8.10 Rc0

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	Cell Temp Model	Rc0	I2	–32768	32767	11703	counts

Description: AD reading at 25°C for calibration point of the translation polynomials

13.2.1.8.11 Adc0

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	Cell Temp Model	Adc0	I2	–32768	32767	11703	counts

Description: ADC reading at 25°C to shift the polynomial calibration point

13.2.1.8.12 Rpad

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	Cell Temp Model	Rpad	I2	–32768	32767	0 [(1)]	Ω

(1) Setting this value to 0 causes the gauge to use the internal factory calibration default.

Description: Pad Resistance (0 to use factory calibration) contribution to thermistor impedance AD conversion.

13.2.1.8.13 Rint

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	Cell Temp Model	Rint	I2	–32768	32767	0[1]	Ω

(1) Setting this value to 0 causes the gauge to use the internal factory calibration default.

Description: Internal pullup resistance (0 to use factory calibration) for thermistor excitation

13.2.1.9 FET Temp Model Using an External Thermistor

The default model is the same as that for cell temperature measurement.

13.2.1.9.1 Coefficient a1

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	FET Temp Model	Coefficient a1	I2	–32768	32767	–11130	—

Description: FET temperature calculation polynomial a1.

13.2.1.9.2 Coefficient a2

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	FET Temp Model	Coefficient a2	I2	–32768	32767	19142	—

Description: FET temperature calculation polynomial a2

13.2.1.9.3 Coefficient a3

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	FET Temp Model	Coefficient a3	I2	–32768	32767	–19262	—

Description: FET temperature calculation polynomial a3

13.2.1.9.4 Coefficient a4

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	FET Temp Model	Coefficient a4	I2	–32768	32767	28203	—

Description: FET temperature calculation polynomial a4

13.2.1.9.5 Coefficient a5

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	FET Temp Model	Coefficient a5	I2	–32768	32767	892	—

Description: FET temperature calculation polynomial a5

13.2.1.9.6 Coefficient b1

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	FET Temp Model	Coefficient b1	I2	–32768	32767	328	—

Description: FET temperature calculation polynomial b1

13.2.1.9.7 Coefficient b2

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	FET Temp Model	Coefficient b2	I2	–32768	32767	–605	—

Description: FET temperature calculation polynomial b2

13.2.1.9.8 Coefficient b3

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	FET Temp Model	Coefficient b3	I2	–32768	32767	–2443	—

Description: FET temperature calculation polynomial b3

13.2.1.9.9 Coefficient b4

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	FET Temp Model	Coefficient b4	I2	–32768	32767	4969	—

Description: FET temperature calculation polynomial b4

13.2.1.9.10 Rc0

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	FET Temp Model	Rc0	I2	–32768	32767	11703	Ω

Description: Resistance at 25°C

13.2.1.9.11 Adc0

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	FET Temp Model	Adc0	I2	–32768	32767	11703	—

Description: ADC reading at 25°C

13.2.1.9.12 Rpad

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	FET Temp Model	Rpad	I2	–32768	32767	0 (1)	Ω

(1) Setting this value to 0 causes the gauge to use the internal factory calibration default.

Description: Pad Resistance (0 to use factory calibration)

13.2.1.9.13 Rint

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	FET Temp Model	Rint	I2	–32768	32767	0[1]	Ω

(1) Setting this value to 0 causes the gauge to use the internal factory calibration default.

Description: Pullup resistor resistance (0 to use factory calibration)

13.2.1.10 Current Deadband

13.2.1.10.1 Deadband

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	Current Deadband	Deadband	U1	0	255	3	mA

Description: Pack-based Deadband to report 0 mA

13.2.1.10.2 Coulomb Counter Deadband

Class	Subclass	Name	Type	Min	Max	Default	Unit
Calibration	Current Deadband	Coulomb Counter Deadband	U1	0	255	9	116 nV

Description: Coulomb counter deadband to report 0 charge (This setting should not be modified.)

Device SMBus Address

The bq40z50-R3 SMBus address (default 0x16) can be changed. The target address should be programmed in ***Address*** and the 2's complement of that value should be programmed in ***Address Check***.

The bq40z50-R3 will check these values upon exit from POR, and if the two data flash values are not valid or the programmed address is 0x00 or 0xFF, then the device defaults to 0x16.

Table 14-1. Address

Class	Subclass	Name	Format	Size in Bytes	Min Value	Max Value	Default Value	Unit
Settings	SMBus	Address	Hex	1	0x00	0xFF	0x16	—

Table 14-2. Address Check

Class	Subclass	Name	Format	Size in Bytes	Min Value	Max Value	Default Value	Unit
Settings	SMBus	Address Check	Hex	1	0x00	0xFF	0xEA	—

For details on SMBus specifications, visit http://www.smbus.org/specs/.

SBS Commands

15.1 0x00 ManufacturerAccess() and 0x44 ManufacturerBlockAccess()

ManufacturerBlockAccess() provides a method of reading and writing data in the Manufacturer Access System (MAC). This block MAC access method is standard for the bq40zxy family. The MAC command is sent via *ManufacturerBlockAccess()* by the SMBus block protocol. The result is returned on *ManufacturerBlockAccess()* via an SMBus block read.

Example: Send a MAC *Gauging()* to enable IT via *ManufacturerBlockAccess().*

1. With Impedance Track disabled, send *Gauging()* (0x0021) to *ManufacturerBlockAccess()*
   a. SMBus block write. Command = 0x44. Data = 21 00 (data must be sent in little endian)
2. IT is enabled, *ManufacturingStatus()[GAUGE_EN]* = 1.

Example: Read *Chemical ID()* (0x0006) via *ManufacturerBlockAccess()*.

1. Send *Chemical ID()* to *ManufacturerBlockAccess().*
   a. SMBus block write. Command = 0x44. Data sent = 06 00 (data must be sent in little endian)
2. Read the result from *ManufacturerBlockAccess().*
   a. SMBus block read. Command = 0x44. Data read = 06 00 00 01 (each data entity is returned in little endian).
   b. The first 2 bytes, “06 00”, is the MAC command.
   c. The second 2 bytes, “00 01”, is the chem ID returning in little endian. That is 0x0100, chem ID 100.

For backwards compatibility with the bq30zxy families, sending MAC commands via *ManufacturerAccess()* (0x00) as well as the returning data on *ManufacturerData()* are supported in bq40z50-R3. Note that MAC commands are sent through *ManufacturerAccess()* (0x00) by an SMBus write word protocol. The result reading from *ManufacturerData()* does not include the MAC command.

Example: Send a MAC *Gauging()* to enable IT via *ManufacturerAccess().*

1. With Impedance Track disabled, send *Gauging()* (0x0021) to *ManufacturerAccess()*.
   a. SMBus word write. Command = 0x00. Data = 00 21 (Data to address 0x00 is big endian.)
2. IT is enabled, *ManufacturingStatus()[GAUGE_EN]* = 1.

Example: Read *Chemical ID()* (0x0006) via *ManufacturerAccess()*.

1. Send *Chemical ID()* to *ManufacturerAccess().*
   a. SMBus word write. Command = 0x00. Data sent = 00 06 (data to address 0x00 is big endian).
2. Read the result from *ManufacturerData().*
   a. SMBus block read. Command = 0x23. Data read = 00 01 (each data entity is returned in little endian).
   b. That is 0x0100, chem ID 100.

The *ManufacturerAccess()* and *ManufacturerBlockAccess()* are interchangeable. The result can be read from *ManufacturerData()* or *ManufacturerBlockAccess()*, regardless of how the MAC command is sent.

Table 15-1. ManufacturerAccess() Command List

Command	Function	Access	Format	Data Read on 0x44 or 0x23	Data Read on 0x2F	Available in SEALED Mode	Type	Unit
0x0001	DeviceType	R	Block	Yes	—	Yes	Hex	—
0x0002	FirmwareVersion	R	Block	Yes	—	Yes	Hex	—

Table 15-1. ManufacturerAccess() Command List (continued)

Command	Function	Access	Format	Data Read on 0x44 or 0x23	Data Read on 0x2F	Available in SEALED Mode	Type	Unit
0x0003	HardwareVersion	R	Block	Yes	—	Yes	Hex	—
0x0004	IFChecksum	R	Block	Yes	—	Yes	Hex	—
0x0005	StaticDFSignature	R	Block	Yes	—	Yes	Hex	—
0x0006	ChemID	R	Block	Yes	—	Yes	Hex	—
0x0008	StaticChemDFSignature	R	Block	Yes	—	Yes	Hex	—
0x0009	AllDFSignature	R	Block	Yes	—	Yes	Hex	—
0x0010	ShutdownMode	W	—	—	—	Yes	Hex	—
0x0011	SleepMode	W	—	—	—	—	Hex	—
0x0013	AutoCCOfset	W	—	—	—	—	Hex	—
0x001D	FuseToggle	W	—	—	—	—	Hex	—
0x001E	PrechargeFETToggle	W	—	—	—	—	Hex	—
0x001F	ChargeFETToggle	W	—	—	—	—	Hex	—
0x0020	DischargeFETToggle	W	—	—	—	—	Hex	—
0x0021	Gauging	W	—	—	—	—	Hex	—
0x0022	FETControl	W	—	—	—	—	Hex	—
0x0023	LifetimeDataCollection	W	—	—	—	—	Hex	—
0x0024	PermanentFailure	W	—	—	—	—	Hex	—
0x0025	BlackBoxRecorder	W	—	—	—	—	Hex	—
0x0026	Fuse	W	—	—	—	—	Hex	—
0x0027	LEDDisplayEnable	W	—	—	—	—	Hex	—
0x0028	LifetimeDataReset	W	—	—	—	—	Hex	—
0x0029	PermanentFailureData Reset	W	—	—	—	—	Hex	—
0x002A	BlackBoxRecorderReset	W	—	—	—	—	Hex	—
0x002B	LEDToggle	W	—	—	—	—	Hex	—
0x002C	LEDDisplayPress	W	—	—	—	—	Hex	—
0x002D	CalibrationMode	W	—	—	—	—	Hex	—
0x002E	LifetimeDataFlush	W	—	—	—	—	Hex	—
0x002F	LifetimeDataSpeedUp Mode	W	—	—	—	—	Hex	—
0x0030	SealDevice	W	—	—	—	—	Hex	—
0x0035	SecurityKeys	R/W	Block	Yes	—	—	Hex	—
0x0037	AuthenticationKey	R/W	Block	—	Yes	—	Hex	—
0x0041	DeviceReset	W	—	—	—	—	Hex	—
0x0050	SafetyAlert	R	Block	Yes	—	Yes	Hex	—
0x0051	SafetyStatus	R	Block	Yes	—	Yes	Hex	—
0x0052	PFAlert	R	Block	Yes	—	Yes	Hex	—
0x0053	PFStatus	R	Block	Yes	—	Yes	Hex	—
0x0054	OperationStatus	R	Block	Yes	—	Yes	Hex	—
0x0055	ChargingStatus	R	Block	Yes	—	Yes	Hex	—
0x0056	GaugingStatus	R	Block	Yes	—	Yes	Hex	—
0x0057	ManufacturingStatus	R	Block	Yes	—	Yes	Hex	—
0x0058	AFERegister	R	Block	Yes	—	Yes	Hex	—
0x005A	NoLoadRemCap	R	Block	Yes	—	Yes	Mixed	Mixed
0x0060	LifetimeDataBlock1	R	Block	Yes	—	Yes	Mixed	Mixed
0x0061	LifetimeDataBlock2	R	Block	Yes	—	Yes	Mixed	Mixed
0x0062	LifetimeDataBlock3	R	Block	Yes	—	Yes	Mixed	Mixed
0x0063	LifetimeDataBlock4	R	Block	Yes	—	Yes	Mixed	Mixed
0x0064	LifetimeDataBlock5	R	Block	Yes	—	Yes	Mixed	Mixed
0x0065	LifetimeDataBlock6	R	Block	Yes	—	Yes	Mixed	Mixed
0x0066	LifetimeDataBlock7	R	Block	Yes	—	Yes	Mixed	Mixed

Table 15-1. ManufacturerAccess() Command List (continued)

Command	Function	Access	Format	Data Read on 0x44 or 0x23	Data Read on 0x2F	Available in SEALED Mode	Type	Unit
0x0067	LifetimeDataBlock8	R	Block	Yes	—	Yes	Mixed	Mixed
0x0068	LifetimeDataBlock9	R	Block	Yes	—	Yes	Mixed	Mixed
0x0069	LifetimeDataBlock10	R	Block	Yes	—	Yes	Mixed	Mixed
0x006A	LifetimeDataBlock11	R	Block	Yes	—	Yes	Mixed	Mixed
0x006B	LifetimeDataBlock12	R	Block	Yes	—	Yes	Mixed	Mixed
0x0070	ManufacturerInfo	R	Block	Yes	—	Yes	Hex	—
0x0071	DAStatus1	R	Block	Yes	—	Yes	Mixed	Mixed
0x0072	DAStatus2	R	Block	Yes	—	Yes	Mixed	Mixed
0x0073	GaugeStatus1	R	Block	Yes	—	Yes	Mixed	Mixed
0x0074	GaugeStatus2	R	Block	Yes	—	Yes	Mixed	Mixed
0x0075	GaugeStatus3	R	Block	Yes	—	Yes	Mixed	Mixed
0x0076	CBStatus	R	Block	Yes	—	Yes	Mixed	Mixed
0x0077	StateofHealth	R	Block	Yes	—	Yes	Mixed	Mixed
0x0078	FilterCapacity	R	Block	Yes	—	Yes	Mixed	Mixed
0x0079	RSOCWrite	W	—	—	—	—	Hex	—
0x007A	ManufacturerInfoB	R	Block	Yes	—	Yes	Mixed	Mixed
0x0098	AccumulationChargeEnable	W	—	—	—	No	—	—
0x0099	AccumulationDischarge Enable	W	—	—	—	No	—	—
0x009A	AccumulationReset	W	—	—	—	Yes	—	—
0x009B	AccumulationStop	W	—	—	—	Yes	—	—
0x009C	AccumulationStart	W	—	—	—	Yes	Signed Int	mAh
0x009D	AccumulationCharge Threshold	RW	Block	Yes	—	Yes	Signed Int	mAh
0x009E	AccumulationDischarge Threshold	RW	Block	Yes	—	Yes	Signed Int	mAh
0x009F	AccumulatedTimeCharge	R	Block	Yes	—	Yes	Mixed	Mixed
0x00B0	ChargingVoltageOverride	RW	Block	Yes	—	Yes	Signed Int	mV
0x00F0	IATAShutdown	W	—	—	—	—	Hex	—
0x00F1	IATARm	W	—	—	—	—	Hex	—
0x00F2	IATAFcc	W	—	—	—	—	Hex	—
0x0F00	ROMMode	W	—	—	—	—	Hex	—
0x3008	WriteTemp	W	Block	Yes	—	Yes	Signed Int	0.1 K
0xF080	ExitCalibrationOutput	R/W	Block	Yes	—	—	Hex	—
0xF081	OutputCCADCCal	R/W	Block	Yes	—	—	Hex	—
0xF082	OutputShortedCCADCCal	R/W	Block	Yes	—	—	Hex	—

15.1.1 ManufacturerAccess() 0x0000

A read word on this command returns the lowest 16 bits of the *OperationStatus()* data.

15.1.2 ManufacturerAccess() 0x0001 Device Type

The bq40z50-R3 device can be checked for the IC part number. The IC part number returns on a subsequent read on *ManufacturerBlockAccess()* or *ManufacturerData()* in the following format: aaAA, where:

Value	Description
AAaa	Device Type

15.1.3 ManufacturerAccess() 0x0002 Firmware Version

The bq40z50-R3 device can be checked for the firmware version of the IC. The firmware revision returns on *ManufacturerBlockAccess()* or *ManufacturerData()* in the following format: DDddVVvvBBbbTTZZzzRREE, where:

Value	Description
DDdd	Device Number
VVvv	Version
BBbb	Build Number
TT	Firmware Type
ZZzz	Impedance Track Version
RR	Reserved
EE	Reserved

15.1.4 ManufacturerAccess() 0x0003 Hardware Version

The bq40z50-R3 device can be checked for the hardware version of the IC. The hardware revision returns on a subsequent read on *ManufacturerBlockAccess()* or *ManufacturerData()*.

15.1.5 ManufacturerAccess() 0x0004 Instruction Flash Signature

The bq40z50-R3 device can return the instruction flash signature. The IF signature returns on a subsequent read on *ManufacturerBlockAccess()* or *ManufacturerData()*.

15.1.6 ManufacturerAccess() 0x0005 Static DF Signature

The bq40z50-R3 device can return the data flash checksum. The signature of all static DF returns on a subsequent read on *ManufacturerBlockAccess()* or *ManufacturerData()*. MSB is set to 1 if the calculated signature does not match the signature stored in DF.

15.1.7 ManufacturerAccess() 0x0006 Chemical ID

This command returns the chemical ID of the OCV tables used in the gauging algorithm. The chemical ID returns on a subsequent read on *ManufacturerBlockAccess()* or *ManufacturerData()*.

15.1.8 ManufacturerAccess() 0x0008 Static Chem DF Signature

The bq40z50-R3 device can return the data flash checksum. The signature of all static chemistry DF returns on subsequent read on *ManufacturerBlockAccess()* or *ManufacturerData()*. MSB is set to 1 if the calculated signature does not match the signature stored in DF.

15.1.9 ManufacturerAccess() 0x0009 All DF Signature

The bq40z50-R3 device can return the data flash checksum. The signature of all DF parameters returns on a subsequent read on *ManufacturerBlockAccess()* or *ManufacturerData()*. MSB is set to 1 if the calculated signature does not match the signature stored in DF. It is expected that this signature will change due to updates of lifetime, gauging, and other information.

15.1.10 ManufacturerAccess() 0x0010 SHUTDOWN Mode

To reduce power consumption, the device can be sent to SHUTDOWN mode before shipping. After sending this command, the *OperationStatus()[SDM]* = 1, an internal counter will start, and the CHG and DSG FETs will be turned off when the counter reaches ***Ship FET Off Time***. When the counter reaches Ship Delay time, the device will enter SHUTDOWN mode if no charger present is detected.

If the device is SEALED, this feature requires the command to be sent twice in a row within 4 seconds (for safety purposes). If the device is in UNSEALED or FULL ACCESS mode, sending the command the second time will cancel the delay and enter shutdown immediately.

To wake up the device, a voltage > ***Charger Present Threshold*** must apply to the PACK pin. The bq40z50-R3 device will power up and a full reset is applied.

15.1.11 ManufacturerAccess() 0x0011 SLEEP Mode

If the sleep conditions are met, the device can be sent to sleep with *ManufacturerAccess()*.

Status	Condition	Action
Enable	0x0011 to *ManufacturerAccess()*	*OperationStatus()[SLEEPM]* = 1
Activate	***DA Configuration[NR]*** = 0 AND *OperationStatus()[PRES]* = 0 AND |*Current()*| < ***Power:Sleep Current***	Turn off CHG FET, DSG FET, PCHG FET The device goes to sleep. The device wakes up every Power***:Sleep Voltage Time*** period to measure voltage and temperature. The device wakes up every Power***:Sleep Current Time*** period to measure current.
Activate	***DA Configuration[NR]*** = 1 AND |*Current()*| < ***Power:Sleep Current***	Turn off PCHG FET Turn off CHG FET if ***FET Options[SLEEPCHG]*** = 0 The device goes to sleep. The device wakes up every Power***:Sleep Voltage Time*** period to measure voltage and temperature. The device wakes up every Power***:Sleep Current Time*** period to measure current.
Exit	***DA Configuration[NR]*** = 0 AND *OperationStatus()[PRES]* = 1	*OperationStatus()[SLEEPM]* = 0 Return to NORMAL mode
Exit	|*Current()*| > Configuration:Sleep Current	*OperationStatus()[SLEEPM]* = 0 Return to NORMAL mode
Exit	Wake Comparator trips	*OperationStatus()[SLEEPM]* = 0 Return to NORMAL mode
Exit	*SafetyAlert()* flag or *PFAlert()* flag set	*OperationStatus()[SLEEPM]* = 0 Return to NORMAL mode

15.1.12 ManufacturerAccess() 0x0013 AutoCCOffset

This command manually starts an ***CC Auto Offset*** calibration. The calibration takes about 16 s.

This value is updated to ***CC Auto Offset***, and is used for cell current measurement when the device is in CHARGING or DISCHARGING state. This offset is not used during RELAX mode. The cell current measurement is a current measurement taken simultaneously as the cell voltage measurement.

15.1.13 ManufacturerAccess() 0x001D Fuse Toggle

This command manually activates/deactivates the FUSE output to ease testing during manufacturing. If the *OperationStatus()[FUSE]* = 0, it indicates the FUSE output is low. Sending this command toggles the FUSE output to be high and the *OperationStatus()[FUSE]* = 1.

15.1.14 ManufacturerAccess() 0x001E PCHG FET Toggle

This command turns on/off the PCHG FET drive function to ease testing during manufacturing. If the *ManufacturingStatus()[PCHG_TEST]* = 0, sending this command turns on the PCHG FET and the *ManufacturingStatus()[PCHG_TEST]* = 1 and vice versa. This toggling command is only enabled if *ManufacturingStatus()[FET_EN]* = 0, indicating an FW FET control is not active and manual control is allowed. A reset clears the *[PCHG_TEST]* flag and turns off the PCHG FET.

15.1.15 ManufacturerAccess() 0x001F CHG FET Toggle

This command turns on/off the CHG FET drive function to ease testing during manufacturing. If the *ManufacturingStatus()[CHG_TEST]* = 0, sending this command turns on the CHG FET and the *ManufacturingStatus()[CHG_TEST]* = 1 and vice versa. This toggling command is only enabled if *ManufacturingStatus()[FET_EN]* = 0, indicating an FW FET control is not active and manual control is allowed. A reset clears the *[CHG_TEST]* flag and turns off the CHG FET.

15.1.16 ManufacturerAccess() 0x0020 DSG FET Toggle

This command turns on/off DSG FET drive function to ease testing during manufacturing. If the *ManufacturingStatus()[DSG_TEST]* = 0, sending this command turns on the DSG FET and the *ManufacturingStatus()[DSG_TEST]* = 1 and vice versa. This toggling command is only enabled if *ManufacturingStatus()[FET_EN]* = 0, indicating an FW FET control is not active and manual control is allowed. A reset clears the *[DSG_TEST]* flag and turns off the DSG FET.

15.1.17 ManufacturerAccess() 0x0021 Gauging

This command enables/disables the gauging function to ease testing during manufacturing. The initial setting is loaded from ***Mfg Status Init[GAUGE_EN]***. If the *ManufacturingStatus()[GAUGE_EN]* = 0, sending this command enables gauging and the *ManufacturingStatus()[GAUGE_EN]* = 1 and vice versa.

In UNSEALED mode, the *ManufacturingStatus()[GAUGE_EN]* status is copied to ***Mfg Status Init[GAUGE_EN]*** when the command is received by the gauge. The bq40z50-R3 device remains on its latest gauging status prior to a reset.

15.1.18 ManufacturerAccess() 0x0022 FET Control

This command enables/disables control of the CHG, DSG, and PCHG FETs by the firmware. The initial setting is loaded from ***Mfg Status Init[FET_EN]***. If the *ManufacturingStatus()[FET_EN]* = 0, sending this command allows the FW to control the PCHG, CHG, and DSG FETs and the *ManufacturingStatus()[FET_EN]* = 1 and vice versa.

In UNSEALED mode, the *ManufacturingStatus()[FET_EN]* status is copied to ***Mfg Status Init[FET_EN]*** when the command is received by the gauge. The bq40z50-R3 device remains on its latest FET control status prior to a reset.

15.1.19 ManufacturerAccess() 0x0023 Lifetime Data Collection

This command enables/disables ***Lifetime Data Collection*** to help streamline production testing. The initial setting is loaded from ***Mfg Status Init[LF_EN]***. If the *ManufacturingStatus()[LF_EN]* = 0, sending this command starts the ***Lifetime Data Collection*** and the *ManufacturingStatus()[LF_EN]* = 1 and vice versa.

In UNSEALED mode, the *ManufacturingStatus()[LF_EN]* status is copied to ***Mfg Status Init[LF_EN]*** when the command is received by the gauge. The bq40z50-R3 device remains on its latest ***Lifetime Data Collection*** setting prior to a reset.

15.1.20 ManufacturerAccess() 0x0024 Permanent Failure

This command enables/disables ***Permanent Failure*** to help streamline production testing.

The initial setting is loaded from ***Mfg Status Init[PF_EN]***. If the *ManufacturingStatus()[PF_EN]* = 0, sending this command enables Permanent Failure protections and the *ManufacturingStatus()[PF_EN]* = 1 and vice versa.

In UNSEALED mode, *ManufacturingStatus()[PF_EN]* status is copied to ***Mfg Status Init[PF_EN]*** when the command is received by the gauge. The bq40z50-R3 device remains on its PF enable/disable setting prior to a reset.

15.1.21 ManufacturerAccess() 0x0025 Black Box Recorder

This command enables/disables Black Box Recorder function to help streamline production testing. The initial setting is loaded from ***Mfg Status Init[BBR_EN]***. If the *ManufacturingStatus()[BBR_EN]* = 0, sending this command enables the Black Box Recorder and the *ManufacturingStatus()[BBR_EN]* = 1 and vice versa.

In UNSEALED mode, the *ManufacturingStatus()[BBR_EN]* status is copied to ***Mfg Status Init[BBR_EN]*** when the command is received by the gauge. The bq40z50-R3 device remains on its latest Black Box Recorder enable/disable setting prior to a reset.

15.1.22 ManufacturerAccess() 0x0026 Fuse

This command enables/disables firmware-based fuse activation to ease testing during manufacturing. The initial setting is loaded from ***Mfg Status Init[FUSE_EN]***. If the *ManufacturingStatus()[FUSE_EN]* = 0, sending this command allows the FW to control the FUSE output and the *ManufacturingStatus()[FUSE_EN]* = 1 and vice versa.

In UNSEALED mode, the *ManufacturingStatus()[FUSE_EN]* status is copied to ***Mfg Status Init[FUSE_EN]*** when the command is received by the gauge. The bq40z50-R3 device remains on its latest Fuse Control setting prior to a reset.

15.1.23 ManufacturerAccess() 0x0027 LED DISPLAY Enable

This command enables/disables the LED display function to ease testing during manufacturing. The initial setting is loaded from ***Mfg Status Init[LED_EN]***. If the *ManufacturingStatus()[LED_EN]* = 0, sending this command will enable the LED display and the *ManufacturingStatus()[LED_EN]* = 1 and vice versa.

In UNSEALED mode, the *ManufacturingStatus()[LED_EN]* status is copied to ***Mfg Status Init[LED_EN]*** when the command is received by the gauge. The bq40z50-R3 device remains on its latest setting prior to a reset.

15.1.24 ManufacturerAccess() 0x0028 Lifetime Data Reset

Sending this command resets ***Lifetime Data*** in data flash to help streamline production testing.

15.1.25 ManufacturerAccess() 0x0029 Permanent Fail Data Reset

Sending this command resets PF data in data flash to help streamline production testing.

15.1.26 ManufacturerAccess() 0x002A Black Box Recorder Reset

Sending this command resets the Black Box Recorder data in data flash to help streamline production testing.

15.1.27 ManufacturerAccess() 0x002B LED TOGGLE

This command toggles the LED display on or off to help streamline testing during manufacturing. When the LED display is off, the *OperationStatus()[LED]* = 0. Sending this command turns on all LED displays with *OperationStatus()[LED]* set to 1, and vice versa.

15.1.28 ManufacturerAccess() 0x002C LED DISPLAY PRESS

This command simulates a low-high-low detection of the $\overline{\text{DISP}}$ pin, activating the LED display according to the LED Support data flash setting. This command forces RSOC to 100% in order to demonstrate all LEDs in use, the full speed, and the brightness.

15.1.29 ManufacturerAccess() 0x002D CALIBRATION Mode

This command disables/enables entry into CALIBRATION mode. Status is indicated by the *ManufacturingStatus()[CAL_EN]* flag. CALIBRATION mode is disabled upon a reset.

Status	Condition	Action
Disable	*ManufacturingStatus()[CAL_EN]* = 1 AND 0x002D to *ManufacturerAccess()*	*ManufacturingStatus()[CAL_EN]* = 0 Disable output of ADC and CC raw data on *ManufacturingData()*
Enable	*ManufacturingStatus()[CAL_EN]* = 0 AND 0x002D to *ManufacturerAccess()*	*ManufacturingStatus()[CAL_EN]* = 1 Enable output of ADC and CC raw data on *ManufacturingData()*, controllable with 0xF081 and 0xF082 on *ManufacturerAccess()*

15.1.30 ManufacturerAccess() 0x002E Lifetime Data Flush

This command flushes the RAM ***Lifetime Data*** to data flash to help streamline evaluation testing.

15.1.31 ManufacturerAccess() 0x002F Lifetime Data SPEED UP Mode

For ease of evaluation testing, this command enables a lifetime SPEED UP mode where every 1 s in real time counts as 1 hour in firmware time. When the lifetime SPEED UP mode is enabled, the *ManufacturingStatus()[LT_TEST]* = 1.

The SPEED UP mode will be disabled if this command is sent again when *[LT_TEST]* = 1, the MAC *LifetimeDataReset()* command is sent, the MAC *SealDevice()* command is sent, or the device is reset.

15.1.32 ManufacturerAccess() 0x0030 Seal Device

This command seals the device for the field, disabling certain SBS commands and access to data flash. See Table 15-1 and Chapter 15 for details.

When the device is sealed, the *OperationStatus()[SEC1, SEC0]* = 1,1. All the test features in *ManufacturingStatus()* will also be disabled.

15.1.33 ManufacturerAccess() 0x0035 Security Keys

This is a read/write command for two-word UNSEAL, FULL ACCESS, Manual PF, and Lifetimes Reset keys.

When reading the keys, data can be read from *ManufacturerData()* or *ManufacturerBlockAccess()*. The keys are returned in the following format: aaAAbbBBccCCddDDeeEEffFFggGGhhHH, where:

Value	Description
AAaa	First word of the UNSEAL key
BBbb	Second word of the UNSEAL key
CCcc	First word of the FULL ACCESS key
DDdd	Second word of the FULL ACCESS key
EEee	First word of the Manual PF key
FFff	Second word of the Manual PF key
GGgg	First word of the Lifetimes Reset key
HHhh	Second word of the Lifetimes Reset key

The default UNSEAL key is 0x0414 and 0x3672. The default FULL ACCESS key is 0xFFFF and 0xFFFF. The default Manual PF key is 0x2857 and 0x2A98. The default Lifetimes Reset key is 0x2B14 and 0x2C8A.

It is highly recommended to change the UNSEAL, FULL ACCESS, Manual PF, and Lifetimes Reset keys from default.

The keys can only be changed through the *ManufacturerBlockAccess()*.

Example: Change UNSEAL key to 0x1234, 0x5678, and leave the other security keys at their default values.

Send an SMBus block write with Command = 0x0035.

Data = MAC command + UNSEAL key + FULL ACCESS KEY + PF key + Lifetimes Reset key
= 35 00 34 12 78 56 FF FF FF FF 57 28 98 2A 14 2B 8A 2C

NOTE: The first word of the keys cannot be the same. That means an UNSEAL key with 0xABCD 0x1234 and FULL ACCESS key with 0xABCD 0x5678 are not valid because the first word is the same.

This is because the first word is used as a “detection” for the right command. This also means the first word cannot be the same as any existing MAC command.

15.1.34 ManufacturerAccess() 0x0037 Authentication Key

This command enables the update of the authentication key into the device. The bq40z50-R3 device must be in FULL ACCESS mode for the authentication key to update.

To update a new authentication key:

- Send the *AuthenticationKey()* + the new 128-bit authentication key to *ManufacturerBlockAccess()* OR
- Send the *AuthenticationKey()* to *ManufacturerAccess()*, then send the 128-bit authentication key to *Authenticate()*.

There is no direct read access to the authentication key. After writing the new authentication to the gauge, the gauge will generate an all-zero challenge and provide the corresponding response for verification.

To verify the new authentication key:

- Read the response from *ManufacturerBlockAccess()* after updating the new authentication key OR
- Read the response from *Authenticate()* after updating the new authentication key.

The bq40z50-R3 device also includes the capability to store the authentication key in secure memory. This is controlled using the ***SHA1_SECURE*** data flash bit; however, the authentication key cannot be written into the device using *AuthenticationKey()* as described above. It must be programmed using a separate method. Also, when using secure memory, the authentication key can only be written once and cannot be changed after it is written.

15.1.35 ManufacturerAccess() 0x0041 Device Reset

This command resets the device.

NOTE: Command 0x0012 also resets the device (for backwards compatibility with the bq30zxy device).

15.1.36 ManufacturerAccess() 0x0050 SafetyAlert

This command returns the *SafetyAlert()* flags on *ManufacturerBlockAccess()* or *ManufacturerData()*.

31	30	29	28	27	26	25	24	23	22	21	20	19	18	17	16
RSVD	RSVD	OCDL	COVL	UTD	UTC	PCHGC	CHGV	CHGC	OC	CTOS	CTO	PTOS	PTO	RSVD	OTF
15	**14**	**13**	**12**	**11**	**10**	**9**	**8**	**7**	**6**	**5**	**4**	**3**	**2**	**1**	**0**
RSVD	CUVC	OTD	OTC	ASCDL	RSVD	ASCCL	RSVD	AOLDL	RSVD	OCD2	OCD1	OCC2	OCC1	COV	CUV

RSVD (Bits 31–30): Reserved. Do not use.

OCDL (Bit 29): Overcurrent in Discharge
- 1 = Detected
- 0 = Not Detected

COVL (Bit 28): Cell Overvoltage Latch
- 1 = Detected
- 0 = Not Detected

UTD (Bit 27): Undertemperature During Discharge
- 1 = Detected
- 0 = Not Detected

UTC (Bit 26): Undertemperature During Charge
- 1 = Detected
- 0 = Not Detected

PCHGC (Bit 25): Over-Precharge Current
- 1 = Detected
- 0 = Not Detected

CHGV (Bit 24): Overcharging Voltage
- 1 = Detected
- 0 = Not Detected

CHGC (Bit 23): Overcharging Current
- 1 = Detected
- 0 = Not Detected

OC (Bit 22): Overcharge
- 1 = Detected
- 0 = Not Detected

CTOS (Bit 21): Charge Timeout Suspend
- 1 = Detected
- 0 = Not Detected

CTO (Bit 20): Charge Timeout
- 1 = Detected
- 0 = Not Detected

PTOS (Bit 19): Precharge Timeout Suspend
- 1 = Detected
- 0 = Not Detected

PTO (Bit 18): Precharge Timeout
- 1 = Detected
- 0 = Not Detected

RSVD (Bit 17): Reserved. Do not use.

OTF (Bit 16): Overtemperature FET
- 1 = Detected
- 0 = Not Detected

RSVD (Bit 15): Reserved. Do not use.

CUVC (Bit 14): Cell Undervoltage Compensated
- 1 = Detected
- 0 = Not Detected

OTD (Bit 13): Overtemperature During Discharge
- 1 = Detected
- 0 = Not Detected

OTC (Bit 12): Overtemperature During Charge
- 1 = Detected
- 0 = Not Detected

ASCDL (Bit 11): Short-Circuit During Discharge Latch
- 1 = Detected
- 0 = Not Detected

RSVD (Bit 10): Reserved. Do not use.

ASCCL (Bit 9): Short-Circuit During Charge Latch
- 1 = Detected

0 = Not Detected

RSVD (Bit 8): Reserved. Do not use.

AOLDL (Bit 7): Overload During Discharge Latch

1 = Detected

0 = Not Detected

RSVD (Bit 6): Reserved. Do not use.

OCD2 (Bit 5): Overcurrent During Discharge 2

1 = Detected

0 = Not Detected

OCD1 (Bit 4): Overcurrent During Discharge 1

1 = Detected

0 = Not Detected

OCC2 (Bit 4): Overcurrent During Charge 2

1 = Detected

0 = Not Detected

OCC1 (Bit 2): Overcurrent During Charge 1

1 = Detected

0 = Not Detected

COV (Bit 1): Cell Overvoltage

1 = Detected

0 = Not Detected

CUV (Bit 0): Cell Undervoltage

1 = Detected

0 = Not Detected

15.1.37 ManufacturerAccess() 0x0051 SafetyStatus

This command returns the *SafetyStatus()* flags on *ManufacturerBlockAccess()* or *ManufacturerData()*.

31	30	29	28	27	26	25	24	23	22	21	20	19	18	17	16
RSVD	RSVD	OCDL	COVL	UTD	UTC	PCHGC	CHGV	CHGC	OC	RSVD	CTO	RSVD	PTO	RSVD	OTF
15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
RSVD	CUVC	OTD	OTC	ASCDL	ASCD	ASCCL	ASCC	AOLDL	AOLD	OCD2	OCD1	OCC2	OCC1	COV	CUV

RSVD (Bits 31–30): Reserved. Do not use.

OCDL (Bit 29): Overcurrent in Discharge

1 = Detected

0 = Not Detected

COVL (Bit 28): Cell Overvoltage Latch

1 = Detected

0 = Not Detected

UTD (Bit 27): Undertemperature During Discharge

1 = Detected

0 = Not Detected

UTC (Bit 26): Undertemperature During Charge
- 1 = Detected
- 0 = Not Detected

PCHGC (Bit 25): Over-Precharge Current
- 1 = Detected
- 0 = Not Detected

CHGV (Bit 24): Overcharging Voltage
- 1 = Detected
- 0 = Not Detected

CHGC (Bit 23): Overcharging Current
- 1 = Detected
- 0 = Not Detected

OC (Bit 22): Overcharge
- 1 = Detected
- 0 = Not Detected

RSVD (Bit 21): Reserved. Do not use.

CTO (Bit 20): Charge Timeout
- 1 = Detected
- 0 = Not Detected

RSVD (Bit 19): Reserved. Do not use.

PTO (Bit 18): Precharge Timeout
- 1 = Detected
- 0 = Not Detected

RSVD (Bit 17): Reserved. Do not use.

OTF (Bit 16): Overtemperature FET
- 1 = Detected
- 0 = Not Detected

RSVD (Bit 15): Reserved. Do not use.

CUVC (Bit 14): Cell Undervoltage Compensated
- 1 = Detected
- 0 = Not Detected

OTD (Bit 13): Overtemperature During Discharge
- 1 = Detected
- 0 = Not Detected

OTC (Bit 12): Overtemperature During Charge
- 1 = Detected
- 0 = Not Detected

ASCDL (Bit 11): Short-circuit During Discharge Latch
- 1 = Detected
- 0 = Not Detected

ASCD (Bit 10): Short-circuit During Discharge
- 1 = Detected
- 0 = Not Detected

ASCCL (Bit 9): Short-circuit During Charge Latch
1 = Detected
0 = Not Detected

ASCC (Bit 8): Short-circuit During Charge
1 = Detected
0 = Not Detected

AOLDL (Bit 7): Overload During Discharge Latch
1 = Detected
0 = Not Detected

AOLD (Bit 6): Overload During Discharge
1 = Detected
0 = Not Detected

OCD2 (Bit 5): Overcurrent During Discharge 2
1 = Detected
0 = Not Detected

OCD1 (Bit 4): Overcurrent During Discharge 1
1 = Detected
0 = Not Detected

OCC2 (Bit 3): Overcurrent During Charge 2
1 = Detected
0 = Not Detected

OCC1 (Bit 2): Overcurrent During Charge 1
1 = Detected
0 = Not Detected

COV (Bit 1): Cell Overvoltage
1 = Detected
0 = Not Detected

CUV (Bit 0): Cell Undervoltage
1 = Detected
0 = Not Detected

15.1.38 ManufacturerAccess() 0x0052 PFAlert

This command returns the *PFAlert()* flags on *ManufacturerBlockAccess()* or *ManufacturerData()*.

31	30	29	28	27	26	25	24	23	22	21	20	19	18	17	16
TS4	TS3	TS2	TS1	RSVD	RSVD	RSVD	RSVD	RSVD	2LVL	AFEC	AFER	FUSE	OCDL	DFE TF	CFE TF
15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
ASC DL	ASC CL	AOL DL	VIMA	VIMR	CD	IMP	CB	QIM	SOTF	COVL	SOT	SOCD	SOCC	SOV	SUV

TS4 (Bit 31): Open Thermistor–TS4 Failure
1 = Detected
0 = Not Detected

TS3 (Bit 30): Open Thermistor–TS3 Failure

1 = Detected
0 = Not Detected

TS2 (Bit 29): Open Thermistor–TS2 Failure
1 = Detected
0 = Not Detected

TS1 (Bit 28): Open Thermistor–TS1 Failure
1 = Detected
0 = Not Detected

RSVD (Bits 27–23): Reserved. Do not use.

2LVL (Bit 22): Second Level Protector Failure
1 = Detected
0 = Not Detected

AFEC (Bit 21): AFE Communication Failure
1 = Detected
0 = Not Detected

AFER (Bit 20): AFE Register Failure
1 = Detected
0 = Not Detected

FUSE (Bit 19): Chemical Fuse Failure
1 = Detected
0 = Not Detected

OCDL (Bit 18): Overcurrent in Discharge
1 = Detected
0 = Not Detected

DFETF (Bit 17): Discharge FET Failure
1 = Detected
0 = Not Detected

CFETF (Bit 16): Charge FET Failure
1 = Detected
0 = Not Detected

ASCDL (Bit 15): Short Circuit in Discharge
1 = Detected
0 = Not Detected

ASCCL (Bit 14): Short Circuit in Charge
1 = Detected
0 = Not Detected

AOLDL (Bit 13): Overload in Discharge
1 = Detected
0 = Not Detected

VIMA (Bit 12): Voltage Imbalance While Pack Is Active Failure
1 = Detected
0 = Not Detected

VIMR (Bit 11): Voltage Imbalance While Pack Is At Rest Failure
1 = Detected

0 = Not Detected

CD (Bit 10): Capacity Degradation Failure
1 = Detected
0 = Not Detected

IMP (Bit 9): Impedance Failure
1 = Detected
0 = Not Detected

CB (Bit 8): Cell Balancing Failure
1 = Detected
0 = Not Detected

QIM (Bit 7): QMax Imbalance Failure
1 = Detected
0 = Not Detected

SOTF (Bit 6): Safety Overtemperature FET Failure
1 = Detected
0 = Not Detected

COVL (Bit 5): Cell Overvoltage Latch
1 = Detected
0 = Not Detected

SOT (Bit 4): Safety Overtemperature Cell Failure
1 = Detected
0 = Not Detected

SOCD (Bit 3): Safety Overcurrent in Discharge
1 = Detected
0 = Not Detected

SOCC (Bit 2): Safety Overcurrent in Charge
1 = Detected
0 = Not Detected

SOV (Bit 1): Safety Cell Overvoltage Failure
1 = Detected
0 = Not Detected

SUV (Bit 0): Safety Cell Undervoltage Failure
1 = Detected
0 = Not Detected

15.1.39 ManufacturerAccess() 0x0053 PFStatus

This command returns the *PFStatus()* flags on *ManufacturerBlockAccess()* or *ManufacturerData()*.

31	30	29	28	27	26	25	24	23	22	21	20	19	18	17	16
TS4	TS3	TS2	TS1	RSVD	DFW	FORC E	IFC	PTC	2LVL	AFEC	AFER	FUSE	OCDL	DFE TF	CFE TF
15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
ASC DL	ASC CL	AOL DL	VIMA	VIMR	CD	IMP	CB	QIM	SOTF	COVL	SOT	SOCD	SOCC	SOV	SUV

TS4 (Bit 31): Open Thermistor–TS4 Failure
1 = Detected
0 = Not Detected

TS3 (Bit 30): Open Thermistor–TS3 Failure
1 = Detected
0 = Not Detected

TS2 (Bit 29): Open Thermistor–TS2 Failure
1 = Detected
0 = Not Detected

TS1 (Bit 28): Open Thermistor–TS1 Failure
1 = Detected
0 = Not Detected

RSVD (Bit 27): Reserved. Do not use.

DFW (Bit 26): Data Flash Wearout Failure
1 = Detected
0 = Not Detected

FORCE (Bit 25): Manual PF

IFC (Bit 24): Instruction Flash Checksum Failure
1 = Detected
0 = Not Detected

PTC (Bit 23): PTC Failure
1 = Detected
0 = Not Detected

2LVL (Bit 22): Second Level Protector Failure
1 = Detected
0 = Not Detected

AFEC (Bit 21): AFE Communication Failure
1 = Detected
0 = Not Detected

AFER (Bit 20): AFE Register Failure
1 = Detected
0 = Not Detected

FUSE (Bit 19): Chemical Fuse Failure
1 = Detected
0 = Not Detected

OCDL (Bit 18): Overcurrent in Discharge
1 = Detected
0 = Not Detected

DFETF (Bit 17): Discharge FET Failure
1 = Detected
0 = Not Detected

CFETF (Bit 16): Charge FET Failure
1 = Detected

0 = Not Detected

ASCDL (Bit 15): Short Circuit in Discharge

1 = Detected

0 = Not Detected

ASCCL (Bit 14): Short Circuit in Charge

1 = Detected

0 = Not Detected

AOLDL (Bit 13): Overload in Discharge

1 = Detected

0 = Not Detected

VIMA (Bit 12): Voltage Imbalance While Pack Is Active Failure

1 = Detected

0 = Not Detected

VIMR (Bit 11): Voltage Imbalance While Pack At Rest Failure

1 = Detected

0 = Not Detected

CD (Bit 10): Capacity Degradation Failure

1 = Detected

0 = Not Detected

IMP (Bit 9): Impedance Failure

1 = Detected

0 = Not Detected

CB (Bit 8): Cell Balancing Failure

1 = Detected

0 = Not Detected

QIM (Bit 7): QMax Imbalance Failure

1 = Detected

0 = Not Detected

SOTF (Bit 6): Safety Overtemperature FET Failure

1 = Detected

0 = Not Detected

COVL (Bit 5): Cell Overvoltage Latch

1 = Detected

0 = Not Detected

SOT (Bit 4): Safety Overtemperature Cell Failure

1 = Detected

0 = Not Detected

SOCD (Bit 3): Safety Overcurrent in Discharge

1 = Detected

0 = Not Detected

SOCC (Bit 2): Safety Overcurrent in Charge

1 Detected

0 Not Detected

SOV (Bit 1): Safety Cell Overvoltage Failure

1 = Detected

0 = Not Detected

SUV (Bit 0): Safety Cell Undervoltage Failure

1 = Detected

0 = Not Detected

15.1.40 ManufacturerAccess() 0x0054 OperationStatus

This command returns the *OperationStatus()* flags on *ManufacturerBlockAccess()* or *ManufacturerData()*.

31	30	29	28	27	26	25	24	23	22	21	20	19	18	17	16
IOSHUT	PSSHUT	DISCONN	CB	SLPCC	SLPAD	SMBLCAL	INIT	SLEEPM	XL	CAL_OFFSET	CAL	AUTOCALM	AUTH	LED	SDM
15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
SLEEP	XCHG	XDSG	PF	SS	SDV	SEC1	SEC0	BTP_INT	EMSHUT	FUSE	ACTHR	PCHG	CHG	DSG	PRES

IOSHUT (Bit 31): IO-based shutdown

1 = Active

0 = Inactive

PSSHUT (Bit 30): Power saving shutdown

1 = Active

0 = Inactive

DISCONN (Bit 29): System disconnect

1 = Active

0 = Inactive

CB (Bit 28): Cell balancing status

1 = Active

0 = Inactive

SLPCC (Bit 27): CC measurement in SLEEP mode

1 = Active

0 = Inactive

SLPAD (Bit 26): ADC measurement in SLEEP mode

1 = Active

0 = Inactive

SMBLCAL (Bit 25): Auto CC calibration when the bus is low. This bit may not be read by the host because the FW will clear it when a communication is detected.

1 = Auto CC calibration starts

0 = When the bus is high or communication is detected for the case of ***[IN_SYSTEM_SLEEP]*** = 1.

INIT (Bit 24): Initialization after full reset

1 = Active

0 = Inactive

SLEEPM (Bit 23): SLEEP mode triggered via command

1 = Active

0 = Inactive

XL (Bit 22): 400-kHz SMBus mode
- 1 = Active
- 0 = Inactive

CAL_OFFSET (Bit 21): Calibration Output (raw CC offset data)
- 1 = Active when MAC *OutputShortedCCADCCal()* is sent and the raw shorted CC data for calibration is available.
- 0 = When the raw shorted CC data for calibration is not available.

CAL (Bit 20): Calibration Output (raw ADC and CC data)
- 1 = Active when either the MAC *OutputCCADCCal()* or *OutputShortedCCADCCal()* is sent and the raw CC and ADC data for calibration is available.
- 0 = When the raw CC and ADC data for calibration is not available.

AUTOCALM (Bit 19): ***CC Auto Offset*** Calibration by MAC *AutoCCOffset()*
- 1 = The gauge receives the MAC *AutoCCOffset()* and starts the ***CC Auto Offset*** calibration.
- 0 = Clear when the calibration is completed.

AUTH (Bit 18): Authentication in progress
- 1 = Active
- 0 = Inactive

LED (Bit 17): LED Display
- 1 = LED display is on.
- 0 = LED display is off.

SDM (Bit 16): Shutdown triggered via command
- 1 = Active
- 0 = Inactive

SLEEP (Bit 15): SLEEP mode conditions met
- 1 = Active
- 0 = Inactive

XCHG (Bit 14): Charging disabled
- 1 = Active
- 0 = Inactive

XDSG (Bit 13): Discharging disabled
- 1 = Active
- 0 = Inactive

PF (Bit 12): PERMANENT FAILURE mode status
- 1 = Active
- 0 = Inactive

SS (Bit 11): SAFETY status. This is the ORd value of all the Safety Status bits.
- 1 = Active
- 0 = Inactive

SDV (Bit 10): Shutdown triggered via low battery stack voltage
- 1 = Active
- 0 = Inactive

SEC1, SEC0 (Bits 9–8): SECURITY mode
- 0, 0 = Reserved
- 0, 1 = Full Access
- 1, 0 = Unsealed

1, 1 = Sealed

BTP_INT (Bit 7): Battery Trip Point Interrupt. Setting and clearing this bit depends on various conditions. See Section 6.9 for details.

EMSHUT (Bit 6): Emergency FET Shutdown

1 = Active

0 = Inactive

FUSE (Bit 5): Fuse status

1 = Active

0 = Inactive

ACTHR (Bit 4): Accumulated Charge Threshold

1 = Active

0 = Inactive

PCHG (Bit 3): Precharge FET status

1 = Active

0 = Inactive

CHG (Bit 2): CHG FET status

1 = Active

0 = Inactive

DSG (Bit 1): DSG FET status

1 = Active

0 = Inactive

PRES (Bit 0): System present low

1 = Active

0 = Inactive

15.1.41 ManufacturerAccess() 0x0055 ChargingStatus

This command returns the *ChargingStatus()* and Temperature Range flags on *ManufacturerBlockAccess()* or *ManufacturerData()*.

								23	22	21	20	19	18	17	16
								RSVD	RSVD	ERETM	ERM	NCT	CCC	CVR	CCR
15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
VCT	MCHG	SU	IN	HV	MV	LV	PV	RSVD	OT	HT	STH	RT	STL	LT	UT

RSVD (Bits 23–22): Reserved. Do not use.

ERETM (Bit 21): ELEVATED RSOC and TEMPERATURE modes

1 = Active

0 = Inactive

ERM (Bit 20): ELEVATED RSOC mode

1 = Active

0 = Inactive

NCT (Bit 19): Near Charge Termination. This flag indicates the pack may be within 40 seconds of charge termination. When smoothing is enabled and while NCT is high, *RemainingCapacity()* will be smoothed to 100% over the next 40 seconds.

1 = Active

0 = Inactive

CCC (Bit 18): Charging Loss Compensation

1 = Active

0 = Inactive

CVR (Bit 17): Charging Voltage Rate of Change

1 = Active

0 = Inactive

CCR (Bit 16): Charging Current Rate of Change

1 = Active

0 = Inactive

VCT (Bit 15): Charge Termination

1 = Active

0 = Inactive

MCHG (Bit 14): Maintenance Charge

1 = Active

0 = Inactive

SU (Bit 13): Suspend Charge

1 = Active

0 = Inactive

IN (Bit 12): Charge Inhibit

1 = Active

0 = Inactive

HV (Bit 11): High Voltage Region

1 = Active

0 = Inactive

MV (Bit 10): Mid Voltage Region

1 = Active

0 = Inactive

LV (Bit 9): Low Voltage Region

1 = Active

0 = Inactive

PV (Bit 8): Precharge Voltage Region

1 = Active

0 = Inactive

Temperature Range Flags (Bits 7–0):

RSVD (Bit 7): Reserved. Do not use.

OT (Bit 6): Overtemperature Region

1 = Active

0 = Inactive

HT (Bit 5): High Temperature Region

1 = Active

0 = Inactive

STH (Bit 4): Standard Temperature High Region

1 = Active

0 = Inactive

RT (Bit 3): Recommended Temperature Region

1 = Active

0 = Inactive

STL (Bit 2): Standard Temperature Low Region

1 = Active

0 = Inactive

LT (Bit 1): Low Temperature Region

1 = Active

0 = Inactive

UT (Bit 0): Undertemperature Region

1 = Active

0 = Inactive

15.1.42 ManufacturerAccess() 0x0056 GaugingStatus

This command returns the *GaugingStatus()* flags on *ManufacturerBlockAccess()* or *ManufacturerData()*.

								23	22	21	20	19	18	17	16
								RSVD	RSVD	RSVD	OCV FR	LDMD	RX	QMax	VDQ
15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
NSFM	RSVD	SLP QMax	QEN	VOK	R_DIS	RSVD	REST	CF	DSG	EDV	BAL_ EN	TC	TD	FC	FD

RSVD (Bits 23–21): Reserved. Do not use.

OCVFR (Bit 20): Open Circuit Voltage in Flat Region (During RELAX)

1 = Detected

0 = Not Detected

LDMD (Bit 19): LOAD mode

1 = Constant Power

0 = Constant Current

RX (Bit 18): Resistance Update (toggles after every resistance update)

QMax (Bit 17): QMax Update (toggles after every QMax update)

VDQ (Bit 16): Discharge Qualified for Learning (opposite of the R_DIS flag)

1 = Detected

0 = Not Detected

NSFM (Bit 15): Negative Scale Factor Mode

1 = Negative Ra Scaling Factor Detected

0 = Negative Ra Scaling Factor Not Detected

RSVD (Bit 14): Reserved. Do not use.

SLPQMax (Bit 13): OCV update in SLEEP mode

1 = Active. OCV reading in process

0 = Inactive. Completed OCV reading

QEN (Bit 12): Impedance Track Gauging (Ra and QMax updates are enabled.)

1 = Enabled

0 = Disabled

VOK (Bit 11): Voltages are OK for QMax update. This flag is updated at exit of the RELAX mode.

1 = A DOD is saved for next QMax update.

0 = No DOD saved and QMax update is not possible.

R_DIS (Bit 10): Resistance Updates

1 = Disabled

0 = Enabled

RSVD (Bit 9): Reserved. Do not use.

REST (Bit 8): Rest

1 = OCV Reading Taken

0 = OCV Reading Not Taken or Not in RELAX

CF (Bit 7): Condition Flag

1 = *MaxError()* > Max Error Limit (condition cycle needed)

0 = *MaxError()* < Max Error Limit (condition cycle not needed)

DSG (Bit 6): Discharge/Relax

1 = Charging Not Detected

0 = Charging Detected

EDV (Bit 5): End-of-Discharge Termination Voltage

1 = Termination voltage reached during discharge

0 = Termination voltage not reached, or not in DISCHARGE mode

BAL_EN (Bit 4): Cell Balancing

1 = Cell balancing is possible if enabled.

0 = Cell balancing is not allowed.

TC (Bit 3): Terminate Charge

1 = Detected

0 = Not Detected

TD (Bit 2): Terminate Discharge

1 = Detected

0 = Not Detected

FC (Bits 1): Fully Charged

1 = Detected

0 = Not Detected

FD (Bit 0): Fully Discharged

1 = Detected

0 = Not Detected

15.1.43 ManufacturerAccess() 0x0057 ManufacturingStatus

This command returns the *ManufacturingStatus()* flags on *ManufacturerBlockAccess()* or *ManufacturerData()*.

15	14	13	12	11	10	9	8
CAL_EN	LT_TEST	RSVD	RSVD	RSVD	RSVD	LED_EN	FUSE_EN

7	6	5	4	3	2	1	0
BBR_EN	PF_EN	LF_EN	FET_EN	GAUGE_EN	DSG_EN	CHG_EN	PCHG_EN

CAL_EN (Bit 15): CALIBRATION mode
- 1 = Enabled
- 0 = Disabled

LT_TEST (Bit 14): LIFETIME SPEED UP mode
- 1 = Enabled
- 0 = Disabled

RSVD (Bits 13–10): Reserved. Do not use.

LED_EN (Bit 9): LED display is enabled with the push button.
- 1 = LED display is on when the push button is pressed.
- 0 = LED display is off when the push button is pressed.

FUSE_EN (Bit 8): Fuse action
- 1 = Enabled
- 0 = Disabled

BBR_EN (Bit 7): Black Box Recorder
- 1 = Enabled
- 0 = Disabled

PF_EN (Bit 6): Permanent Failure
- 1 = Enabled
- 0 = Disabled

LF_EN (Bit 5): ***Lifetime Data Collection***
- 1 = Enabled
- 0 = Disabled

FET_EN (Bit 4): All FET action
- 1 = Enabled
- 0 = Disabled

GAUGE_EN (Bit 3): Gas gauging
- 1 = Enabled
- 0 = Disabled

DSG_EN (Bit 2): Discharge FET test
- 1 = Discharge FET test activated
- 0 = Disabled

CHG_EN (Bit 1): Charge FET test
- 1 = Charge FET test activated
- 0 = Disabled

PCHG_EN (Bit 0): Precharge FET test
- 1 = Precharge FET test activated
- 0 = Disabled

15.1.44 ManufacturerAccess() 0x0058 AFE Register

This command returns the *AFERegister()* values on *ManufacturerBlockAccess()* or *ManufacturerData()*. These are the AFE hardware registers and are intended for internal debug use only.

Status	Condition
Activate	0x0058 to *ManufacturerAccess()*

Action: Output AFE Register values on *ManufacturerBlockAccess()* or *ManufacturerData()* in the following format: AABBCCDDEEFFGGHHIIJJKKLLMMNNOOPPQQRRSSTTUU where:

Value	Description
AA	AFE Interrupt Status. AFE Hardware interrupt status (for example, wake time, push-button, and so on)
BB	AFE FET Status. AFE FET status (for example, CHG FET, DSG FET, PCHG FET, FUSE input, and so on)
CC	AFE RXIN. AFE I/O port input status
DD	AFE Latch Status. AFE protection latch status
EE	AFE Interrupt Enable. AFE interrupt control settings
FF	AFE Control. AFE FET control enable setting
GG	AFE RXIEN. AFE I/O input enable settings
HH	AFE RLOUT. AFE I/O pins output status
II	AFE RHOUT. AFE I/O pins output status
JJ	AFE RHINT. AFE I/O pins interrupt status
KK	AFE Cell Balance. AFE cell balancing enable settings and status
LL	AFE ADC/CC Control. AFE ADC/CC Control settings
MM	AFE ADC Mux Control. AFE ADC channel selections
NN	AFE LED Control
OO	AFE Control. AFE control on various HW based features
PP	AFE Timer Control. AFE comparator and timer control
QQ	AFE Protection. AFE protection delay time control
RR	AFE OCD. AFE OCD settings
SS	AFE SCC. AFE SCC settings
TT	AFE SCD1. AFE SCD1 settings
UU	AFE SCD2. AFE SCD2 settings

15.1.45 ManufacturerAccess() 0x005A No Load Rem Cap

This read-only word command returns the equivalent of *RemainingCapacity()* under a no load condition.

a. *RemainingCapacity()* is calculated by the device with compensation based on Load Select (for example, max, average, current last run, and so on).
b. Because the RTC power consumption is expected to be relatively small, the new parameter provides a better representation of how much actual capacity is available when only powering the RTC circuit.

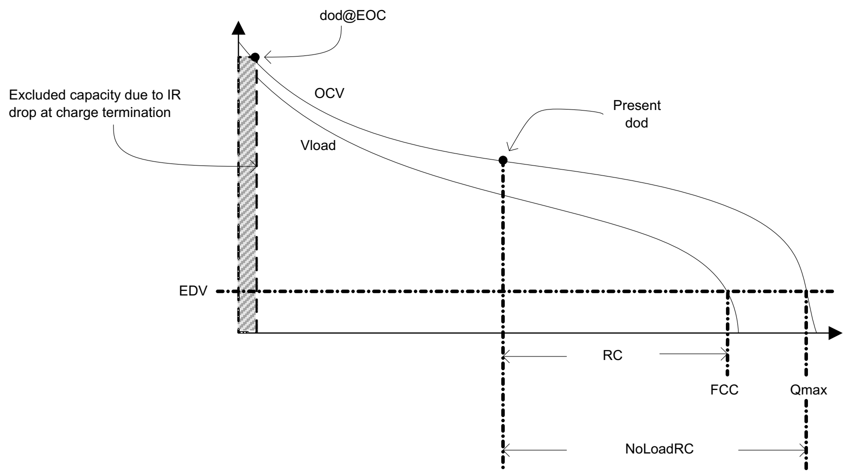


Figure 15-1. No Load

15.1.46 ManufacturerAccess() 0x0060 Lifetime Data Block 1

This command returns the ***Lifetime Data*** with the following format:

aaAAbbBBccCCddDDeeEEffFFggGGhhHHiiIIjjJJkkKKllLLmmMMNNOOPPQQRRSS.

Value	Description
AAaa	Cell 1 Max Voltage
BBbb	Cell 2 Max Voltage
CCcc	Cell 3 Max Voltage
DDdd	Cell 4 Max Voltage
EEee	Cell 1 Min Voltage
FFff	Cell 2 Min Voltage
GGgg	Cell 3 Min Voltage
HHhh	Cell 4 Min Voltage
IIii	Max Delta Cell Voltage
JJjj	Max Charge Current
KKkk	Max Discharge Current
LLll	Max Avg Dsg Current
MMmm	Max Avg Dsg Power
NN	Max Temp Cell
OO	Min Temp Cell
PP	Max Delta Cell Temperature
QQ	Max Temp Int Sensor
RR	Min Temp Int Sensor
SS	Max Temp FET

15.1.47 ManufacturerAccess() 0x0061 Lifetime Data Block 2

This command returns the ***Lifetime Data*** with the following format:

AABBCCDDeeEEffFFggGGhhHHiiIIjjJJkkKKllLL.

Value	Description
AA	No. of Shutdowns
BB	No. of Partial Resets
CC	No. of Full Resets
DD	No. of WDT Resets

Value	Description
FFffEEee	CB Time Cell 1
HHhhGGgg	CB Time Cell 2
JJjjIIii	CB Time Cell 3
LLllKKkk	CB Time Cell 4

15.1.48 ManufacturerAccess() 0x0062 Lifetime Data Block 3

This command returns the ***Lifetime Data*** with the following format:

aaAAbbBB.

Value	Description
BBbbAAaa	Total FW Runtime

15.1.49 ManufacturerAccess() 0x0063 Lifetime Data Block 4

This command returns the ***Lifetime Data*** with the following format:

aaAAbbBBccCCddDDeeEEffFFggGGhhHHiiIIjjJJkkKKllLLmmMMnnNNooOOppPP.

Value	Description
AAaa	No. of COV Events
BBbb	Last COV Event
CCcc	No. of CUV Events
DDdd	Last CUV Event
EEee	No. of OCD1 Events
FFff	Last OCD1 Event
GGgg	No. of OCD2 Events
HHhh	Last OCD2 Event
IIii	No. of OCC1 Events
JJjj	Last OCC1 Event
KKkk	No. of OCC2 Events
LLll	Last OCC2 Event
MMmm	No. of AOLD Events
NNnn	Last AOLD Event
OOoo	No. of ASCD Events
PPpp	Last ASCD Event

15.1.50 ManufacturerAccess() 0x0064 Lifetime Data Block 5

This command returns the ***Lifetime Data*** with the following format:

aaAAbbBBccCCddDDeeEEffFFggGGhhHHiiIIjjJJkkKKllLLmmMMnnNNooOOppPP.

Value	Description
AAaa	No. of ASCC Events
BBbb	Last ASCC Event
CCcc	No. of OTC Events
DDdd	Last OTC Event
EEee	No. of OTD Events
FFff	Last OTD Event
GGgg	No. of OTF Events
HHhh	Last OTF Event
IIii	No. Valid Charge Term
JJjj	Last Valid Charge Term

Value	Description
KKkk	No. of Qmax Updates
LLll	Last Qmax Update
MMmm	No. of Ra Updates
NNnn	Last Ra Update
OOoo	No. of Ra Disable
PPpp	Last Ra Disable

15.1.51 ManufacturerAccess() 0x0065 Lifetime Data Block 6

This command returns the ***Lifetime Data*** with the following format:

aaAAbbBBccCCddDDeeEEffFFggGGhhHHiillJJjjkkKKllLLmmMMnnNNooOOppPP.

Value	Description
BBbbAAaa	Time Spent In UT RSOC A
DDddCCcc	Time Spent In UT RSOC B
FFffEEee	Time Spent In UT RSOC C
HHhhGGgg	Time Spent In UT RSOC D
JJjjIIii	Time Spent In UT RSOC E
LLllKKkk	Time Spent In UT RSOC F
NNnnMMmm	Time Spent In UT RSOC G
PPppOOoo	Time Spent In UT RSOC H

15.1.52 ManufacturerAccess() 0x0066 Lifetime Data Block 7

This command returns the ***Lifetime Data*** with the following format:

aaAAbbBBccCCddDDeeEEffFFggGGhhHHiillJJjjkkKKllLLmmMMnnNNooOOppPP.

Value	Description
BBbbAAaa	Time Spent In LT RSOC A
DDddCCcc	Time Spent In LT RSOC B
FFffEEee	Time Spent In LT RSOC C
HHhhGGgg	Time Spent In LT RSOC D
JJjjIIii	Time Spent In LT RSOC E
LLllKKkk	Time Spent In LT RSOC F
NNnnMMmm	Time Spent In LT RSOC G
PPppOOoo	Time Spent In LT RSOC H

15.1.53 ManufacturerAccess() 0x0067 Lifetime Data Block 8

This command returns the ***Lifetime Data*** with the following format:

aaAAbbBBccCCddDDeeEEffFFggGGhhHHiillJJjjkkKKllLLmmMMnnNNooOOppPP.

Value	Description
BBbbAAaa	Time Spent In STL RSOC A
DDddCCcc	Time Spent In STL RSOC B
FFffEEee	Time Spent In STL RSOC C
HHhhGGgg	Time Spent In STL RSOC D
JJjjIIii	Time Spent In STL RSOC E
LLllKKkk	Time Spent In STL RSOC F
NNnnMMmm	Time Spent In STL RSOC G
PPppOOoo	Time Spent In STL RSOC H

15.1.54 ManufacturerAccess() 0x0068 Lifetime Data Block 9

This command returns the ***Lifetime Data*** with the following format: aaAAbbBBccCCddDDeeEEffFFggGGhhHHiiIIjjJJkkKKllLLmmMMnnNNooOOppPP.

Value	Description
BBbbAAaa	Time Spent In RT RSOC A
DDddCCcc	Time Spent In RT RSOC B
FFffEEee	Time Spent In RT RSOC C
HHhhGGgg	Time Spent In RT RSOC D
JJjjIIii	Time Spent In RT RSOC E
LLllKKkk	Time Spent In RT RSOC F
NNnnMMmm	Time Spent In RT RSOC G
PPppOOoo	Time Spent In RT RSOC H

15.1.55 ManufacturerAccess() 0x0069 Lifetime Data Block 10

This command returns the ***Lifetime Data*** with the following format: aaAAbbBBccCCddDDeeEEffFFggGGhhHHiiIIjjJJkkKKllLLmmMMnnNNooOOppPP.

Value	Description
BBbbAAaa	Time Spent In STH RSOC A
DDddCCcc	Time Spent In STH RSOC B
FFffEEee	Time Spent In STH RSOC C
HHhhGGgg	Time Spent In STH RSOC D
JJjjIIii	Time Spent In STH RSOC E
LLllKKkk	Time Spent In STH RSOC F
NNnnMMmm	Time Spent In STH RSOC G
PPppOOoo	Time Spent In STH RSOC H

15.1.56 ManufacturerAccess() 0x006A Lifetime Data Block 11

This command returns the ***Lifetime Data*** with the following format: aaAAbbBBccCCddDDeeEEffFFggGGhhHHiiIIjjJJkkKKllLLmmMMnnNNooOOppPP.

Value	Description
BBbbAAaa	Time Spent In HT RSOC A
DDddCCcc	Time Spent In HT RSOC B
FFffEEee	Time Spent In HT RSOC C
HHhhGGgg	Time Spent In HT RSOC D
JJjjIIii	Time Spent In HT RSOC E
LLllKKkk	Time Spent In HT RSOC F
NNnnMMmm	Time Spent In HT RSOC G
PPppOOoo	Time Spent In HT RSOC H

15.1.57 ManufacturerAccess() 0x006B Lifetime Data Block 12

This command returns the ***Lifetime Data*** with the following format: aaAAbbBBccCCddDDeeEEffFFggGGhhHHiiIIjjJJkkKKllLLmmMMnnNNooOOppPP.

Value	Description
BBbbAAaa	Time Spent In OT RSOC A
DDddCCcc	Time Spent In OT RSOC B
FFffEEee	Time Spent In OT RSOC C
HHhhGGgg	Time Spent In OT RSOC D
JJjjIIii	Time Spent In OT RSOC E
LLllKKkk	Time Spent In OT RSOC F
NNnnMMmm	Time Spent In OT RSOC G
PPppOOoo	Time Spent In OT RSOC H

15.1.58 ManufacturerAccess() 0x0070 ManufacturerInfo

This command returns ManufacturerInfo on *ManufacturerBlockAccess()* or *ManufacturerData()*.

Status	Condition	Action
Activate	0x0070 to *ManufacturerAccess()*	Output 32 bytes of ManufacturerInfo on *ManufacturerBlockAccess()* or *ManufacturerData()* in the following format: AABBCCDDEEFFGGHHIIJJKKLLMMNNOOPPQQRRSSTTUUVVWWXXYYZZ112233445566

15.1.59 ManufacturerAccess() 0x0071 DAStatus1

This command returns the cell voltages, PACK voltage, BAT voltage, cell currents, cell powers, power, and average power on *ManufacturerBlockAccess()* or *ManufacturerData()*.

Status	Condition
Activate	0x0071 to *ManufacturerBlockAccess()* or *ManufacturerAccess()*

Action: Output 32 bytes of data on *ManufacturerBlockAccess()* or *ManufacturerData()* in the following format: aaAAbbBBccCCddDDeeEEffFFggGGhhHHiiIIjjJJkkKKllLLmmMMnnNNooOOppPP where:

Value	Description	Unit
AAaa	Cell Voltage 1	mV
BBbb	Cell Voltage 2	mV
CCcc	Cell Voltage 3	mV
DDdd	Cell Voltage 4	mV
EEee	BAT voltage. Voltage at the BAT pin. This is different than *Voltage()*, which is the sum of all the cell voltages.	mV
FFff	PACK voltage. Voltage at the PACK+ pin.	mV
GGgg	Cell Current 1. Simultaneous current measured during Cell Voltage 1 measurement	mA
HHhh	Cell Current 2. Simultaneous current measured during Cell Voltage 2 measurement	mA
IIii	Cell Current 3. Simultaneous current measured during Cell Voltage 3 measurement	mA
JJjj	Cell Current 4. Simultaneous current measured during Cell Voltage 4 measurement	mA
KKkk	Cell Power 1. Calculated using Cell Voltage1 and Cell Current 1 data	cW
LLll	Cell Power 2. Calculated using Cell Voltage2 and Cell Current 2 data	cW
MMmm	Cell Power 3. Calculated using Cell Voltage3 and Cell Current 3 data	cW
NNnn	Cell Power 4. Calculated using Cell Voltage4 and Cell Current 4 data	cW
OOoo	Power calculated by *Voltage()* × *Current()*	cW
PPpp	Average Power	cW

15.1.60 ManufacturerAccess() 0x0072 DAStatus2

This command returns the internal temperature sensor, TS1, TS2, TS3, TS4, cell temp, FET temp, and gauging temperature on *ManufacturerBlockAccess()* or *ManufacturerData()*.

Status	Condition
Activate	0x0072 to *ManufacturerBlockAccess()* or *ManufacturerAccess()*

Action: Output 16 bytes of temperature data values on *ManufacturerBlockAccess()* or *ManufacturerData()* in the following format: aaAAbbBBccCCddDDeeEEffFFggGGhhHH where:

Value	Description	Unit
AAaa	Int Temperature	0.1 K
BBbb	TS1 Temperature	0.1 K
CCcc	TS2 Temperature	0.1 K
DDdd	TS3 Temperature	0.1 K
EEee	TS4 Temperature	0.1 K
FFff	Cell Temperature	0.1 K
GGgg	FET Temperature	0.1 K
HHhh	Gauging Temperature	0.1 K

15.1.61 ManufacturerAccess() 0x0073 GaugeStatus1

This command instructs the device to return Impedance Track related gauging information on *ManufacturerBlockAccess()* or *ManufacturerData()*.

Status	Condition
Activate	0x0073 to *ManufacturerBlockAccess()* or *ManufacturerAccess()*

Action: Output 32 bytes of IT data values on *ManufacturerBlockAccess()* or *ManufacturerData()* in the following format: aaAAbbBBccCCddDDeeEEffFFggGGhhHHiiIIjjJJkkKKllLLmmMMnnNNooOOppPP where:

Value	Description	Unit
AAaa	True Rem Q. True remaining capacity in mAh from IT simulation before any filtering or smoothing function. This value can be negative or higher than FCC.	mAh
BBbb	True Rem E. True remaining energy in cWh from IT simulation before any filtering or smoothing function. This value can be negative or higher than FCC.	cWh
CCcc	Initial Q. Initial capacity calculated from IT simulation	mAh
DDdd	Initial E. Initial energy calculated from IT simulation	cWh
EEee	True FCC Q. True full charge capacity from IT simulation without the effects of any smoothing function	mAh
FFff	True FCC E. True full charge energy from IT simulation without the effects of any smoothing function	cWh
GGgg	T_sim. Temperature during the last simulation run.	0.1 K
HHhh	T_ambient. Current assumed ambient temperature used by the IT algorithm for thermal modeling	0.1 K
IIii	RaScale 0. Ra table scaling factor of Cell 1	—
JJjj	RaScale 1. Ra table scaling factor of Cell 2	—
KKkk	RaScale 2. Ra table scaling factor of Cell 3	—
LLll	RaScale 3. Ra table scaling factor of Cell 4	—
MMmm	CompRes 0. Last temperature compensated Resistance of Cell 1	2^{-10} Ω
NNnn	CompRes 1. Last temperature compensated Resistance of Cell 2	2^{-10} Ω
OOoo	CompRes 2. Last temperature compensated Resistance of Cell 3	2^{-10} Ω
PPpp	CompRes 3. Last temperature compensated Resistance of Cell 4	2^{-10} Ω

15.1.62 ManufacturerAccess() 0x0074 GaugeStatus2

This command instructs the device to return Impedance Track related gauging information on *ManufacturerBlockAccess()* or *ManufacturerData()*.

Status	Condition
Activate	0x0074 to *ManufacturerBlockAccess()* or *ManufacturerAccess()*

Action: Output 32 bytes of IT data values on *ManufacturerBlockAccess()* or *ManufacturerData()* in the following format: AABBCCDDEEFFggGGhhHHiiIIjjJJkkKKllLLmmMMnnNNooOOppPPqqQQrrRRssSS where:

Value	Description	Unit
AA	Pack Grid. Active pack impedance grid point (minimum of Cell Grid 0 to Cell Grid 3). This data is only valid during DISCHARGE mode when *[R_DIS]* = 0. If *[R_DIS]* = 1 or not discharging, this value is not updated.	—
BB	BB: LStatus—Learned status of resistance table Bit 3 | Bit 2 | Bit 1| Bit 0 QMax | ITEN | CF1 | CF0 CF1, CF0: QMax Status 0,0 = Battery OK 0,1 = QMax is first updated in learning cycle. 1,0 = QMax and resistance table updated in learning cycle ITEN: IT enable 0 = IT disabled 1 = IT enabled QMax: QMax update in field 0 = QMax has not been updated in the field. 1= QMax updated in the field.	—
CC	Cell Grid 0. Active grid point of Cell 1. This data is only valid during DISCHARGE mode when *[R_DIS]* = 0. If *[R_DIS]* = 1 or not discharging, this value is not updated.	—
DD	Cell Grid 1. Active grid point of Cell 2. This data is only valid during DISCHARGE mode when *[R_DIS]* = 0. If *[R_DIS]* = 1 or not discharging, this value is not updated.	—
EE	Cell Grid 2. Active grid point of Cell 3. This data is only valid during DISCHARGE mode when *[R_DIS]* = 0. If *[R_DIS]* = 1 or not discharging, this value is not updated.	—
FF	Cell Grid 3. Active grid point of Cell 4. This data is only valid during DISCHARGE mode when *[R_DIS]* = 0. If *[R_DIS]* = 1 or not discharging, this value is not updated.	—
HHhhGGgg	State Time. Time passed since the last state change (DISCHARGE, CHARGE, REST)	s
IIii	DOD0_0. Depth of discharge for Cell 1	—
JJjj	DOD0_1. Depth of discharge for Cell 2	—
KKkk	DOD0_2. Depth of discharge for Cell 3	—
LLll	DOD0_3. Depth of discharge for Cell 4	—
MMmm	DOD0 Passed Q. Passed capacity since the last DOD0 update	mAh
NNnn	DOD0 Passed E. Passed energy since last DOD0 update	cWh
OOoo	DOD0 Time. Time passed since the last DOD0 update	hr/16
PPpp	DODEOC 0. Depth of discharge at end of charge of Cell 1	—
QQqq	DODEOC 1. Depth of discharge at end of charge of Cell 2	—
RRrr	DODEOC 2. Depth of discharge at end of charge of Cell 3	—
SSss	DODEOC 3. Depth of discharge at end of charge of Cell 4	—

15.1.63 ManufacturerAccess() 0x0075 GaugeStatus3

This command instructs the device to return Impedance Track related gauging information on *ManufacturerBlockAccess()* or *ManufacturerData()*.

Status	Condition
Activate	0x0075 to *ManufacturerBlockAccess()* or *ManufacturerAccess()*

Action: Output 24 bytes of IT data values on *ManufacturerBlockAccess()* or *ManufacturerData()* in the following format: aaAAbbBBccCCddDDeeEEffFFggGGhhHHiiIIjjJJkkKKllLL where:

Value	Description	Unit
AAaa	QMax 0. QMax of Cell 1	mAh
BBbb	QMax 1. QMax of Cell 2	mAh
CCcc	QMax 2. QMax of Cell 3	mAh
DDdd	QMax 3. QMax of Cell 4	mAh

Value	Description	Unit
EEee	QMax DOD0_0. DOD0 saved to be used for next QMax update of Cell 1. The value is only valid when *[VOK]* = 1.	—
FFff	QMax DOD0_1. DOD0 saved to be used for next QMax update of Cell 2. The value is only valid when *[VOK]* = 1.	—
GGgg	QMax DOD0_2. DOD0 saved to be used for next QMax update of Cell 3 . The value is only valid when *[VOK]* = 1.	—
HHhh	QMax DOD0_3. DOD0 saved to be used for next QMax update of Cell 4. The value is only valid when *[VOK]* = 1.	—
IIii	QMax Passed Q. Pass capacity since last QMax DOD value is saved.	mAh
JJjj	QMax Time. Time passed since last QMax DOD value is saved.	hr/16
KKkk	Temp k. Thermal Model temperature factor	—
LLll	Temp a. Thermal Model temperature	—

15.1.64 ManufacturerAccess() 0x0076 CBStatus

This command instructs the device to return cell balance time information on *ManufacturerBlockAccess()* or *ManufacturerData()*.

Status	Condition
Activate	0x0076 to *ManufacturerBlockAccess()* or *ManufacturerAccess()*

Action: Output 19 bytes of IT data values on *ManufacturerBlockAccess()* or *ManufacturerData()* in the following format: aaAAbbBBccCCddDDeeEEffFFggGGhhHHiiIIjj where:

Value	Description	Unit
AAaa	Cell balance time 0. Calculated cell balancing time of Cell 1	s
BBbb	Cell balance time 1. Calculated cell balancing time of Cell 2	s
CCcc	Cell balance time 2. Calculated cell balancing time of Cell 3	s
DDdd	Cell balance time 3. Calculated cell balancing time of Cell 4	s
EEee	Cell 1 balance DOD	—
FFff	Cell 1 balance DOD	—
GGgg	Cell 1 balance DOD	—
HHhh	Cell 1 balance DOD	—
IIii	Total DOD Charge	—
jj	Cell Balance Status Bit 3 | Bit 2 | Bit 1 | Bit 0 CELL4 | CELL3 | CELL2 | CELL1 CELL1: Cell 1 balance circuit 0 = Inactive 1 = Active CELL2: Cell 2 balance circuit 0 = Inactive 1 = Active CELL3: Cell 3 balance circuit 0 = Inactive 1 = Active CELL4: Cell 4 balance circuit 0 = Inactive 1 = Active	—

15.1.65 ManufacturerAccess() 0x0077 StateofHealth

This command returns the state-of-health FCC in mAh and energy in cWh with the following format: aaAAbbBB.

Value	Description	Unit
AAaa	State-of-Health FCC	mAh
BBbb	State-of-Health energy	cWh

15.1.66 ManufacturerAccess() 0x0078 FilterCapacity

This command instructs the device to return the filtered remaining capacity and full charge capacity even if ***[SMOOTH]*** = 0 on *ManufacturerBlockAccess()* or *ManufacturerData()*.

Status	Condition
Activate	0x0078 to *ManufacturerBlockAccess()* or *ManufacturerAccess()*

Action: Output 8 bytes of IT data values on *ManufacturerBlockAccess()* or *ManufacturerData()* in the following format: aaAAbbBBccCCddDD where:

Value	Description	Unit
AAaa	Filtered remaining capacity	mAh
BBbb	Filtered remaining energy	cWh
CCcc	Filtered full charge capacity	mAh
DDdd	Filtered full charge energy	cWh

15.1.67 ManufacturerAccess() 0x0079 RSOCWrite

This command is typically used for testing purposes and will allow a specific value to be loaded into RSOC. However, subsequent IT simulation can overwrite this value. This command works only in UNSEALED mode. Additionally, this command will work with or without smoothing enabled.

15.1.68 ManufacturerAccess() 0x007A ManufacturerInfoB

This command returns ***ManufacturerInfoB*** on *ManufacturerBlockAccess()* or *ManufacturerData()*.

Status	Condition	Action
Activate	0x007A to *ManufacturerAccess()*	Output 4 bytes of ManufacturerInfo2 on *ManufacturerBlockAccess()* or *ManufacturerData()* in the following format: AABBCCDD

15.1.69 ManufacturerAccess() 0x0098 AccumulationChargeEnable

This command enables accumulated charge measurement in the CHARGE direction by setting ***[ACCHG_EN]***.

15.1.70 ManufacturerAccess() 0x0099 AccumulationDischargeEnable

This command enables accumulated charge measurement in the DISCHARGE direction by setting ***[ACDSG_EN]***.

15.1.71 ManufacturerAccess() 0x009A AccumulationReset

This command resets the accumulated charge and time values, and clears *[ACTHR]* if previously triggered.

15.1.72 ManufacturerAccess() 0x009B AccumulationStop

This command stops the accumulated charge and time accumulation.

15.1.73 ManufacturerAccess() 0x009C AccumulationStart

This command starts the accumulated charge and time accumulation.

15.1.74 ManufacturerAccess() 0x009D AccumulationChargeThreshold

This command can be used to set ***Accum Charge Threshold*** with the following format: aaAA.

Value	Description	Unit
AAAaa	Accum Charge Threshold	mAh

15.1.75 ManufacturerAccess() 0x009E AccumulationDischargeThreshold

This command can be used to set ***Accum Discharge Threshold*** with the following format: aaAA.

Value	Description	Unit
AAAaa	Accum Discharge Threshold	mAh

15.1.76 ManufacturerAccess() 0x009F AccumulatedChargeTime

This command returns the accumulated charge and time values in the following format: aaAAbbBBccCC.

Value	Description	Unit
BBbbAAaa	Accumulated Time	s
CCcc	Accumulated Charge	mAh

15.1.77 ManufacturerAccess() 0x00B0 ChargingVoltageOverride

This command enables writing the five advanced charge algorithm charging voltage values in SEALED mode to data flash in the following format: aaAAbbBBccCCddDDeeEE where:

Value	Description	Unit
AAaa	Low Temperature Charging Voltage	mV
BBbb	Standard Temperature Low Charging Voltage	mV
CCcc	Standard Temperature High Charging Voltage	mV
DDdd	High Temperature Charging Voltage	mV
EEee	Recommended Temperature Charging Voltage	mV

15.1.78 ManufacturerAccess() 0x00F0 IATAShutdown

This command, when used in conjunction with the *[IATA_SHUT]* bit in the *IATA Flag* register, enables the gauge to enter IATA shutdown (provided certain other requirements are met).

15.1.79 ManufacturerAccess() 0x00F1 IATARm

This command is used in relation to IATA to read out the stored ***IATARm*** value.

15.1.80 ManufacturerAccess() 0x00F2 IATAFcc

This command is used in relation to IATA to read out the stored ***IATAFcc*** value.

15.1.81 ManufacturerAccess() 0x0F00 ROM Mode

This command sends the device into ROM mode in preparation for firmware reprogramming. To enter ROM mode, the device must be in FULL ACCESS mode. To return from ROM mode to FW mode, issue the SMBus command 0x08.

NOTE: Command 0x0033 also puts the device in ROM mode (for backwards compatibility with the bq30zxy device).

15.1.82 ManufacturerAccess() 0x3008 WriteTemp

This command, available in SEALED and UNSEALED modes, is used to write the temperature register when enabled by setting ***[SMB_CELL_TEMP]*** = 1 in the SBS Configuration register. In this case, the gauge's cell temperature inputs (TS1 through TS3) are ignored.

NOTE: When this feature is used, the temperature must be written in 0.1 K.

15.1.83 ManufacturerAccess() 0x4000–0x5FFF DataFlashAccess

Accessing data flash (DF) is only supported by the *ManufacturerBlockAccess()* by addressing the physical address. Numeric data items in DF are in little endian byte order.

To write to the DF, send the starting address, followed by the DF data block. The DF data block is the intended revised DF data to be updated to DF. The size of the DF data block ranges from 1 byte to 32 bytes. All individual numeric data items must be sent in little endian byte order.

Write to DF example:

Assuming: data1 locates at address 0x4000 and data2 locates at address 0x4002.
Both data1 and data2 are U2 type.

To update data1 and data2, send an SMBus block write with command = 0x44
block = starting address + DF data block
= 0x00 + 0x40 + data1_LowByte + data1_HighByte + data2_LowByte + data2_HighByte

To read the DF, send an SMBus block write to the *ManufacturerBlockAccess()*, followed by the starting address, then send an SMBus block read to the *ManufacturerBlockAccess()*. The return data contains the starting address followed by 32 bytes of DF data; items are in little endian byte order.

Read from DF example:

Assuming: data1 locates at address 0x4000 and data2 locates at address 0x4002.
a. Send SMBus write block with command 0x44, block = 0x00 + 0x40
b. Send SMBus read block with command 0x44
The returned block = starting address + 32 bytes of DF data
= 0x00 + 0x40 + data1_LowByte + data1_HighByte + data2_LowByte + data2_HighByte.... data31_Byte + data32_Byte

The gauge supports an auto-increment on the address during a DF read. This greatly reduces the time required to read out the entire DF. Continue with the read from the DF example. If another SMBus read block is sent with command 0x44, the gauge returns another 32 bytes of DF data, starting with address 0x4020.

15.1.84 ManufacturerAccess() 0xF080 and 0xF081 Output CCADCCal Control

These commands control the device to output the raw values for calibration purposes on *ManufacturerBlockAccess()* or *ManufacturerData()*. All values are updated every 250 ms, and the format of each value is 2's complement, MSB first.

Status	Condition
Disable	*ManufacturingStatus()[CAL]* = 1 AND 0xF080 to *ManufacturerAccess()*

Action: *OperationStatus()[CAL]* = 0, *[CAL_OFFSET]* = 0
Stop output of ADC and CC data on *ManufacturerBlockAccess()* or *ManufacturerData()*

Status	Condition
Enable	0xF081 to *ManufacturerAccess()*

Action: *OperationStatus()[CAL]* = 1, *[CAL_OFFSET]* = 0
Outputs the raw CC and AD values on *ManufacturerBlockAccess()* or *ManufacturerData()* in the format of ZZYYaaAAbbBBccCCddDDeeEEffFFggGGhhHHiiIIjjJJkkKK:

Value	Description
ZZ	Rolling 8-bit counter, increments when values are refreshed.
YY	Status, 1 when *ManufacturerAccess()* = 0xF081, 2 when *ManufacturerAccess()* = 0xF082
AAaa	Current (coulomb counter)
BBbb	Cell Voltage 1
CCcc	Cell Voltage 2
DDdd	Cell Voltage 3
EEee	Cell Voltage 4
FFff	PACK Voltage
GGgg	BAT Voltage
HHhh	Cell Current 1
IIii	Cell Current 2
JJjj	Cell Current 3
KKkk	Cell Current 4

15.1.85 ManufacturerAccess() 0xF082 OutputShortedCCADCCal

This command instructs the device to output the raw values for calibration purposes on *ManufacturerBlockAccess()* or *ManufacturerData()*. All values are updated every 250 ms and the format of each value is 2's complement, MSB first. This mode includes an internal short on the coulomb counter inputs for measuring its offset.

Status	Condition
Disable	*ManufacturingStatus()[CAL]* = 1 AND 0xF080 to *ManufacturerAccess()*

Action: *OperationStatus()[CAL]* = 0, *[CAL_OFFSET]* = 0
Stop output of ADC and CC data on *ManufacturerBlockAccess()* or *ManufacturerData()*

Status	Condition
Enable	0xF081 to *ManufacturerAccess()*

Action: *OperationStatus()[CAL]* = 1, *[CAL_OFFSET]* = 1
Outputs the raw CC and AD values on *ManufacturerBlockAccess()* or *ManufacturerData()* in the format of ZZYYaaAAbbBBccCCddDDeeEEffFFggGGhhHHiiIIjjJJkkKK:

Value	Description
ZZ	Rolling 8-bit counter, increments when values are refreshed.
YY	Status, 1 when *ManufacturerAccess()* = 0xF081, 2 when *ManufacturerAccess()* = 0xF082
AAaa	Current (coulomb counter)
BBbb	Cell Voltage 1
CCcc	Cell Voltage 2
DDdd	Cell Voltage 3
EEee	Cell Voltage 4
FFff	PACK Voltage
GGgg	BAT Voltage
HHhh	Cell Current 1
IIii	Cell Current 2
JJjj	Cell Current 3
KKkk	Cell Current 4

15.2 0x01 RemainingCapacityAlarm()

This read/write word function sets a low capacity alarm threshold for the cell stack.

SBS Cmd	Name	Access			Proto-col	Type	Min	Max	Default	Unit
		SE	US	FA						
0x01	*RemainingCapacityAlarm()*	R/W			Word	U2	0	700	300	mAh
										cWh

NOTE: If *BatteryMode()[CAPM]* = 0, then the data reports in mAh.

If *BatteryMode()[CAPM]* = 1, then the data reports in cWh.

15.3 0x02 RemainingTimeAlarm()

This read/write word function sets a low remaining time-to-fully discharge alarm threshold for the cell stack.

SBS Cmd	Name	Access			Proto-col	Type	Min	Max	Default	Unit
		SE	US	FA						
0x02	*RemainingTimeAlarm()*	R/W			Word	U2	0	30	10	min

15.4 0x03 BatteryMode()

This read/write word function sets various battery operating mode options.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Unit
		SE	US	FA					
0x03	*BatteryMode()*	R/W			Word	H2	0x0000	0xFFFF	—

15	14	13	12	11	10	9	8
CAPM	CHGM	AM	RSVD	RSVD	RSVD	PB	CC

7	6	5	4	3	2	1	0
CF	RSVD	RSVD	RSVD	RSVD	RSVD	PBS	ICC

CAPM (Bit 15): CAPACITY Mode (R/W)

1 = Reports in 10 mW or cWh

0 = Reports in mA or mAh (default)

CHGM (Bit 14): CHARGER Mode (R/W)

1 = Disables *ChargingVoltage()* and *ChargingCurrent()* broadcasts to the host and smart battery charger (default)

0 = Enables *ChargingVoltage()* and *ChargingCurrent()* broadcasts to the host and smart battery charger

AM (Bit 13): ALARM Mode (R/W)

1 = Disables alarm warning broadcasts to the host and smart battery charger

0 = Enables alarm warning broadcasts to the host and smart battery charger (default)

RSVD (Bits 12–10): Reserved. Do not use.

PB (Bit 9): Primary Battery

1 = Battery operating in its primary role

0 = Battery operating in its secondary role (default)

CC (Bit 8): Charge Controller Enabled (R/W)

- 1 = Internal charge controller enabled
- 0 = Internal charge controller disabled (default)

CF (Bit 7): Condition Flag (R)

- 1 = Conditioning cycle requested
- 0 = Battery OK

RSVD (Bits 6–2): Reserved. Do not use.

PBS (Bit 1): Primary Battery Support (R)

- 1 = Primary or Secondary Battery Support
- 0 = Function is not supported. (default)

ICC (Bit 0): Internal Charge Controller (R)

- 1 = Function is supported.
- 0 = Function is not supported. (default)

15.5 0x04 AtRate()

This read/write word function sets the value used in calculating *AtRateTimeToFull()* and *AtRateTimeToEmpty()*.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x04	*AtRate()*	R/W			Word	I2	–32768	32767	0	mA cW

NOTE: If *BatteryMode()[CAPM]* = 0, then the data reports in mA.

If *BatteryMode()[CAPM]* = 1, then the data reports in cW.

15.6 0x05 AtRateTimeToFull()

This word read function returns the remaining time-to-fully charge the battery stack.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Unit
		SE	US	FA					
0x05	*AtRateTimeToFull()*	R			Word	U2	0	65535	min

NOTE: 65535 indicates not being charged.

15.7 0x06 AtRateTimeToEmpty()

This word read function returns the remaining time-to-fully discharge the battery stack.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Unit
		SE	US	FA					
0x06	*AtRateTimeToEmpty()*	R			Word	U2	0	65535	min

NOTE: 65535 indicates not being discharged.

15.8 0x07 AtRateOK()

This read-word function returns a Boolean value that indicates whether the battery can deliver *AtRate()* for at least 10 s.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Unit
		SE	US	FA					
0x07	*AtRateOK()*	R			Word	U2	0	65535	—

NOTE: 0 = False. The gauge *cannot* deliver energy for 10 s, based on the discharge rate indicated in *AtRate()*.

> 0 = True. The gauge *can* deliver energy for 10 s, based on the discharge rate indicated in *AtRate()*.

15.9 0x08 Temperature()

This read-word function returns the temperature in units 0.1 K. The source of this temperature is configured by ***TSx Mode*** and ***[CTEMP1], [CTEMP0]*** bits in the ***DA Configuration***. This temperature is used for all cell-related protections, permanent fail, and the advanced charging algorithm.

The temperature used for FET-related protections and permanent fail is FET Temperature, configured by the ***TSx Mode*** and ***FTEMP*** bits in ***DA Configuration***, and is read with *DAStatus2()*.

The temperature used for gauging is Gauging Temperature, configured by the ***[TS1], [TS0]*** bits in the ***IT Gauging Ext*** configuration, and is read with *DAStatus2()*. The recommended configuration for Gauging Temperature is the minimum cell temperature.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Unit
		SE	US	FA					
0x08	*Temperature()*	R			Word	U2	0	65535	0.1 K

15.10 0x09 Voltage()

This read-word function returns the sum of the measured cell voltages.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Unit
		SE	US	FA					
0x09	*Voltage()*	R			Word	U2	0	65535	mV

15.11 0x0A Current()

This read-word function returns the measured current from the coulomb counter. If the input to the device exceeds the maximum value, the value is clamped at the maximum and does not roll over.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Unit
		SE	US	FA					
0x0A	*Current()*	R			Word	I2	–32767	32768	mA

15.12 0x0B AverageCurrent()

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Unit
		SE	US	FA					
0x0B	*AverageCurrent()*	R			Word	I2	–32767	32768	mA

15.13 0x0C MaxError()

This read-word function returns the expected margin of error, in %, in the state-of-charge calculation with a range of 1 to 100%.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Unit
		SE	US	FA					
0x0C	*MaxError()*	R			Word	U1	0	100	%

Condition	Action
Full device reset	*MaxError()* = 100%
RA-table only updated	*MaxError()* = 5%
QMax only updated	*MaxError()* = 3%
RA-table and QMax updated	*MaxError()* = 1%
Each *CycleCount()* increment after last valid QMax update	*MaxError()* increment by 0.05%
The ***Configuration:Max Error Time Cycle Equivalent*** period passed since the last valid QMax update	*MaxError()* increment by 0.05%.

15.14 0x0D RelativeStateOfCharge()

This read-word function returns the predicted remaining battery capacity as a percentage of *FullChargeCapacity()*.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Unit
		SE	US	FA					
0x0D	*RelativeStateOfCharge()*	R			Word	U1	0	100	%

15.15 0x0E AbsoluteStateOfCharge()

This read-word function returns the predicted remaining battery capacity as a percentage.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Unit
		SE	US	FA					
0x0E	*AbsoluteStateOfCharge()*	R			Word	U1	0	100	%

15.16 0x0F RemainingCapacity()

This read-word function returns the predicted remaining battery capacity.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Unit
		SE	US	FA					
0x0F	*RemainingCapacity()*	R	R	R	Word	U2	0	65535	mAh cWh

NOTE: If *BatteryMode()[CAPM]* = 0, then the data reports in mAh.

If *BatteryMode()[CAPM]* = 1, then the data reports in cWh.

15.17 0x10 FullChargeCapacity()

This read-word function returns the predicted battery capacity when fully charged. The value returned will not be updated during charging.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Unit
		SE	US	FA					
0x10	*FullChargeCapacity()*	R	R	R	Word	U2	0	65535	mAh cWh

NOTE: If *BatteryMode()[CAPM]* = 0, then the data reports in mAh.
If *BatteryMode()[CAPM]* = 1, then the data reports in cWh.

15.18 0x11 RunTimeToEmpty()

This read-word function returns the predicted minutes of run time based on the present rate of discharge.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Unit
		SE	US	FA					
0x11	*RunTimeToEmpty()*	R	R	R	Word	U2	0	65535	min

NOTE: 65535 = Battery is not being discharged.

15.19 0x12 AverageTimeToEmpty()

This read-word function returns the predicted minutes of run time based on *AverageCurrent()*.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Unit
		SE	US	FA					
0x12	*AverageTimeToEmpty()*	R	R	R	Word	U2	0	65535	min

NOTE: 65535 = Battery is not being discharged.

15.20 0x13 AverageTimeToFull()

This read-word function returns the predicted time-to-full charge based on *AverageCurrent()*.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Unit
		SE	US	FA					
0x13	*AverageTimeToFull()*	R	R	R	Word	U2	0	65535	min

NOTE: 65535 = Battery is not being charged.

15.21 0x14 ChargingCurrent()

This read-word function returns the desired charging current.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Unit
		SE	US	FA					
0x14	*ChargingCurrent()*	R	R	R	Word	U2	0	65535	mA

NOTE: 65535 = Request maximum current

15.22 0x15 ChargingVoltage()

This read-word function returns the desired charging voltage.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Unit
		SE	US	FA					
0x15	*ChargingVoltage()*	R	R	R	Word	U2	0	65535	mV

NOTE: 65535 = Request maximum voltage

15.23 0x16 BatteryStatus()

This read-word function returns various battery status information.

SBS Cmd	Name	Access			Protocol	Type	Min	Max
		SE	US	FA				
0x16	*BatteryStatus()*	R	R	R	Word	H2	—	—

15	14	13	12	11	10	9	8
OCA	TCA	RSVD	OTA	TDA	RSVD	RCA	RTA

7	6	5	4	3	2	1	0
INIT	DSG	FC	FD	EC3	EC2	EC1	EC0

OCA (Bit 15): Overcharged Alarm

1 = Detected

0 = Not Detected

TCA (Bit 14): Terminate Charge Alarm

1 = Detected

0 = Not Detected

RSVD (Bit 13): Undefined

OTA (Bit 12): Overtemperature Alarm

1 = Detected

0 = Not Detected

TDA (Bit 11): Terminate Discharge Alarm

1 = Detected

0 = Not Detected

RSVD (Bit 10): Undefined

RCA (Bit 9): Remaining Capacity Alarm

1 = *RemainingCapacity()* < *RemainingCapacityAlarm()* when in DISCHARGE or RELAX mode

0 = *RemainingCapacity()* ≥ *RemainingCapacityAlarm()*

RTA (Bit 8): Remaining Time Alarm

1 = *AverageTimeToEmpty()* < *RemainingTimeAlarm() or*

0 = *AverageTimeToEmpty()* ≥ *RemainingTimeAlarm()*

INIT (Bit 7): Initialization

1 = Gauge initialization is complete.

0 = Initialization is in progress.

DSG (Bit 6): Discharging or Relax
- 1 = Battery is in DISCHARGE or RELAX mode.
- 0 = Battery is in CHARGE mode.

FC (Bit 5): Fully Charged
- 1 = Battery fully charged when *GaugingStatus()[FC]* = 1
- 0 = Battery not fully charged

FD (Bit 4): Fully Discharged
- 1 = Battery fully depleted
- 0 = Battery not depleted

EC3,EC2,EC1,EC0 (Bits 3–0): Error Code
- 0x0 = OK
- 0x1 = Busy
- 0x2 = Reserved Command
- 0x3 = Unsupported Command
- 0x4 = AccessDenied
- 0x5 = Overflow/Underflow
- 0x6 = BadSize
- 0x7 = UnknownError
- 0x8 = Incomplete

15.24 0x17 CycleCount()

This read-word function returns the number of discharge cycles the battery has experienced. The default value is stored in the data flash value ***Cycle Count***, which is updated in runtime.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Unit
		SE	US	FA					
0x17	*CycleCount()*	R	R/W	R/W	Word	U2	0	65535	cycles

15.25 0x18 DesignCapacity()

This read-word function returns the theoretical pack capacity. The default value is stored in the data flash value ***Design Capacity mAh*** or ***Design Capacity cWh.***

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x18	*DesignCapacity()*	R	R/W	R/W	Word	U2	0	65535	4400	mAh
									6336	cWh

NOTE: If *BatteryMode()[CAPM]* = 0, then the data reports in mAh.

If *BatteryMode()[CAPM]* = 1, then the data reports in cWh.

15.26 0x19 DesignVoltage()

This read-word function returns the theoretical pack voltage. The default value is stored in data flash value ***Design Voltage***.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x19	*DesignVoltage()*	R	R/W	R/W	Word	U2	7000	18000	14400	mV

15.27 0x1A SpecificationInfo()

SBS Cmd	Name	Access			Protocol	Type	Min	Max
		SE	US	FA				
0x1A	*SpecificationInfo()*	R	R/W	R/W	Word	H2	0x0000	0xFFFF

15	14	13	12	11	10	9	8
IPScale	IPScale	IPScale	IPScale	VScale	VScale	VScale	VScale

7	6	5	4	3	2	1	0
Version	Version	Version	Version	Revision	Revision	Revision	Revision

IPScale (Bits 15–12): IP Scale Factor
Not supported by the gas gauge
MUST be set to 0, 0, 0, 0.

VScale (Bits 11–8): Voltage Scale Factor
Not supported by the gas gauge
MUST be set to 0, 0, 0, 0.

Version (Bits 7–4): Version
0,0,0,1 = Version 1.0
0,0,1,1 = Version 1.1
0,0,1,1 = Version 1.1 with optional PEC support

Revision (Bits 3–0): Revision
0,0,0,1 = Version 1.0 and 1.1 (default)

15.28 0x1B ManufacturerDate()

This read-word function returns the pack's manufacturer date.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default
		SE	US	FA					
0x1B	*ManufacturerDate()*	R	R/W	R/W	Word	U2		65535	0

NOTE: *ManufacturerDate()* value in the following format: Day + Month×32 + (Year–1980)×512

15.29 0x1C SerialNumber()

This read-word function returns the assigned pack serial number.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x1C	*SerialNumber()*	R	R/W	R/W	Word	H2	0x0000	0xFFFF	0x0001	

15.30 0x20 ManufacturerName()

This read-block function returns the pack manufacturer's name.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x20	*ManufacturerName()*	R	R	R	Block	S20+1	—	—	Texas Inst.	ASCII

15.31 0x21 DeviceName()

This read-block function returns the assigned pack name.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x21	*DeviceName()*	R	R	R	Block	S20+1	—	—	bq40z50-R3	ASCII

15.32 0x22 DeviceChemistry()

This read-block function returns the battery chemistry used in the pack.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x22	*DeviceChemistry()*	R	R	R	Block	S4+1	—	—	LION	ASCII

15.33 0x23 ManufacturerData()

This read-block function returns ***ManufacturerInfo*** by default. The command also returns a response to MAC command in order to maintain compatibility of the MAC system in bq30zxy family.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Unit
		SE	US	FA					
0x23	*ManufacturerData()*	R	R	R	Block	Mixed	—	—	—

15.34 0x2F Authenticate()

This read/write block function provides SHA-1 authentication to send the challenge and read the response in the default mode. It is also used to input a new authentication key when the MAC *AuthenticationKey()* is used.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Unit
		SE	US	FA					
0x2F	*Authenticate()*	R/W	R/W	R/W	Block	H20+1	—	—	—

15.35 0x3C CellVoltage4()

This read-word function returns the Cell 4 voltage.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x3C	*CellVoltage4()*	R	R	R	Word	U2	—	65535	0	mV

15.36 0x3D CellVoltage3()

This read-word function returns the Cell 3 voltage.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x3D	*CellVoltage3()*	R	R	R	Word	U2	—	65535	0	mV

15.37 0x3E CellVoltage2()

This read-word function returns the Cell 2 voltage.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x3E	*CellVoltage2()*	R	R	R	Word	U2	—	65535	0	mV

15.38 0x3F CellVoltage1()

This read-word function returns the Cell 1 voltage.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x3F	*CellVoltage1()*	R	R	R	Word	U2	—	65535	0	mV

15.39 0x48 GPIORead()

This read-only command returns a 4-bit field, with each bit providing the input level read from each of the 4 pins, which can be configured as GPIOs. The command returns valid data for all pins that are configured as GPIO, including those that are configured to drive an output.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x48	*GPIORead()*	R	R	R	Word	U2	—	65535	0	—

15	14	13	12	11	10	9	8
RSVD	RSVD	RSVD	RSVD	RSVD	RSVD	RSVD	RSVD

7	6	5	4	3	2	1	0
RSVD	RSVD	RSVD	RSVD	LEDCNTLC	LEDCNTLB	LEDCNTA	DISP

15.40 0x49 GPIOWrite()

This write-only command sets the output drive of each GPIO pin that is configured as a GPIO. The data associated with pins not configured as GPIOs is not impacted. The format of the command is an 8-bit field, with two bits associated with each GPIO pin. The two bits set the output drive status as: 0,0 = drive output low; 0,1 = drive output high; 1,0 = set output hi-Z; 1,1 = set output hi-Z.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x49	*GPIOWrite()*	W	W	W	Word	U2	—	65535	0	—

15	14	13	12	11	10	9	8
RSVD	RSVD	RSVD	RSVD	RSVD	RSVD	RSVD	RSVD

7	6	5	4	3	2	1	0
LEDCNTLC1	LEDCNTLC0	LEDCNTLB1	LEDCNTLB0	LEDCNTLA1	LEDCNTLA0	DISP1	DISP0

RSVD (Bits 15–8): Reserved. Do not use.

LEDCNTLC1, LEDCNTLC0 (Bits 7–6): LEDCNTLC (pin 22) output drive

1, 1 = Set output hi-Z (default)
1, 0 = Set output hi-Z
0, 1 = Drive output high
0, 0 = Drive output low

LEDCNTLB1, LEDCNTLB0 (Bits 5–4): LEDCNTLB (pin 21) output drive

1, 1 = Set output hi-Z (default)
1, 0 = Set output hi-Z
0, 1 = Drive output high
0, 0 = Drive output low

LEDCNTLA1, LEDCNTLA0 (Bits 3–2): LEDCNTLA (pin 20) output drive

1, 1 = Set output hi-Z (default)
1, 0 = Set output hi-Z
0, 1 = Drive output high
0, 0 = Drive output low

DISP1, DISP0 (Bits 1–0): $\overline{\text{DISP}}$ (pin 17) output drive

1, 1 = Set output hi-Z (default)
1, 0 = Set output hi-Z
0, 1 = Drive output high
0, 0 = Drive output low

15.41 0x4A BTPDischargeSet()

This read/write word command updates the BTP set threshold for DISCHARGE mode for the next BTP interrupt, deasserts the present BTP interrupt, and clears the *OperationStatus()[BTP_INT]* bit.

SBS Cmd	Name	Access			Format	Size in Bytes	Min	Max	Default	Unit
		SE	US	FA						
0x4A	*BTPDischargeSet()*	R/W	R/W	R/W	I2	2	0	32767	150	mAh

15.42 0x4B BTPChargeSet()

The read/write word command updates the BTP set threshold for CHARGE mode for the next BTP interrupt, deasserts the present BTP interrupt, and clears the *OperationStatus()[BTP_INT]* bit.

SBS Cmd	Name	Access			Format	Size in Bytes	Min	Max	Default	Unit
		SE	US	FA						
0x4B	*BTPChargeSet()*	R/W	R/W	R/W	I2	2	0	32767	175	mAh

15.43 0x4F StateofHealth()

This read word command returns the SOH information of the battery in percentage of ***Design Capacity*** and ***Design Capacity cWh***.

15.44 0x50 SafetyAlert()

This command returns the *SafetyAlert()* flags. For a description of each bit flag, see the *ManufacturerAccess()* version of the same command in Section 15.1.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x50	*SafetyAlert()*	—	R	R	Block	H4	0x00000000	0xFFFFFFFF	—	—

15.45 0x51 SafetyStatus()

This command returns the *SafetyStatus()* flags. For a description of each bit flag, see the *ManufacturerAccess()* version of the same command in Section 15.1.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x51	*SafetyStatus()*	—	R	R	Block	H4	0x00000000	0xFFFFFFFF	—	—

15.46 0x52 PFAlert()

This command returns the *PFAlert()* flags. For a description of each bit flag, see the *ManufacturerAccess()* version of the same command in Section 15.1.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x52	*PFAlert()*	—	R	R	Block	H4	0x00000000	0xFFFFFFFF	—	—

15.47 0x53 PFStatus()

This command returns the *PFStatus()* flags. For a description of each bit flag, see the *ManufacturerAccess()* version of the same command in Section 15.1.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x53	*PFStatus()*	—	R	R	Block	H4	0x00000000	0xFFFFFFFF	—	—

15.48 0x54 OperationStatus()

This command returns the *OperationStatus()* flags. For a description of each bit flag, see the *ManufacturerAccess()* version of the same command in Section 15.1.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x54	*OperationStatus()*	—	R	R	Block	H4	0x00000000	0xFFFFFFFF	—	—

15.49 0x55 ChargingStatus()

This command returns the *ChargingStatus()* flags. For a description of each bit flag, see the *ManufacturerAccess()* version of the same command in Section 15.1.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x55	*ChargingStatus()*	—	R	R	Block	H4	0x00000000	0xFFFFFFFF	—	—

15.50 0x56 GaugingStatus()

This command returns the *GaugingStatus()* flags. For a description of each bit flag, see the *ManufacturerAccess()* version of the same command in Section 15.1.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x56	*GaugingStatus()*	—	R	R	Block	H4	0x00000000	0xFFFFFFFF	—	—

15.51 0x57 ManufacturingStatus()

This command returns the *ManufacturingStatus()* flags. For a description of each bit flag, see the *ManufacturerAccess()* version of the same command in Section 15.1.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x57	*ManufacturingStatus()*	—	R	R	Block	H4	0x00000000	0xFFFFFFFF	—	—

15.52 0x58 AFERegister()

This command returns a snapshot of the AFE register settings. For a description of returned data values, see the *ManufacturerAccess()* version of the same command in Section 15.1.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x58	*AFERegister()*	—	R	R	Block	—	—	—	—	—

15.53 0x59 MaxTurboPwr()

This command reads the maximal peak power value for 10-ms pulse occurring on top of 10-s 2 C-rate pulse.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x59	*MaxTurboPwr()*	R/W	R/W	R/W	Word	I2	0	32767	na	cW

15.54 0x5A SusTurboPwr()

This command reads the maximal peak power value for 10-s pulse, sustained turbo power, in cW.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x5A	*SusTurboPwr()*	R/W	R/W	R/W	Word	I2	0	32767	na	cW

15.55 0x5B TurboPackR()

This command sets the ***Pack Resistance*** value of the battery pack serial resistance, including resistance associated with FETs, traces, sense resistors, and so on.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x5B	TurboPackR()	R/W	R/W	R/W	Word	I2	0	32767		mΩ

15.56 0x5C TurboSysR()

This command sets the ***System Resistance*** value of the system serial resistance along the path from the battery to the system power converter input that includes FETs, traces, sense resistors, and so on.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x5C	*TurboSysR()*	R/W	R/W	R/W	Word	I2	0	32767		mΩ

15.57 0x5D TurboEdv()

This command sets the minimal voltage at the system power converter input at which the system will still operate. This command writes to the data flash value ***Min System Voltage***. It writes it once on the first use to adjust for possible changes in the system design from the time the battery pack was designed.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x5D	*TurboEdv()*	R/W	R/W	R/W	Word	I2	0	32767		mV

15.58 0x5E MaxTurboCurr()

This command reads the maximal peak current value, max turbo current, in mA. The gauge computes a new RAM value of max turbo current every second. Max turbo current is initialized to present the value of max turbo current on reset or power up.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x5E	*MaxTurboCurr()*	R/W	R/W	R/W	Word	I2	0	32767	—	mA

15.59 0x5F SusTurboCurr()

This command reads the sustained peak current value, sustained turbo current, in mA. The gauge computes a new RAM value sustained turbo current every second. Sustained turbo current is initialized to the present value of max turbo current on reset or power up.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x5F	*SusTurboCurr()*	—	R/W	R/W	Word	I2	0	32767	—	mA

15.60 0x60 LifetimeDataBlock1()

This command returns the first block of ***Lifetime Data***. For a description of returned data values, see the *ManufacturerAccess()* version of the same command in Section 15.1.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x60	*LifeTimeDataBlock1()*	—	R	R	Block	—	—	—	—	—

15.61 0x61 LifetimeDataBlock2()

This command returns the second block of ***Lifetime Data***. For a description of returned data values, see the *ManufacturerAccess()* version of the same command in Section 15.1.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x61	*LifeTimeDataBlock2()*	—	R	R	Block	—	—	—	—	—

15.62 0x62 LifetimeDataBlock3()

This command returns the third block of ***Lifetime Data***. For a description of returned data values, see the *ManufacturerAccess()* version of the same command in Section 15.1.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x62	*LifeTimeDataBlock3()*	—	R	R	Block	—	—	—	—	—

15.63 0x63 LifetimeDataBlock4()

This command returns the fourth block of ***Lifetime Data***. For a description of returned data values, see the *ManufacturerAccess()* version of the same command in Section 15.1.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x63	*LifeTimeDataBlock4()*	—	R	R	Block	—	—	—	—	—

15.64 0x64 LifetimeDataBlock5()

This command returns the fifth block of ***Lifetime Data***. For a description of returned data values, see the *ManufacturerAccess()* version of the same command in Section 15.1.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x64	*LifeTimeDataBlock5()*	—	R	R	Block	—	—	—	—	—

15.65 0x65 LifetimeDataBlock6()

This command returns the sixth block of ***Lifetime Data***. For a description of returned data values, see the *ManufacturerAccess()* version of the same command in Section 15.1.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x65	*LifeTimeDataBlock6()*	—	R	R	Block	—	—	—	—	—

15.66 0x66 LifetimeDataBlock7()

This command returns the seventh block of ***Lifetime Data***. For a description of returned data values, see the *ManufacturerAccess()* version of the same command in Section 15.1.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x66	*LifeTimeDataBlock7()*	—	R	R	Block	—	—	—	—	—

15.67 0x67 LifetimeDataBlock8()

This command returns the eighth block of ***Lifetime Data***. For a description of returned data values, see the *ManufacturerAccess()* version of the same command in Section 15.1.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x67	*LifeTimeDataBlock8()*	—	R	R	Block	—	—	—	—	—

15.68 0x68 TurboRhfEffective()

This command returns the effective impedance based on the pack's ability to provide currents in the time frame of milliseconds. The value for Rhf of all cells is combined and added to any other non-cell pack resistance, such as ***Pack Resistance*** and ***System Resistance***. Used in conjunction with *TurboVload()*, this helps to determine which trigger voltage threshold to use so that the system does not fall below its dropout voltage.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x68	*TurboRhfEffective()*	R	R	R	Word	I2	0	32767	—	mΩ

15.69 0x69 TurboVload()

The value of *TurboVload()* is taken from the cell model and combined with that of the other cells, as Vload is a parameter modeling the entire pack. *TurboVload()* may be explained as the total voltage the cells would show after providing power for a long period; after all current stops, the voltage is measured about 1 ms afterwards.

Used in conjunction with *TurboRhfEffective()*, this helps to determine which trigger voltage threshold to use so that the system does not fall below its dropout voltage.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x69	*TurboVload()*	R	R	R	Word	I2	0	32767	—	mV

15.70 0x6A LifetimeDataBlock 11()

This command returns the eleventh block of ***Lifetime Data***. For a description of returned data values, see the *ManufacturerAccess()* version of the same command in Section 15.1

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x6A	*LifeTimeDataBlock11()*	—	R	R	Block	—	—	—	—	—

15.71 0x6B LifetimeDataBlock12()

This command returns the twelfth block of ***Lifetime Data***. For a description of returned data values, see the *ManufacturerAccess()* version of the same command in Section 15.1

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x6B	*LifeTimeDataBlock12()*	—	R	R	Block	—	—	—	—	—

15.72 0x70 ManufacturerInfo()

This command returns manufacturer information. For a description of returned data values, see the *ManufacturerAccess()* version of the same command in Section 15.1.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x70	*ManufacturerInfo()*	R	R/W	R/W	Block	—	—	—	—	—

15.73 0x71 DAStatus1()

This command returns the cell voltages, PACK voltage, BAT voltage, cell currents, cell powers, power, and average power. For a description of returned data values, see the *ManufacturerAccess()* version of the same command in Section 15.1.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x71	*DAStatus1()*	—	R	R	Block	—	—	—	—	—

15.74 0x72 DAStatus2()

This command returns the internal temperature sensor, TS1, TS2, TS3, TS4, and cell, FET, and gauging temperatures. For a description of returned data values, see the *ManufacturerAccess()* version of the same command in Section 15.1.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x72	*DAStatus2()*	—	R	R	Block	—	—	—	—	—

15.75 0x73 GaugeStatus1()

This command instructs the device to return Impedance Track gauging information. For a description of returned data values, see the *ManufacturerAccess()* version of the same command in Section 15.1.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x73	*GaugeStatus1()*	—	R	R	Block	—	—	—	—	—

15.76 0x74 GaugeStatus2()

This command instructs the device to return Impedance Track gauging information. For a description of returned data values, see the *ManufacturerAccess()* version of the same command in Section 15.1.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x74	*GaugeStatus2()*	—	R	R	Block	—	—	—	—	—

15.77 0x75 GaugeStatus3()

This command instructs the device to return Impedance Track gauging information. For a description of returned data values, see the *ManufacturerAccess()* version of the same command in Section 15.1.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x75	*GaugeStatus3()*	—	R	R	Block	—	—	—	—	—

15.78 0x76 CBStatus()

This command instructs the device to return cell balance time information. For a description of returned data values, see the *ManufacturerAccess()* version of the same command in Section 15.1.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x76	*CBStatus()*	—	R	R	Block	—	—	—	—	—

15.79 0x77 StateofHealth()

This command instructs the device to return the state-of-health full charge capacity and energy. For a description of returned data values, see the *ManufacturerAccess()* version of the same command in Section 15.1.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x77	*StateofHealth()*	—	R	R	Block	—	—	—	—	—

15.80 0x78 FilteredCapacity()

This command instructs the device to return the filtered capacity and energy even if ***[SMOOTH]*** = 0. For a description of returned data values, see the *ManufacturerAccess()* version of the same command in Section 15.1.

SBS Cmd	Name	Access			Protocol	Type	Min	Max	Default	Unit
		SE	US	FA						
0x78	*FilteredCapacity()*	—	R	R	Block	—	—	—	—	—

Data Flash Values

16.1 Data Formats

16.1.1 Unsigned Integer

Unsigned integers are stored without changes as 1-byte, 2-byte, or 4-byte values in little endian byte order.

0
U1 MSB

0	1
U2 LSB	U2 MSB

0	1	2	3
U4 L LSB	U4 L MSB	U4 H LSB	U4 H MSB

16.1.2 Integer

Integer values are stored in 2's-complement format in 1-byte, 2-byte, or 4-byte values in little endian byte order.

0
I1 MSB

0	1
I2 LSB	I2 MSB

0	1	2	3
I4 L LSB	I4 L MSB	I4 H LSB	I4 H MSB

16.1.3 Floating Point

Floating point values are stored using the IEEE754 Single Precision 4-byte format in little endian byte order.

0	1	2	3
Fract [0–7]	Fract [8–15]	Exp[0] + Fract[16–22]	Sign + Exp[1–7]

Where:

Exp: 8-bit exponent stored with an offset bias of 127. The values 00 and FF have unique meanings.

Fract: 23-bit fraction. If the exponent is > 0, then the mantissa is 1.fract. If the exponent is zero, then the mantissa is 0.fract.

The floating point value depends on the unique cases of the exponent:

- If the exponent is FF and the fraction is zero, this represents +/– infinity.
- If the exponent is FF and the fraction is non-zero this represents "not a number" (NaN).
- If the exponent is 00 then the value is a subnormal number represented by $(-1)^{sign} \times 2^{-126} \times 0.\text{fraction}$.
- Otherwise, the value is a normalized number represented by $(-1)^{sign} \times 2^{(exponent - 127)} \times 1.\text{fraction}$.

16.1.4 Hex

Bit register definitions are stored in unsigned integer format.

16.1.5 String

String values are stored with length byte first, followed by a number of data bytes defined with the length byte.

0	1	. . .	N
Length	Data0	. . .	DataN

16.2 Settings

16.2.1 Configuration

16.2.1.1 FET Options

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Configuration	FET Options	H1	0x00	0xFF	0x20	Hex

7	6	5	4	3	2	1	0
PACK_FUSE	SLEEPCHG	CHGFET	CHGIN	CHGSU	OTFET	RSVD	PCHG_COMM

PACK_FUSE (Bit 7): Source of voltage to check for ***Min Blow Fuse Voltage***

1 = PACK voltage

0 = Battery stack voltage

SLEEPCHG (Bit 6): CHG FET enabled during sleep

1 = CHG FET remains on during sleep

0 = CHG FET off during sleep (default)

CHGFET (Bit 5): FET action on setting of *GaugeStatus()[TC]*

1 = Charging and Precharging disabled, FET off

0 = FET active (default)

CHGIN (Bit 4): FET action in CHARGE INHIBIT mode

1 = Charging and Precharging disabled, FETs off

0 = FET active (default)

CHGSU (Bit 3): FET action in CHARGE SUSPEND mode

1 = Charging and Precharging disabled, FETs off

0 = FET active (default)

OTFET (Bit 2): FET action in OVERTEMPERATURE mode

1 = CHG and DSG FETs will be turned off for overtemperature conditions

0 = No FET action for overtemperature condition (default)

RSVD (Bit 1): Reserved. Do not use.

PCHG_COMM (Bit 0): Precharge FET selection

1 = CHG FET

0 = PCHG FET (default)

16.2.1.2 SBS Gauging Configuration

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Configuration	SBS Gauging Configuration	H1	0x00	0xFF	0x04	Hex

7	6	5	4	3	2	1	0
RSVD	RSVD	RSVD	1PERCENT_HOLD	RSOC_RND_OFF	LOCK0	RSOC_HOLD	RSOCL

RSVD (Bits 7–5): Reserved. Do not use.

1PERCENT_HOLD (Bit 4): Setting this bit prevents RSOC from going below 1% until ***Terminate Voltage*** is detected.

1 = Enabled

0 = Disabled

RSOC_RND_OFF (Bit 3): Enables a round-off option of RSOC (instead of a ceiling function available by default)

1 = Enables RSOC round-off

0 = Disables RSOC round-off (A ceiling function is used instead.)

LOCK0 (Bit 2): Keep *RemainingCapacity()* and *RelativeStateOfCharge()* from jumping back during relaxation after 0 was reached during discharge.

1 = Enabled (default)

0 = Disabled

RSOC_HOLD (Bit 1): Prevent RSOC from increasing during discharge

1 = RSOC not allowed to increase during discharge

0 = RSOC not limited (default)

RSOCL (Bit 0): *RelativeStateOfCharge()* and *RemainingCapacity()* behavior at end of charge

1 = Held at 99% until valid charge termination. On entering valid charge termination update to 100%

0 = Actual value shown (default)

16.2.1.3 SBS Configuration

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Configuration	SBS Configuration	H1	0x7F	0xFF	0x20	Hex

7	6	5	4	3	2	1	0
FLASH_ BUSY_WAIT	SMB_CELL _TEMP	BLT1	BLT0	XL	HPE	CPE	BCAST

FLASH_BUSY_WAIT (Bit 7): This enables clock stretching during a flash program or erase operation.

1 = The bq40z50-R3 device will clock stretch (up to the timeout for SMBus devices) during flash operations.

0 = The bq40z50-R3 device will NACK any SMBus engine interrupt that occurs during a flash operation (program or erase).

Note: There is some potential for read errors with this bit. For example, when the master is reading data from the device, there is no NACK from the gauge; therefore, the "NACK" in the hardware releases the bus without writing new data to the SMBDA register, which means the read is whatever is present at the time. PECs should catch this error.

SMB_CELL_TEMP (Bit 6): Enables the host to write the temperature register via MAC command *WriteTemp()*. This enables bypassing the gauge's cell temperature inputs (TS1...TS3).

1 = Host can set the temperature (and bypass TS1...TS4).

0 = Host cannot set the temperature (temperature is set by the gauge's thermistors).

BLT1 (Bit 5): Bus low timeout

1,1 = 3-s SBS bus low timeout

1,0 = 2-s SBS bus low timeout (default)

0,1 = 1-s SBS bus low timeout

0,0 = No SBS bus low timeout

BLT0 (Bit 4): Bus low timeout

1,1 = 3-s SBS bus low timeout

1,0 = 2-s SBS bus low timeout (default)

0,1 = 1-s SBS bus low timeout

0,0 = No SBS bus low timeout

XL (Bit 3): Enables 400-kHz COM mode

1 = 400-kHz bus speed

0 = Normal SBS bus speed (default)

HPE (Bit 2): PEC on host communication

1 = Enabled

0 = Disabled (default)

CPE (Bit 1): PEC on charger broadcast

1 = Enabled

0 = Disabled (default)

BCAST (Bit 0): Enables alert and charging broadcast from device to the host

1 = Enabled

0 = Disabled (default)

16.2.1.4 Auth Config

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Configuration	Auth Config	H1	0x00	0x04	0x00	Hex

7	6	5	4	3	2	1	0
RSVD	RSVD	RSVD	RSVD	RSVD	SHA1_ SECURE	RSVD	RSVD

RSVD (Bits 7–3): Reserved. Do not use.

SHA1_SECURE (Bit 2): Enables secure memory usage for encryption key storage

1 = Enables secure memory usage

0 = Disables secure memory usage

RSVD (Bits 1–0): Reserved. Do not use.

16.2.1.5 Power Config

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Configuration	Power Config	H2	0x00	0x01	0x00	Hex

15	14	13	12	11	10	9	8
RSVD	RSVD	RSVD	IO_PUL	IO_POL	IO_SHUT	SLEEPWKCHG	SLP_ACCUM
7	**6**	**5**	**4**	**3**	**2**	**1**	**0**
RSVD	RSVD	CHECK_ WAKE_FET	CHECK_ WAKE	EMSHUT _EXIT_COMM	EMSHUT _EXIT_VPACK	PWR_SAVE _VSHUT	AUTO_SHIP _EN

RSVD (Bits 15–13): Reserved. Do not use.

IO_PUL_DIS (Bit 12): IO-Based Shutdown Pullup Disable

1 = Pullup disabled

0 = Pullup enabled (active only during read)

IO_POL (Bit 11): IO Based Shutdown Polarity

1 = Active high

0 = Active low

IO_SHUT (Bit 10): Enables the IO Based Shutdown feature

1 = Enabled

0 = Disabled

SLEEPWKCHG (Bit 9): Enables the sleep wake charge feature

1 = Enables sleep wake charge feature

0 = Disables sleep wake charge feature

SLP_ACCUM (Bit 8): Enables charge accumulation while in SLEEP mode

1 = Enables charge accumulation in SLEEP mode

0 = Disables charge accumulation in SLEEP mode

RSVD (Bits 7–6): Reserved. Do not use.

CHECK_WAKE_FET (Bit 5): Enables the CHG and DSG FETs not to be forced off during the ***Delay*** timer period

1 = FETs are not to be forced off during the ***Delay*** timer period.

0 = FETs are forced off during the ***Delay*** timer period.

CHECK_WAKE (Bit 4): Enables option to manage unintended wakeup from SHUTDOWN.

1 = Enables this option for unintended wakeup

0 = Disables this option for unintended wakeup

EMSHUT_EXIT_COMM (Bit 3): Enables exit from Emergency FET Shutdown if valid SMBus communication is received. Valid SMBus communication means a valid gauge address and any command is received (that is, an invalid command with a valid address is acceptable).

1 = Enables valid communication reception based exit from EMSHUT

0 = Disables valid communication reception based exit from EMSHUT

EMSHUT_EXIT_VPACK (Bit 2): This bit enables exit from an emergency FET shutdown if the voltage at the PACK pin > ***Charger Present Threshold*** for two samples (~2 s).

1 = Enables PACK voltage based exit from EMSHUT

0 = Disables PACK voltage based exit from EMSHUT

PWR_SAVE_VSHUT (Bit 1): Enables POWER SAVE SHUTDOWN when specific thresholds have been reached.

1 = Enables POWER SAVE SHUTDOWN

0 = Disables POWER SAVE SHUTDOWN

AUTO_SHIP_EN (Bit 0): *Automatically Shut Down for Shipment*

1 = Enables auto shutdown after the device is in SLEEP mode without communication for a set period of time.

0 = Disables the auto shutdown feature

16.2.1.6 IO Config

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Configuration	IO Config	H1	0x0	0x03	0x00	Hex

7	6	5	4	3	2	1	0
RSVD	RSVD	RSVD	RSVD	GPIO_PF	GPIO_EN	BTP_POL	BTP_EN

RSVD (Bits 7–4): Reserved. Do not use.

GPIO_PF (Bit 3): GPIO control during permanent failure

1 = Enabled

0 = Disabled

GPIO_EN (Bit 2): GPIO Mode Enable

1 = Enabled

0 = Disabled

BTP_POL (Bit 1): Controls polarity of the BTP pin

1 = BTP pin is asserted high when BTP is triggered.

0 = BTP pin is asserted low when BTP is triggered (default).

BTP_EN (Bit 0): Enables assertion of the BTP pin

1 = Enables assertion of the BTP pin when BTP is triggered.

0 = Disables assertion of the BTP pin when BTP is triggered (default).

16.2.1.7 GPIO Sealed Access Config

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Configuration	GPIO Sealed Access Config	H2	0x0000	0x000F	0x0000	Hex

15	14	13	12	11	10	9	8
RSVD	RSVD	RSVD	RSVD	RSVD	RSVD	RSVD	RSVD

7	6	5	4	3	2	1	0
RSVD	RSVD	RSVD	RSVD	LEDCNTLC_PIN22	LEDCNTLB_PIN21	LEDCNTLA_PIN20	DISP_PIN17

RSVD (Bits 15–4): Reserved. Do not use.

LEDCNTLC_PIN22 (Bit 3): LEDCNTLC (Pin 22) SEALED mode access

1 = Enabled

0 = Disabled

LEDCNTLB_PIN21 (Bit 2): LEDCNTLB (Pin 21) SEALED mode access

1 = Enabled

0 = Disabled

LEDCNTLA_PIN20 (Bit 1): LEDCNTLA (Pin 20) SEALED mode access

1 = Enabled

0 = Disabled

DISP_PIN17 (Bit 0): $\overline{\text{DISP}}$ (Pin 17) SEALED mode access

1 = Enabled

0 = Disabled

16.2.1.8 Flag Map Set Up 1

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Configuration	Flag Map Set Up 1	H2	0x0000	0xFFFF	0x0000	Hex

15	14	13	12	11	10	9	8
FLAG_EN	RSVD	FLAG_OD	FLAG_OR	RSVD	FLAG_GPIO1	FLAG_GPIO0	FLAG_POL

7	6	5	4	3	2	1	0
FLAG_BIT3	FLAG_BIT2	FLAG_BIT1	FLAG_BIT0	FLAG_REG3	FLAG_REG2	FLAG_REG1	FLAG_REG0

FLAG_EN (Bit 15): Enable/disable the control

1 = Enable

0 = Disable

RSVD (Bit 14): Reserved. Do not use.

FLAG_OD (Bit 13): Determines whether the GPIO pin is driven between two levels as hi-Z/driven-low (that is, open drain) or as driven-high/driven-low (that is, active high).
Note: The *[FLAG_OD]* bit cannot be set differently by separate controls when mapped to the same GPIO pin.

1 = Hi-Z/driven-low

0 = Driven-high/driven-low

FLAG_OR (Bit 12): The flag OR'ed vs AND'ed with other flags mapped to the same GPIO pin. This OR/AND operation takes place after the polarity from *FLAG_POL* is evaluated.

1 = OR Operation

0 = AND Operation

RSVD (Bit 11): Reserved. Do not use.

FLAG_GPIO1, FLAG_GPIO0 (Bit 10, 9): The flag mapped to a GPIO pin

0, 0 = DISP (RH0, Pin 17)
0, 1 = LEDCNTLA (RL0, Pin 20)
1, 0 = LEDCNTLB (RL1, Pin 21)
1, 1 = LEDCNTLC (RL2, Pin 22)

FLAG_POL (Bit 8): Polarity of the flag when mapped to a GPIO pin

1 = Invert flag polarity
0 = No change to flag polarity

FLAG_BIT3, FLAG_BIT2, FLAG_BIT1, FLAG_BIT0 (Bit 7, Bit 6, Bit 5, Bit 4): Bit position within the 16-bit register of the flag

0, 0, 0, 0 = Bit 0
0, 0, 0, 1 = Bit 1
0, 0, 1, 0 = Bit 2
0, 0, 1, 1 = Bit 3
0, 1, 0, 0 = Bit 4
0, 1, 0, 1 = Bit 5
0, 1, 1, 0 = Bit 6
0, 1, 1, 1 = Bit 7
1, 0, 0, 0 = Bit 8
1, 0, 0, 1 = Bit 9
1, 0, 1, 0 = Bit 10
1, 0, 1, 1 = Bit 11
1, 1, 0, 0 = Bit 12
1, 1, 0, 1 = Bit 13
1, 1, 1, 0 = Bit 14
1, 1, 1, 1 = Bit 15

FLAG_REG3, FLAG_REG2, FLAG_REG1, FLAG_REG0 (Bit 3, Bit 2, Bit 1, Bit 0): Address of the register that contains the flag

0, 0, 0, 0 = *BatteryMode()*
0, 0, 0, 1 = *BatteryStatus()*
0, 0, 1, 0 = *OperationStatusA()*, lower 16 bits of *OperationStatus()*
0, 0, 1, 1 = *OperationStatusB()*, higher 16 bits of *OperationStatus()*
0, 1, 0, 0 = *ChargingStatus()*
0, 1, 0, 1 = *TempStatus()*
0, 1, 1, 0 = *GaugingStatus()*
0, 1, 1, 1 = *ITStatus()*
1, 0, 0, 0 = *SafetyStatusAB()*, lower 16 bits of *SafetyStatus()*
1, 0, 0, 1 = *SafetyStatusCD()*, higher 16 bits of *SafetyStatus()*
1, 0, 1, 0 = Any Safety Status bit in *SafetyStatus()*
1, 0, 1, 1 = *PFStatusAB()*, lower 16 bits of *PFStatus()*
1, 1, 0, 0 = *PFStatusCD()*, higher 16 bits of *PFStatus()*
1, 1, 0, 1 = Any PF Status bit in *PFStatus()*
1, 1, 1, 0 = Unused
1, 1, 1, 1 = Unused

16.2.1.9 Flag Map Set Up 2

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Configuration	Flag Map Set Up 2	H2	0x0000	0xFFFF	0x0000	Hex

15	14	13	12	11	10	9	8
FLAG_EN	RSVD	FLAG_OD	FLAG_OR	RSVD	FLAG_GPIO1	FLAG_GPIO0	FLAG_POL

7	6	5	4	3	2	1	0
FLAG_BIT3	FLAG_BIT2	FLAG_BIT1	FLAG_BIT0	FLAG_REG3	FLAG_REG2	FLAG_REG1	FLAG_REG0

FLAG_EN (Bit 15): Enable/disable the control

1 = Enable
0 = Disable

RSVD (Bit 14): Reserved. Do not use.

FLAG_OD (Bit 13): This bit determines whether the GPIO pin is driven between two levels as hi-Z/driven-low (that is, open drain) or as driven-high/driven-low (that is, active high).
Note: The *[FLAG_OD]* bit cannot be set differently by separate controls when mapped to the same GPIO pin.

1 = Hi-Z/driven-low
0 = Driven-high/driven-low

FLAG_OR (Bit 12): The flag OR'ed vs AND'ed with other flags mapped to the same GPIO pin. This OR/AND operation takes place after the polarity from FLAG_POL is evaluated.

1 = OR Operation
0 = AND Operation

RSVD (Bit 11): Reserved. Do not use.

FLAG_GPIO1, FLAG_GPIO0 (Bit 10, 9): The flag mapped to a GPIO pin

0, 0 = DISP (RH0, Pin 17)
0, 1 = LEDCNTLA (RL0, Pin 20)
1, 0 = LEDCNTLB (RL1, Pin 21)
1, 1 = LEDCNTLC (RL2, Pin 22)

FLAG_POL (Bit 8): Polarity of the flag when mapped to a GPIO pin

1 = Invert flag polarity
0 = No change to flag polarity

FLAG_BIT3, FLAG_BIT2, FLAG_BIT1, FLAG_BIT0 (Bit 7, Bit 6, Bit 5, Bit 4): Bit position within the 16-bit register of the flag

0, 0, 0, 0 = Bit 0
0, 0, 0, 1 = Bit 1
0, 0, 1, 0 = Bit 2
0, 0, 1, 1 = Bit 3
0, 1, 0, 0 = Bit 4
0, 1, 0, 1 = Bit 5
0, 1, 1, 0 = Bit 6
0, 1, 1, 1 = Bit 7
1, 0, 0, 0 = Bit 8
1, 0, 0, 1 = Bit 9
1, 0, 1, 0 = Bit 10

1, 0, 1, 1 = Bit 11
1, 1, 0, 0 = Bit 12
1, 1, 0, 1 = Bit 13
1, 1, 1, 0 = Bit 14
1, 1, 1, 1 = Bit 15

FLAG_REG3, FLAG_REG2, FLAG_REG1, FLAG_REG0 (Bit 3, Bit 2, Bit 1, Bit 0): Address of the register that contains the flag

0, 0, 0, 0 = *BatteryMode()*
0, 0, 0, 1 = *BatteryStatus()*
0, 0, 1, 0 = *OperationStatusA()*, lower 16 bits of *OperationStatus()*
0, 0, 1, 1 = *OperationStatusB()*, higher 16 bits of *OperationStatus()*
0, 1, 0, 0 = *ChargingStatus()*
0, 1, 0, 1 = *TempStatus()*
0, 1, 1, 0 = *GaugingStatus()*
0, 1, 1, 1 = *ITStatus()*
1, 0, 0, 0 = *SafetyStatusAB()*, lower 16 bits of *SafetyStatus()*
1, 0, 0, 1 = *SafetyStatusCD()*, higher 16 bits of *SafetyStatus()*
1, 0, 1, 0 = Any Safety Status bit in *SafetyStatus()*
1, 0, 1, 1 = *PFStatusAB()*, lower 16 bits of *PFStatus()*
1, 1, 0, 0 = *PFStatusCD()*, higher 16 bits of *PFStatus()*
1, 1, 0, 1 = Any PF Status bit in *PFStatus()*
1, 1, 1, 0 = Unused
1, 1, 1, 1 = Unused

16.2.1.10 Flag Map Set Up 3

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Configuration	Flag Map Set Up 3	H2	0x0000	0xFFFF	0x0000	Hex

15	14	13	12	11	10	9	8
FLAG_EN	RSVD	FLAG_OD	FLAG_OR	RSVD	FLAG_GPIO1	FLAG_GPIO0	FLAG_POL

7	6	5	4	3	2	1	0
FLAG_BIT3	FLAG_BIT2	FLAG_BIT1	FLAG_BIT0	FLAG_REG3	FLAG_REG2	FLAG_REG1	FLAG_REG0

FLAG_EN (Bit 15): Enable/disable the control

1 = Enable
0 = Disable

RSVD (Bit 14): Reserved. Do not use.

FLAG_OD (Bit 13): This bit determines whether the GPIO pin is driven between two levels as hi-Z/driven-low (that is, open drain) or as driven-high/driven-low (that is, active high).
Note: The *[FLAG_OD]* bit cannot be set differently by separate controls when mapped to the same GPIO pin.

1 = Hi-Z/driven-low
0 = Driven-high/driven-low

FLAG_OR (Bit 12): The flag OR'ed vs AND'ed with other flags mapped to the same GPIO pin. This OR/AND operation takes place after the polarity from *[FLAG_POL]* is evaluated.

1 = OR Operation
0 = AND Operation

RSVD (Bit 11): Reserved. Do not use.

FLAG_GPIO1, FLAG_GPIO0 (Bit 10, 9): The flag mapped to a GPIO pin
0, 0 = DISP (RH0, Pin 17)
0, 1 = LEDCNTLA (RL0, Pin 20)
1, 0 = LEDCNTLB (RL1, Pin 21)
1, 1 = LEDCNTLC (RL2, Pin 22)

FLAG_POL (Bit 8): Polarity of the flag when mapped to a GPIO pin
1 = Invert flag polarity
0 = No change to flag polarity

FLAG_BIT3, FLAG_BIT2, FLAG_BIT1, FLAG_BIT0 (Bit 7, Bit 6, Bit 5, Bit 4): Bit position within the 16-bit register of the flag
0, 0, 0, 0 = Bit 0
0, 0, 0, 1 = Bit 1
0, 0, 1, 0 = Bit 2
0, 0, 1, 1 = Bit 3
0, 1, 0, 0 = Bit 4
0, 1, 0, 1 = Bit 5
0, 1, 1, 0 = Bit 6
0, 1, 1, 1 = Bit 7
1, 0, 0, 0 = Bit 8
1, 0, 0, 1 = Bit 9
1, 0, 1, 0 = Bit 10
1, 0, 1, 1 = Bit 11
1, 1, 0, 0 = Bit 12
1, 1, 0, 1 = Bit 13
1, 1, 1, 0 = Bit 14
1, 1, 1, 1 = Bit 15

FLAG_REG3, FLAG_REG2, FLAG_REG1, FLAG_REG0 (Bit 3, Bit 2, Bit 1, Bit 0): Address of the register containing the flag
0, 0, 0, 0 = *BatteryMode()*
0, 0, 0, 1 = *BatteryStatus()*
0, 0, 1, 0 = *OperationStatusA()*, lower 16 bits of *OperationStatus()*
0, 0, 1, 1 = *OperationStatusB()*, higher 16 bits of *OperationStatus()*
0, 1, 0, 0 = *ChargingStatus()*
0, 1, 0, 1 = *TempStatus()*
0, 1, 1, 0 = *GaugingStatus()*
0, 1, 1, 1 = *ITStatus()*
1, 0, 0, 0 = *SafetyStatusAB()*, lower 16 bits of *SafetyStatus()*
1, 0, 0, 1 = *SafetyStatusCD()*, higher 16 bits of *SafetyStatus()*
1, 0, 1, 0 = Any Safety Status bit in *SafetyStatus()*
1, 0, 1, 1 = *PFStatusAB()*, lower 16 bits of *PFStatus()*
1, 1, 0, 0 = *PFStatusCD()*, higher 16 bits of *PFStatus()*
1, 1, 0, 1 = Any PF Status bit in *PFStatus()*
1, 1, 1, 0 = Unused

1, 1, 1, 1 = Unused

16.2.1.11 Flag Map Set Up 4

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Configuration	Flag Map Set Up 4	H2	0x0000	0xFFFF	0x0000	Hex

15	14	13	12	11	10	9	8
FLAG_EN	RSVD	FLAG_OD	FLAG_OR	RSVD	FLAG_GPIO1	FLAG_GPIO0	FLAG_POL

7	6	5	4	3	2	1	0
FLAG_BIT3	FLAG_BIT2	FLAG_BIT1	FLAG_BIT0	FLAG_REG3	FLAG_REG2	FLAG_REG1	FLAG_REG0

FLAG_EN (Bit 15): Enable/disable the control

1 = Enable

0 = Disable

RSVD (Bit 14): Reserved. Do not use.

FLAG_OD (Bit 13): This bit determines whether the GPIO pin is driven between two levels as hi-Z/driven-low (that is, open drain) or as driven-high/driven-low (that is, active high).
Note: The *[FLAG_OD]* bit cannot be set differently by separate controls when mapped to the same GPIO pin.

1 = Hi-Z/driven-low

0 = Driven-high/driven-low

FLAG_OR (Bit 12): Flag OR'ed vs AND'ed with other flags mapped to the same GPIO pin. This OR/AND operation takes place after the polarity from *[FLAG_POL]* is evaluated.

1 = OR Operation

0 = AND Operation

RSVD (Bit 11): Reserved. Do not use.

FLAG_GPIO1, FLAG_GPIO0 (Bit 10, 9): Flag mapped to a GPIO pin

0, 0 = DISP (RH0, Pin 17)

0, 1 = LEDCNTLA (RL0, Pin 20)

1, 0 = LEDCNTLB (RL1, Pin 21)

1, 1 = LEDCNTLC (RL2, Pin 22)

FLAG_POL (Bit 8): Polarity of the flag when mapped to a GPIO pin

1 = Invert flag polarity

0 = No change to flag polarity

FLAG_BIT3, FLAG_BIT2, FLAG_BIT1, FLAG_BIT0 (Bit 7, Bit 6, Bit 5, Bit 4): Bit position within the 16-bit register of the flag

0, 0, 0, 0 = Bit 0

0, 0, 0, 1 = Bit 1

0, 0, 1, 0 = Bit 2

0, 0, 1, 1 = Bit 3

0, 1, 0, 0 = Bit 4

0, 1, 0, 1 = Bit 5

0, 1, 1, 0 = Bit 6

0, 1, 1, 1 = Bit 7

1, 0, 0, 0 = Bit 8

1, 0, 0, 1 = Bit 9
1, 0, 1, 0 = Bit 10
1, 0, 1, 1 = Bit 11
1, 1, 0, 0 = Bit 12
1, 1, 0, 1 = Bit 13
1, 1, 1, 0 = Bit 14
1, 1, 1, 1 = Bit 15

FLAG_REG3, FLAG_REG2, FLAG_REG1, FLAG_REG0 (Bit 3, Bit 2, Bit 1, Bit 0): Address of the register that contains the flag

0, 0, 0, 0 = *BatteryMode()*
0, 0, 0, 1 = *BatteryStatus()*
0, 0, 1, 0 = *OperationStatusA()*, lower 16 bits of *OperationStatus()*
0, 0, 1, 1 = *OperationStatusB()*, higher 16 bits of *OperationStatus()*
0, 1, 0, 0 = *ChargingStatus()*
0, 1, 0, 1 = *TempStatus()*
0, 1, 1, 0 = *GaugingStatus()*
0, 1, 1, 1 = *ITStatus()*
1, 0, 0, 0 = *SafetyStatusAB()*, lower 16 bits of *SafetyStatus()*
1, 0, 0, 1 = *SafetyStatusCD()*, higher 16 bits of *SafetyStatus()*
1, 0, 1, 0 = Any Safety Status bit in *SafetyStatus()*
1, 0, 1, 1 = *PFStatusAB()*, lower 16 bits of *PFStatus()*
1, 1, 0, 0 = *PFStatusCD()*, higher 16 bits of *PFStatus()*
1, 1, 0, 1 = Any PF Status bit in *PFStatus()*
1, 1, 1, 0 = Unused
1, 1, 1, 1 = Unused

16.2.1.12 LED Configuration

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Configuration	LED Configuration	H1	0x0000	0xFFFF	0x00D0	Hex

15	14	13	12	11	10	9	8
RSVD	RSVD	RSVD	RSVD	LED ONFC	BLINK MIDPT	LEDIF CUV	LED PFON

7	6	5	4	3	2	1	0
LEDC1	LEDC0	LEDPF1	LEDPF0	LEDMODE	LEDCHG	LEDRCA	LEDR

RSVD (Bits 15–12): Reserved. Do not use.

LEDONFC (Bit 11): Enables the LED display to stay on showing charge even after full charge (FC) has been achieved. With this bit set, the LED will stay on after FC until the ***LED FC Time*** has expired.

1 = Enables LED display functionality after FC until the ***LED FC Time*** has expired
0 = Disables LED display after FC

BLINKMIDPT (Bit 10): Enables LED blinking until the midpoint of each LED segment. The blinking occurs between the bottom and the midway point of each programmed segment level; thus, providing more granularity as to where the charge level is within that LED segment.

1 = Enables LED blinking until the midway point of each segment charge levels
0 = Disables LED blinking

LEDIFCUV (Bit 9): Enables LED display functionality even under CUV conditions without a charger connected (no charging occurring). This option should be used with care so as to not discharge the battery too low.

- 1 = Enables LED display functionality even under CUV conditions without a charger connected
- 0 = Disables LED display functionality even under CUV conditions without a charger connected

LEDPFON (Bit 8): LED in PF Mode Enable

- 1 = Display available in PF Mode
- 0 = Display not available in PF mode (default)

LEDC1, LEDC0 (Bit 7, Bit 6): LED Current sink

- 0, 0 = 0.94-mA average LED current (default)
- 0, 1 = 1.87-mA average LED current
- 1, 0 = 2.81-mA average LED current
- 1, 1 = 3.75-mA average LED current

LEDPF1, LEDPF0 (Bit 5, Bit 4): LED Display PF Error Code

- 0, 0 = PF Error Code not available
- 0, 1 = PF Error Code shown after SOC if $\overline{\text{DISP}}$ is held low for LED Hold Time (default)
- 1, 0 = PF Error code shown if the $\overline{\text{DISP}}$ button is pressed (high-to-low transition of the pin is detected).
- 1, 1 = PF Error Code shown after SOC

LEDMODE (Bit 3): LED Display Capacity Selector

- 1 = Display ASOC/DC
- 0 = Display RSOC (default)

LEDCHG (Bit 2): LED Display During Charging

- 1 = Enabled
- 0 = Disabled

LEDRCA (Bit 1): Flashing of LED Display when [RCA] is set.

- 1 = Enabled
- 0 = Disabled

LEDR (Bit 0): LED Display activation at exit of device reset

- 1 = Enabled
- 0 = Disabled

16.2.1.13 SOC Flag Config A

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Configuration	SOC Flag Config A	H2	0x0000	0x0FFF	0x0C8C	Hex

15	14	13	12	11	10	9	8
RSVD	RSVD	RSVD	RSVD	TCSETVCT	FCSETVCT	RSVD	RSVD

7	6	5	4	3	2	1	0
TCCLEAR RSOC	TCSETRSOC	TCCLEARV	TCSETV	TDCLEAR RSOC	TDSETRSOC	TDCLEARV	TDSETV

RSVD (Bits 15–12): Reserved. Do not use.

TCSETVCT (Bit 11): Enables the TC flag set by primary charge termination

- 1 = Enabled (default)
- 0 = Disabled

FCSETVCT (Bit 10): Enables the FC flag set by primary charge termination

- 1 = Enabled (default)
- 0 = Disabled

RSVD (Bits 9–8): Reserved. Do not use.

TCCLEARRSOC (Bit 7): Enables the TC flag clear by RSOC threshold

- 1 = Enabled (default)
- 0 = Disabled

TCSETRSOC (Bit 6): Enables the TC flag set by RSOC threshold

- 1 = Enabled
- 0 = Disabled (default)

TCCLEARV (Bit 5): Enables the TC flag clear by cell voltage threshold

- 1 = Enabled
- 0 = Disabled (default)

TCSETV (Bit 4): Enables the TC flag set by cell voltage threshold

- 1 = Enabled
- 0 = Disabled (default)

TDCLEARRSOC (Bit 3): Enables the TD flag clear by RSOC threshold

- 1 = Enabled (default)
- 0 = Disabled

TDSETRSOC (Bit 2): Enables the TD flag set by RSOC threshold

- 1 = Enabled (default)
- 0 = Disabled

TDCLEARV (Bit 1): Enables the TD flag clear by cell voltage threshold

- 1 = Enabled
- 0 = Disabled (default)

TDSETV (Bit 0): Enables the TD flag set by cell voltage threshold

- 1 = Enabled
- 0 = Disabled (default)

16.2.1.14 SOC Flag Config B

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Configuration	SOC Flag Config B	H1	0x00	0xFF	0x8C	Hex

7	6	5	4	3	2	1	0
FCCLEAR RSOC	FCSETRSOC	FCCLEARV	FCSETV	FDCLEAR RSOC	FDSETRSOC	FDCLEARV	FDSETV

FCCLEARRSOC (Bit 7): Enables the FC flag clear by RSOC threshold
- 1 = Enabled (default)
- 0 = Disabled

FCSETRSOC (Bit 6): Enables the FC flag set by RSOC threshold
- 1 = Enabled
- 0 = Disabled (default)

FCCLEARV (Bit 5): Enables the FC flag clear by cell voltage threshold
- 1 = Enabled
- 0 = Disabled (default)

FCSETV (Bit 4): Enables the FC flag set by cell voltage threshold
- 1 = Enabled
- 0 = Disabled (default)

FDCLEARRSOC (Bit 3): Enables the FD flag clear by RSOC threshold
- 1 = Enabled (default)
- 0 = Disabled

FDSETRSOC Bit 2: Enables the FD flag set by RSOC threshold
- 1 = Enabled (default)
- 0 = Disabled

FDCLEARV (Bit 1): Enables the FD flag clear by cell voltage threshold
- 1 = Enabled
- 0 = Disabled (default)

FDSETV (Bit 0): Enables the FD flag set by cell voltage threshold
- 1 = Enabled
- 0 = Disabled (default)

16.2.1.15 IT Gauging Configuration

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Configuration	IT Gauging Configuration	H2	0x0000	0xFFFF	0xD0FE	Hex

15	14	13	12	11	10	9	8
DOD_R SCALE_EN	RELAX_ SMOOTH_OK	TDELTAV	SMOOTH	RELAX_ JUMP_OK	DELAY_ DROP_TO_0	CELL_TERM	FAST_ QMAX_FLD

7	6	5	4	3	2	1	0
FAST_QMAX_ LRN	RSOC_CONV	LFP_RELAX	DOD0EW	OCVFR	RFACTSTEP	CSYNC	CCT

DOD_RSCALE_EN (Bit 15): Configures which DOD the new RScale is to be applied.
- 1 = The RScale is only applied to DODs higher than the DOD where the RScale was calculated.
- 0 = The RScale is applied to all DODs during IT simulations.

RELAX_SMOOTH_OK (Bit 14): Smooth RSOC during RELAX mode
- 1 = Enabled (default)
- 0 = Disabled

TDELTAV (Bit 13): TURBO Mode Delta Voltage
- 1 = Must set this flag to 1 to support TURBO mode.
- 0 = Use of ***DeltaVoltage*** learned as the maximal difference between instantaneous and average voltage (default).

SMOOTH (Bit 12): Smooth RSOC
- 1 = Smoothed *FullChargeCapacity()* and *RemainingCapacity()* is used (default).
- 0 = True *FullChargeCapacity()* and *RemainingCapacity()* is used.

RELAX_JUMP_OK (Bit 11): Allows RSOC jump during RELAX mode
- 1 = Enabled
- 0 = Disabled (default)

DELAY_DROP_TO_0 (Bit 10): Delay
- 1 = Enabled
- 0 = Disabled (default)

CELL_TERM (Bit 9): Cell Based Termination
- 1 = Cell based termination
- 0 = Stack voltage based termination (default)

FAST_QMAX_FLD (Bit 8): Fast Qmax Update in Field
- 1 = Enabled
- 0 = Disabled (default)

FAST_QMAX_LRN (Bit 7): Fast Qmax Update in Learning
- 1 = Enabled (default)
- 0 = Disabled

RSOC_CONV (Bit 6): RSOC Convergence (Fast Scaling)
- 1 = Enabled (default)
- 0 = Disabled

LFP_RELAX (Bit 5): Lithium Iron Phosphate Relax
- 1 = Enabled (default)
- 0 = Disabled

DOD0EW (Bit 4): DOD0 Error Weighting
- 1 = Enabled (default)
- 0 = Disabled

OCVFR (Bit 3): Open Circuit Voltage Flat Region

1 = Enabled (default)
0 = Disabled

RFACTSTEP (Bit 2): Ra Factor Step
1 = Enabled (default).
0 = Disabled

CSYNC (Bit 1): Sync *RemainingCapacity()* with *FullChargeCapacity()* at valid charge termination
1 = Synchronized (default)
0 = Not synchronized

CCT (Bit 0): Cycle Count Threshold
1 = Use CC % of *FullChargeCapacity()*
0 = Use CC % of *DesignCapacity()* (default)

16.2.1.16 IT Gauging Ext

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Configuration	IT Gauging Ext	H2	0x0000	0x00FF	0X005A	Hex

15	14	13	12	11	10	9	8
RSVD	RSVD	RSVD	RSVD	RSVD	RSVD	RSVD	RSVD

7	6	5	4	3	2	1	0
RSVD	TS1	TS0	THERM _SAT	THERM _IV	AMB_PRED	CHG_100_ SMOOTH_OK	DSG_0_ SMOOTH_OK

RSVD (Bits 15–7): Reserved. Do not use.

TS1 (Bit 6), TS0 (Bit 5): These two bits are used in conjunction to select which one of the individual temperature sensors (TS 1…4) is used by the IT algorithm.
1,1 = Not used
1,0 = Min Temperature is used (IT uses the temperature sensor with the lowest temperature).
0,1 = Avg Temperature is used (IT uses the average temperature of all 4 temperature sensors).
0,0 = Max Temperature is used (IT uses the temperature sensor with the highest temperature). (Default)

THERM_SAT (Bit 4): Thermal saturation enables adjustment of the IT thermal model
1 = Enables adjustment of the IT thermal model
0 = Disables adjustment of the IT thermal model

THERM_IV (Bit 3): Enables freeze of the temperature model at certain points in IT to prevent overestimation by the thermal model
1 = Enables Freeze of the temperature model
0 = Disables Freeze of the temperature model

AMB_PRED (Bit 2): Enables ambient temperature prediction in modes other than RELAX
1 = Enables ambient temperature prediction
0 = Disables ambient temperature prediction

CHG_100_SMOOTH_OK (Bit 1): Enables smoothing in the charge direction when there is a jump to 100%
1 = Enables smoothing to 100%
0 = Disables smoothing to 100%

DSG_0_SMOOTH_OK (Bit 0): Enables smoothing in the discharge direction when there is a jump to 0%. When enabled, this smoothing option must be used in conjunction with ***Term Smooth Start Cell V Delta***, ***Term Smooth Time***, and ***Term Smooth Final Cell V Delta***. If not configured properly, this smoothing option can cause remaining capacity to report 0 too early.

1 = Enables smoothing to 0%

0 = Disables smoothing to 0%

16.2.1.17 Charging Configuration

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Configuration	Charging Configuration	H2	0x0000	0xFFFF	0x0000	Hex

15	14	13	12	11	10	9	8
RSVD	RSVD	RSVD	HT_INIHIB_DIS	HIBAT_CHG	TAPER_VOLT	RTORFCC	RUNTIME_DEGRADE

7	6	5	4	3	2	1	0
CYCLE_DEGRADE	SOH_DEGRADE	DEGRADE_CC	COMP_IR	CS_CV	SOC_CHARGE	CCC	CRATE

RSVD (Bits 15–13): Reserved

HT_INHIB_DIS (Bit 12): High Temperature Disable

1 = HT inhibit disabled

0 = HT inhibit enabled

HIBAT_CHG (Bit 11): See the *Charging Voltage* sections below.

1 = Enabled

0 = Disabled

TAPER_VOLT (Bit 10): Use fixed ***Charge Term Charging Voltage***

1 = Uses fixed ***Charge Term Charging Voltage*** for Charge Termination

0 = Uses *ChargingVoltage()* for Charge Termination

RTORCC (Bit 9): Use the first of runtime or cycle count degrade when also enabled

1 = Enabled

0 = Disabled

RUNTIME_DEGRADE (Bit 8): Runtime-based charging voltage or charging current degradation

1 = Degrade CC/CV based on runtime

0 = No degradation of CC/CV based on runtime

CYCLE_DEGRADE (Bit 7): ***Cycle Count*** based charging voltage or charging current degradation

1 = Degrade CC/CV based on ***Cycle Count***

0 = No degradation of CC/CV based on ***Cycle Count***

SOH_DEGRADE (Bit 6): SOH-based charging voltage or charging current degradation

1 = Degrade CC/CV based on SOH

0 = No degradation of CC/CV based on SOH

DEGRADE_CC (Bit 5): Enables charging current degradation based on ***Cycle Count*** or SOH.

1 = Enables Charging Current degradation

0 = Disables Charging Current degradation

COMP_IR (Bit 4): Allows IR compensation at the system level to ensure the correct voltage level required for a specific charging voltage at the battery terminals

1 = Enables system level IR compensation

0 = Disables system level IR compensation

CS_CV (Bit 3): This enables the cell swelling control under specific cell voltage and cell temperature thresholds by reducing the charging voltage.

1 = Enables cell swelling control

0 = Disables cell swelling control

SOC_CHARGE (Bit 2)

1 = Enables SOC threshold to replace voltage thresholds (CLV, CMV, and CHV) in ***Advanced Charging Algorithm***

0 = Uses voltage thresholds (CLV, CMV, and CHV) in ***Advanced Charging Algorithm***

CCC (Bit 1)

1 = Enables Charging Loss Compensation feature

0 = Disables Charging Loss Compensation (default)

CRATE (Bit 0): ChargeCurrent rate

1 = *ChargingCurrent()* adjusted based on *FullChargeCapacity()* / *DesignCapacity()*

0 = No adjustment to *ChargingCurrent()* (default)

16.2.1.18 Temperature Enable

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Configuration	Temperature Enable	H1	0x00	0x1F	0x06	Hex

7	6	5	4	3	2	1	0
RSVD	RSVD	RSVD	TS4	TS3	TS2	TS1	TSint

RSVD (Bits 7–5): Reserved. Do not use.

TS4 (Bit 4): Enable TS4

1 = Enables TS4 (default)

0 = Disables TS4

TS3 (Bit 3): Enable TS3

1 = Enables TS3 (default)

0 = Disables TS3

TS2 (Bit 2): Enable TS2

1 = Enables TS2 (default)

0 = Disables TS2

TS1 (Bit 1): Enable TS1

1 = Enables TS1 (default)

0 = Disables TS1

TSint (Bit 0): Enable internal TS

1 = Enables internal TS

0 = Disables internal TS (default)

16.2.1.19 Temperature Mode

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Configuration	Temperature Mode	H1	0x00	0x1F	0x04	Hex

7	6	5	4	3	2	1	0
RSVD	RSVD	RSVD	TS4 Mode	TS3 Mode	TS2 Mode	TS1 Mode	TSInt Mode

RSVD (Bits 7–5): Reserved. Do not use.

TS4 Mode (Bit 4): Cell temperature or FET temperature
- 1 = FET temperature
- 0 = Cell temperature (default)

TS3 Mode (Bit 3): Cell temperature or FET temperature
- 1 = FET temperature
- 0 = Cell temperature (default)

TS2 Mode (Bit 2): Cell temperature or FET temperature
- 1 = FET temperature (default)
- 0 = Cell temperature

TS1 Mode (Bit 1): Cell temperature or FET temperature
- 1 = FET temperature
- 0 = Cell temperature (default)

TSInt Mode (Bit 0): Cell temperature or FET temperature
- 1 = FET temperature
- 0 = Cell temperature (default)

16.2.1.20 DA Configuration

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Configuration	DA Configuration	H1	0x00	0xFF	0x12	Hex

15	14	13	12	11	10	9	8
CTEMP1	CTEMP0	RSVD	RSVD	RSVD	RSVD	RSVD	EMSHUT_ PEXIT_DIS

7	6	5	4	3	2	1	0
FTEMP	DISCONN_EN	EMSHUT_EN	SLEEP	IN_SYSTEM _SLEEP	NR	CC1	CC0

CTEMP (Bits 15–14): Defines which temperature sensor's output is displayed by the SBS *Temperature()* command
- 1, 1 = Not used
- 1, 0 = Minimum temperature
- 0, 1 = Average temperature
- 0, 0 = Maximum temperature

RSVD (Bits 13–9): Reserved. Do not use.

EMSHUT_PEXIT_DIS (BIT 8): Disables the SHUTDN pin exit option of the Emergency FET Shutdown feature (when a high-to-low transition on the SHUTDN pin is detected).

1 = Prevents usage of SHUTDN pin as exit option
0 = Allows usage of SHUTDN pin as an exit option (default)

FTEMP (Bit 7): FET temperature protection source

1 = Average
0 = MAX (default)

DISCONN_EN (Bit 6): System Disconnect

1 = Enabled
0 = Disabled

EMSHUT_EN (Bit 5): Emergency FET Shutdown Enable

1 = Enables
0 = Disables

SLEEP (Bit 4): SLEEP mode

1 = Enables SLEEP mode (default)
0 = Disables SLEEP mode

IN_SYSTEM_SLEEP (Bit 3): In-system SLEEP mode

1 = Enables
0 = Disables (default)

NR (Bit 2): Use $\overline{\text{PRES}}$ in system detection

1 = NON-REMOVABLE mode
0 = Use $\overline{\text{PRES}}$, REMOVABLE mode (default)

CC1, CC0 (Bit 1,0): Cell Count

1,1 = 4 cells
1,0 = 3 cells (default)
0,1 = 2 cells
0,0 = 1 cell

16.2.1.21 Balancing Configuration

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Configuration	Balancing Configuration	H1	0x00	0xFF	0x01	Hex

7	6	5	4	3	2	1	0
RSVD	RSVD	CBS	CB_RLX_DOD 0EW	CB_CHG_DOD 0EW	CBR	CBM	CB

RSVD (Bits 7–6): Reserved. Do not use.

CBS (Bit 5): Cell balancing in sleep

1 = Enables CBS
0 = Disables CBS

CB_RLX_DOD0EW (Bit 4):

1 = Use Error Weighted DOD0 for cell balancing time updates when in RELAX mode
0 = Use DOD0 for cell balancing time updates when in RELAX mode

CB_CHG_DOD0EW (Bit 3):

1 = Use Error Weighted DOD0 for cell balancing time updates when in CHARGE mode
0 = Use DOD0 for cell balancing time updates when in CHARGE mode

CBR (Bit 2): Cell balancing at rest
1 = Enables cell balancing at rest
0 = Disables cell balancing at rest (default)

CBM (Bit 1): Internal versus external cell balancing
1 = Enables external cell balancing
0 = Enables internal cell balancing (default)

CB (Bit 0): Cell balancing
1 = Cell balancing enabled (default)
0 = Cell balancing disabled

16.2.1.22 Elevated Degrade Configuration

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Configuration	Elevated Degrade Configuration	H1	0x00	0xFF	0x15	Hex

7	6	5	4	3	2	1	0
RSVD	RSVD	RSVD	ERETM_MAX_T	ERETM_MODE	ERETM_TIME	ERM_MODE	ERM_TIME

RSVD (Bits 7–5): Reserved. Do not use.

ERETM_MAX_T (Bit 4):
1 = Enables ***ERETM Temperature Max Threshold*** for immediate *[ERETM]* mode
0 = Disables ***ERETM Temperature Max Threshold*** for immediate *[ERETM]* mode

ERETM_MODE (Bit 3):
1 = Uses voltage thresholds for ERETM
0 = Uses RSOC thresholds for ERETM

ERETM_TIME (Bit 2):
1 = Enables ERETM
0 = Disables ERETM

ERM_MODE (Bit 1):
1 = Uses voltage thresholds for ERM
0 = Uses RSOC thresholds for ERM

ERM_TIME (Bit 0):
1 = Enables ERM
0 = Disables ERM

16.2.1.23 Lifetimes Configuration

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Configuration	Lifetimes Configuration	H2	0x0000	0xFFFF	0x0000	Hex

15	14	13	12	11	10	9	8
RSVD	RSVD	RSVD	RSVD	RSVD	RSVD	RSVD	RSVD

7	6	5	4	3	2	1	0
RSVD	RSVD	RSVD	RSVD	RSVD	RSVD	RSVD	SEALED_RESET

RSVD (Bits 15–1): Reserved. Do not use.

SEALED_RESET (Bit 0): Enables reset of ***Lifetime Data***

1 = Enabled

0 = Disabled

16.2.2 Fuse

16.2.2.1 Permanent Fail Fuse A

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Fuse	Permanent Fail Fuse A	H1	0x00	0xFF	0x00	—

7	6	5	4	3	2	1	0
QIM	SOTF	RSVD	SOT	SOCD	SOCC	SOV	SUV

Fuse blow action for *PFStatus()* bits:

QIM (Bit 7): QMax Imbalance

1 = Enabled

0 = Disabled (default)

SOTF (Bit 6): Safety Overtemperature FET

1 = Enabled

0 = Disabled (default)

RSVD (Bit 5): Reserved. Do not use.

SOT (Bit 4): Safety Overtemperature

1 = Enabled

0 = Disabled (default)

SOCD (Bit 3): Safety Overcurrent in Discharge

1 = Enabled

0 = Disabled (default)

SOCC (Bit 2): Safety Overcurrent in Charge

1 = Enabled

0 = Disabled (default)

SOV (Bit 1): Safety Cell Overvoltage

1 = Enabled

0 = Disabled (default)

SUV (Bit 0): Safety Cell Undervoltage

1 = Enabled

0 = Disabled (default)

16.2.2.2 Permanent Fail Fuse B

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Fuse	Permanent Fail Fuse B	H1	0x00	0xFF	0x00	Hex

7	6	5	4	3	2	1	0
RSVD	RSVD	RSVD	VIMA	VIMR	CD	IMP	CB

Fuse blow action for *PFStatus()* bits:

RSVD (Bits 7–5): Reserved. Do not use.

VIMA (Bit 4): Voltage Imbalance Active

1 = Enabled

0 = Disabled (default)

VIMR (Bit 3): Voltage Imbalance At Rest

1 = Enabled

0 = Disabled (default)

CD (Bit 2): Capacity Degradation

1 = Enabled

0 = Disabled (default)

IMP (Bit 1): Cell impedance

1 = Enabled

0 = Disabled (default)

CB (Bit 0): Cell balancing

1 = Enabled

0 = Disabled (default)

16.2.2.3 Permanent Fail Fuse C

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Fuse	Permanent Fail Fuse C	H1	0x00	0xFF	0x00	Hex

7	6	5	4	3	2	1	0
PTC	2LVL	AFEC	AFER	FUSE	RSVD	DFETF	CFETF

Fuse blow action for *PFStatus()* bits:

PTC (Bit 7): Permanent Fail Flag Display

1 = Enables ***PFStatus[PTC]*** = 1 when PTC fault is triggered. Function should be enabled/disabled by the PTCEN pin connection.

0 = Disables ***PFStatus[PTC]*** = 1 when PTC fault is triggered. Function should be enabled/disabled by the PTCEN pin connection.

2LVL (Bit 6): Input indicating a fuse trigger by an external 2nd-level protection

1 = Enabled

0 = Disabled (default)

AFEC (Bit 5): AFE Communication

1 = Enabled

0 = Disabled (default)

AFER (Bit 4): AFE Register

1 = Enabled

0 = Disabled (default)

FUSE (Bit 3): Fuse input to indicate a chemical fuse failure

1 = Enabled

0 = Disabled (default)

RSVD (Bit 2): Reserved. Do not use.

DFETF (Bit 1): Discharge FET

1 = Enabled

0 = Disabled (default)

CFETF (Bit 0): Charge FET

1 = Enabled

0 = Disabled (default)

16.2.2.4 Permanent Fail Fuse D

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Fuse	Permanent Fail Fuse D	H1	0x00	0xFF	0x00	Hex

7	6	5	4	3	2	1	0
TS4	TS3	TS2	TS1	RSVD	DFW	FORCE	IFC

Fuse blow action for *PFStatus()* bits:

TS4 (Bit 7)

1 = Enabled

0 = Disabled (default)

TS3 (Bit 6)

1 = Enabled

0 = Disabled (default)

TS2 (Bit 5)

1 = Enabled

0 = Disabled (default)

TS1 (Bit 4)

1 = Enabled

0 = Disabled (default)

RSVD (Bit 3): Reserved. Do not use.

DFW (Bit 2): DF wearout

1 = Enabled

0 = Disabled (default)

FORCE (Bit 1): Manual PF

1 = Enabled

0 = Disabled (default)

IFC (Bit 0)

1 = Enabled
0 = Disabled (default)

16.2.2.5 Min Blow Fuse Voltage

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Fuse	Min Blow Fuse Voltage	I2	0	65535	3500	mV

Description: Minimum voltage required to attempt fuse blow, pack based, FET failures bypass this requirement to blow the fuse.

16.2.2.6 Fuse Blow Timeout

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Fuse	Fuse Blow Timeout	U1	0	255	30	s

Description: Time to keep the fuse blow voltage high

16.2.2.7 GPIO Timeout

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Fuse	GPIO Timeout	U2	0	65535	30	s

Description: Time to keep the GPIO control during permanent failure asserted. Set to 0 to disable timeout.

16.2.3 BTP

16.2.3.1 Init Discharge Set

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	BTP	Init Discharge Set	I2	0	32767	150	mAh

Description: Initial value for *BTPDischargeSet()*

16.2.3.2 Init Charge Set

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	BTP	Init Charge Set	I2	0	32767	175	mAh

Description: Initial value for *BTPChargeSet()*

16.2.4 Protection

16.2.4.1 Protection Configuration

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Protection	Protection Configuration	H1	0x00	0x03	0x00	Hex

7	6	5	4	3	2	1	0
RSVD	RSVD	RSVD	RSVD	RSVD	CUDEP_REQ_CHG	CUV_RECOV_CHG	SUV_MODE

RSVD (Bits 7–3): Reserved. Do not use.

CUDEP_REQ_CHG (Bit 2): Request *ChargingVoltage()* and *ChargingCurrent()* during the copper deposition check while the FETs are off when ***[SUV_MODE]*** is enabled to prevent the charger from turning off before the check is complete.

1 = Enabled (default)

0 = Disabled (default)

CUV_RECOV_CHG (Bit 1): Require charge to recover *SafetyStatus()[CUV]*

1 = Enabled

0 = Disabled (default)

SUV_MODE (Bit 0): Copper deposition check for *PFStatus()[CUV]*

1 = Enabled

0 = Disabled (default)

16.2.4.2 Enabled Protections A

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Protection	Enabled Protections A	H1	0x00	0xFF	0xFF	Hex

7	6	5	4	3	2	1	0
AOLDL	RSVD_ONE	OCD2	OCD1	OCC2	OCC1	COV	CUV

AOLDL (Bit 7): Overload in Discharge latch

1 = Enabled (default)

0 = Disabled

RSVD_ONE (Bit 6): Reserved and programmed to 1. Do not use.

OCD2 (Bit 5): Overcurrent in Discharge 2nd Tier

1 = Enabled (default)

0 = Disabled

OCD1 (Bit 4): Overcurrent in Discharge 1st Tier

1 = Enabled (default)

0 = Disabled

OCC2 (Bit 3): Overcurrent in Charge 2nd Tier

1 = Enabled (default)

0 = Disabled

OCC1 (Bit 2): Overcurrent in Charge 1st Tier

1 = Enabled (default)

0 = Disabled

COV (Bit 1): Cell Overvoltage

1 = Enabled (default)

0 = Disabled

CUV (Bit 0): Cell Undervoltage

1 = Enabled (default)
0 = Disabled

16.2.4.3 Enabled Protections B

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Protection	Enabled Protections B	H1	0x00	0xFF	0xFF	Hex

7	6	5	4	3	2	1	0
RSVD	CUVC	OTD	OTC	ASCDL	RSVD_ONE	ASCCL	ASCC

RSVD (Bit 7): Reserved. Do not use.

CUVC (Bit 6): I*R compensated CUV

1 = Enabled (default)
0 = Disabled

OTD (Bit 5): Overtemperature in discharge

1 = Enabled (default)
0 = Disabled

OTC (Bit 4): Overtemperature in charge

1 = Enabled (default)
0 = Disabled

ASCDL (Bit 3): Short circuit in discharge latch

1 = Enabled (default)
0 = Disabled

RSVD_ONE (Bit 2): Reserved and programmed to 1. Do not use.

ASCCL (Bit 1): Short circuit in charge latch

1 = Enabled (default)
0 = Disabled

ASCC (Bit 0): Short circuit in charge

1 = Enabled (default)
0 = Disables the *SafetyAlert()* and *SafetyStatus()* flag only and does NOT disable the FET actions.

16.2.4.4 Enabled Protections C

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Protection	Enabled Protections C	H1	0x00	0xFF	0xFF	Hex

7	6	5	4	3	2	1	0
CHGC	OC	RSVD	CTO	RSVD	PTO	HWDF	OTF

CHGC (Bit 7): *ChargingCurrent()* higher than requested

1 = Enabled (default)

0 = Disabled

OC (Bit 6): Overcharge

1 = Enabled (default)

0 = Disabled

RSVD (Bit 5): Reserved. Do not use.

CTO (Bit 4): Charging timeout

1 = Enabled (default)

0 = Disabled

RSVD (Bit 3): Reserved. Do not use.

PTO (Bit 2): Precharging timeout

1 = Enabled (default)

0 = Disabled

HWDF (Bit 1): SBS Host watchdog timeout

1 = Enabled (default)

0 = Disabled

OTF (Bit 0): FET overtemperature

1 = Enabled (default)

0 = Disabled

16.2.4.5 Enabled Protections D

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Protection	Enabled Protections D	H1	0x00	0xFF	0xFF	Hex

7	6	5	4	3	2	1	0
RSVD	RSVD	OCDL	COVL	UTD	UTC	PCHGC	CHGV

RSVD (Bits 7–6): Reserved. Do not use.

OCDL (Bit 5): Overcurrent in Discharge related PF

1 = Enabled (default)

0 = Disabled

COVL (Bit 4): Cell Overvoltage Latch related PF

1 = Enabled (default)

0 = Disabled

UTD (Bit 3): Undertemperature While Not Charging

1 = Enabled (default)

0 = Disabled

UTC (Bit 2): Undertemperature While Charging

1 = Enabled (default)

0 = Disabled

PCHGC (Bit 1): *ChargingCurrent()* higher than requested in precharge

1 = Enabled (default)

0 = Disabled

CHGV (Bit 0): *ChargingVoltage()* higher than requested

1 = Enabled (default)

0 = Disabled

16.2.5 Permanent Failure

16.2.5.1 Enabled PF A

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Permanent Failure	Enabled PF A	H1	0x00	0xFF	0x00	Hex

7	6	5	4	3	2	1	0
QIM	SOTF	COVL	SOT	SOCD	SOCC	SOV	SUV

QIM (Bit 7): QMax Imbalance

1 = Enabled

0 = Disabled (default)

OTF (Bit 6): Overtemperature FET

1 = Enabled

0 = Disabled (default)

COVL (Bit 5): Cell Overvoltage Latch

1 = Enabled

0 = Disabled (default)

SOT (Bit 4): Safety Overtemperature

1 = Enabled

0 = Disabled (default)

SOCD (Bit 3): Safety Overcurrent in Discharge

1 = Enabled

0 = Disabled (default)

SOCC (Bit 2): Safety Overcurrent in Charge

1 = Enabled

0 = Disabled (default)

SOV (Bit 1): Safety Cell Overvoltage

1 = Enabled

0 = Disabled (default)

SUV (Bit 0): Safety Cell Undervoltage

1 = Enabled

0 = Disabled (default)

16.2.5.2 Enabled PF B

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Permanent Failure	Enabled PF B	H1	0x00	0xFF	0x00	Hex

7	6	5	4	3	2	1	0
ASCDL	ASCCL	AOLDL	VIMA	VIMR	CD	IMP	CB

ASCDL (Bit 7): Short Circuit in Discharge—PF Enable

1 = Enabled
0 = Disabled (default)

ASCCL (Bit 6): Short Circuit in Charge—PF Enable

1 = Enabled
0 = Disabled (default)

AOLDL (Bit 5): Overload in Discharge—PF Enable

1 = Enabled
0 = Disabled (default)

VIMA (Bit 4): Voltage Imbalance Active

1 = Enabled
0 = Disabled (default)

VIMR (Bit 3): Voltage Imbalance At Rest

1 = Enabled
0 = Disabled (default)

CD (Bit 2): Capacity Degradation

1 = Enabled
0 = Disabled (default)

IMP (Bit 1): Cell impedance

1 = Enabled
0 = Disabled (default)

CB (Bit 0): Cell balancing

1 = Enabled
0 = Disabled (default)

16.2.5.3 Enabled PF C

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Permanent Failure	Enabled PF C	H1	0x00	0xFF	0x00	Hex

7	6	5	4	3	2	1	0
PTC	2LVL	AFEC	AFER	FUSE	OCDL	DFETF	CFETF

PTC (Bit 7): Permanent Fail Flag Display

1 = Enables ***PFStatus[PTC]*** = 1 when PTC fault is triggered. Function should be enabled/disabled by the PTCEN pin connection.

0 = Disables the ***PFStatus[PTC]*** = 1 when PTC fault is triggered. Function should be enabled/disabled by the PTCEN pin connection.

2LVL (Bit 6): FUSE input indicating a fuse trigger by an external 2nd-level protection

1 = Enabled

0 = Disabled (default)

AFEC (Bit 5): AFE Communication

1 = Enabled

0 = Disabled (default)

AFER (Bit 4): AFE Register

1 = Enabled

0 = n/a (default)

FUSE (Bit 3): Fuse

1 = Enabled

0 = Disabled (default)

OCDL (Bit 2): Overcurrent in Discharge—PF Enable

1 = Enabled

0 = Disabled (default)

DFETF (Bit 1): Discharge FET

1 = Enabled

0 = Disabled (default)

CFETF (Bit 0): Charge FET

1 = Enabled

0 = Disabled (default)

16.2.5.4 Enabled PF D

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Permanent Failure	Enabled PF D	H1	0x00	0xFF	0x00	Hex

7	6	5	4	3	2	1	0
TS4	TS3	TS2	TS1	RSVD	RSVD	FORCE	RSVD

TS4 (Bit 7)

1 = Enabled (default)

0 = Disabled

TS3 (Bit 6)

1 = Enabled (default)

0 = Disabled

TS2 (Bit 5)

1 = Enabled (default)

0 = Disabled

TS1 (Bit 4)

1 = Enabled (default)

0 = Disabled

RSVD (Bits 3–2): Reserved. Do not use.

FORCE (Bit 1): Manual PF. See *Manual Permanent Failure* for more information.

1 = Enabled (default)

0 = Disabled

RSVD (Bit 0): Reserved. Do not use.

16.2.6 AFE

16.2.6.1 AFE Protection Control

Class	Subclass	Name	Type	Min	Max	Default	Unit
Configuration	AFE	AFE Protection Control	H1	0x00	0xFF	0x70	Hex

7	6	5	4	3	2	1	0
RSTRIM	RSTRIM	RSTRIM	RSTRIM	RSVD	RSVD	SCDDx2	RSNS

RSTRIM (Bits 7–4): *Unsupport* function. Should leave the default setting 0x7. Changing this setting may cause an error to the AFE current protection accuracy.

RSVD (Bits 3–2): Reserved. Do not use.

SCDDx2 (Bit 1): Double SCD Delay Times

1 = 2 × SCD delay times

0 = Normal SCD delay times (default)

RSNS (Bit 0): AOLD, ASCC, ASCD1, ASCD2 Thresholds

1 = Normal AFE Protection Thresholds

0 = 0.5 × AFE Protection Thresholds (default)

16.2.7 ZVCHG Exit Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Configuration	AFE	ZVCHG Exit Threshold	I2	0	80000	2200	mV

Description: *Voltage()* threshold where the gauge will exit ZVCHG mode when CFET is used for precharging.

16.3 Accumulated Charge Measurement

16.3.1 Accum Discharge Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Accumulated Charge	Discharge Threshold	I2	–32767	0	-1000	mAh

16.3.2 Accum Charge Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Accumulated Charge	Charge Threshold	I2	0	32767	1000	mAh

16.4 Manufacturing

16.4.1 Manufacturing Status Init

Class	Subclass	Name	Type	Min	Max	Default	Unit
Settings	Manufacturing	Manufacturing Status Init	H2	0x0000	0xFFFF	0x0000	Hex

15	14	13	12	11	10	9	8
RSVD	RSVD	RSVD	RSVD	ACCHG_EN	ACDSG_EN	LED_EN	FUSE_EN

7	6	5	4	3	2	1	0
BBR_EN	PF_EN	LF_EN	FET_EN	GAUGE_EN	RSVD	RSVD	RSVD

RSVD (Bits 15–12): Reserved. Do not use.

ACCCG_EN (Bit 11): Accumulated Charge Measurement in CHARGE direction
- 1 = Enabled
- 0 = Disabled

ACDSG_EN (Bit 10): Accumulated Charge Measurement in DISCHARGE direction
- 1 = Enabled
- 0 = Disabled

LED_EN (Bit 9): LED Display
- 1 = Enabled
- 0 = Disabled

FUSE_EN (Bit 8): FUSE action
- 1 = Enabled
- 0 = Disabled (default)

BBR_EN (Bit 7): Black Box Recorder
- 1 = Enabled
- 0 = Disabled (default)

PF_EN (Bit 6): Permanent Fail
- 1 = Enabled
- 0 = Disabled (default)

LF_EN (Bit 5): ***Lifetime Data Collection***
- 1 = Enabled
- 0 = Disabled

FET_EN (Bit 4): FET action
- 1 = Enabled
- 0 = Disabled (default)

GAUGE_EN (Bit 3): Gauging
- 1 = Enabled

0 = Disabled (default)

RSVD (Bits 2–0): Reserved. Do not use.

16.5 Advanced Charging Algorithm

16.5.1 Temperature Ranges

16.5.1.1 T1 Temp

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Temperature Ranges	T1 Temp	I1	–128	127	0	°C

Description: T1 low temperature range lower limit

16.5.1.2 T2 Temp

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Temperature Ranges	T2 Temp	I1	–128	127	12	°C

Description: T2 low temperature range to standard temperature range

16.5.1.3 T5 Temp

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Temperature Ranges	T5 Temp	I1	–128	127	20	°C

Description: T5 recommended temperature range lower limit

16.5.1.4 T6 Temp

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Temperature Ranges	T6 Temp	I1	–128	127	25	°C

Description: T6 recommended temperature range upper limit

16.5.1.5 T3 Temp

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Temperature Ranges	T3 Temp	I1	–128	127	30	°C

Description: T3 standard temperature range to high temperature range

16.5.1.6 T4 Temp

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Temperature Ranges	T4 Temp	I1	–128	127	55	°C

Description: T4 high temperature range upper limit

16.5.1.7 Hysteresis

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Temperature Ranges	Hysteresis Temp	I1	–128	127	1	°C

Description: This is the temperature hysteresis applied when temperature is decreasing.

16.5.2 Low Temp Charging

16.5.2.1 Voltage

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Low Temp Charging	Voltage	I2	0	32767	4000	mV

Description: Sets the *ChargingVoltage()* for the low temperature range

16.5.2.2 Current Low

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Low Temp Charging	Current Low	I2	0	32767	132	mA

Description: Sets the *ChargingCurrent()* for the low temperature range, low voltage range

16.5.2.3 Current Med

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Low Temp Charging	Current Med	I2	0	32767	352	mA

Description: Sets the *ChargingCurrent()* for the low temperature range, medium voltage range

16.5.2.4 Current High

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Low Temp Charging	Current High	I2	0	32767	264	mA

Description: Sets the *ChargingCurrent()* for the low temperature range, high voltage range

16.5.3 Standard Temp Low Charging

16.5.3.1 Voltage

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Standard Temp Low Charging	Voltage	I2	0	32767	4200	mV

Description: Sets the *ChargingVoltage()* for the standard temperature range

16.5.3.2 Current Low

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Standard Temp Low Charging	Current Low	I2	0	32767	1980	mA

Description: Sets the *ChargingCurrent()* for the standard temperature range, low voltage range

16.5.3.3 Current Med

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Standard Temp Low Charging	Current Med	I2	0	32767	4004	mA

Description: Sets the *ChargingCurrent()* for the standard temperature range, medium voltage range

16.5.3.4 Current High

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Standard Temp Low Charging	Current High	I2	0	32767	2992	mA

Description: Sets the *ChargingCurrent(* for the standard temperature range, high voltage range

16.5.4 Standard Temp High Charging

16.5.4.1 Voltage

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Standard Temp High Charging	Voltage	I2	0	32767	4200	mV

Description: Sets the *ChargingVoltage()* for the standard temperature range

16.5.4.2 Current Low

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Standard Temp High Charging	Current Low	I2	0	32767	1980	mA

Description: Sets the *ChargingCurrent()* for the standard temperature range, low voltage range

16.5.4.3 Current Med

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Standard Temp High Charging	Current Med	I2	0	32767	4004	mA

Description: Sets the *ChargingCurrent()* for the standard temperature range, medium voltage range

16.5.4.4 Current High

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Standard Temp High Charging	Current High	I2	0	32767	2992	mA

Description: Sets the *ChargingCurrent(* for the standard temperature range, high voltage range

16.5.5 High Temp Charging

16.5.5.1 Voltage

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	High Temp Charging	Voltage	I2	0	32767	4000	mV

Description: Sets the *ChargingVoltage()* for the high temperature range

16.5.5.2 Current Low

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	High Temp Charging	Current Low	I2	0	32767	1012	mA

Description: Sets the *ChargingCurrent()* for the high temperature range, low voltage range

16.5.5.3 Current Med

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	High Temp Charging	Current Med	I2	0	32767	1980	mA

Description: Sets the *ChargingCurrent()* for the high temperature range, medium voltage range

16.5.5.4 Current High

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	High Temp Charging	Current High	I2	0	32767	1496	mA

Description: Sets the *ChargingCurrent()* for the high temperature range, high voltage range

16.5.6 Rec Temp Charging

16.5.6.1 Voltage

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Rec Temp Charging	Voltage	I2	0	32767	4100	mV

Description: Sets the *ChargingVoltage()* for the recommended temperature range

16.5.6.2 Current Low

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Rec Temp Charging	Current Low	I2	0	32767	2508	mA

Description: Sets the *ChargingCurrent()* for the recommended temperature range, low voltage range

16.5.6.3 Current Med

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Rec Temp Charging	Current Med	I2	0	32767	4488	mA

Description: Sets the *ChargingCurrent()* for the recommended temperature range, medium voltage range

16.5.6.4 Current High

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Rec Temp Charging	Current High	I2	0	32767	3520	mA

Description: Sets the *ChargingCurrent()* for the recommended temperature range, high voltage range

16.5.7 PreCharging

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	PCHG	Current	I2	0	32767	88	mA

Description: Precharge *ChargingCurrent()*

16.5.8 Maintenance Charging

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	MCHG	Current	I2	0	32767	44	mA

Description: Maintenance *ChargingCurrent()*

16.5.9 Voltage Range

16.5.9.1 Precharge Start Voltage

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Voltage Range	Precharge Start Voltage	I2	0	32767	2500	mV

Description: Min cell voltage to enter PRECHARGE mode

16.5.9.2 Charging Voltage Low

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Voltage Range	Charging Voltage Low	I2	0	32767	2900	mV

Description: Precharge Voltage range to ***Charging Voltage Low*** range

16.5.9.3 Charging Voltage Med

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Voltage Range	Charging Voltage Med	I2	0	32767	3600	mV

Description: ***Charging Voltage Low*** range to ***Charging Voltage Med*** range

16.5.9.4 Charging Voltage High

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Voltage Range	Charging Voltage High	I2	0	32767	4000	mV

Description: ***Charging Voltage Med*** to ***Charging Voltage High*** range

16.5.9.5 Charging Voltage Hysteresis

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Voltage Range	Charging Voltage Hysteresis	U1	0	255	0	mV

Description: ***Charging Voltage Hysteresis*** applied when voltage is decreasing.

16.5.10 Termination Config

16.5.10.1 Charge Term Taper Current

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Termination Config	Charge Term Taper Current	I2	0	32767	250	mA

Description: Valid charge termination taper current qualifier threshold

16.5.10.2 Charge Term Voltage

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Termination Config	Charge Term Voltage	I2	0	32767	75	mV

Description: Valid charge termination delta voltage qualifier, max cell-based

16.5.11 Charging Rate of Change

16.5.11.1 Current Rate

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Charging Rate of Change	Current Rate	U1	1	255	1	steps/s

Description: Number of steps to add between any two *ChargingCurrent()* settings

16.5.11.2 Voltage Rate

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Charging Rate of Change	Voltage Rate	U1	1	255	1	steps/s

Description: Number of steps to add between any two *ChargingVoltage()* settings

16.5.12 Charge Loss Compensation

16.5.12.1 CCC Current Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Charge Loss Compensation	CCC Current Threshold	I2	0	32767	3520	mA

Description: CONSTANT CURRENT CHARGE mode *ChargingCurrent()* threshold to activate Charge Loss Compensation

16.5.12.2 CCC Voltage Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Charge Loss Compensation	CCC Voltage Threshold	I2	0	32767	4200	mV

Description: CONSTANT CURRENT CHARGE mode max *ChargingVoltage()* increase limit

16.5.13 Cell Balancing Config

16.5.13.1 Balance Time per mAh Cell 1

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Cell Balancing Config	Balance Time per mAh Cell 1	U2	0	65535	367	s/mAh

Description: Required balance time per mAh for Cell 1. For information on how to calculate balancing time, see Section 7.1.

16.5.13.2 Balance Time per mAh Cell 2–4

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Cell Balancing Config	Balance Time per mAh Cell 2–4	U2	0	65535	514	s/mAh

Description: Required balance time per mAh for Cells 2 to 4. For information on how to calculate balancing time, see Section 7.1.

16.5.13.3 Min Start Balance Delta

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Cell Balancing Config	Min Start Balance Delta	U1	0	255	3	mV

Description: Minimum cell voltage delta to start cell balancing during ***Relax Balance Interval*** checks. This condition is checked in RELAX mode and so it only applies if cell balancing at rest is enabled.

16.5.13.4 Start Rsoc for Bal in Sleep

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charge Algorithm	Cell Balancing Config	Start Rsoc for Bal in Sleep	U1	0	100	95	%

Description: This sets the RSOC threshold below which cell balancing in sleep (if enabled) will be permitted to start. This works in conjunction with the ***Start time for Bal in Sleep*** requirement.

16.5.13.5 End Rsoc for Bal in Sleep

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charge Algorithm	Cell Balancing Config	End Rsoc for Bal in Sleep	U1	0	100	60	%

Description: This sets the RSOC threshold below which cell balancing in sleep (if enabled) if active will be terminated.

16.5.13.6 Start Time for Bal in Sleep

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charge Algorithm	Cell Balancing Config	Start Time for Bal in Sleep	U2	0	65520	100	h

Description: This sets the minimum time threshold the gauge must be in sleep to allow below cell balancing in sleep (if enabled) to start. This works in conjunction with the ***Start Rsoc for Bal in Sleep*** requirement.

16.5.13.7 Relax Balance Interval

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Cell Balancing Config	Relax Balance Interval	U4	0	4294967295	18000	s

Description: Interval during RELAX mode to check for cell imbalance. This parameter applies to cell balancing at rest only.

16.5.13.8 Min RSOC for Balancing

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Cell Balancing Config	Min RSOC for Balancing	U1	0	100	80	%

Description: Minimum *RelativeStateOfCharge()* threshold for cell balancing. This condition is checked during relaxation and so it only applies if cell balancing at rest is enabled.

16.5.14 Degrade Mode 1

16.5.14.1 Cycle Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Degrade Mode 1	Cycle Threshold	U2	0	65535	50	—

Description: This sets the cycle count related threshold at/above which the first Level (Mode 1) CV and CC degradations can begin if *[CYCLE_DEGRADE]* is set.

16.5.14.2 SOH Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Degrade Mode 1	SOH Threshold	U1	0	100	95	%

Description: This sets the SOH-related threshold at/above which the first Level (Mode 1) CV and CC degradations can begin if *[SOH_DEGRADE]* is set.

16.5.14.3 Runtime Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Degrade Mode 1	Runtime Threshold	U2	0	65535	8760	hrs

Description: This sets the runtime-related threshold at/above which the first level (Mode 1) CV and CC degradations can begin if *[RUNTIME_DEGRADE]* is set.

16.5.14.4 Voltage Degradation

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Degrade Mode 1	Voltage Degradation	I2	0	32767	40	mV

Description: This sets the amount of voltage degradation from the charging voltage that will occur at the Mode 1 level if this feature is enabled.

16.5.14.5 Current Degradation

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Degrade Mode 1	Current Degradation	I2	0	100	10	%

Description: This sets the percentage of current degradation from the charging current that will occur at the Mode 1 level if this feature is enabled.

16.5.15 Degrade Mode 2

16.5.15.1 Cycle Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Degrade Mode 2	Cycle Threshold	U2	0	65535	150	—

Description: This sets the cycle count related threshold at/above which the first level (Mode 2) CV and CC degradations can begin if CYCLE_DEGRADE is set.

16.5.15.2 SOH Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Degrade Mode 2	SOH Threshold	U1	0	100	80	%

Description: This sets the SOH related threshold at/above which the first level (Mode 2) CV and CC degradations can begin if SOH_DEGRADE is set.

16.5.15.3 Runtime Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Degrade Mode 2	Runtime Threshold	U2	0	65535	17520	hrs

Description: This sets the runtime-related threshold at/above which the first level (Mode 2) CV and CC degradations can begin if RUNTIME_DEGRADE is set.

16.5.15.4 Voltage Degradation

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Degrade Mode 2	Voltage Degradation	I2	0	32767	10	mV

Description: This sets the amount of voltage degradation from the charging voltage that will occur at the Mode 2 level if this feature is enabled.

16.5.15.5 Current Degradation

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Degrade Mode 2	Current Degradation	I2	0	100	20	%

Description: This sets the percentage of current degradation from the charging current that will occur at the Mode 2 level if this feature is enabled.

16.5.16 Degrade Mode 3

16.5.16.1 Cycle Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Degrade Mode 3	Cycle Threshold	U2	0	65535	350	—

Description: This sets the cycle count related threshold at/above which the first Level (Mode 3) CV and CC degradations can begin if CYCLE_DEGRADE is set.

16.5.16.2 SOH Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Degrade Mode 3	SOH Threshold	U1	0	100	60	%

Description: This sets the SOH related threshold at/above which the first Level (Mode 3) CV and CC degradations can begin if SOH_DEGRADE is set.

16.5.16.3 Runtime Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Degrade Mode 3	Runtime Threshold	U2	0	65535	26280	hrs

Description: This sets the runtime-related threshold at/above which the first Level (Mode 3) CV and CC degradations can begin if RUNTIME_DEGRADE is set.

16.5.16.4 Voltage Degradation

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Degrade Mode 3	Voltage Degradation	I2	0	32767	70	mV

Description: This sets the amount of voltage degradation from the charging voltage that will occur at the Mode 3 level if this feature is enabled.

16.5.16.5 Current Degradation

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Degrade Mode 3	Current Degradation	I2	0	100	40	%

Description: This sets the percentage of current degradation from the charging current that will occur at the Mode 3 level if this feature is enabled.

16.5.16.6 Cycle Count Start Runtime

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Degrade Mode	Cycle Count Start Runtime	U1	0	255	1	-

Description: This sets the cycle count threshold above which runtime begins to accumulate for runtime degradation.

16.5.16.7 Runtime Degrade

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charging Algorithm	Degrade Mode	Runtime Degrade	U2	0	65535	0	hrs

Description: This is the accumulated runtime for runtime degradation.

16.5.17 IR Correction

16.5.17.1 Averaging Interval

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charge Algorithm	IR Correction	Averaging Interval	U1	1	255	12	s

Description: To prevent overcharging by the IR compensation scheme (in case the ***System Resistance*** is set too high) the IT algorithm runs an averaging calculation to reduce the charging voltage if needed. This averaging calculation is averaged over the averaging interval defined in this register.

16.5.18 CS Degrade

16.5.18.1 Temperature Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charge Algorithm	CS Degrade	Temperature Threshold	I2	0	32767	3232	0.1 K

Description: This sets the temperature threshold that the cell temperature is compared to in the cell swelling control feature.

16.5.18.2 Voltage Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charge Algorithm	CS Degrade	Voltage Threshold	I2	0	32767	4200	mV

Description: This sets the voltage threshold that the max cell voltage is compared to in the cell swelling control feature.

16.5.18.3 Time Interval

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charge Algorithm	CS Degrade	Time Interval	U2	0	14400	300	s

Description: This sets the time period that the cell swelling control feature compares with how long the max cell voltage and cell temperature have been above their thresholds. After which the charging voltage is stepped down.

16.5.18.4 Delta Voltage

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charge Algorithm	CS Degrade	Delta Voltage	I2	0	32767	25	mV

Description: This sets the voltage level that the charging voltage will be stepped down as part of the swelling control feature.

16.5.18.5 Min CV

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charge Algorithm	CS Degrade	Min CV	I2	0	32767	3000	mV

Description: This sets the lowest level that the charging voltage will be allowed to step down to as part of the swelling control feature.

16.5.19 Elevated Degrade

16.5.19.1 ERM Reset RSoC Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charge Algorithm	Elevated Degrade	ERM Reset RSoC Threshold	U1	0	100	85	%

Description: This sets the RSOC value by which ***Elevated Degrade*** will reset when ***[ERM_MODE]*** is cleared.

16.5.19.2 ERM Reset Voltage Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charge Algorithm	Elevated Degrade	ERM Reset Voltage Threshold	I2	0	32767	3700	mV

Description: This sets the RSOC value by which ***Elevated Degrade*** will reset when ***[ERM_MODE]*** is set.

16.5.19.3 ERM RSoC Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charge Algorithm	Elevated Degrade	ERM RSoC Threshold	U1	0	100	90	%

Description: This sets the RSOC threshold above which ***Accumulated ERM Time*** will count when ***[ERM_MODE]*** is cleared.

16.5.19.4 ERM Voltage Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charge Algorithm	Elevated Degrade	ERM Voltage Threshold	I2	0	32767	4000	mV

Description: This sets the voltage threshold above which ***Accumulated ERM Time*** will count when ***[ERM_MODE]*** is set.

16.5.19.5 ERM Time Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charge Algorithm	Elevated Degrade	ERM Time Threshold	U2	0	65535	10000	hrs

Description: This sets the time threshold above which *[ERM]* is set.

16.5.19.6 ERETM RSoC Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charge Algorithm	Elevated Degrade	ERETM RSoC Threshold	U1	0	100	90	%

Description: This sets the RSOC threshold above which ***Accumulated ERETM Time*** will count when ***[ERETM_MODE]*** is cleared.

16.5.19.7 ERETM Voltage Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charge Algorithm	Elevated Degrade	ERETM Voltage Threshold	I2	0	32767	4200	mV

Description: This sets the voltage threshold above which ***Accumulated ERETM Time*** will count when the temperature condition is met and ***[ERETM_MODE]*** is set.

16.5.19.8 ERETM Temperature Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charge Algorithm	Elevated Degrade	ERETM Temperature Threshold	I2	0	32767	3123	0.1 K

Description: This sets the temperature threshold above which ***Accumulated ERETM Time*** will count when RSOC or voltage condition is met.

16.5.19.9 ERETM Temperature Max Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charge Algorithm	Elevated Degrade	ERETM Temperature Max Threshold	I2	0	32767	3223	0.1 K

Description: This sets the temperature threshold above which *[ERETM]* immediately sets.

16.5.19.10 ERETM Time Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charge Algorithm	Elevated Degrade	ERETM Time Threshold	U2	0	65535	10000	h

Description: This sets the time threshold above which *[ERM]* is set and *ChargingVoltage()* is set to ***ERETM Charging Voltage*** upon the next CHARGE cycle.

16.5.19.11 Accumulated ERM Time

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charge Algorithm	Elevated Degrade	Accumulated ERM Time	U2	0	65535	0	h

Description: This is the accumulated ERM time counted by the device.

16.5.19.12 Accumulated ERETM Time

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charge Algorithm	Elevated Degrade	Accumulated ERETM Time	U2	0	65535	0	h

Description: This is the accumulated ERETM time counted by the device.

16.5.19.13 ERETM Status

Class	Subclass	Name	Type	Min	Max	Default	Unit
Advanced Charge Algorithm	Elevated Degrade	ERETM Status	U1	0x00	0x03	0x00	Hex

7	6	5	4	3	2	1	0
RSVD	RSVD	RSVD	RSVD	RSVD	RVSD	ERETM_DEGRADE	ERETM_ACTIVE

RSVD (Bits 7–2): Reserved. Do not use.

ERETM_DEGRADE (Bit 1): This is the ERETM active flag the gauge sets when ERETM is active and beginning the next CHARGE cycle.

1 = ERETM degrade active

0 = ERETM degrade not active

ERETM_ACTIVE (Bit 0): ERETM conditions have been met and *ChargingVoltage()* will be degraded starting with next charge cycle

1 = ERETM conditions met

0 = ERETM conditions not met

16.6 Power

16.6.1 Power

Class	Subclass	Name	Type	Min	Max	Default	Unit
Power	Power	Valid Update Voltage	I2	0	32767	3500	mV

Description: Min stack voltage threshold for Flash update

16.6.2 Shutdown

16.6.2.1 Shutdown Voltage

Class	Subclass	Name	Type	Min	Max	Default	Unit
Power	Shutdown	Shutdown Voltage	I2	0	32767	1750	mV

Description: Cell-based shutdown voltage trip threshold

16.6.2.2 Shutdown Time

Class	Subclass	Name	Type	Min	Max	Default	Unit
Power	Shutdown	Shutdown Time	U2	0	255	10	s

Description: Cell-based shutdown voltage trip delay

16.6.2.3 IO Shutdown Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Power	Shutdown	IO Shutdown Delay	U1	0	255	1	250ms

Description: IO shutdown input debounce time

16.6.2.4 IO Shutdown Timeout

Class	Subclass	Name	Type	Min	Max	Default	Unit
Power	Shutdown	IO Shutdown Timeout	U1	0	255	8	250ms

Description: This is the IO shutdown activation timeout when ***[IO_TIMEOUT]*** is set and PACK voltage > ***Charger Present Threshold***.

16.6.2.5 Charger Present Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Power	Shutdown	Charger Present Threshold	I2	0	32767	3000	mV

Description: PACK pin charger present detect threshold for shutdown hardware. This value should not be greater than 3 V, unless the charger output is less than 3 V.

16.6.3 Sleep

16.6.3.1 Sleep Current

Class	Subclass	Name	Type	Min	Max	Default	Unit
Power	Sleep	Sleep Current	I2	0	32767	10	mA

Description: |*Current()*| threshold to enter SLEEP mode. If this parameter is set to 0, then the ***deadband*** will effectively become the ***Sleep Current*** setting, because any current below the ***deadband*** will set the *Current()* = 0 mA.

16.6.3.2 Bus Timeout

Class	Subclass	Name	Type	Min	Max	Default	Unit
Power	Sleep	Bus Timeout	U1	0	255	5	s

Description: Bus low or no communication time to enter SLEEP mode

16.6.3.3 Voltage Time

Class	Subclass	Name	Type	Min	Max	Default	Unit
Power	Sleep	Voltage Time	U1	0	255	5	s

Description: *Voltage()* sampling period in SLEEP mode

16.6.3.4 Current Time

Class	Subclass	Name	Type	Min	Max	Default	Unit
Power	Sleep	Current Time	U1	0	255	20	s

Description: *Current()* sampling period in SLEEP mode

16.6.3.5 Wake Comparator

Class	Subclass	Name	Type	Min	Max	Default	Unit
Power	Sleep	Wake Comparator	H1	0x00	0xFF	0x00	Hex

7	6	5	4	3	2	1	0
RSVD	RSVD	RSVD	RSVD	WK1	WK0	RSVD	RSVD

RSVD (Bits 7–4): Reserved. Do not use.

WK1, WK0 (Bits 3–2): Wake Comparator Threshold

1,1 = ±5 mV
1,0 = ±2.5 mV
0,1 = ±1.25 mV
0,0 = ±0.625 mV

RSVD (Bits 1–0): Reserved. Do not use.

16.6.4 Ship

16.6.4.1 FET Off Time

Class	Subclass	Name	Type	Min	Max	Default	Unit
Power	Ship	FET Off Time	U1	0	127	10	s

Description: Delay time to turn off FETs prior to entering SHUTDOWN mode. This setting should not be longer than the ***Ship Delay*** setting.

16.6.4.2 Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Power	Ship	Delay	U1	0	254	20	s

Description: Delay time to enter SHUTDOWN mode after FETs are turned off.

16.6.4.3 Auto Ship Time

Class	Subclass	Name	Type	Min	Max	Default	Unit
Power	Ship	Auto Ship time	U2	0	65535	1440	min

Description: The bq40z50-R3 device will automatically enter SHUTDOWN mode after staying in SLEEP mode without communication for this amount of time when ***Power Config[AUTO_SHIP_EN]*** = 1.

16.6.5 Power Off

Class	Subclass	Name	Type	Min	Max	Default	Unit
Power	Power Off	Timeout	U2	0	65535	30	min

Description: Timeout to exit the Emergency FET Shutdown condition

16.6.6 Manual FET Control

Class	Subclass	Name	Type	Min	Max	Default	Unit
Power	Manual FET Control	MFC Delay	U1	0	255	60	0.25 s

Description: Delay time to turn off FETs through MFC

16.6.7 IATA

16.6.7.1 IATA Config

Class	Subclass	Name	Type	Min	Max	Default	Unit
Power	IATA	IATA Config	H1	0x00	0xFF	0x03	Hex

7	6	5	4	3	2	1	0
RSVD	RSVD	RSVD	RSVD	RSVD	RSVD	ISTORE_RM	ISTORE_FCC

RSVD (Bits 7–2): Reserved. Do not use.

ISTORE_RM (Bit 1): This bit defines whether the stored value of RM (***IATA RM***) or the true value is displayed during the ***IATA Delay Time*** period.

1 = Stored value of RM (IATA RM) is displayed during the ***IATA Delay Time*** period. (default)

0 = True (present) value of RM is displayed.

ISTORE_FCC (Bit 0): This bit defines whether the stored value of FCC (***IATA FCC***) or the true value is displayed during the ***IATA Delay Time*** period.

1 = Stored value of FCC (***IATA FCC***) is displayed during the ***IATA Delay Time*** period. (default)

0 = True (present) value of FCC is displayed.

16.6.7.2 IATA Delay Time

Class	Subclass	Name	Type	Min	Max	Default	Unit
Power	IATA	IATA Delay Time	U2	0	65535	10	s

Description: ***IATA Delay Time*** holds the time that the stored RM and FCC values are displayed initially on wake up from IATA shutdown.

16.6.7.3 IATA RSOC Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Power	IATA	IATA RSOC Threshold	U1	0	100	30	%

Description: ***IATA RSOC Threshold*** holds the RSOC threshold above which IATA shutdown will not be allowed.

16.6.7.4 IATA DeltaV Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Power	IATA	IATA DeltaV Threshold	U1	0	255	50	mV

Description: Holds the Delta threshold allowed between the max cell voltage and the min cell voltage in the pack. If this threshold is exceeded, only the True (that is, present) value of FCC and RC are displayed on wake up from IATA shutdown.

16.6.7.5 IATA Wake AbsRSOC

Class	Subclass	Name	Type	Min	Max	Default	Unit
Power	IATA	IATA Wake AbsRSOC	U1	0	100	10	%

Description: On wake up from ***IATA*** shutdown, if ***IATA Delay Time*** = 0, and if true RSOC is ≤ ***IATA Wake AbsRSOC***, then the true value of remaining capacity and FCC will be immediately displayed on wake up.

16.6.7.6 IATA Delta RSOC

Class	Subclass	Name	Type	Min	Max	Default	Unit
Power	IATA	IATA Delta RSOC	U1	0	100	3	%

Description: On wake up from IATA shutdown, if ***IATA Delay Time*** = 0 and if true RSOC is > ***IATA Wake AbsRSOC***, then only after a change in true RSOC ≥ ***IATA Delta RSOC*** is detected, will the display switch from the stored ***IATA RM*** and ***IATA FCC*** values to the true value of remaining capacity and FCC.

16.6.7.7 IATA MIN Temperature

Class	Subclass	Name	Type	Min	Max	Default	Unit
Power	IATA	IATA MIN Temperature	I2	–32767	32767	100	0.1C

Description: ***IATA MIN Temperature*** holds the min temperature below which, on wake up from IATA, only the true (present) value of FCC and RM is displayed.

16.6.7.8 IATA MAX Temperature

Class	Subclass	Name	Type	Min	Max	Default	Unit
Power	IATA	IATA MAX Temperature	I2	0	32767	400	0.1C

Description: ***IATA MAX Temperature*** holds the max temperature above which, on wake up from IATA, only the true (present) value of FCC and RM is displayed.

16.6.7.9 IATA MIN Voltage

Class	Subclass	Name	Type	Min	Max	Default	Unit
Power	IATA	IATA MIN Voltage	I2	0	32767	3000	mV

Description: ***IATA MIN Voltage*** holds the min voltage below which, on wake up from IATA, only the true (present) value of FCC and RM is displayed.

16.6.7.10 IATA MAX Voltage

Class	Subclass	Name	Type	Min	Max	Default	Unit
Power	IATA	IATA MAX Voltage	I2	0	32767	3600	mV

Description: ***IATA MAX Voltage*** holds the max voltage above which, on wake up from IATA, only the true (present) value of FCC and RM is displayed.

16.6.8 IATA STORE

16.6.8.1 IATA Flag

Class	Subclass	Name	Type	Min	Max	Default	Unit
Power	IATA STORE	IATA Flag	H1	0x00	0xFF	0x03	Hex

7	6	5	4	3	2	1	0
RSVD	RSVD	RSVD	RSVD	RSVD	RSVD	RSVD	IATA_SHUT

RSVD (Bits 7–1): Reserved. Do not use.

IATA_SHUT (Bit 0): Enables the IATA shutdown to proceed. This bit is automatically set if the *IATA_SHUTDOWN()* MAC command is used. This bit needs to be manually set if the normal *ShutdownMode()* MAC command is expected to do an IATA shutdown.

1 = IATA shutdown is enabled.

0 = IATA shutdown is disabled.

16.6.8.2 IATA RM mAH

Class	Subclass	Name	Type	Min	Max	Default	Unit
Power	IATA STORE	IATA RM mAH	I2	0	32767	0	mAh

Description: ***IATA RM mAH*** stores the remaining capacity (in mAh) at the time an IATA shutdown occurs.

16.6.8.3 IATA RM cWH

Class	Subclass	Name	Type	Min	Max	Default	Unit
Power	IATA STORE	IATA RM cWH	I2	0	32767	0	cWh

Description: ***IATA RM cWH*** stores the remaining capacity (in cWh) at the time an IATA shutdown occurs.

16.6.8.4 IATA FCC mAH

Class	Subclass	Name	Type	Min	Max	Default	Unit
Power	IATA STORE	IATA FCC mAH	I2	0	32767	0	mAh

Description: ***IATA FCC mAH*** stores the value of FCC (in mAh) at the time an IATA shutdown occurs.

16.6.8.5 IATA FCC cWH

Class	Subclass	Name	Type	Min	Max	Default	Unit
Power	IATA STORE	IATA FCC cWH	I2	0	32767	0	cWh

Description: ***IATA FCC cWH*** stores the value of FCC (in cWh) at the time an IATA shutdown occurs.

16.6.9 Unintended Wakeup

16.6.9.1 Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Power	Unintended Wakeup	Delay	U1	0	240	2	s

Description: This sets the time in which communication is checked. If during this ***Delay*** timer period there is no valid communication with the device, then the device goes back into shutdown (with FETs turned off). If there is valid communication within the ***Delay*** timer period, then the device stays in wake and continues like a normal wakeup.

16.6.9.2 Count

Class	Subclass	Name	Type	Min	Max	Default	Unit
Power	Unintended Wakeup	Count	U1	0	255	3	—

Description: The number of times the gauge wakes up from shutdown unintentionally is recorded. This "unintentional wakeup" counter is reset when the gauge wakes up and sees valid communication. If this count exceeds the threshold set by this register (***Count*** with the default of 3), then the next time the gauge wakes up from shutdown, it will execute a normal wakeup without looking for valid communication (and the counter recording wakeup will be reset). If ***Count*** is set to 0, then no threshold exists and the gauge will only wake up with valid communications.

16.7 LED Support

16.7.1 LED Config

16.7.1.1 LED Flash Period

Class	Subclass	Name	Type	Min	Max	Default	Unit
LED Support	LED Config	LED Flash Period	U2	32	65535	512	488 µs

Description: LED flashing period for alarm display

16.7.1.2 LED Blink Period

Class	Subclass	Name	Type	Min	Max	Default	Unit
LED Support	LED Config	LED Blink Period	U2	32	65535	1024	488 µs

Description: LED blinking period for state-of-charge display

16.7.1.3 LED Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
LED Support	LED Config	LED Delay	U2	16	65535	100	488 µs

Description: Delay time from LED to LED for state-of-charge display

16.7.1.4 LED Hold Time

Class	Subclass	Name	Type	Min	Max	Default	Unit
LED Support	LED Config	LED Hold Time	U1	1	63	16	0.25 s

Description: LED display active time

16.7.1.5 LED FC Time

Class	Subclass	Name	Type	Min	Max	Default	Unit
LED Support	LED Config	LED FC Time	U1	0	94	4	15 min

Description: This threshold sets the time the LED will be left on after FC is achieved (assuming the ***[LEDONFC]*** bit is set). It is set in segments of 15 min. It is not recommended to leave the LED on for extended periods after FC is achieved due to the potential of short charge / discharge cycling, which can reduce the battery life.

16.7.1.6 CHG Flash Alarm

Class	Subclass	Name	Type	Min	Max	Default	Unit
LED Support	LED Config	CHG Flash Alarm	I1	0	100	10	%

Description: *RelativeStateOfCharge()* alarm threshold during charging

16.7.1.7 CHG Thresh 1

Class	Subclass	Name	Type	Min	Max	Default	Unit
LED Support	LED Config	CHG Thresh 1	I1	0	100	0	%

Description: *RelativeStateOfCharge()* threshold for LED1 during charging

16.7.1.8 CHG Thresh 2

Class	Subclass	Name	Type	Min	Max	Default	Unit
LED Support	LED Config	CHG Thresh 2	I1	0	100	20	%

Description: *RelativeStateOfCharge()* threshold for LED2 during charging

16.7.1.9 CHG Thresh 3

Class	Subclass	Name	Type	Min	Max	Default	Unit
LED Support	LED Config	CHG Thresh 3	I1	0	100	40	%

Description: *RelativeStateOfCharge()* threshold for LED3 during charging

16.7.1.10 CHG Thresh 4

Class	Subclass	Name	Type	Min	Max	Default	Unit
LED Support	LED Config	CHG Thresh 4	I1	0	100	60	%

Description: *RelativeStateOfCharge()* threshold for LED4 during charging

16.7.1.11 CHG Thresh 5

Class	Subclass	Name	Type	Min	Max	Default	Unit
LED Support	LED Config	CHG Thresh 5	I1	0	100	80	%

Description: *RelativeStateOfCharge()* threshold for LED5 during charging

16.7.1.12 DSG Flash Alarm

Class	Subclass	Name	Type	Min	Max	Default	Unit
LED Support	LED Config	DSG Flash Alarm	I1	0	100	10	%

Description: *RelativeStateOfCharge()* alarm threshold during discharging

16.7.1.13 DSG Thresh 1

Class	Subclass	Name	Type	Min	Max	Default	Unit
LED Support	LED Config	DSG Thresh 1	I1	0	100	0	%

Description: *RelativeStateOfCharge()* threshold for LED1 during discharging

16.7.1.14 DSG Thresh 2

Class	Subclass	Name	Type	Min	Max	Default	Unit
LED Support	LED Config	DSG Thresh 2	I1	0	100	20	%

Description: *RelativeStateOfCharge()* threshold for LED2 during discharging

16.7.1.15 DSG Thresh 3

Class	Subclass	Name	Type	Min	Max	Default	Unit
LED Support	LED Config	DSG Thresh 3	I1	0	100	40	%

Description: *RelativeStateOfCharge()* threshold for LED3 during discharging

16.7.1.16 DSG Thresh 4

Class	Subclass	Name	Type	Min	Max	Default	Unit
LED Support	LED Config	DSG Thresh 4	I1	0	100	60	%

Description: *RelativeStateOfCharge()* threshold for LED4 during discharging

16.7.1.17 DSG Thresh 5

Class	Subclass	Name	Type	Min	Max	Default	Unit
LED Support	LED Config	DSG Thresh 5	I1	0	100	80	%

Description: *RelativeStateOfCharge()* threshold for LED5 during discharging

16.8 System Data

16.8.1 Manufacturer Info

Class	Subclass	Name	Type	Min	Max	Default	Units
System Data	Manufacturer Data	ManufacturerInfo	S33	—	—	abcdefghijklmnopqrstu vwzxy012345	—

Description: *ManufacturerInfo()* value

16.8.2 Integrity

16.8.2.1 Static DF Signature

Class	Subclass	Name	Type	Min	Max	Default	Units
System Data	Integrity	Static DF Signature	H2	0x0	0x7FFF	0x0	Hex

Description: Static data flash signature. Use MAC *StaticDFSignature()* (with MSB set to 0) to initialize this value.

16.8.2.2 Static Chem DF

Class	Subclass	Name	Type	Min	Max	Default	Units
System Data	Integrity	Static Chem DF Signature	H2	0x0	0x7FFF	0x0	Hex

Description: Static chemistry data signature. Use MAC *StaticChemDFSignature()* (with MSB set to 0) to initialize this value.

16.8.2.3 All DF Signature

Class	Subclass	Name	Type	Min	Max	Default	Units
System Data	Integrity	All DF Signature	H2	0x0	0x7FFF	0x0	Hex

Description: Static data flash signature. Use MAC *AllDFSignature()* (with MSB set to 0) to initialize this value.

16.9 Lifetimes

16.9.1 Voltage

16.9.1.1 Cell 1 Max Voltage

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Voltage	Cell 1 Max Voltage	I2	0	32767	0	mV

Description: Maximum reported cell voltage 1

16.9.1.2 Cell 2 Max Voltage

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Voltage	Cell 2 Max Voltage	I2	0	32767	0	mV

Description: Maximum reported cell voltage 2

16.9.1.3 Cell 3 Max Voltage

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Voltage	Cell 3 Max Voltage	I2	0	32767	0	mV

Description: Maximum reported cell voltage 3

16.9.1.4 Cell 4 Max Voltage

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Voltage	Cell 4 Max Voltage	I2	0	32767	0	mV

Description: Maximum reported cell voltage 4

16.9.1.5 Cell 1 Min Voltage

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Voltage	Cell 1 Min Voltage	I2	0	32767	32767	mV

Description: Minimum reported cell voltage 1

16.9.1.6 Cell 2 Min Voltage

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Voltage	Cell 2 Min Voltage	I2	0	32767	32767	mV

Description: Minimum reported cell voltage 2

16.9.1.7 Cell 3 Min Voltage

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Voltage	Cell 3 Min Voltage	I2	0	32767	32767	mV

Description: Minimum reported cell voltage 3

16.9.1.8 Cell 4 Min Voltage

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Voltage	Cell 4 Min Voltage	I2	0	32767	32767	mV

Description: Minimum reported cell voltage 4

16.9.1.9 Max Delta Cell Voltage

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Voltage	Max Delta Cell Voltage	I2	0	32767	0	mV

Description: Maximum reported delta between cell voltages 1..4

16.9.2 Current

16.9.2.1 Max Charge Current

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Current	Max Charge Current	I2	0	32767	0	mA

Description: Maximum reported *Current()* in charge direction

16.9.2.2 Max Discharge Current

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Current	Max Discharge Current	I2	–32768	0	0	mA

Description: Maximum reported *Current()* in discharge direction

16.9.2.3 Max Avg Dsg Current

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Current	Max Avg Dsg Current	I2	–32768	0	0	mA

Description: Maximum reported *AverageCurrent()* in discharge direction

16.9.2.4 Max Avg Dsg Power

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Current	Max Avg Dsg Power	I2	–32768	0	0	cW

Description: Maximum reported average power in the discharge direction

16.9.3 Temperature

16.9.3.1 Max Temp Cell

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Temperature	Max Temp Cell	I1	–128	127	–128	°C

Description: Maximum reported cell temperature

16.9.3.2 Min Temp Cell

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Temperature	Min Temp Cell	I1	–128	127	127	°C

Description: Minimum reported cell temperature

16.9.3.3 Max Delta Cell Temp

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Temperature	Max Delta Cell Temp	I1	–128	127	0	°C

Description: Maximum reported temperature delta for TSx inputs configured as cell temperature

16.9.3.4 Max Temp Int Sensor

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Temperature	Max Temp Int Sensor	I1	–128	127	–128	°C

Description: Maximum reported internal temperature sensor temperature

16.9.3.5 Min Temp Int Sensor

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Temperature	Min Temp Int Sensor	I1	–128	127	127	°C

Description: Minimum reported internal temperature sensor temperature

16.9.3.6 Max Temp Fet

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Temperature	Max Temp Fet	I1	–128	127	–128	°C

Description: Maximum reported FET temperature

16.9.4 Safety Events

16.9.4.1 No Of COV Events

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Safety Events	No Of COV Events	U2	0	32767	0	events

Description: Total number of *SafetyStatus()[COV]* events

16.9.4.2 Last COV Event

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Safety Events	Last COV Event	U2	0	32767	0	cycles

Description: Last *SafetyStatus()[COV]* event in *CycleCount()* cycles

16.9.4.3 No Of CUV Events

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Safety Events	No Of CUV Events	U2	0	32767	0	events

Description: Total number of *SafetyStatus()[CUV]* events

16.9.4.4 Last CUV Event

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Safety Events	Last CUV Event	U2	0	32767	0	cycles

Description: Last *SafetyStatus()[CUV]* event in *CycleCount()* cycles

16.9.4.5 No Of OCD1 Events

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Safety Events	No Of OCD1 Events	U2	0	32767	0	events

Description: Total number of *SafetyStatus()[OCD1]* events

16.9.4.6 Last OCD1 Event

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Safety Events	Last OCD1 Event	U2	0	32767	0	cycles

Description: Last *SafetyStatus()[OCD1]* event in *CycleCount()* cycles

16.9.4.7 No Of OCD2 Events

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Safety Events	No Of OCD2 Events	U2	0	32767	0	events

Description: Total number of *SafetyStatus()[OCD2]* events

16.9.4.8 Last OCD2 Event

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Safety Events	Last OCD2 Event	U2	0	32767	0	cycles

Description: Last *SafetyStatus()[OCD2]* event in *CycleCount()* cycles

16.9.4.9 No Of OCC1 Events

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Safety Events	No Of OCC1 Events	U2	0	32767	0	events

Description: Total number of *SafetyStatus()[OCC1]* events

16.9.4.10 Last OCC1 Event

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Safety Events	Last OCC1 Event	U2	0	32767	0	cycles

Description: Last *SafetyStatus()[OCC1]* event in *CycleCount()* cycles

16.9.4.11 No Of OCC2 Events

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Safety Events	No Of OCC2 Events	U2	0	32767	0	events

Description: Total number of *SafetyStatus()[OCC2]* events

16.9.4.12 Last OCC2 Event

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Safety Events	Last OCC2 Event	U2	0	32767	0	cycles

Description: Last *SafetyStatus()[OCC2]* event in *CycleCount()* cycles

16.9.4.13 No Of AOLD Events

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Safety Events	No Of AOLD Events	U2	0	32767	0	events

Description: Total number of *SafetyStatus()[AOLD]* events

16.9.4.14 Last AOLD Event

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Safety Events	Last AOLD Event	U2	0	32767	0	cycles

Description: Last *SafetyStatus()[AOLD]* event in *CycleCount()* cycles

16.9.4.15 No Of ASCD Events

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Safety Events	No Of ASCD Events	U2	0	32767	0	events

Description: Total number of *SafetyStatus()[ASCD]* events

16.9.4.16 Last ASCD Event

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Safety Events	Last ASCD Event	U2	0	32767	0	cycles

Description: Last *SafetyStatus()[ASCD]* event in *CycleCount()* cycles

16.9.4.17 No Of ASCC Events

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Safety Events	No Of ASCC Events	U2	0	32767	0	events

Description: Total number of *SafetyStatus()[ASCC]* events

16.9.4.18 Last ASCC Event

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Safety Events	Last ASCC Event	U2	0	32767	0	cycles

Description: Last *SafetyStatus()[ASCC]* event in *CycleCount()* cycles

16.9.4.19 No Of OTC Events

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Safety Events	No Of OTC Events	U2	0	32767	0	events

Description: Total number of *SafetyStatus()[OTC]* events

16.9.4.20 Last OTC Event

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Safety Events	Last OTC Event	U2	0	32767	0	cycles

Description: Last *SafetyStatus()[OTC]* event in *CycleCount()* cycles

16.9.4.21 No Of OTD Events

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Safety Events	No Of OTD Events	U2	0	32767	0	events

Description: Total number of *SafetyStatus()[OTD]* events

16.9.4.22 Last OTD Event

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Safety Events	Last OTD Event	U2	0	32767	0	cycles

Description: Last *SafetyStatus()[OTD]* event in *CycleCount()* cycles

16.9.4.23 No Of OTF Events

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Safety Events	No Of OTF Events	U2	0	32767	0	events

Description: Total number of *SafetyStatus()[OTF]* events

16.9.4.24 Last OTF Event

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Safety Events	Last OTF Event	U2	0	32767	0	cycles

Description: *Last SafetyStatus()[OTF]* event in *CycleCount()* cycles

16.9.5 Charging Events

16.9.5.1 No Valid Charge Term

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Charging Events	No Valid Charge Term	U2	0	32767	0	events

Description: Total number of valid charge termination events

16.9.5.2 Last Valid Charge Term

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Charging Events	Last Valid Charge Term	U2	0	32767	0	cycles

Description: Last valid charge termination in *CycleCount()* cycles

16.9.6 Gauging Events

16.9.6.1 No Of Qmax Updates

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Gauging Events	No Of Qmax Updates	U2	0	32767	0	events

Description: Total number of *GaugingStatus()[QMax]* toggles

16.9.6.2 Last Qmax Update

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Gauging Events	Last Qmax Update	U2	0	32767	0	cycles

Description: The *CycleCount()* cycles made at the last event of *GaugingStatus()[QMax]* update

16.9.6.3 No Of Ra Updates

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Gauging Events	No Of Ra Updates	U2	0	32767	0	events

Description: Total number of *GaugingStatus()[RX]* toggles

16.9.6.4 Last Ra Update

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Gauging Events	Last Ra Update	U2	0	32767	0	cycles

Description: Last *GaugingStatus()[RX]* toggle in *CycleCount()* cycles

16.9.6.5 No Of Ra Disable

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Gauging Events	No Of Ra Disable	U2	0	32767	0	events

Description: Total number of *GaugingStatus()[R_DIS]* = 1 event

16.9.6.6 Last Ra Disable

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Gauging Events	Last Ra Disable	U2	0	32767	0	cycles

Description: The *CycleCount()* cycles of the last update event of *GaugingStatus()[R_DIS]* = 1

16.9.7 Power Events

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Power Events	No of Shutdowns	U1	0	255	0	events

Description: Total number of shutdown events

16.9.8 Cell Balancing

16.9.8.1 CB Time Cell 1

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Cell Balancing	CB Time Cell 1	U4	0	4294967295	0	s

Description: Total performed cell balancing bypass time Cell 0

16.9.8.2 CB Time Cell 2

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Cell Balancing	CB Time Cell 2	U4	0	4294967295	0	s

Description: Total performed cell balancing bypass time Cell 1

16.9.8.3 CB Time Cell 3

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Cell Balancing	CB Time Cell 3	U4	0	4294967295	0	s

Description: Total performed cell balancing bypass time Cell 2

16.9.8.4 CB Time Cell 4

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Cell Balancing	CB Time Cell 4	U4	0	4294967295	0	s

Description: Total performed cell balancing bypass time Cell 3

16.9.9 Time

16.9.9.1 Total Firmware Runtime

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Time	Total Firmware Runtime	U4	0	4294967295	0	s

Description: Total firmware runtime between resets

16.9.9.2 Time Spent in UT

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Time	Time Spent in UT RSOC A	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in UT RSOC B	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in UT RSOC C	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in UT RSOC D	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in UT RSOC E	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in UT RSOC F	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in UT RSOC G	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in UT RSOC H	U4	0	4294967295	0	s

Description: Firmware runtime spent below T1 broken up according to running RSOC:

The RSOC A slot defines the range greater than or equal to ***Time RSOC Threshold A***.

RSOC B is the range greater than or equal to ***Time RSOC Threshold B*** and less than ***Time RSOC Threshold A***.

RSOC C is the range greater than or equal to ***Time RSOC Threshold C*** and less than ***Time RSOC Threshold B***.

RSOC D is the range greater than or equal to ***Time RSOC Threshold D*** and less than ***Time RSOC Threshold C***.

RSOC E is the range greater than or equal to ***Time RSOC Threshold E*** and less than ***Time RSOC Threshold D***.

RSOC F is the range greater than or equal to ***Time RSOC Threshold F*** and less than ***Time RSOC Threshold E***.

RSOC G is the range greater than or equal to ***Time RSOC Threshold G*** and less than ***Time RSOC Threshold F***.

RSOC H is the range less than ***Time RSOC Threshold G***.

16.9.9.3 Time Spent in LT

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Time	Time Spent in LT RSOC A	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in LT RSOC B	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in LT RSOC C	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in LT RSOC D	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in LT RSOC E	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in LT RSOC F	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in LT RSOC G	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in LT RSOC H	U4	0	4294967295	0	s

Description: Total firmware runtime spent between T1 and T2 broken up according to running RSOC:

The RSOC A slot defines the range greater than or equal to ***Time RSOC Threshold A***.

RSOC B is the range greater than or equal to ***Time RSOC Threshold B*** and less than ***Time RSOC Threshold A***.

RSOC C is the range greater than or equal to ***Time RSOC Threshold C*** and less than ***Time RSOC Threshold B***.

RSOC D is the range greater than or equal to ***Time RSOC Threshold D*** and less than ***Time RSOC Threshold C***.

RSOC E is the range greater than or equal to ***Time RSOC Threshold E*** and less than ***Time RSOC Threshold D***.

RSOC F is the range greater than or equal to ***Time RSOC Threshold F*** and less than ***Time RSOC Threshold E***.

RSOC G is the range greater than or equal to ***Time RSOC Threshold G*** and less than ***Time RSOC Threshold F***.

RSOC H is the range less than ***Time RSOC Threshold G***.

16.9.9.4 Time Spent in STL

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Time	Time Spent in STL RSOC A	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in STL RSOC B	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in STL RSOC C	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in STL RSOC D	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in STL RSOC E	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in STL RSOC F	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in STL RSOC G	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in STL RSOC H	U4	0	4294967295	0	s

Description: Total firmware runtime spent between T2 and T5 broken up according to running RSOC:

The RSOC A slot defines the range greater than or equal to ***Time RSOC Threshold A***.

RSOC B is the range greater than or equal to ***Time RSOC Threshold B*** and less than ***Time RSOC Threshold A***.

RSOC C is the range greater than or equal to ***Time RSOC Threshold C*** and less than ***Time RSOC Threshold B***.

RSOC D is the range greater than or equal to ***Time RSOC Threshold D*** and less than ***Time RSOC Threshold C***.

RSOC E is the range greater than or equal to ***Time RSOC Threshold E*** and less than ***Time RSOC Threshold D***.

RSOC F is the range greater than or equal to ***Time RSOC Threshold F*** and less than ***Time RSOC Threshold E***.

RSOC G is the range greater than or equal to ***Time RSOC Threshold G*** and less than ***Time RSOC Threshold F***.

RSOC H is the range less than ***Time RSOC Threshold G***.

16.9.9.5 Time Spent in RT

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Time	Time Spent in RT RSOC A	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in RT RSOC B	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in RT RSOC C	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in RT RSOC D	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in RT RSOC E	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in RT RSOC F	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in RT RSOC G	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in RT RSOC H	U4	0	4294967295	0	s

Description: Total firmware runtime spent between T5 and T6 broken up according to running RSOC:

The RSOC A slot defines the range greater than or equal to ***Time RSOC Threshold A***.

RSOC B is the range greater than or equal to ***Time RSOC Threshold B*** and less than ***Time RSOC Threshold A***.

RSOC C is the range greater than or equal to ***Time RSOC Threshold C*** and less than ***Time RSOC Threshold B***.

RSOC D is the range greater than or equal to ***Time RSOC Threshold D*** and less than ***Time RSOC Threshold C***.

RSOC E is the range greater than or equal to ***Time RSOC Threshold E*** and less than ***Time RSOC Threshold D***.

RSOC F is the range greater than or equal to ***Time RSOC Threshold F*** and less than ***Time RSOC Threshold E***.

RSOC G is the range greater than or equal to ***Time RSOC Threshold G*** and less than ***Time RSOC Threshold F***.

RSOC H is the range less than ***Time RSOC Threshold G***.

16.9.9.6 Time Spent in STH

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Time	Time Spent in STH RSOC A	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in STH RSOC B	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in STH RSOC C	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in STH RSOC D	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in STH RSOC E	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in STH RSOC F	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in STH RSOC G	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in STH RSOC H	U4	0	4294967295	0	s

Description: Total firmware runtime spent between T6 and T3 broken up according to running RSOC:

The RSOC A slot defines the range greater than or equal to ***Time RSOC Threshold A***.

RSOC B is the range greater than or equal to ***Time RSOC Threshold B*** and less than ***Time RSOC Threshold A***.

RSOC C is the range greater than or equal to ***Time RSOC Threshold C*** and less than ***Time RSOC Threshold B***.

RSOC D is the range greater than or equal to ***Time RSOC Threshold D*** and less than ***Time RSOC Threshold C***.

RSOC E is the range greater than or equal to ***Time RSOC Threshold E*** and less than ***Time RSOC Threshold D***.

RSOC F is the range greater than or equal to ***Time RSOC Threshold F*** and less than ***Time RSOC Threshold E***.

RSOC G is the range greater than or equal to ***Time RSOC Threshold G*** and less than ***Time RSOC Threshold F***.

RSOC H is the range less than ***Time RSOC Threshold G***.

16.9.9.7 Time Spent in HT

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Time	Time Spent in HT RSOC A	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in HT RSOC B	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in HT RSOC C	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in HT RSOC D	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in HT RSOC E	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in HT RSOC F	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in HT RSOC G	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in HT RSOC H	U4	0	4294967295	0	s

Description: Total firmware runtime spent between T3 and T4 broken up according to running RSOC:

The RSOC A slot defines the range greater than or equal to ***Time RSOC Threshold A***.

RSOC B is the range greater than or equal to ***Time RSOC Threshold B*** and less than ***Time RSOC Threshold A***.

RSOC C is the range greater than or equal to ***Time RSOC Threshold C*** and less than ***Time RSOC Threshold B***.

RSOC D is the range greater than or equal to ***Time RSOC Threshold D*** and less than ***Time RSOC Threshold C***.

RSOC E is the range greater than or equal to ***Time RSOC Threshold E*** and less than ***Time RSOC Threshold D***.

RSOC F is the range greater than or equal to ***Time RSOC Threshold F*** and less than ***Time RSOC Threshold E***.

RSOC G is the range greater than or equal to ***Time RSOC Threshold G*** and less than ***Time RSOC Threshold F***.

RSOC H is the range less than ***Time RSOC Threshold G***.

16.9.9.8 Time Spent in OT

Class	Subclass	Name	Type	Min	Max	Default	Unit
Lifetimes	Time	Time Spent in OT RSOC A	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in OT RSOC B	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in OT RSOC C	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in OT RSOC D	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in OT RSOC E	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in OT RSOC F	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in OT RSOC G	U4	0	4294967295	0	s
Lifetimes	Time	Time Spent in OT RSOC H	U4	0	4294967295	0	s

Description: Total firmware runtime spent above T4 broken up according to running RSOC:

The RSOC A slot defines the range greater than or equal to ***Time RSOC Threshold A***.

RSOC B is the range greater than or equal to ***Time RSOC Threshold B*** and less than ***Time RSOC Threshold A***.

RSOC C is the range greater than or equal to ***Time RSOC Threshold C*** and less than ***Time RSOC Threshold B***.

RSOC D is the range greater than or equal to ***Time RSOC Threshold D*** and less than ***Time RSOC Threshold C***.

RSOC E is the range greater than or equal to ***Time RSOC Threshold E*** and less than ***Time RSOC Threshold D***.

RSOC F is the range greater than or equal to ***Time RSOC Threshold F*** and less than ***Time RSOC Threshold E***.

RSOC G is the range greater than or equal to ***Time RSOC Threshold G*** and less than ***Time RSOC Threshold F***.

RSOC H is the range less than ***Time RSOC Threshold G***.

16.10 Protections

16.10.1 CUV—Cell Undervoltage

16.10.1.1 Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	CUV	Threshold	I2	0	32767	2500	mV

Description: Cell undervoltage trip threshold

16.10.1.2 Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	CUV	Delay	U1	0	255	2	s

Description: Cell undervoltage trip delay

16.10.1.3 Recovery

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	CUV	Recovery	I2	0	32767	3000	mV

Description: Cell undervoltage recovery threshold

16.10.2 CUVC—Cell Undervoltage

16.10.2.1 Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	CUVC	Threshold	I2	0	32767	2400	mV

Description: Cell undervoltage trip threshold

16.10.2.2 Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	CUVC	Delay	U1	0	255	2	s

Description: Cell undervoltage trip delay

16.10.2.3 Recovery

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	CUVC	Recovery	I2	0	32767	3000	mV

Description: Cell undervoltage recovery threshold

16.10.3 COV—Cell Overvoltage

16.10.3.1 Threshold Low Temp

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	COV	Threshold Low Temp	I2	0	32767	4300	mV

Description: Cell overvoltage low temperature range trip threshold

16.10.3.2 Threshold Standard Temp Low

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	COV	Threshold Standard Temp Low	I2	0	32767	4300	mV

Description: Cell overvoltage standard temperature low range trip threshold

16.10.3.3 Threshold Standard Temp High

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	COV	Threshold Standard Temp High	I2	0	32767	4300	mV

Description: Cell overvoltage standard temperature high range trip threshold

16.10.3.4 Threshold High Temp

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	COV	Threshold High Temp	I2	0	32767	4300	mV

Description: Cell overvoltage high temperature range trip threshold

16.10.3.5 Threshold Rec Temp

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	COV	Threshold Rec Temp	I2	0	32767	4300	mV

Description: Cell overvoltage recommended temperature range trip threshold

16.10.3.6 Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	COV	Delay	U1	0	255	2	s

Description: Cell overvoltage trip delay

16.10.3.7 Recovery Low Temp

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	COV	Recovery Low Temp	I2	0	32767	3900	mV

Description: Cell overvoltage low temperature range recovery threshold

16.10.3.8 Recovery Standard Temp Low

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	COV	Recovery Standard Temp Low	I2	0	32767	3900	mV

Description: Cell overvoltage standard temperature low recovery range threshold

16.10.3.9 Recovery Standard Temp High

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	COV	Recovery Standard Temp High	I2	0	32767	3900	mV

Description: Cell overvoltage standard temperature high recovery range threshold

16.10.3.10 Recovery High Temp

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	COV	Recovery High Temp	I2	0	32767	3900	mV

Description: Cell overvoltage high temperature range recovery threshold

16.10.3.11 Recovery Rec Temp

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	COV	Recovery Rec Temp	I2	0	32767	3900	mV

Description: Cell overvoltage recommended temperature range recovery threshold

16.10.3.12 Cell Overvoltage Latch Limit

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	COV	Latch Limit	I2	0	255	0	counts

Description: Cell overvoltage latch counter trip threshold

16.10.3.13 Cell Overvoltage Counter Decrement Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	COV	Counter Dec Delay	I2	0	255	10	s

Description: Cell overvoltage counter decrement delay

16.10.3.14 Reset

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	COV	Reset	I2	0	255	15	s

Description: Cell overvoltage latch reset time

16.10.4 OCC1—Overcurrent In Charge 1

16.10.4.1 Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	OCC1	Threshold	I2	–32768	32767	6000	mA

Description: Overcurrent in Charge 1 trip threshold

16.10.4.2 Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	OCC1	Delay	U1	0	255	6	s

Description: Overcurrent in Charge 1 trip delay

16.10.5 OCC2—Overcurrent In Charge 2

16.10.5.1 Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	OCC2	Threshold	I2	–32768	32767	8000	mA

Description: Overcurrent in Charge 2 trip threshold

16.10.5.2 Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	OCC2	Delay	U1	0	255	3	s

Description: Overcurrent in Charge 2 trip delay

16.10.6 OCC—Overcurrent In Charge Recovery

16.10.6.1 Recovery Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	OCC	Recovery Threshold	I2	–32768	32767	–200	mA

Description: Overcurrent in Charge 1 and 2 recovery threshold

16.10.6.2 Recovery Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	OCC	Recovery Delay	U1	0	255	5	s

Description: Overcurrent in Charge 1 and 2 recovery delay

16.10.7 OCD1—Overcurrent In Discharge 1

16.10.7.1 Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	OCD1	Threshold	I2	–32768	32767	–6000	mA

Description: Overcurrent in Discharge 1 trip threshold

16.10.7.2 Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	OCD1	Delay	U1	0	255	6	s

Description: Overcurrent in Discharge 1 trip delay

16.10.8 OCD2—Overcurrent In Discharge 2

16.10.8.1 Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	OCD2	Threshold	I2	–32768	32767	–8000	mA

Description: Overcurrent in Discharge 2 trip threshold

16.10.8.2 Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	OCD2	Delay	U1	0	255	3	s

Description: Overcurrent in Discharge 2 trip delay

16.10.9 OCD—Overcurrent In Discharge Recovery

16.10.9.1 Recovery Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	OCD	Recovery Threshold	I2	–32768	32767	200	mA

Description: Overcurrent in Discharge 1 and 2 recovery threshold

16.10.9.2 Recovery Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	OCD	Recovery Delay	U1	0	255	5	s

Description: Overcurrent in Discharge 1 and 2 recovery delay

16.10.9.3 Latch Limit

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	OCD	Latch Limit	I2	0	255	0	counts

Description: Overcurrent in Discharge (OCD) latch counter trip threshold

16.10.9.4 Counter Dec Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	OCD	Counter Dec Delay	I2	0	255	10	s

Description: Overcurrent in Discharge (OCD) counter decrement delay

16.10.9.5 Reset

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	OCD	Reset	I2	0	255	15	s

Description: Overcurrent in Discharge (OCD) latch reset time

16.10.10 AOLD—Overload in Discharge

16.10.10.1 Latch Limit

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	AOLD	Latch Limit	U1	0	255	0	counts

Description: Overload latch counter trip threshold

16.10.10.2 Counter Dec Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	AOLD	Counter Dec Delay	U1	0	255	10	s

Description: Overload latch counter decrement delay

16.10.10.3 Recovery

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	AOLD	Recovery	U1	0	255	5	s

Description: Overload recovery time

16.10.10.4 Reset

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	AOLD	Reset	U1	0	255	15	s

Description: Overload latch reset time

16.10.10.5 Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	AOLD	Threshold	H1	0x0	0xFF	0xF4	Hex

Description: ***AOLD:Threshold*** Setting

Bits 7–4: OLDD: AOLD delay time

Bits 3–0: OLDV: AOLD threshold

16.10.11 ASCC—Short Circuit In Charge

16.10.11.1 Latch Limit

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	ASCC	Latch Limit	U1	0	255	0	counts

Description: Short Circuit in Charge Latch counter trip threshold

16.10.11.2 Counter Dec Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	ASCC	Counter Dec Delay	U1	0	255	10	s

Description: Short Circuit in Charge counter decrement delay

16.10.11.3 Recovery

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	ASCC	Recovery	U1	0	255	5	s

Description: Short Circuit in Charge recovery time

16.10.11.4 Reset

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	ASCC	Reset	U1	0	255	15	s

Description: Short Circuit in Charge latch reset time

16.10.11.5 Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	ASCC	Threshold	H1	0x0	0xFF	0x77	Hex

Description: ***ASCC:Threshold*** Setting

Bits 7–4: SCCD: SCC delay time
Bit 3: Reserved
Bits 2–0: SCCV: SCC threshold

16.10.12 ASCD—Short Circuit in Discharge

16.10.12.1 Latch Limit

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	ASCD	Latch Limit	U1	0	255	0	counts

Description: Short Circuit in Discharge Latch counter trip threshold

16.10.12.2 Counter Dec Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	ASCD	Counter Dec Delay	U1	0	255	10	s

Description: Short Circuit in Discharge counter decrement delay

16.10.12.3 Recovery

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	ASCD	Recovery	U1	0	255	5	s

Description: Short Circuit in Discharge recovery time

16.10.12.4 Reset

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	ASCD	Reset	U1	0	255	15	s

Description: Short Circuit in Discharge latch reset time

16.10.12.5 Thresholds 1 and 2

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	ASCD	Threshold 1	H1	0x00	0xFF	0x77	Hex
Protections	ASCD	Threshold 2	H1	0x00	0xFF	0xE7	Hex

Threshold 1 Description: ***ASCD:Threshold 1*** Setting

Bits 7–4: SCD1D–SCD1 delay time

Bit 3: Reserved

Bits 2–0: SCD1V: SCD1 threshold

Threshold 2 Description: ***ASCD:Threshold 2*** Setting

Bits 7–4: SCD2D–SCD2 delay time

Bit 3: Reserved

Bits 2–0: SCD2V: SCD2 threshold

16.10.13 OTC—Overtemperature in Charge

16.10.13.1 Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	OTC	Threshold	I2	–400	1500	550	0.1°C

Description: Overtemperature in Charge trip threshold

16.10.13.2 Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	OTC	Delay	U1	0	255	2	s

Description: Overtemperature in Charge Cell trip delay

16.10.13.3 Recovery

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	OTC	Recovery	I2	–400	1500	500	0.1°C

Description: Overtemperature in Charge Cell recovery threshold

16.10.14 OTD—Overtemperature in Discharge

16.10.14.1 Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	OTD	Threshold	I2	–400	1500	600	0.1°C

Description: Overtemperature in Discharge trip threshold

16.10.14.2 Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	OTD	Delay	U1	0	255	2	s

Description: Overtemperature in Discharge trip delay

16.10.14.3 Recovery

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	OTD	Recovery	I2	–400	1500	550	0.1°C

Description: Overtemperature in Discharge recovery threshold

16.10.15 OTF—Overtemperature FET

16.10.15.1 Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	OTF	Threshold	I2	–400	1500	800	0.1°C

Description: Overtemperature FET trip threshold

16.10.15.2 Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	OTF	Delay	U1	0	255	2	s

Description: Overtemperature FET trip delay

16.10.15.3 Recovery

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	OTF	Recovery	I2	–400	1500	650	0.1°C

Description: Overtemperature FET recovery threshold

16.10.16 UTC—Undertemperature in Charge

16.10.16.1 Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	UTC	Threshold	I2	–400	1500	0	0.1°C

Description: Undertemperature in Charge trip threshold

16.10.16.2 Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	UTC	Delay	U1	0	255	2	s

Description: Undertemperature in Charge Cell trip delay

16.10.16.3 Recovery

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	UTC	Recovery	I2	–400	1500	50	0.1°C

Description: Undertemperature in Charge Cell recovery threshold

16.10.17 UTD—Undertemperature in Discharge

16.10.17.1 Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	UTD	Threshold	I2	–400	1500	0	0.1°C

Description: Undertemperature in Discharge trip threshold

16.10.17.2 Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	UTD	Delay	U1	0	255	2	s

Description: Undertemperature in Discharge trip delay

16.10.17.3 Recovery

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	UTD	Recovery	I2	–400	1500	50	0.1°C

Description: Undertemperature in Discharge recovery threshold

16.10.18 HWD—Host Watchdog

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	HWD	Delay	U1	0	255	10	s

Description: SBS Host watchdog trip delay

16.10.19 PTO—PRECHARGE Mode Time Out

16.10.19.1 Charge Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	PTO	Charge Threshold	I2	–32768	32767	2000	mA

Description: Precharge Timeout Current Threshold

16.10.19.2 Suspend Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	PTO	Suspend Threshold	I2	–32768	32767	1800	mA

Description: Precharge Timeout Suspend Threshold

16.10.19.3 Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	PTO	Delay	U2	0	65535	1800	s

Description: Precharge Timeout Trip Delay

16.10.19.4 Reset

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	PTO	Reset	I2	–32768	32767	2	mAh

Description: Precharge Timeout Reset Threshold

16.10.20 CTO—Fast Charge Mode Time Out

16.10.20.1 Charge Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	CTO	Charge Threshold	I2	–32768	32767	2500	mA

Description: Fast-Charge Timeout Current Threshold

16.10.20.2 Suspend Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	CTO	Suspend Threshold	I2	–32768	32767	2000	mA

Description: Fast-Charge Timeout Suspend Threshold

16.10.20.3 Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	CTO	Delay	U2	0	65535	54000	s

Description: Fast-Charge Timeout Trip Delay

16.10.20.4 Reset

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	CTO	Reset	I2	0	32767	2	mAh

Description: Fast-Charge Timeout Reset Threshold

16.10.21 OC—Overcharge

16.10.21.1 Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	OC	Threshold	I2	–32768	32767	300	mAh

Description: Overcharge trip threshold

16.10.21.2 Recovery

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	OC	Recovery	I2	–32768	32767	2	mAh

Description: Overcharge recovery threshold

16.10.21.3 RSOC Recovery

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	OC	RSOC Recovery	U1	0	100	90	%

Description: Overcharge *RelativeStateOfCharge()* recovery threshold

16.10.22 CHGV—ChargingVoltage

16.10.22.1 Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	CHGV	Threshold	I2	–32768	32767	500	mV

Description: *ChargingVoltage()* delta trip threshold

16.10.22.2 Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	CHGV	Delay	U1	0	255	30	s

Description: *ChargingVoltage()* delta trip delay

16.10.22.3 Recovery

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	CHGV	Recovery	I2	–32768	32767	–500	mV

Description: *ChargingVoltage()* delta recovery threshold

16.10.23 CHGC—ChargingCurrent

16.10.23.1 Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	CHGC	Threshold	I2	–32768	32767	500	mA

Description: *ChargingCurrent()* delta trip threshold

16.10.23.2 Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	CHGC	Delay	U1	0	255	2	s

Description: *ChargingCurrent()* delta trip delay

16.10.23.3 Recovery Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	CHGC	Recovery Threshold	I2	–32768	32767	100	mA

Description: *ChargingCurrent()* delta recovery threshold

16.10.23.4 Recovery Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	CHGC	Recovery Delay	U1	0	255	2	s

Description: *ChargingCurrent()* delta recovery delay

16.10.24 PCHGC—Pre-ChargingCurrent

16.10.24.1 Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	PCHGC	Threshold	I2	–32768	32767	50	mA

Description: *Pre-ChargingCurrent()* trip threshold

16.10.24.2 Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	PCHGC	Delay	U1	0	255	2	s

Description: *Pre-ChargingCurrent()* trip delay

16.10.24.3 Recovery Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	PCHGC	Recovery Threshold	I2	–32768	32767	10	mA

Description: *Pre-ChargingCurrent()* recovery threshold

16.10.24.4 Recovery Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Protections	PCHGC	Recovery Delay	U1	0	255	2	s

Description: *Pre-ChargingCurrent()* recovery delay

16.11 Permanent Fail

16.11.1 SUV—Safety Cell Undervoltage

16.11.1.1 Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	SUV	Threshold	I2	0	32767	2200	mV

Description: Safety Cell Undervoltage trip threshold

16.11.1.2 Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	SUV	Delay	U1	0	255	5	s

Description: Safety Cell Undervoltage trip delay

16.11.2 SOV—Safety Cell Overvoltage

16.11.2.1 Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	SOV	Threshold	I2	0	32767	4500	mV

Description: Safety Cell Overvoltage trip threshold

16.11.2.2 Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	SOV	Delay	U1	0	255	5	s

Description: Safety Cell Overvoltage trip delay

16.11.3 SOCC—Safety Overcurrent in Charge

16.11.3.1 Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	SOCC	Threshold	I2	–32768	32767	10000	mA

Description: Safety Overcurrent in Charge trip threshold

16.11.3.2 Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	SOCC	Delay	U1	0	255	5	s

Description: Safety Overcurrent in Charge trip delay

16.11.4 SOCD—Safety Overcurrent in Discharge

16.11.4.1 Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	SOCD	Threshold	I2	–32768	32767	–10000	mA

Description: Safety Overcurrent in Discharge trip threshold

16.11.4.2 Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	SOCD	Delay	U1	0	255	5	s

Description: Safety Overcurrent in Discharge trip delay

16.11.5 SOT—Overtemperature Cell

16.11.5.1 Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	SOT	Threshold	I2	–400	1500	650	0.1°C

Description: Overtemperature Cell trip threshold

16.11.5.2 Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	SOT	Delay	U1	0	255	5	s

Description: Overtemperature Cell trip delay

16.11.6 SOTF—Overtemperature FET

16.11.6.1 Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	SOTF	Threshold	I2	–400	1500	1000	0.1°C

Description: Overtemperature FET trip threshold

16.11.6.2 Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	SOTF	Delay	U1	0	255	5	s

Description: Overtemperature FET trip delay

16.11.7 Open Thermistor—NTC Thermistor Failure

16.11.7.1 Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	Open Thermistor	Threshold	I2	0	32767	2232	0.1 K

Description: Temperature threshold for open thermistor

16.11.7.2 Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	Open Thermistor	Delay	U1	0	255	5	s

Description: Trip delay for open thermistor

16.11.7.3 FET Delta

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	Open Thermistor	FET Delta	I2	0	–400	1500	0.1 K

Description: Delta from internal temperature to enable Open Thermistor check for FET thermistors

16.11.7.4 Cell Delta

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	Open Thermistor	Cell Delta	I2	0	–400	1500	0.1 K

Description: Delta from internal temperature to enable Open Thermistor check for cell thermistors

16.11.8 QIM—QMax Imbalance

16.11.8.1 Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	QIM	Threshold	I2	0	32767	100	0.10%

Description: QMax Imbalance trip threshold

16.11.8.2 Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	QIM	Delay	U1	0	255	2	updates

Description: QMax Imbalance trip delay

16.11.9 CB—Cell Balance

16.11.9.1 Max Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	CB	Max Threshold	I2	0	32767	120	2 h

Description: Cell Balance max trip threshold

16.11.9.2 Delta Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	CB	Delta Threshold	U1	0	255	20	2 h

Description: Cell Balance cell delta trip threshold

16.11.9.3 Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	CB	Delay	U1	0	255	2	cycles

Description: Cell Balance trip delay

16.11.10 VIMR—Voltage Imbalance At Rest

16.11.10.1 Check Voltage

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	VIMR	Check Voltage	I2	0	5000	3500	mV

Description: Voltage Imbalance At Rest Check Voltage

16.11.10.2 Check Current

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	VIMR	Check Current	I2	0	32767	10	mA

Description: Voltage Imbalance At Rest Check Current

16.11.10.3 Delta Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	VIMR	Delta Threshold	I2	0	5000	200	mV

Description: Voltage Imbalance At Rest trip threshold

16.11.10.4 Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	VIMR	Delay	U1	0	255	5	s

Description: Voltage Imbalance At Rest Check trip delay

16.11.10.5 Duration

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	VIMR	Duration	U2	0	65535	100	s

Description: Voltage Imbalance At Rest Check Duration

16.11.11 VIMA—Voltage Imbalance Active

16.11.11.1 Check Voltage

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	VIMA	Check Voltage	I2	0	5000	3700	mV

Description: Voltage Imbalance Active Check Voltage

16.11.11.2 Check Current

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	VIMA	Check Current	I2	0	32767	50	mA

Description: Voltage Imbalance Active Check Current

16.11.11.3 Delta Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	VIMA	Delta Threshold	I2	0	5000	300	mV

Description: Voltage Imbalance Active Trip Threshold

16.11.11.4 Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	VIMA	Delay	U1	0	255	5	s

Description: Voltage Imbalance Active Check Trip Delay

16.11.12 IMP—Impedance Imbalance

16.11.12.1 Delta Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	IMP	Delta Threshold	I2	0	32767	300	%

Description: Impedance Imbalance Delta Threshold

16.11.12.2 Max Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	IMP	Max Threshold	I2	0	32767	400	%

Description: Impedance Imbalance Max Threshold

16.11.12.3 Ra Update Counts

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	IMP	Ra Update Counts	U1	0	255	2	counts

Description: Impedance Imbalance Trip Delay

16.11.13 CD—Capacity Degradation

16.11.13.1 Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	CD	Threshold	I2	0	32767	4200	mAh

Description: Capacity Degradation Threshold

16.11.13.2 Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	CD	Delay	U1	0	255	2	cycles

Description: Capacity Degradation Trip Delay

16.11.14 CFET—CHG FET Failure

16.11.14.1 OFF Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	CFET	OFF Threshold	I2	0	500	5	mA

Description: CHG FET OFF current trip threshold

16.11.14.2 Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	CFET	Delay	U1	0	255	5	s

Description: CHG FET OFF trip delay

16.11.15 DFET—DFET Failure

16.11.15.1 OFF Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	DFET	OFF Threshold	I2	–500	0	–5	mA

Description: DSG FET OFF current trip threshold

16.11.15.2 Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	DFET	Delay	U1	0	255	5	s

Description: DSG FET OFF trip delay

16.11.16 FUSE—FUSE Failure

16.11.16.1 Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	FUSE	Threshold	I2	0	255	5	mA

Description: FUSE activation fail trip threshold

16.11.16.2 Delay

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	FUSE	Delay	U1	0	255	5	s

Description: FUSE activation fail trip delay

16.11.17 AFER—AFE Register

16.11.17.1 Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	AFER	Threshold	U1	0	255	100	—

Description: AFE Register comparison fail trip threshold

16.11.17.2 Delay Period

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	AFER	Delay Period	U1	0	255	5	s

Description: AFE Register comparison counter decrement period

16.11.17.3 Compare Period

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	AFER	Compare Period	U1	0	255	5	s

Description: AFE Register comparison compare period

16.11.18 AFEC—AFE Communication

16.11.18.1 Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	AFEC	Threshold	U1	0	255	100	—

Description: AFE Communication fail trip threshold

16.11.18.2 Delay Period

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	AFEC	Delay Period	U1	0	255	5	s

Description: AFE Communication counter decrement period

16.11.19 2LVL—2nd Level OV

Class	Subclass	Name	Type	Min	Max	Default	Unit
Permanent Fail	2LVL	Delay	U1	0	255	5	s

Description: 2nd Level Protector trip detection delay

16.12 PF Status

The data in this class is saved at the time of the PF event.

16.12.1 Device Status Data

16.12.1.1 Safety Alert A

Class	Subclass	Name	Type	Min	Max	Default	Units
PF Status	Device Status Data	Safety Alert A	H1	0x00	0xFF	0x00	Hex

Description: Accumulated safety flags since PF event

16.12.1.2 Safety Status A

Class	Subclass	Name	Type	Min	Max	Default	Units
PF Status	Device Status Data	Safety Status A	H1	0x00	0xFF	0x00	Hex

Description: Accumulated safety flags since PF event

16.12.1.3 Safety Alert B

Class	Subclass	Name	Type	Min	Max	Default	Units
PF Status	Device Status Data	Safety Alert B	H1	0x00	0xFF	0x00	Hex

Description: Accumulated safety flags since PF event

16.12.1.4 Safety Status B

Class	Subclass	Name	Type	Min	Max	Default	Units
PF Status	Device Status Data	Safety Status B	H1	0x00	0xFF	0x00	Hex

Description: Accumulated safety flags since PF event

16.12.1.5 Safety Alert C

Class	Subclass	Name	Type	Min	Max	Default	Units
PF Status	Device Status Data	Safety Alert C	H1	0x00	0xFF	0x00	Hex

Description: Accumulated safety flags since PF event

16.12.1.6 Safety Status C

Class	Subclass	Name	Type	Min	Max	Default	Units
PF Status	Device Status Data	Safety Status C	H1	0x00	0xFF	0x00	Hex

Description: Accumulated safety flags since PF event

16.12.1.7 Safety Alert D

Class	Subclass	Name	Type	Min	Max	Default	Units
PF Status	Device Status Data	Safety Alert D	H1	0x00	0xFF	0x00	Hex

Description: Accumulated safety flags since PF event

16.12.1.8 Safety Status D

Class	Subclass	Name	Type	Min	Max	Default	Units
PF Status	Device Status Data	Safety Status D	H1	0x00	0xFF	0x00	Hex

Description: Accumulated safety flags since PF event

16.12.1.9 PF Alert A

Class	Subclass	Name	Type	Min	Max	Default	Units
PF Status	Device Status Data	PF Alert A	H1	0x00	0xFF	0x00	Hex

Description: Accumulated PF flags since PF event

16.12.1.10 PF Status A

Class	Subclass	Name	Type	Min	Max	Default	Units
PF Status	Device Status Data	PF Status A	H1	0x00	0xFF	0x00	Hex

Description: Accumulated PF flags since PF event

16.12.1.11 PF Alert B

Class	Subclass	Name	Type	Min	Max	Default	Units
PF Status	Device Status Data	PF Alert B	H1	0x00	0xFF	0x00	Hex

Description: Accumulated PF flags since PF event

16.12.1.12 PF Status B

Class	Subclass	Name	Type	Min	Max	Default	Units
PF Status	Device Status Data	PF Status B	H1	0x00	0xFF	0x00	Hex

Description: Accumulated PF flags since PF event

16.12.1.13 PF Alert C

Class	Subclass	Name	Type	Min	Max	Default	Units
PF Status	Device Status Data	PF Alert C	H1	0x00	0xFF	0x00	Hex

Description: Accumulated PF flags since PF event

16.12.1.14 PF Status C

Class	Subclass	Name	Type	Min	Max	Default	Units
PF Status	Device Status Data	PF Status C	H1	0x00	0xFF	0x00	Hex

Description: Accumulated PF flags since PF event

16.12.1.15 PF Alert D

Class	Subclass	Name	Type	Min	Max	Default	Units
PF Status	Device Status Data	PF Alert D	H1	0x00	0xFF	0x00	Hex

Description: Accumulated PF flags since PF event

16.12.1.16 PF Status D

Class	Subclass	Name	Type	Min	Max	Default	Units
PF Status	Device Status Data	PF Status D	H1	0x00	0xFF	0x00	Hex

Description: Accumulated PF flags since PF event

16.12.1.17 Fuse Flag

Class	Subclass	Name	Type	Min	Max	Default	Units
PF Status	Device Status Data	Fuse Flag	H2	0x0000	0xFFFF	0x0000	Hex

Description: Flag set to indicate fuse blow

16.12.1.18 Operation Status A

Class	Subclass	Name	Type	Min	Max	Default	Units
PF Status	Device Status Data	Operation Status A	H2	0x0000	0xFFFF	0x0000	Hex

Description: *OperationStatus()* data at the time of the PF event

16.12.1.19 Operation Status B

Class	Subclass	Name	Type	Min	Max	Default	Units
PF Status	Device Status Data	Operation Status B	H2	0x0000	0xFFFF	0x0000	Hex

Description: *OperationStatus()* data at the time of the PF event

16.12.1.20 Temp Range

Class	Subclass	Name	Type	Min	Max	Default	Units
PF Status	Device Status Data	Temp Range	H1	0x00	0xFF	0x00	Hex

Description: Temperature range status at the time of the PF event. The temperature range information returned by *ChargingStatus()*

16.12.1.21 Charging Status A

Class	Subclass	Name	Type	Min	Max	Default	Units
PF Status	Device Status Data	Charging Status A	H1	0x00	0xFF	0x00	Hex

Description: The charging status at the time of the PF event. See *ManufacturerAccess() 0x0055 ChargingStatus* for the bit definitions.

7	6	5	4	3	2	1	0
VCT	MCHG	SU	IN	HV	MV	LV	PV

16.12.1.22 Charging Status B

Class	Subclass	Name	Type	Min	Max	Default	Units
PF Status	Device Status Data	Charging Status B	H1	0x00	0xFF	0x00	Hex

Description: The charging status at the time of the PF event. See *ManufacturerAccess() 0x0055 ChargingStatus*for the bit definitions.

7	6	5	4	3	2	1	0
VCT	RSVD	RSVD	RSVD	RSVD	CCC	CVR	CCR

16.12.1.23 Gauging Status

Class	Subclass	Name	Type	Min	Max	Default	Units
PF Status	Device Status Data	Gauging Status	H1	0x00	0xFF	0x00	Hex

Description: The gauging status at the time of the PF event. See *ManufacturerAccess() 0x0056 GaugingStatus* for bit definitions.

7	6	5	4	3	2	1	0
CF	DSG	EDV	BAL_EN	TCA	TDA	FC	FD

16.12.1.24 IT Status

Class	Subclass	Name	Type	Min	Max	Default	Units
PF Status	Device Status Data	IT Status	H2	0x0000	0xFFFF	0x0000	Hex

Description: The Impedance Track status at the time of the PF event. See *ManufacturerAccess() 0x0056 GaugingStatus* for the bit definitions.

15	14	13	12	11	10	9	8
RSVD	RSVD	SLPQ MAX	QEN	VOK	RDIS	RSVD	

7	6	5	4	3	2	1	0
RSVD	RSVD	RSVD	OCVFR	LDMD	RX	QMAX	VDQ

16.12.2 Device Voltage Data (at the Time of PF Event)

16.12.2.1 Cell 1 Voltage

Class	Subclass	Name	Type	Min	Max	Default	Unit
PF Status	Device Voltage Data	Cell 1 Voltage	I2	–32768	32767	0	mV

Description: Cell 1 voltage

16.12.2.2 Cell 2 Voltage

Class	Subclass	Name	Type	Min	Max	Default	Unit
PF Status	Device Voltage Data	Cell 2 Voltage	I2	–32768	32767	0	mV

Description: Cell 2 voltage

16.12.2.3 Cell 3 Voltage

Class	Subclass	Name	Type	Min	Max	Default	Unit
PF Status	Device Voltage Data	Cell 3 Voltage	I2	–32768	32767	0	mV

Description: Cell 3 voltage

16.12.2.4 Cell 4 Voltage

Class	Subclass	Name	Type	Min	Max	Default	Unit
PF Status	Device Voltage Data	Cell 4 Voltage	I2	–32768	32767	0	mV

Description: Cell 4 voltage

16.12.2.5 Battery Direct Voltage

Class	Subclass	Name	Type	Min	Max	Default	Unit
PF Status	Device Voltage Data	Battery Direct Voltage	I2	–32768	32767	0	mV

Description: Battery voltage

16.12.2.6 Pack Voltage

Class	Subclass	Name	Type	Min	Max	Default	Unit
PF Status	Device Voltage Data	Pack Voltage	I2	–32768	32767	0	mV

Description: PACK voltage

16.12.3 Device Current Data

Class	Subclass	Name	Type	Min	Max	Default	Unit
PF Status	Device Current Data	Current	I2	–32768	32767	0	mV

Description: *Current()*

16.12.4 Device Temperature Data (at the Time of PF Event)

16.12.4.1 Internal Temperature

Class	Subclass	Name	Type	Min	Max	Default	Unit
PF Status	Device Temperature Data	Internal Temperature	I2	–32768	32767	0	0.1 K

Description: Internal temperature sensor temperature

16.12.4.2 External 1 Temperature

Class	Subclass	Name	Type	Min	Max	Default	Unit
PF Status	Device Temperature Data	External 1 Temperature	I2	–32768	32767	0	0.1 K

Description: External TS1 temperature

16.12.4.3 External 2 Temperature

Class	Subclass	Name	Type	Min	Max	Default	Unit
PF Status	Device Temperature Data	External 2 Temperature	I2	–32768	32767	0	0.1 K

Description: External TS2 temperature

16.12.4.4 External 3 Temperature

Class	Subclass	Name	Type	Min	Max	Default	Unit
PF Status	Device Temperature Data	External 3 Temperature	I2	–32768	32767	0	0.1 K

Description: External TS3 temperature

16.12.4.5 External 4 Temperature

Class	Subclass	Name	Type	Min	Max	Default	Unit
PF Status	Device Temperature Data	External 4 Temperature	I2	–32768	32767	0	0.1 K

Description: External TS4 temperature

16.12.5 Device Gauging Data (at the Time of PF Event)

16.12.5.1 Cell 1DOD0

Class	Subclass	Name	Type	Min	Max	Default	Unit
PF Status	Device Gauging Data	Cell 1 DOD0	I2	–32768	32767	0	—

Description: Cell 1 depth of discharge

16.12.5.2 Cell 2 DOD0

Class	Subclass	Name	Type	Min	Max	Default	Unit
PF Status	Device Gauging Data	Cell 2 DOD0	I2	–32768	32767	0	—

Description: Cell 2 depth of discharge

16.12.5.3 Cell 3 DOD0

Class	Subclass	Name	Type	Min	Max	Default	Unit
PF Status	Device Gauging Data	Cell 3 DOD0	I2	–32768	32767	0	—

Description: Cell 3 depth of discharge

16.12.5.4 Cell 4 DOD0

Class	Subclass	Name	Type	Min	Max	Default	Unit
PF Status	Device Gauging Data	Cell 4 DOD0	I2	–32768	32767	0	—

Description: Cell 4 depth of discharge

16.12.5.5 Passed Charge

Class	Subclass	Name	Type	Min	Max	Default	Unit
PF Status	Device Gauging Data	Passed Charge	I2	–32768	32767	0	mAh

Description: Passed charge since last QMax update

16.12.6 AFE Regs

The ***AFE Regs*** data is intended for Texas Instruments' use to help with internal firmware diagnostics.

16.12.6.1 AFE Interrupt Status

Class	Subclass	Name	Type	Min	Max	Default	Unit
PF Status	AFE Regs	AFE Interrupt Status	H1	0x00	0xFF	0x00	Hex

Description: AFE Interrupt Status Register Contents

16.12.6.2 AFE FET Status

Class	Subclass	Name	Type	Min	Max	Default	Unit
PF Status	AFE Regs	AFE FET Status	H1	0x00	0xFF	0x00	Hex

Description: AFE FET Status Register Contents

16.12.6.3 AFE RXIN

Class	Subclass	Name	Type	Min	Max	Default	Unit
PF Status	AFE Regs	AFE RXIN	H1	0x00	0xFF	0x00	Hex

Description: AFE Rxin Register Contents

16.12.6.4 AFE Latch Status

Class	Subclass	Name	Type	Min	Max	Default	Unit
PF Status	AFE Regs	AFE Latch Status	H1	0x00	0xFF	0x00	Hex

Description: AFE Latch Status Register Contents

16.12.6.5 AFE Interrupt Enable

Class	Subclass	Name	Type	Min	Max	Default	Unit
PF Status	AFE Regs	AFE Interrupt Enable	H1	0x00	0xFF	0x00	Hex

Description: AFE Interrupt Enable Register Contents

16.12.6.6 AFE FET Control

Class	Subclass	Name	Type	Min	Max	Default	Unit
PF Status	AFE Regs	AFE FET Control	H1	0x00	0xFF	0x00	Hex

Description: AFE FET Control Register Contents

16.12.6.7 AFE RXIEN

Class	Subclass	Name	Type	Min	Max	Default	Unit
PF Status	AFE Regs	AFE RXIEN	H1	0x00	0xFF	0x00	Hex

Description: AFE RXIEN Register Contents

16.12.6.8 AFE RLOUT

Class	Subclass	Name	Type	Min	Max	Default	Unit
PF Status	AFE Regs	AFE RLOUT	H1	0x00	0xFF	0x00	Hex

Description: AFE RLOUT Register Contents

16.12.6.9 AFE RHOUT

Class	Subclass	Name	Type	Min	Max	Default	Unit
PF Status	AFE Regs	AFE RHOUT	H1	0x00	0xFF	0x00	Hex

Description: AFE RHOUT Register Contents

16.12.6.10 AFE RHINT

Class	Subclass	Name	Type	Min	Max	Default	Unit
PF Status	AFE Regs	AFE RHINT	H1	0x00	0xFF	0x00	Hex

Description: AFE RHINT Register Contents

16.12.6.11 AFE Cell Balance

Class	Subclass	Name	Type	Min	Max	Default	Unit
PF Status	AFE Regs	AFE Cell Balance	H1	0x00	0xFF	0x00	Hex

Description: AFE Cell Balance Register Contents

16.12.6.12 AFE AD/CC Control

Class	Subclass	Name	Type	Min	Max	Default	Unit
PF Status	AFE Regs	AFE AD/CC Control	H1	0x00	0xFF	0x00	Hex

Description: AFE AD/CC Control Register Contents

16.12.6.13 AFE ADC Mux

Class	Subclass	Name	Type	Min	Max	Default	Unit
PF Status	AFE Regs	AFE ADC Mux	H1	0x00	0xFF	0x00	Hex

Description: AFE ADC Mux Register Contents

16.12.6.14 AFE LED Output

Class	Subclass	Name	Type	Min	Max	Default	Unit
PF Status	AFE Regs	AFE LED Output	H1	0x00	0xFF	0x00	Hex

Description: AFE LED Output Register Contents

16.12.6.15 AFE State Control

Class	Subclass	Name	Type	Min	Max	Default	Unit
PF Status	AFE Regs	AFE State Control	H1	0x00	0xFF	0x00	Hex

Description: AFE State Control Register Contents

16.12.6.16 AFE LED/Wake Control

Class	Subclass	Name	Type	Min	Max	Default	Unit
PF Status	AFE Regs	AFE LED/Wake Control	H1	0x00	0xFF	0x00	Hex

Description: AFE LED/Wake Control Register Contents

16.12.6.17 AFE Protection Control

Class	Subclass	Name	Type	Min	Max	Default	Unit
PF Status	AFE Regs	AFE Protection Control	H1	0x00	0xFF	0x00	Hex

Description: AFE Protection Control Register Contents

16.12.6.18 AFE OCD

Class	Subclass	Name	Type	Min	Max	Default	Unit
PF Status	AFE Regs	AFE OCD	H1	0x00	0xFF	0x00	Hex

Description: AFE OCD Register Contents

16.12.6.19 AFE SCC

Class	Subclass	Name	Type	Min	Max	Default	Unit
PF Status	AFE Regs	AFE SCC	H1	0x00	0xFF	0x00	Hex

Description: AFE SCC Register Contents

16.12.6.20 AFE SCD1

Class	Subclass	Name	Type	Min	Max	Default	Unit
PF Status	AFE Regs	AFE SCD1	H1	0x00	0xFF	0x00	Hex

Description: AFE SCD1 Register Contents

16.12.6.21 AFE SCD2

Class	Subclass	Name	Type	Min	Max	Default	Unit
PF Status	AFE Regs	AFE SCD2	H1	0x00	0xFF	0x00	Hex

Description: AFE SCD2 Register Contents

16.13 Black Box

16.13.1 Safety Status

Class	Subclass	Name	Type	Min	Max	Default	Unit	Description
Black Box	Safety Status	1st Status Status A	H1	0x00	0xFF	0x00	Hex	*SafetyStatus()* data
Black Box	Safety Status	1st Status Status B	H1	0x00	0xFF	0x00	Hex	*SafetyStatus()* data
Black Box	Safety Status	1st Safety Status C	H1	0x00	0xFF	0x00	Hex	*SafetyStatus()* data
Black Box	Safety Status	1st Safety Status D	H1	0x00	0xFF	0x00	Hex	*SafetyStatus()* data
Black Box	Safety Status	1st Time to Next Event	U1	0	255	0	s	Time from 1st event to 2nd event
Black Box	Safety Status	2nd Status Status A	H1	0x00	0xFF	0x00	Hex	*SafetyStatus()* data
Black Box	Safety Status	2nd Status Status B	H1	0x00	0xFF	0x00	Hex	*SafetyStatus()* data
Black Box	Safety Status	2nd Safety Status C	H1	0x00	0xFF	0x00	Hex	*SafetyStatus()* data
Black Box	Safety Status	2nd Safety Status D	H1	0x00	0xFF	0x00	Hex	*SafetyStatus()* data
Black Box	Safety Status	2nd Time to Next Event	U1	0	255	0	s	Time from 2nd event to 3rd event
Black Box	Safety Status	3rd Status Status A	H1	0x00	0xFF	0x00	Hex	*SafetyStatus()* data
Black Box	Safety Status	3rd Status Status B	H1	0x00	0xFF	0x00	Hex	*SafetyStatus()* data
Black Box	Safety Status	3rd Safety Status C	H1	0x00	0xFF	0x00	Hex	*SafetyStatus()* data
Black Box	Safety Status	3rd Safety Status D	H1	0x00	0xFF	0x00	Hex	*SafetyStatus()* data
Black Box	Safety Status	3rd Time to Next Event	U1	0	255	0	s	Time since 3rd event

16.13.2 PF Status

Class	Subclass	Name	Type	Min	Max	Default	Unit	Description
Black Box	PF Status	1st PF Status A	H1	0x00	0xFF	0x00	Hex	*PFStatus()* data
Black Box	PF Status	1st PF Status B	H1	0x00	0xFF	0x00	Hex	*PFStatus()* data
Black Box	PF Status	1st PF Status C	H1	0x00	0xFF	0x00	Hex	*PFStatus()* data
Black Box	PF Status	1st PF Status D	H1	0x00	0xFF	0x00	Hex	*PFStatus()* data
Black Box	PF Status	1st Time to Next Event	U1	0	255	0	s	Time from 1st event to 2nd event
Black Box	PF Status	2nd PF Status A	H1	0x00	0xFF	0x00	Hex	*PFStatus()* data
Black Box	PF Status	2nd PF Status B	H1	0x00	0xFF	0x00	Hex	*PFStatus()* data
Black Box	PF Status	2nd PF Status C	H1	0x00	0xFF	0x00	Hex	*PFStatus()* data
Black Box	PF Status	2nd PF Status D	H1	0x00	0xFF	0x00	Hex	*PFStatus()* data
Black Box	PF Status	2nd Time to Next Event	U1	0	255	0	s	Time from 2nd event to 3rd event
Black Box	PF Status	3rd PF Status A	H1	0x00	0xFF	0x00	Hex	*PFStatus()* data

Class	Subclass	Name	Type	Min	Max	Default	Unit	Description
Black Box	PF Status	3rd PF Status B	H1	0x00	0xFF	0x00	Hex	*PFStatus()* data
Black Box	PF Status	3rd PF Status C	H1	0x00	0xFF	0x00	Hex	*PFStatus()* data
Black Box	PF Status	3rd PF Status D	H1	0x00	0xFF	0x00	Hex	*PFStatus()* data
Black Box	PF Status	3rd Time to Next Event	U1	0	255	0	s	Time since 3rd event

16.14 Gas Gauging

16.14.1 Current Thresholds

16.14.1.1 Dsg Current Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	Current Thresholds	Dsg Current Threshold	I2	–32768	32767	100	mA

Description: DISCHARGE mode *Current()* threshold

16.14.1.2 Chg Current Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	Current Thresholds	Chg Current Threshold	I2	–32768	32767	50	mA

Description: CHARGE mode *Current()* threshold

16.14.1.3 Quit Current

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	Current Thresholds	Quit Current	I2	0	32767	10	mA

Description: |*Current()*| threshold to enter rest mode

16.14.1.4 Dsg Relax Time

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	Current Thresholds	Dsg Relax Time	U1	0	255	1	s

Description: Discharge to relax timeout. When discharge is stopped, the device will exit the DISCHARGE mode after this time is passed.

16.14.1.5 Chg Relax Time

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	Current Thresholds	Chg Relax Time	U1	0	255	60	s

Description: Charge to relax timeout. When charging is stopped, the device will exit the CHARGE mode after this time is passed.

16.14.2 Design

16.14.2.1 Design Capacity mAh

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	Design	Design Capacity mAh	I2	0	32767	4400	mAh

Description: ***Design Capacity*** in mAh. This is reported by *DesignCapacity()* if ***[CAPM]*** = 0.

16.14.2.2 Design Capacity in cWh

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	Design	Design Capacity cWh	I2	0	32767	6336	cWh

Description: ***Design Capacity*** in cWh. This is reported by *DesignCapacity()* if ***[CAPM]*** = 1.

16.14.2.3 Design Voltage

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	Design	Design Voltage	I2	0	32767	14400	mV

Description: Design Voltage. This is reported by *DesignVoltage()*.

16.14.3 Cycle

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	Cycle	Cycle Count Percentage	U1	0	100	90	%

Description: This threshold increments the cycle count if the accumulated discharge is more than this set percentage of *FullChargeCapacity()* (if ***[CCT]*** = 1) or *DesignCapacity()* (if ***[CCT]*** = 0).

NOTE: A minimum of 10% of *DesignCapacity()* change of the accumulated discharge is required for cycle count increment. This is to prevent an erroneous cycle count increment due to extremely low *FullChargeCapacity()*.

16.14.4 FD

16.14.4.1 Set Voltage Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	FD	Set Voltage Threshold	I2	0	5000	3000	mV

Description: *GaugingStatus()[FD]* and *BatteryStatus()[FD]* cell voltage set threshold

16.14.4.2 Clear Voltage Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	FD	Clear Voltage Threshold	I2	0	5000	3100	mV

Description: *GaugingStatus()[FD]* and *BatteryStatus()[FD]* cell voltage clear threshold

16.14.4.3 Set RSOC % Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	FD	Set RSOC % Threshold	U1	0	100	0	%

Description: *GaugingStatus()[FD]* and *BatteryStatus()[FD] RelativeStateOfCharge()* set threshold

16.14.4.4 Clear RSOC % Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	FD	Clear RSOC % Threshold	U1	0	100	5	%

Description: *GaugingStatus()[FD]* and *BatteryStatus()[FD] RelativeStateOfCharge()* clear threshold

16.14.5 FC

16.14.5.1 Set Voltage Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	FC	Set Voltage Threshold	I2	0	5000	4200	mV

Description: *GaugingStatus()[FC]* and *BatteryStatus()[FC]* cell voltage set threshold

16.14.5.2 Clear Voltage Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	FC	Clear Voltage Threshold	I2	0	5000	4100	mV

Description: *GaugingStatus()[FC]* and *BatteryStatus()[FC]* cell voltage clear threshold

16.14.5.3 Set RSOC % Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	FC	Set RSOC % Threshold	U1	0	100	100	%

Description: *GaugingStatus()[FC]* and *BatteryStatus()[FC] RelativeStateOfCharge()* set threshold

16.14.5.4 Clear RSOC % Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	FC	Clear RSOC % Threshold	U1	0	100	95	%

Description: *GaugingStatus()[FC]* and *BatteryStatus()[FC] RelativeStateOfCharge()* clear threshold

16.14.6 TD

GaugingStatus()[TD] sets *BatteryStatus()[TDA]* when in DISCHARGE mode.

16.14.6.1 Set Voltage Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	TD	Set Voltage Threshold	I2	0	5000	3200	mV

Description: *GaugingStatus()[TD]* cell voltage set threshold

16.14.6.2 Clear Voltage Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	TD	Clear Voltage Threshold	I2	0	5000	3300	mV

Description: *GaugingStatus()[TD]* cell voltage clear threshold

16.14.6.3 Set RSOC % Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	TD	Set RSOC % Threshold	U1	0	100	6	%

Description: *GaugingStatus()[TD] RelativeStateOfCharge()* set threshold

16.14.6.4 Clear RSOC % Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	TD	Clear RSOC % Threshold	U1	0	100	8	%

Description: *GaugingStatus()[TD] RelativeStateOfCharge()* clear threshold

16.14.7 TC

GaugingStatus()[TC] sets *BatteryStatus()[TCA]* when in CHARGE mode

16.14.7.1 Set Voltage Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	TC	Set Voltage Threshold	I2	0	5000	4200	mV

Description: *GaugingStatus()[TC]* cell voltage set threshold

16.14.7.2 Clear Voltage Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	TC	Clear Voltage Threshold	I2	0	5000	4100	mV

Description: *GaugingStatus()[TC]* cell voltage clear threshold

16.14.7.3 Set RSOC % Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	TC	Set RSOC % Threshold	U1	0	100	100	%

Description: *GaugingStatus()[TC] RelativeStateOfCharge()* set threshold

16.14.7.4 Clear RSOC % Threshold

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	TC	Clear RSOC % Threshold	U1	0	100	95	%

Description: *GaugingStatus()[TC] RelativeStateOfCharge()* clear threshold

16.14.8 State

16.14.8.1 QMax

Class	Subclass	Name	Type	Min	Max	Default	Unit	Description
Gas Gauging	State	QMax Cell 1	I2	0	32767	4400	mAh	QMax Cell 1
Gas Gauging	State	QMax Cell 2	I2	0	32767	4400	mAh	QMax Cell 2
Gas Gauging	State	QMax Cell 3	I2	0	32767	4400	mAh	QMax Cell 3
Gas Gauging	State	QMax Cell 4	I2	0	32767	4400	mAh	QMax Cell 4
Gas Gauging	State	QMax Pack	I2	0	32767	4400	mAh	QMax of the whole stack
Gas Gauging	State	Qmax Cycle Count	U2	0	65535	0	—	The *CycleCount()* when Qmax updated

16.14.8.2 Update Status

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	State	Update Status	H1	0x00	0x0E	0x00	Hex

7	6	5	4	3	2	1	0
RSVD	RSVD	RSVD	RSVD	QMax	Enable	Update1	Update0

RSVD (Bits 7–4): Reserved. Do not use.

QMax update in the field (Bit 3)

1 = Updated

0 = Not updated

Enable (Bit 2): Impedance Track gauging and lifetime updating enable

1 = Enabled

0 = Disabled

Update1, Update0 (Bits 1–0): Update Status

0,0 = Impedance Track gauging and lifetime updating is disabled.

0,1 = QMax updated

1,0 = QMax and Ra table have been updated.

16.14.8.3 Cell 1–4 Chg Voltage at EoC

16.14.8.3.1 Cell 1 Chg Voltage at EoC

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	State	Cell 1 Chg Voltage at EoC	I2	0	32767	4200	mV

Description: Cell 1 voltage value at end of charge

16.14.8.3.2 Cell 2 Chg Voltage at EoC

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	State	Cell 2 Chg Voltage at EoC	I2	0	32767	4200	mV

Description: Cell 2 voltage value at end of charge

16.14.8.3.3 Cell 3 Chg Voltage at EoC

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	State	Cell 3 Chg Voltage at EoC	I2	0	32767	4200	mV

Description: Cell 3 voltage value at end of charge

16.14.8.3.4 Cell 4 Chg Voltage at EoC

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	State	Cell 4 Chg Voltage at EoC	I2	0	32767	4200	mV

Description: Cell 4 voltage value at end of charge

16.14.8.4 Current at EoC

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	State	Current at EoC	I2	0	32767	250	mA

Description: Current at end of charge

16.14.8.5 Average Last Run

16.14.8.5.1 Avg I Last Run

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	State	Avg I Last Run	I2	–32768	32767	–2000	mA

Description: Average current last discharge cycle

16.14.8.5.2 Avg P Last Run

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	State	Avg P Last Run	I2	–32768	32767	–3022	10 mW

Description: Average power last discharge cycle

16.14.8.6 Delta Voltage

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	State	Delta Voltage	I2	–32768	32767	0	mV

Description: *Voltage()* delta between normal and short load spikes to optimize run time calculation

16.14.8.7 Temp

16.14.8.7.1 Temp k

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	State	Temp k	I2	0	32767	100	0.1°C/ 2560 mW

Description: Initial thermal model temperature factor

16.14.8.7.2 Temp a

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	State	Temp a	I2	0	32767	1000	—

Description: Initial thermal model temperature

16.14.8.8 Max Avg Last Run

16.14.8.8.1 Max Avg I Last Run

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	State	Max Avg I Last Run	I2	–32768	32767	–2000	mA

Description: Max current last discharge cycle

16.14.8.8.2 Max Avg P Last Run

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	State	Max Avg P Last Run	I2	–32768	32767	–3022	cW

Description: Max power last discharge cycle

16.14.9 Cycle Count

Class	Subclass	Name	Type	Min	Max	Default	Unit	Description
Gas Gauging	State	Cycle Count	U2	0	65535	0	—	Cycle Count

Description: Value reported by *CycleCount()*. The gauge updates this automatically when accumulated discharge exceeds the threshold set by ***Cycle Count Percentage***.

16.14.10 IT Config

16.14.10.1 Load Select

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	IT Cfg	Load Select	U1	0	7	7	—

Description: Defines load compensation mode used by the gauging algorithm

16.14.10.2 Fast Scale Load Select

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	IT Cfg	Fast Scale Load Select	U1	0	7	3	—

Description: Defines load compensation mode used by the gauging algorithm in the fast scaling region

16.14.10.3 Load Mode

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	IT Cfg	Load Mode	U1	0	1	0	—

Description: Defines unit used by the gauging algorithm:

1 = Constant Power

0 = Constant Current

16.14.10.4 Design Resistance

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	IT Cfg	Design Resistance	I2	1	32767	42	mΩ

Description: Averaged cell resistance at ***Reference Grid*** point. This is automatically updated when the gauge sets ***Update Status*** to 0x6. To automatically update again, set ***Update Status*** to 0x4 or manually set when ***Update Status*** is set to 0x6.

16.14.10.5 User Rate-mA

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	IT Cfg	User Rate-mA	I2	–9000	0	0	mA

Description: Discharge rate used for capacity calculation selected by ***Load Select*** = 6

16.14.10.6 User Rate-cW

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	IT Cfg	User Rate-cW	I2	–32768	0	0	cW

Description: Discharge rate used for capacity calculation selected by ***Load Select*** = 6

16.14.10.7 Reserve Cap-mAh

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	IT Cfg	Reserve Cap-mAh	I2	0	9000	0	mAh

Description: Capacity reserved available when the gauging algorithm reports 0% *RelativeStateOfCharge()*. The gauge predicts to report a capacity of 0 when approximately ***Reserve Cap-mAh*** remains. This parameter is used when Load Mode = 0 and predictions are made assuming a constant current load.

16.14.10.8 Reserve Cap-cWh

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	IT Cfg	Reserve Cap-cWh	I2	0	32000	0	cWh

Description: Capacity reserved available when the gauging algorithm reports 0% *RelativeStateOfCharge()*. The gauge predicts to report a capacity of 0 when approximately ***Reserve Cap-cWh*** remains. This parameter is used when Load Mode = 1 and predictions are made using a constant power load.

16.14.10.9 Resistance Update Voltage

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	IT Cfg	Resistance Update Voltage	I2	0	32767	50	mV

Description: The difference between the voltage based on DoD and the measured voltage is estimated as the IR drop. If this IR drop is less than the value in this register, then the resistance calculation is not done and the resistance table is not updated.

16.14.10.10 Ra Filter

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	IT Cfg	Ra Filter	U2	0	999	500	%

Description: Filter value used in Ra Updates and specifies what percentage or Ra update is from the new value (100% setting) versus the old value (setting). The recommended setting is 80% if the ***[RSOC_CONV]*** feature is enabled. Otherwise, the setting should be 50% as default.

16.14.10.11 Ra Max Delta

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	IT Cfg	Ra Max Delta	U1	0	255	15	%

Description: Maximum value of allowed Ra change

16.14.10.12 Reference Grid

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	IT Cfg	Reference Grid	U1	0	14	4	—

Description: ***Reference Grid*** point used by ***Design Resistance***. The default setting should be used if the ***[RSOC_CONV]*** feature is enabled. Otherwise, grid point 11 should be used to ensure resistance updates fast enough at the grid where discharge termination occurs.

16.14.10.13 Resistance Parameter Filter

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	IT Cfg	Resistance Parameter Filter	U2	1	65535	65142	—

Description: This is one of the filters used for a resistance update. Reducing this filter setting can improve low temperature performance at high rates. The default setting is 41 s.

It is recommended to keep this filter within the range of 4 s (DF setting = 61680) up to the default 41 s (DF setting = 65142). Examining the ***Term Voltage Delta*** setting and ***Fast Scale Start SOC*** should be done prior to adjusting this parameter when trying to improve the RSOC performance.

The following is the formula to convert the DF setting into the actual filter time constant in units of seconds:

Filter time constant = [0.25 / (1 – (DF_Value / 65536))] – 0.25.

16.14.10.14 Near EDV Ra Param Filter

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	IT Cfg	Near EDV Ra Param Filter	U2	1	65535	59220	—

Description: Ra filter used in the fast scaling region if ***[FF_NEAR_EDV]*** = 1. Default value should be used.

16.14.10.15 Cell 1..4 Interconnect Resistance

16.14.10.15.1 Cell 1 Interconnect Resistance

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	IT Cfg	Cell 1 Interconnect Resistance	I2	0	32767	0	mΩ

Description: This is the interconnect resistance value entered by the user that represents the interconnect resistance between the negative rail and the bottom of Cell 1, plus the interconnect resistance of the connection from the bottom of the first cell to the gauge. The measured *CellVoltage1()* is compensated for the voltage drop introduced by this resistance.

16.14.10.15.2 Cell 2 Interconnect Resistance

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	IT Cfg	Cell 2 Interconnect Resistance	I2	0	32767	0	mΩ

Description: This is the interconnect resistance value entered by the user that represents the interconnect resistance between the top of Cell 1 and the bottom of the Cell 2, plus the interconnect resistance of the connection from the bottom of Cell 2 to the gauge. The measured *CellVoltage2()* is compensated for the voltage drop introduced by this resistance.

16.14.10.15.3 Cell 3 Interconnect Resistance

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	IT Cfg	Cell 3 Interconnect Resistance	I2	0	32767	0	mΩ

Description: This is the interconnect resistance value entered by the user that represents the interconnect resistance between the top of Cell 2 and the bottom of the Cell 3, plus the interconnect resistance of the connection from the bottom of Cell 3 to the gauge. The measured *CellVoltage3()* is compensated for the voltage drop introduced by this resistance.

16.14.10.15.4 Cell 4 Interconnect Resistance

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	IT Cfg	Cell 4 Interconnect Resistance	I2	0	32767	0	mΩ

Description: This is the interconnect resistance value entered by the user that represents the interconnect resistance between the top of Cell 3 and the bottom of the Cell 4, plus the interconnect resistance of the connection from the bottom of Cell 4 to the gauge. The measured *CellVoltage4()* is compensated for the voltage drop introduced by this resistance.

16.14.10.16 Max Current Change %

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	IT Cfg	Max Current Change %	U1	0	100	10	%

Description: Close to the end of discharge, if the change in current exceeds this threshold, the resistance update and Ra scale update are not allowed to prevent incorrect FCC drops.

16.14.10.17 Qmax Delta

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	IT Cfg	Qmax Delta	U1	3	100	5	%

Description: Maximum allowed Qmax change from its previous value. The Qmax change will be capped by this setting if the delta from the previous Qmax is larger than ***Qmax Delta***. ***Qmax Delta*** is a percentage of ***Design Capacity***.

16.14.10.18 Qmax Upper Bound

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	IT Cfg	Qmax Upper Bound	U1	100	255	130	%

Description: Maximum Qmax value over the lifetime of the pack. If the updated Qmax value is larger than this setting, the updated Qmax will be capped to ***Qmax Upper Bound***. ***Qmax Upper Bound*** is a percentage of ***Design Capacity***.

16.14.10.19 Term Voltage

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	IT Cfg	Term Voltage	I2	0	32767	9000	mV

Description: Min stack voltage to be used for capacity calculation

16.14.10.20 Term Voltage Delta

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	IT Cfg	Term Voltage Delta	I2	0	32767	300	mV

Description: Controls when the ***[RSOC_CONV]*** feature becomes active. The recommended setting is 3.3 – ***Term Voltage***/Number Cells.

The default setting is 300 mV, which is assuming a typical 3-V termination voltage per cell. If a different termination voltage is used, this parameter should be adjusted accordingly.

16.14.10.21 Simulation Near Term Delta

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	IT Cfg	Simulation Near Term Delta	I2	0	32767	250	mV

Description: Voltage delta from ***Term Voltage***, which defines "near EDV" for IT simulations. If ***Term Voltage*** is increased, ***Simulation Near Term Delta*** should be decreased to keep ***Term Voltage*** + ***Simulation Near Term Delta*** around 3.2 V–3.5 V, the knee of the discharge curve.

16.14.10.22 Term Min Cell V

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	IT Cfg	Term Min Cell V	I2	0	32767	2800	mV

Description: Minimum cell termination voltage used when ***[CELL_TERM]*** = 1. This is intended to enable the IT algorithm to reach 0% before CUV is triggered; therefore, this value should be set at or above ***CUV:Threshold***.

16.14.10.23 Fast Scale Start SOC

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	IT Cfg	Fast Scale Start SOC	U1	0	100	10	%

Description: Controls the start of convergence when ***[RSOC_CONV]*** = 1 based on RSOC %. Raising this setting can improve the RSOC drop at the end of discharge. However, the RSOC % chosen for this setting must be kept after the sharp drop of the discharge curve (the knee of the discharge curve).

16.14.10.24 Pack Resistance

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	IT Cfg	Pack Resistance	I2	0	32767	30	mΩ

Description: Pack-side resistance value accessed using *TURBO_PACK_R()*

16.14.10.25 Max Simulation Iterations

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	IT Cfg	Max Simulation Iterations	U1	20	50	30	—

Description: ***Max Simulation Iterations*** enables the user to set the max number of simulation iterations IT is allowed to do. If the user finds that the watchdog is tripping, this number can be lowered. The default is set at the optimal setting of 30. For 4-series cell applications, a setting of 50 is not recommended.

16.14.10.26 System Resistance

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	IT Cfg	System Resistance	I2	0	32767	0	mΩ

Description: System side resistance value accessed using *TURBO_SYS_R()*

16.14.10.27 DeltaV Max Voltage Delta

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	IT Cfg	DeltaV Max Voltage Delta	I2	–32767	32767	10	mV

Description: This sets the maximum bound of how much DeltaV can change.

16.14.10.28 Smoothing

16.14.10.28.1 Smooth Relax Time

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	Smoothing	Smooth Relax Time	I2	1	32767	1000	s

Description: If ***[RELAX_SMOOTH_OK]*** = 1, the delta remaining capacity and full charge capacity are smoothed over this set period of time. It is recommended to use the default setting.

16.14.10.28.2 Term Smooth Start Cell V Delta

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	Smoothing	Term Smooth Start Cell V Delta	I2	0	32767	150	mV

Description: If the config bit ***[DSG_0_SMOOTH_OK]*** is set, then during discharge and once the pack voltage is below the threshold defined in this register, time-based smoothing is initiated. This will smooth RemCap to 0 mAh over the next ***Term Smooth Time*** seconds. ***Term Smooth Start Cell V Delta*** is a per cell voltage delta. This value is multiplied by the number of cells, added to ***Terminate Voltage***, and checked against *Voltage()*. Smoothing will continue to 0% unless charging starts (even in RELAX mode).

16.14.10.28.3 Term Smooth Time

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	Smoothing	Term Smooth Time	U1	1	32767	20	s

Description: If the config bit ***[DSG_0_SMOOTH_OK]*** is set, then during discharge and once the pack voltage is below the threshold defined in ***Term Smooth Start Cell V Delta***, time-based smoothing is initiated. This will smooth RemCap to 0 mAh over the next ***Term Smooth Time*** seconds.

16.14.10.28.4 Term Smooth Final Cell V Delta

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	Smoothing	Term Smooth Final Cell V Delta	I2	0	32767	100	mV

Description: If the config bit ***[DSG_0_SMOOTH_OK]*** is set, then during discharge and once the conditions for smoothing are reached, smoothing to 0 is initiated. To assure that the gauge reports 0% in low voltage situations, ***Term Smooth Final Cell V Delta*** is used. This value is multiplied by the number of cells, subtracted from ***Terminate Voltage***, and checked against *Voltage()*. Once voltage passes this threshold, 0% will be forced even if smoothing has not completed.

NOTE: This DF can be disabled by setting it to 0, and is typically expected to be set low enough to enable the system to shut down properly (without brownout).

16.14.11 Condition Flag

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	Condition Flag	Max Error Limit	U1	0	100	100	%

Description: Max Error Limit Percentage

16.14.12 Max Error

16.14.12.1 Time Cycle Equivalent

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	Max Error	Time Cycle Equivalent	U1	1	255	12	2 h

Description: After valid QMax update, each passed time period of ***Time Cycle Equivalent*** will increment of *MaxError()* by ***Cycle Delta***.

16.14.12.2 Cycle Delta

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	Max Error	Cycle Delta	U1	0	255	5	0.01%

Description: Each increment of *CycleCount()* after a valid QMax update will increment of *MaxError()* by ***Cycle Delta***. Setting this parameter to 0 disables the *MaxError()* increment by time or cycle increment.

16.14.13 SOH

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	SOH	SOH Load Rate	U1	1	255	50	0.1 h rate

Description: Current rate used in SOH simulation specified in hour-rate (that is, current = C/***SOH Load Rate***)

16.14.14 Turbo Cfg

16.14.14.1 Min System Voltage

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	Turbo Cfg	Min System Voltage	I2	–32768	32767	9000	mV

Description: This is the minimum required system voltage on the battery pack terminals to be used for TURBO mode.

16.14.14.2 Ten Second Max C-Rate

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	Turbo Cfg	Ten Second Max C-Rate	I1	–127	0	–20	0.1 C-rate

Description: This value specifies the maximal discharge current for 10 s.

16.14.14.3 Ten Millisecond Max C-Rate

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	Turbo Cfg	Ten Millisecond Max C-Rate	I1	–127	0	–40	0.1 C-rate

Description: This value specifies the maximal discharge current for 10 ms.

16.14.14.4 Turbo Adjustment Factor

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	Turbo Cfg	Turbo Adjustment Factor	U1	0.5	1.5	1.00	—

Description: This is a resistance correction factor that, if used, would be a one-time adjustment the user computes from a 10-s pulse test.

16.14.14.5 Reserve Energy %

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	Turbo Cfg	Reserve Energy %	I1	0	100	2	%

Description: This is the remaining energy at present average discharge rate (as defined in ***Load Select***) until the maximal peak power reaches the value reported by *MaxPeakPower()*.

16.14.14.6 High Frequency Resistance

Class	Subclass	Name	Type	Min	Max	Default	Unit
Gas Gauging	Turbo Cfg	High Frequency Resistance	I2	0	32767	20	mΩ

Description: This is the high-frequency resistance related to the specific cell chemistry and pack configuration.

16.15 RA Table

16.15.1 R_a0

Class	Subclass	Name	Type	Min	Max	Default	Unit
RA Table	R_a0	Cell 0 R_A Flag	H2	0x0000	0xFFFF	0xFF55	Hex

Description:
This value indicates the validity of the cell impedance table for ***Cell 1***. It is recommended not to change this value manually.

High Byte		Low Byte	
0x00	Cell impedance and QMax updated	0x00	The table is not used and QMax is updated.
0x05	RELAX mode and QMax update in progress	0x55	The table is used.
0x55	DISCHARGE mode and cell impedance updated	0xFF	The table is never used; no QMax or cell impedance update.
0xFF	Cell impedance never updated		

The gauge stores and updates the impedance profile for ***Cell 1***, as shown in the following table:

Class	Subclass	Name	Type	Min	Max	Default	Unit	Description
RA Table	R_a0	Cell 0 R_A 0	I2	0	32767	38	2^{-10} Ω	Cell 0 resistance at grid point 0
RA Table	R_a0	Cell 0 R_A 1	I2	0	32767	41	2^{-10} Ω	Cell 0 resistance at grid point 1
RA Table	R_a0	Cell 0 R_A 2	I2	0	32767	43	2^{-10} Ω	Cell 0 resistance at grid point 2
RA Table	R_a0	Cell 0 R_A 3	I2	0	32767	44	2^{-10} Ω	Cell 0 resistance at grid point 3
RA Table	R_a0	Cell 0 R_A 4	I2	0	32767	42	2^{-10} Ω	Cell 0 resistance at grid point 4
RA Table	R_a0	Cell 0 R_A 5	I2	0	32767	42	2^{-10} Ω	Cell 0 resistance at grid point 5
RA Table	R_a0	Cell 0 R_A 6	I2	0	32767	45	2^{-10} Ω	Cell 0 resistance at grid point 6
RA Table	R_a0	Cell 0 R_A 7	I2	0	32767	48	2^{-10} Ω	Cell 0 resistance at grid point 7
RA Table	R_a0	Cell 0 R_A 8	I2	0	32767	49	2^{-10} Ω	Cell 0 resistance at grid point 8
RA Table	R_a0	Cell 0 R_A 9	I2	0	32767	52	2^{-10} Ω	Cell 0 resistance at grid point 9
RA Table	R_a0	Cell 0 R_A 10	I2	0	32767	56	2^{-10} Ω	Cell 0 resistance at grid point 10
RA Table	R_a0	Cell 0 R_A 11	I2	0	32767	64	2^{-10} Ω	Cell 0 resistance at grid point 11
RA Table	R_a0	Cell 0 R_A 12	I2	0	32767	74	2^{-10} Ω	Cell 0 resistance at grid point 12
RA Table	R_a0	Cell 0 R_A 13	I2	0	32767	128	2^{-10} Ω	Cell 0 resistance at grid point 13
RA Table	R_a0	Cell 0 R_A 14	I2	0	32767	378	2^{-10} Ω	Cell 0 resistance at grid point 14

16.15.2 R_a1

Class	Subclass	Name	Type	Min	Max	Default	Unit
RA Table	R_a1	Cell 1 R_A Flag	H2	0x0000	0xFFFF	0xFF55	Hex

Description:
This value indicates the validity of the cell impedance table for Cell 2. It is recommended not to change this value manually.

High Byte		Low Byte	
0x00	Cell impedance and QMax updated	0x00	The table is not used and QMax is updated.
0x05	RELAX mode and QMax update in progress	0x55	The table is used.
0x55	DISCHARGE mode and cell impedance updated	0xFF	The table is never used; no QMax or cell impedance update.
0xFF	Cell impedance never updated		

The gauge stores and updates the impedance profile for ***Cell 2***, as shown in the following table:

Class	Subclass	Name	Type	Min	Max	Default	Unit	Description
RA Table	R_a1	Cell 1 R_A 0	I2	–32768	32768	38	2^{-10} Ω	Cell 1 resistance at grid point 0
RA Table	R_a1	Cell 1 R_A 1	I2	–32768	32768	41	2^{-10} Ω	Cell 1 resistance at grid point 1
RA Table	R_a1	Cell 1 R_A 2	I2	–32768	32768	43	2^{-10} Ω	Cell 1 resistance at grid point 2
RA Table	R_a1	Cell 1 R_A 3	I2	–32768	32768	44	2^{-10} Ω	Cell 1 resistance at grid point 3
RA Table	R_a1	Cell 1 R_A 4	I2	–32768	32768	42	2^{-10} Ω	Cell 1 resistance at grid point 4
RA Table	R_a1	Cell 1 R_A 5	I2	–32768	32768	42	2^{-10} Ω	Cell 1 resistance at grid point 5
RA Table	R_a1	Cell 1 R_A 6	I2	–32768	32768	45	2^{-10} Ω	Cell 1 resistance at grid point 6
RA Table	R_a1	Cell 1 R_A 7	I2	–32768	32768	48	2^{-10} Ω	Cell 1 resistance at grid point 7
RA Table	R_a1	Cell 1 R_A 8	I2	–32768	32768	49	2^{-10} Ω	Cell 1 resistance at grid point 8
RA Table	R_a1	Cell 1 R_A 9	I2	–32768	32768	52	2^{-10} Ω	Cell 1 resistance at grid point 9
RA Table	R_a1	Cell 1 R_A 10	I2	–32768	32768	56	2^{-10} Ω	Cell 1 resistance at grid point 10
RA Table	R_a1	Cell 1 R_A 11	I2	–32768	32768	64	2^{-10} Ω	Cell 1 resistance at grid point 11
RA Table	R_a1	Cell 1 R_A 12	I2	–32768	32768	74	2^{-10} Ω	Cell 1 resistance at grid point 12
RA Table	R_a1	Cell 1 R_A 13	I2	–32768	32768	128	2^{-10} Ω	Cell 1 resistance at grid point 13
RA Table	R_a1	Cell 1 R_A 14	I2	–32768	32768	378	2^{-10} Ω	Cell 1 resistance at grid point 14

16.15.3 R_a2

Class	Subclass	Name	Type	Min	Max	Default	Unit
RA Table	R_a2	Cell 2 R_A Flag	H2	0x0000	0xFFFF	0xFF55	Hex

Description:
This value indicates the validity of the cell impedance table for Cell 3. It is recommended not to change this value manually.

High Byte		Low Byte	
0x00	Cell impedance and QMax updated	0x00	The table is not used and QMax is updated.
0x05	RELAX mode and QMax update in progress	0x55	The table is used.
0x55	DISCHARGE mode and cell impedance updated	0xFF	The table is never used; no QMax or cell impedance update.
0xFF	Cell impedance never updated		

The gauge stores and updates the impedance profile for Cell 3, as shown in the following table:

Class	Subclass	Name	Type	Min	Max	Default	Unit	Description
RA Table	R_a2	Cell 2 R_A 0	I2	–32768	32768	38	2^{-10} Ω	Cell 2 resistance at grid point 0
RA Table	R_a2	Cell 2 R_A 1	I2	–32768	32768	41	2^{-10} Ω	Cell 2 resistance at grid point 1
RA Table	R_a2	Cell 2 R_A 2	I2	–32768	32768	43	2^{-10} Ω	Cell 2 resistance at grid point 2
RA Table	R_a2	Cell 2 R_A 3	I2	–32768	32768	44	2^{-10} Ω	Cell 2 resistance at grid point 3

Class	Subclass	Name	Type	Min	Max	Default	Unit	Description
RA Table	R_a2	Cell 2 R_A 4	I2	–32768	32768	42	2^{-10} Ω	Cell 2 resistance at grid point 4
RA Table	R_a2	Cell 2 R_A 5	I2	–32768	32768	42	2^{-10} Ω	Cell 2 resistance at grid point 5
RA Table	R_a2	Cell 2 R_A 6	I2	–32768	32768	45	2^{-10} Ω	Cell 2 resistance at grid point 6
RA Table	R_a2	Cell 2 R_A 7	I2	–32768	32768	48	2^{-10} Ω	Cell 2 resistance at grid point 7
RA Table	R_a2	Cell 2 R_A 8	I2	–32768	32768	49	2^{-10} Ω	Cell 2 resistance at grid point 8
RA Table	R_a2	Cell 2 R_A 9	I2	–32768	32768	52	2^{-10} Ω	Cell 2 resistance at grid point 9
RA Table	R_a2	Cell 2 R_A 10	I2	–32768	32768	56	2^{-10} Ω	Cell 2 resistance at grid point 10
RA Table	R_a2	Cell 2 R_A 11	I2	–32768	32768	64	2^{-10} Ω	Cell 2 resistance at grid point 11
RA Table	R_a2	Cell 2 R_A 12	I2	–32768	32768	74	2^{-10} Ω	Cell 2 resistance at grid point 12
RA Table	R_a2	Cell 2 R_A 13	I2	–32768	32768	128	2^{-10} Ω	Cell 2 resistance at grid point 13
RA Table	R_a2	Cell 2 R_A 14	I2	–32768	32768	378	2^{-10} Ω	Cell 2 resistance at grid point 14

16.15.4 R_a3

Class	Subclass	Name	Type	Min	Max	Default	Unit
RA Table	R_a3	Cell 3 R_A Flag	H2	0x0000	0xFFFF	0xFF55	Hex

Description:
This value indicates the validity of the cell impedance table for Cell 4. It is recommended not to change this value manually.

High Byte		Low Byte	
0x00	Cell impedance and QMax updated	0x00	The table is not used and QMax is updated.
0x05	RELAX mode and QMax update in progress	0x55	The table is used.
0x55	DISCHARGE mode and cell impedance updated	0xFF	The table is never used; no QMax or cell impedance update.
0xFF	Cell impedance never updated		

The gauge stores and updates the impedance profile for Cell 4, as shown in the following table:

Class	Subclass	Name	Type	Min	Max	Default	Unit	Description
RA Table	R_a3	Cell 3 R_A 0	I2	–32768	32768	38	2^{-10} Ω	Cell 3 resistance at grid point 0
RA Table	R_a3	Cell 3 R_A 1	I2	–32768	32768	41	2^{-10} Ω	Cell 3 resistance at grid point 1
RA Table	R_a3	Cell 3 R_A 2	I2	–32768	32768	43	2^{-10} Ω	Cell 3 resistance at grid point 2
RA Table	R_a3	Cell 3 R_A 3	I2	–32768	32768	44	2^{-10} Ω	Cell 3 resistance at grid point 3
RA Table	R_a3	Cell 3 R_A 4	I2	–32768	32768	42	2^{-10} Ω	Cell 3 resistance at grid point 4
RA Table	R_a3	Cell 3 R_A 5	I2	–32768	32768	42	2^{-10} Ω	Cell 3 resistance at grid point 5
RA Table	R_a3	Cell 3 R_A 6	I2	–32768	32768	45	2^{-10} Ω	Cell 3 resistance at grid point 6
RA Table	R_a3	Cell 3 R_A 7	I2	–32768	32768	48	2^{-10} Ω	Cell 3 resistance at grid point 7
RA Table	R_a3	Cell 3 R_A 8	I2	–32768	32768	49	2^{-10} Ω	Cell 3 resistance at grid point 8
RA Table	R_a3	Cell 3 R_A 9	I2	–32768	32768	52	2^{-10} Ω	Cell 3 resistance at grid point 9
RA Table	R_a3	Cell 3 R_A 10	I2	–32768	32768	56	2^{-10} Ω	Cell 3 resistance at grid point 10
RA Table	R_a3	Cell 3 R_A 11	I2	–32768	32768	64	2^{-10} Ω	Cell 3 resistance at grid point 11
RA Table	R_a3	Cell 3 R_A 12	I2	–32768	32768	74	2^{-10} Ω	Cell 3 resistance at grid point 12
RA Table	R_a3	Cell 3 R_A 13	I2	–32768	32768	128	2^{-10} Ω	Cell 3 resistance at grid point 13
RA Table	R_a3	Cell 3 R_A 14	I2	–32768	32768	378	2^{-10} Ω	Cell 3 resistance at grid point 14

16.15.5 R_a0x

Class	Subclass	Name	Type	Min	Max	Default	Unit
RA Table	R_a0x	xCell 0 R_A Flag	H2	0x0000	0xFFFF	0xFFFF	Hex

Description:
This value indicates the validity of the cell impedance table for ***Cell 1***. It is recommended not to change this value manually.

High Byte		Low Byte	
0x00	Cell impedance and QMax updated	0x00	The table is not used and QMax is updated.
0x05	RELAX mode and QMax update in progress	0x55	The table is used.
0x55	DISCHARGE mode and cell impedance updated	0xFF	The table is never used; no QMax or cell impedance update.
0xFF	Cell impedance never updated		

The gauge stores and updates the impedance profile for ***Cell 1***, as shown in the following table:

Class	Subclass	Name	Type	Min	Max	Default	Unit	Description
RA Table	R_a0x	xCell 0 R_A 0	I2	–32768	32768	38	$2^{-10}\ \Omega$	Cell 0 resistance at grid point 0
RA Table	R_a0x	xCell 0 R_A 1	I2	–32768	32768	41	$2^{-10}\ \Omega$	Cell 0 resistance at grid point 1
RA Table	R_a0x	xCell 0 R_A 2	I2	–32768	32768	43	$2^{-10}\ \Omega$	Cell 0 resistance at grid point 2
RA Table	R_a0x	xCell 0 R_A 3	I2	–32768	32768	44	$2^{-10}\ \Omega$	Cell 0 resistance at grid point 3
RA Table	R_a0x	xCell 0 R_A 4	I2	–32768	32768	42	$2^{-10}\ \Omega$	Cell 0 resistance at grid point 4
RA Table	R_a0x	xCell 0 R_A 5	I2	–32768	32768	42	$2^{-10}\ \Omega$	Cell 0 resistance at grid point 5
RA Table	R_a0x	xCell 0 R_A 6	I2	–32768	32768	45	$2^{-10}\ \Omega$	Cell 0 resistance at grid point 6
RA Table	R_a0x	xCell 0 R_A 7	I2	–32768	32768	48	$2^{-10}\ \Omega$	Cell 0 resistance at grid point 7
RA Table	R_a0x	xCell 0 R_A 8	I2	–32768	32768	49	$2^{-10}\ \Omega$	Cell 0 resistance at grid point 8
RA Table	R_a0x	xCell 0 R_A 9	I2	–32768	32768	52	$2^{-10}\ \Omega$	Cell 0 resistance at grid point 9
RA Table	R_a0x	xCell 0 R_A 10	I2	–32768	32768	56	$2^{-10}\ \Omega$	Cell 0 resistance at grid point 10
RA Table	R_a0x	xCell 0 R_A 11	I2	–32768	32768	64	$2^{-10}\ \Omega$	Cell 0 resistance at grid point 11
RA Table	R_a0x	xCell 0 R_A 12	I2	–32768	32768	74	$2^{-10}\ \Omega$	Cell 0 resistance at grid point 12
RA Table	R_a0x	xCell 0 R_A 13	I2	–32768	32768	128	$2^{-10}\ \Omega$	Cell 0 resistance at grid point 13
RA Table	R_a0x	xCell 0 R_A 14	I2	–32768	32768	378	$2^{-10}\ \Omega$	Cell 0 resistance at grid point 14

16.15.6 R_a1x

Class	Subclass	Name	Type	Min	Max	Default	Unit
RA Table	R_a1x	xCell 1 R_A Flag	H2	0x0000	0xFFFF	0xFFFF	Hex

Description:
This value indicates the validity of the cell impedance table for ***Cell 2***. It is recommended not to change this value manually.

High Byte		Low Byte	
0x00	Cell impedance and QMax updated	0x00	The table is not used and QMax is updated.
0x05	RELAX mode and QMax update in progress	0x55	The table is used.
0x55	DISCHARGE mode and cell impedance updated	0xFF	The table is never used; no QMax or cell impedance update.

High Byte		Low Byte	
0xFF	Cell impedance never updated		

The gauge stores and updates the impedance profile for ***Cell 2***, as shown in the following table:

Class	Subclass	Name	Type	Min	Max	Default	Unit	Description
RA Table	R_a1x	xCell 1 R_A 0	I2	–32768	32768	38	2^{-10} Ω	Cell 1 resistance at grid point 0
RA Table	R_a1x	xCell 1 R_A 1	I2	–32768	32768	41	2^{-10} Ω	Cell 1 resistance at grid point 1
RA Table	R_a1x	xCell 1 R_A 2	I2	–32768	32768	43	2^{-10} Ω	Cell 1 resistance at grid point 2
RA Table	R_a1x	xCell 1 R_A 3	I2	–32768	32768	44	2^{-10} Ω	Cell 1 resistance at grid point 3
RA Table	R_a1x	xCell 1 R_A 4	I2	–32768	32768	42	2^{-10} Ω	Cell 1 resistance at grid point 4
RA Table	R_a1x	xCell 1 R_A 5	I2	–32768	32768	42	2^{-10} Ω	Cell 1 resistance at grid point 5
RA Table	R_a1x	xCell 1 R_A 6	I2	–32768	32768	45	2^{-10} Ω	Cell 1 resistance at grid point 6
RA Table	R_a1x	xCell 1 R_A 7	I2	–32768	32768	48	2^{-10} Ω	Cell 1 resistance at grid point 7
RA Table	R_a1x	xCell 1 R_A 8	I2	–32768	32768	49	2^{-10} Ω	Cell 1 resistance at grid point 8
RA Table	R_a1x	xCell 1 R_A 9	I2	–32768	32768	52	2^{-10} Ω	Cell 1 resistance at grid point 9
RA Table	R_a1x	xCell 1 R_A 10	I2	–32768	32768	56	2^{-10} Ω	Cell 1 resistance at grid point 10
RA Table	R_a1x	xCell 1 R_A 11	I2	–32768	32768	64	2^{-10} Ω	Cell 1 resistance at grid point 11
RA Table	R_a1x	xCell 1 R_A 12	I2	–32768	32768	74	2^{-10} Ω	Cell 1 resistance at grid point 12
RA Table	R_a1x	xCell 1 R_A 13	I2	–32768	32768	128	2^{-10} Ω	Cell 1 resistance at grid point 13
RA Table	R_a1x	xCell 1 R_A 14	I2	–32768	32768	378	2^{-10} Ω	Cell 1 resistance at grid point 14

16.15.7 R_a2x

Class	Subclass	Name	Type	Min	Max	Default	Unit
RA Table	R_a2x	xCell 2 R_A Flag	H2	0x0000	0xFFFF	0xFFFF	Hex

Description:
This value indicates the validity of the cell impedance table for Cell 3. It is recommended not to change this value manually.

High Byte		Low Byte	
0x00	Cell impedance and QMax updated	0x00	The table is not used and QMax is updated.
0x05	RELAX mode and QMax update in progress	0x55	The table is used.
0x55	DISCHARGE mode and cell impedance updated	0xFF	The table is never used; no QMax or cell impedance update.
0xFF	Cell impedance never updated		

The gauge stores and updates the impedance profile for ***Cell 3***, as shown in the following table:

Class	Subclass	Name	Type	Min	Max	Default	Unit	Description
RA Table	R_a2x	xCell 2 R_A 0	I2	–32768	32768	38	2^{-10} Ω	Cell 2 resistance at grid point 0
RA Table	R_a2x	xCell 2 R_A 1	I2	–32768	32768	41	2^{-10} Ω	Cell 2 resistance at grid point 1
RA Table	R_a2x	xCell 2 R_A 2	I2	–32768	32768	43	2^{-10} Ω	Cell 2 resistance at grid point 2
RA Table	R_a2x	xCell 2 R_A 3	I2	–32768	32768	44	2^{-10} Ω	Cell 2 resistance at grid point 3
RA Table	R_a2x	xCell 2 R_A 4	I2	–32768	32768	42	2^{-10} Ω	Cell 2 resistance at grid point 4
RA Table	R_a2x	xCell 2 R_A 5	I2	–32768	32768	42	2^{-10} Ω	Cell 2 resistance at grid point 5
RA Table	R_a2x	xCell 2 R_A 6	I2	–32768	32768	45	2^{-10} Ω	Cell 2 resistance at grid point 6
RA Table	R_a2x	xCell 2 R_A 7	I2	–32768	32768	48	2^{-10} Ω	Cell 2 resistance at grid point 7

Class	Subclass	Name	Type	Min	Max	Default	Unit	Description
RA Table	R_a2x	xCell 2 R_A 8	I2	–32768	32768	49	2^{-10} Ω	Cell 2 resistance at grid point 8
RA Table	R_a2x	xCell 2 R_A 9	I2	–32768	32768	52	2^{-10} Ω	Cell 2 resistance at grid point 9
RA Table	R_a2x	xCell 2 R_A 10	I2	–32768	32768	56	2^{-10} Ω	Cell 2 resistance at grid point 10
RA Table	R_a2x	xCell 2 R_A 11	I2	–32768	32768	64	2^{-10} Ω	Cell 2 resistance at grid point 11
RA Table	R_a2x	xCell 2 R_A 12	I2	–32768	32768	74	2^{-10} Ω	Cell 2 resistance at grid point 12
RA Table	R_a2x	xCell 2 R_A 13	I2	–32768	32768	128	2^{-10} Ω	Cell 2 resistance at grid point 13
RA Table	R_a2x	xCell 2 R_A 14	I2	–32768	32768	378	2^{-10} Ω	Cell 2 resistance at grid point 14

16.15.8 R_a3x

Class	Subclass	Name	Type	Min	Max	Default	Unit
RA Table	R_a3x	xCell 3 R_A Flag	H2	0x0000	0xFFFF	0xFFFF	Hex

Description:
This value indicates the validity of the cell impedance table for ***Cell 4***. It is recommended not to change this value manually.

High Byte		Low Byte	
0x00	Cell impedance and QMax updated	0x00	The table is not used and QMax is updated.
0x05	RELAX mode and QMax update in progress	0x55	The table is used.
0x55	DISCHARGE mode and cell impedance updated	0xFF	The table is never used; no QMax or cell impedance update.
0xFF	Cell impedance never updated		

The gauge stores and updates the impedance profile for ***Cell 4***, as shown in the following table:

Class	Subclass	Name	Type	Min	Max	Default	Unit	Description
RA Table	R_a3x	xCell 3 R_A 0	I2	–32768	32768	38	2^{-10} Ω	Cell 3 resistance at grid point 0
RA Table	R_a3x	xCell 3 R_A 1	I2	–32768	32768	41	2^{-10} Ω	Cell 3 resistance at grid point 1
RA Table	R_a3x	xCell 3 R_A 2	I2	–32768	32768	43	2^{-10} Ω	Cell 3 resistance at grid point 2
RA Table	R_a3x	xCell 3 R_A 3	I2	–32768	32768	44	2^{-10} Ω	Cell 3 resistance at grid point 3
RA Table	R_a3x	xCell 3 R_A 4	I2	–32768	32768	42	2^{-10} Ω	Cell 3 resistance at grid point 4
RA Table	R_a3x	xCell 3 R_A 5	I2	–32768	32768	42	2^{-10} Ω	Cell 3 resistance at grid point 5
RA Table	R_a3x	xCell 3 R_A 6	I2	–32768	32768	45	2^{-10} Ω	Cell 3 resistance at grid point 6
RA Table	R_a3x	xCell 3 R_A 7	I2	–32768	32768	48	2^{-10} Ω	Cell 3 resistance at grid point 7
RA Table	R_a3x	xCell 3 R_A 8	I2	–32768	32768	49	2^{-10} Ω	Cell 3 resistance at grid point 8
RA Table	R_a3x	xCell 3 R_A 9	I2	–32768	32768	52	2^{-10} Ω	Cell 3 resistance at grid point 9
RA Table	R_a3x	xCell 3 R_A 10	I2	–32768	32768	56	2^{-10} Ω	Cell 3 resistance at grid point 10
RA Table	R_a3x	xCell 3 R_A 11	I2	–32768	32768	64	2^{-10} Ω	Cell 3 resistance at grid point 11
RA Table	R_a3x	xCell 3 R_A 12	I2	–32768	32768	74	2^{-10} Ω	Cell 3 resistance at grid point 12
RA Table	R_a3x	xCell 3 R_A 13	I2	–32768	32768	128	2^{-10} Ω	Cell 3 resistance at grid point 13
RA Table	R_a3x	xCell 3 R_A 14	I2	–32768	32768	378	2^{-10} Ω	Cell 3 resistance at grid point 14

16.16 SBS Configuration

16.16.1 Data

16.16.1.1 Remaining Capacity Alarm

16.16.1.1.1 Remaining Ah Capacity Alarm

Class	Subclass	Name	Type	Min	Max	Default	Unit
SBS Configuration	Data	Remaining Ah Capacity Alarm	U2	0	700	300	mAh

Description: *RemainingCapacityAlarm()* value in mAh

16.16.1.1.2 Remaining Wh Capacity Alarm

Class	Subclass	Name	Type	Min	Max	Default	Unit
SBS Configuration	Data	Remaining Wh Capacity Alarm	U2	0	1000	432	cWh

Description: *RemainingCapacityAlarm()* value in cWh

16.16.1.2 RemainingTimeAlarm

Class	Subclass	Name	Type	Min	Max	Default	Unit
SBS Configuration	Data	Remaining Time Alarm	U2	0	30	10	min

Description: *RemainingTimeAlarm()* value

16.16.1.3 Initial Battery Mode

Class	Subclass	Name	Type	Min	Max	Default	Unit
SBS Configuration	Data	Initial Battery Mode	H2	0x0000	0xFFFF	0x0081	Hex

15	14	13	12	11	10	9	8
CAPM	CHGM	AM	RSVD	RSVD	RSVD	PB	CC

7	6	5	4	3	2	1	0
CF	RSVD	RSVD	RSVD	RSVD	RSVD	PBS	ICC

CAPM (Bit 15): Capacity_Mode (R/W)

1 = Report in cW or cWh

0 = Report in mA or mAh (default)

CHGM (Bit 14): Charger_Mode (R/W)

1 = Disables *ChargingVoltage()* and *ChargingCurrent()* broadcasts to the host and smart battery charger (default)

0 = Enables *ChargingVoltage()* and *ChargingCurrent()* broadcasts to the host and smart battery charger

AM (Bit 13): ALARM Mode (R/W)

1 = Disables *AlarmWarning()* broadcasts to the host and smart battery charger

0 = Enables *AlarmWarning()* broadcasts to the host and smart battery charger (default)

RSVD (Bits 12–10): Reserved. Do not use.

PB (Bit 9): Primary_Battery (R/W)

1 = Battery operating in its primary role

0 = Battery operating in its secondary role (default)

CC (Bit 8): Charge_Controller_Enabled (R/W)

1 = Internal charge control enabled

0 = Internal charge control disabled (default)

CF (Bit 7): Condition_Flag (R)

1 = Conditioning cycle requested

0 = Battery is okay.

RSVD (Bits 6–2): Reserved. Do not use.

PBS (Bit 1): Primary_Battery_Support (R)

1 = Primary or secondary battery support

0 = Function is not supported. (default)

ICC (Bit 0): Internal_Charge_Controller (R)

1 = Function is supported.

0 = Function is not supported. (default)

16.16.1.4 Specification Information

Class	Subclass	Name	Type	Min	Max	Default	Unit
SBS Configuration	Data	Specification Information	H2	0x0000	0xFFFF	0x0031	Hex

15	14	13	12	11	10	9	8
IPScale	IPScale	IPScale	IPScale	VScale	VScale	VScale	VScale

7	6	5	4	3	2	1	0
Version	Version	Version	Version	Revision	Revision	Revision	Revision

SpecificationInformation() values

IPScale (Bits 15–12): IP Scale Factor

0,0,0,0 = Reported currents and capacities scaled by 10E0 except *ChargingVoltage()* and *ChargingCurrent()*

0,0,0,1 = Reported currents and capacities scaled by 10E1 except *ChargingVoltage()* and *ChargingCurrent()*

0,0,1,0 = Reported currents and capacities scaled by 10E2 except *ChargingVoltage()* and *ChargingCurrent()*

0,0,1,1 = Reported currents and capacities scaled by 10E3 except *ChargingVoltage()* and *ChargingCurrent()*

VScale (Bits 11–8): Voltage Scale Factor

0,0,0,0 = Reported voltages scaled by 10E0

0,0,0,1 = Reported voltages scaled by 10E1

0,0,1,0 = Reported voltages scaled by 10E2

0,0,1,1 = Reported voltages scaled by 10E3

Version (Bits 7–4): Version

0,0,0,1 = Version 1.0

0,0,1,1 = Version 1.1

0,0,1,1 = Version 1.1 with optional PEC support

Revision (Bits 3–0): Revision

0,0,0,1 = Version 1.0 and 1.1 (default)

16.16.1.5 Manufacturer Date

Class	Subclass	Name	Type	Min	Max	Default	Unit
SBS Configuration	Data	Manufacturer Date	U2	0	65535	01/01/80	Date

Description: *ManufacturerDate()* value in the following format: Day + Month×32 + (Year–1980) × 512

16.16.1.6 Serial Number

Class	Subclass	Name	Type	Min	Max	Default	Unit
SBS Configuration	Data	Serial Number	H2	0x0000	0xFFFF	0x0001	Hex

Description: *SerialNumber()* value

16.16.1.7 Manufacturer Name

Class	Subclass	Name	Type	Min	Max	Default	Unit
SBS Configuration	Data	Manufacturer Name	S20+1	—	—	Texas Instruments	ASCII

Description: *ManufacturerName()* value

16.16.1.8 Device Name

Class	Subclass	Name	Type	Min	Max	Default	Unit
SBS Configuration	Data	Device Name	S20+1	—	—	bq40z50-R3	ASCII

Description: *DeviceName()* value

16.16.1.9 Device Chemistry

Class	Subclass	Name	Type	Min	Max	Default	Unit
SBS Configuration	Data	Device Chemistry	S4+1	—	—	LION	ASCII

Description: *DeviceChemistry()* value

16.17 Data Flash Summary

Table 16-1. Data Flash Table

Class	Subclass	Address	Name	Type	Min Value	Max Value	Default	Units
Calibration	Voltage	0x4000	Cell Gain	I2	–32767	32767	12101	—
Calibration	Voltage	0x4002	Pack Gain	U2	0	65535	49669	—
Calibration	Voltage	0x4004	BAT Gain	U2	0	65535	48936	—
Calibration	Current	0x4006	CC Gain	F4	1.00E–01	4.00E+00	3.58422	—
Calibration	Current	0x400A	Capacity Gain	F4	2.98262E+04	1.193046E+06	1069035.256	—
Calibration	Current Offset	0x400E	CC Offset	I2	–32767	32767	0	—

Table 16-1. Data Flash Table (continued)

Class	Subclass	Address	Name	Type	Min Value	Max Value	Default	Units
Calibration	Current Offset	0x4010	Coulomb Counter Offset Samples	U2	0	65535	64	—
Calibration	Current Offset	0x4012	Board Offset	I2	–32768	32767	0	—
Calibration	Current Offset	0x40C0	CC Auto Config	H1	0x00	0x07	0x03	Hex
Calibration	Current Offset	0x40C1	CC Auto Offset	I2	–10000	10000	0	—
Calibration	Temperature	0x4014	Internal Temp Offset	I1	–128	127	0	0.1°C
Calibration	Temperature	0x4015	External1 Temp Offset	I1	–128	127	0	0.1°C
Calibration	Temperature	0x4016	External2 Temp Offset	I1	–128	127	0	0.1°C
Calibration	Temperature	0x4017	External3 Temp Offset	I1	–128	127	0	0.1°C
Calibration	Temperature	0x4018	External4 Temp Offset	I1	–128	127	0	0.1°C
Calibration	Internal Temp Model	0x4800	Int Gain	I2	–32768	32767	–12143	—
Calibration	Internal Temp Model	0x4802	Int base offset	I2	–32768	32767	6232	—
Calibration	Internal Temp Model	0x4804	Int Minimum AD	I2	–32768	32767	0	—
Calibration	Internal Temp Model	0x4806	Int Maximum Temp	I2	0	32767	6232	0.1 K
Calibration	Cell Temperature Model	0x4808	Coeff a1	I2	–32768	32767	–11130	—
Calibration	Cell Temperature Model	0x480A	Coeff a2	I2	–32768	32767	19142	—
Calibration	Cell Temperature Model	0x480C	Coeff a3	I2	–32768	32767	–19262	—
Calibration	Cell Temperature Model	0x480E	Coeff a4	I2	–32768	32767	28203	—
Calibration	Cell Temperature Model	0x4810	Coeff a5	I2	–32768	32767	892	—
Calibration	Cell Temperature Model	0x4812	Coeff b1	I2	–32768	32767	328	—
Calibration	Cell Temperature Model	0x4814	Coeff b2	I2	–32768	32767	–605	—
Calibration	Cell Temperature Model	0x4816	Coeff b3	I2	–32768	32767	–2443	—
Calibration	Cell Temperature Model	0x4818	Coeff b4	I2	–32768	32767	4696	—
Calibration	Cell Temperature Model	0x481A	Rc0	I2	–32768	32767	11703	—
Calibration	Cell Temperature Model	0x481C	Adc0	I2	–32768	32767	11703	—
Calibration	Cell Temperature Model	0x481E	Rpad	I2	–32768	32767	0	—
Calibration	Cell Temperature Model	0x4820	Rint	I2	–32768	32767	0	—
Calibration	Fet Temperature Model	0x4822	Coeff a1	I2	–32768	32767	–11130	—
Calibration	Fet Temperature Model	0x4824	Coeff a2	I2	–32768	32767	19142	—
Calibration	Fet Temperature Model	0x4826	Coeff a3	I2	–32768	32767	–19262	—
Calibration	Fet Temperature Model	0x4828	Coeff a4	I2	–32768	32767	28203	—
Calibration	Fet Temperature Model	0x482A	Coeff a5	I2	–32768	32767	892	—
Calibration	Fet Temperature Model	0x482C	Coeff b1	I2	–32768	32767	328	—
Calibration	Fet Temperature Model	0x482E	Coeff b2	I2	–32768	32767	–605	—
Calibration	Fet Temperature Model	0x4830	Coeff b3	I2	–32768	32767	–2443	—

Table 16-1. Data Flash Table (continued)

Class	Subclass	Address	Name	Type	Min Value	Max Value	Default	Units
Calibration	Fet Temperature Model	0x4832	Coeff b4	I2	–32768	32767	4696	—
Calibration	Fet Temperature Model	0x4834	Rc0	I2	–32768	32767	11703	—
Calibration	Fet Temperature Model	0x4836	Adc0	I2	–32768	32767	11703	—
Calibration	Fet Temperature Model	0x4838	Rpad	I2	–32768	32767	0	—
Calibration	Fet Temperature Model	0x483A	Rint	I2	–32768	32767	0	—
Calibration	Current Deadband	0x4846	Deadband	U1	0	255	3	mA
Calibration	Current Deadband	0x4847	Coulomb Counter Deadband	U1	0	255	9	116 nV
Calibration	Interconnect Resistance	0x4EC0	Cell 1	I2	0	1000	0	mΩ
Calibration	Interconnect Resistance	0x4EC2	Cell 2	I2	0	1000	0	mΩ
Calibration	Interconnect Resistance	0x4EC4	Cell 3	I2	0	1000	0	mΩ
Calibration	Interconnect Resistance	0x4EC6	Cell 4	I2	0	1000	0	mΩ
Settings	Configuration	0x4A89	FET Options	H2	0x0	0x00FF	0x0020	Hex
Settings	Configuration	0x4A8B	Sbs Gauging Configuration	H2	0x0	0x001F	0x0004	Hex
Settings	Configuration	0x4A8D	Sbs Configuration	H2	0x0	0x00FF	0x0020	Hex
Settings	Configuration	0x4A8F	Auth Config	H1	0x0	0x04	0x00	Hex
Settings	Configuration	0x4A90	Power Config	H2	0x0	0x3FBF	0x0000	Hex
Settings	Configuration	0x4A92	IO Config	H2	0x0	0x000F	0x0000	Hex
Settings	Configuration	0x4A98	GPIO Sealed Access Config	H2	0x0	0x000F	0x0000	Hex
Settings	Configuration	0x4A9A	Flag Map Set Up 1	H2	0x0000	0xFFFF	0x0000	Hex
Settings	Configuration	0x4A9C	Flag Map Set Up 2	H2	0x0000	0xFFFF	0x0000	Hex
Settings	Configuration	0x4A9E	Flag Map Set Up 3	H2	0x0000	0xFFFF	0x0000	Hex
Settings	Configuration	0x4AA0	Flag Map Set Up 4	H2	0x0000	0xFFFF	0x0000	Hex
Settings	Configuration	0x4B00	LED Configuration	H2	0x0	0x0FFF	0x00D0	Hex
Settings	Configuration	0x4C08	SOC Flag Config A	H2	0x0	0x0FFF	0x0C8C	Hex
Settings	Configuration	0x4C0A	SOC Flag Config B	H2	0x0	0x00FF	0x008C	Hex
Settings	Configuration	0x4C40	Balancing Configuration	H2	0x0	0x00FF	0x0001	Hex
Settings	Configuration	0x4C80	IT Gauging Configuration	H2	0x0	0xFFFF	0xD0FE	Hex
Settings	Configuration	0x4C84	IT Gauging Ext	H2	0x0000	0x00FF	0x005A	Hex
Settings	Configuration	0x4DC0	Charging Configuration	H2	0x0	0xFFFF	0x0	Hex
Settings	Configuration	0x4E40	Temperature Enable	H1	0x0	0x1F	0x06	Hex
Settings	Configuration	0x4E41	Temperature Mode	H1	0x0	0x1F	0x04	Hex
Settings	Configuration	0x4E42	DA Configuration	H2	0x0	0xFFFF	0x0012	Hex
Settings	Configuration	0x4F00	Elevated Degrade Configuration	H1	0x0	0xFF	0x15	Hex
Settings	Fuse	0x4A80	PF Fuse A	H1	0x0	0xFF	0x0	Hex
Settings	Fuse	0x4A81	PF Fuse B	H1	0x0	0xFF	0x0	Hex
Settings	Fuse	0x4A82	PF Fuse C	H1	0x0	0xFF	0x0	Hex
Settings	Fuse	0x4A83	PF Fuse D	H1	0x0	0xFF	0x0	Hex
Settings	Fuse	0x4A84	Min Blow Fuse Voltage	I2	0	65535	3500	mV
Settings	Fuse	0x4A86	Fuse Blow Timeout	U1	0	255	30	s
Settings	Fuse	0x4A87	GPIO Timeout	U2	0	65535	30	s
Settings	BTP	0x4A94	Init Discharge Set	I2	0	32767	150	mAh
Settings	BTP	0x4A96	Init Charge Set	I2	0	32767	175	mAh
Settings	SMBus	0x4AA2	Address	H1	0x0	0xFF	0x16	—
Settings	SMBus	0x4AA3	Address Check	H1	0x0	0xFF	0xEA	—
Settings	Lifetimes	0x4E80	Lifetimes Configuration	H2	0x0	0x00FF	0x0000	Hex

Table 16-1. Data Flash Table (continued)

Class	Subclass	Address	Name	Type	Min Value	Max Value	Default	Units
Settings	Lifetimes	0x4E83	Time RSOC Threshold A	U1	0	100	95	%
Settings	Lifetimes	0x4E84	Time RSOC Threshold B	U1	0	100	90	%
Settings	Lifetimes	0x4E85	Time RSOC Threshold C	U1	0	100	80	%
Settings	Lifetimes	0x4E86	Time RSOC Threshold D	U1	0	100	50	%
Settings	Lifetimes	0x4E87	Time RSOC Threshold E	U1	0	100	20	%
Settings	Lifetimes	0x4E88	Time RSOC Threshold F	U1	0	100	10	%
Settings	Lifetimes	0x4E89	Time RSOC Threshold G	U1	0	100	5	%
Settings	Protection	0x4CC0	Protection Configuration	H2	0x0	0x0007	0x0000	Hex
Settings	Protection	0x4CC2	Enabled Protections A	H1	0x0	0xFF	0xFF	Hex
Settings	Protection	0x4CC3	Enabled Protections B	H1	0x0	0xFF	0x7F	Hex
Settings	Protection	0x4CC4	Enabled Protections C	H1	0x0	0xFF	0xD5	Hex
Settings	Protection	0x4CC5	Enabled Protections D	H1	0x0	0xFF	0x0F	Hex
Settings	Permanent Failure	0x4D49	Enabled PF A	H1	0x0	0xFF	0x0	Hex
Settings	Permanent Failure	0x4D4A	Enabled PF B	H1	0x0	0xFF	0x0	Hex
Settings	Permanent Failure	0x4D4B	Enabled PF C	H1	0x0	0xFF	0x0	Hex
Settings	Permanent Failure	0x4D4C	Enabled PF D	H1	0x0	0xFF	0x0	Hex
Settings	AFE	0x4E45	AFE Protection Control	H1	0x0	0xFF	0x70	Hex
Settings	AFE	0x4E4B	ZVCHG Exit Threshold	I2	0	8000	2200	mV
Settings	Manufacturing	0x47C0	Mfg Status init	H2	0x0	0xFFFF	0x0000	Hex
Settings	Accumulated Charge	0x4F40	Accum Discharge Threshold	I2	–32768	0	–1000	mAh
Settings	Accumulated Charge	0x4F42	Accum Charge Threshold	I2	0	32767	1000	mAh
Advanced Charge Algorithm	Temperature Ranges	0x4DC2	T1 Temp	I2	2332	3932	2732	0.1 K
Advanced Charge Algorithm	Temperature Ranges	0x4DC4	T2 Temp	I2	2332	3932	2852	0.1 K
Advanced Charge Algorithm	Temperature Ranges	0x4DC6	T5 Temp	I2	2332	3932	2932	0.1 K
Advanced Charge Algorithm	Temperature Ranges	0x4DC8	T6 Temp	I2	2332	3932	2982	0.1 K
Advanced Charge Algorithm	Temperature Ranges	0x4DCA	T3 Temp	I2	2332	3932	3032	0.1 K
Advanced Charge Algorithm	Temperature Ranges	0x4DCC	T4 Temp	I2	2332	3932	3282	0.1 K
Advanced Charge Algorithm	Temperature Ranges	0x4DCE	Hysteresis Temp	I2	0	150	10	0.1 K
Advanced Charge Algorithm	Low Temp Charging	0x46C0	Voltage	I2	0	32767	4000	mV
Advanced Charge Algorithm	Low Temp Charging	0x4DD2	Current Low	I2	0	32767	132	mA
Advanced Charge Algorithm	Low Temp Charging	0x4DD4	Current Med	I2	0	32767	352	mA
Advanced Charge Algorithm	Low Temp Charging	0x4DD6	Current High	I2	0	32767	264	mA
Advanced Charge Algorithm	Standard Temp Low Charging	0x46C2	Voltage	I2	0	32767	4200	mV
Advanced Charge Algorithm	Standard Temp Low Charging	0x4DDA	Current Low	I2	0	32767	1980	mA
Advanced Charge Algorithm	Standard Temp Low Charging	0x4DDC	Current Med	I2	0	32767	4004	mA
Advanced Charge Algorithm	Standard Temp Low Charging	0x4DDE	Current High	I2	0	32767	2992	mA
Advanced Charge Algorithm	Standard Temp High Charging	0x46C4	Voltage	I2	0	32767	4200	mV
Advanced Charge Algorithm	Standard Temp High Charging	0x4DE2	Current Low	I2	0	32767	1980	mA

Table 16-1. Data Flash Table (continued)

Class	Subclass	Address	Name	Type	Min Value	Max Value	Default	Units
Advanced Charge Algorithm	Standard Temp High Charging	0x4DE4	Current Med	I2	0	32767	4004	mA
Advanced Charge Algorithm	Standard Temp High Charging	0x4DE6	Current High	I2	0	32767	2992	mA
Advanced Charge Algorithm	High Temp Charging	0x46C6	Voltage	I2	0	32767	4000	mV
Advanced Charge Algorithm	High Temp Charging	0x4DEA	Current Low	I2	0	32767	1012	mA
Advanced Charge Algorithm	High Temp Charging	0x4DEC	Current Med	I2	0	32767	1980	mA
Advanced Charge Algorithm	High Temp Charging	0x4DEE	Current High	I2	0	32767	1496	mA
Advanced Charge Algorithm	Rec Temp Charging	0x46C8	Voltage	I2	0	32767	4100	mV
Advanced Charge Algorithm	Rec Temp Charging	0x4DF2	Current Low	I2	0	32767	2508	mA
Advanced Charge Algorithm	Rec Temp Charging	0x4DF4	Current Med	I2	0	32767	4488	mA
Advanced Charge Algorithm	Rec Temp Charging	0x4DF6	Current High	I2	0	32767	3520	mA
Advanced Charge Algorithm	Pre-Charging	0x4DF8	Current	I2	0	32767	88	mA
Advanced Charge Algorithm	Maintenance Charging	0x4DFA	Current	I2	0	32767	44	mA
Advanced Charge Algorithm	Voltage Range	0x4DFC	Precharge Start Voltage	I2	0	32767	2500	mV
Advanced Charge Algorithm	Voltage Range	0x4DFE	Charging Voltage Low	I2	0	32767	2900	mV
Advanced Charge Algorithm	Voltage Range	0x4E00	Charging Voltage Med	I2	0	32767	3600	mV
Advanced Charge Algorithm	Voltage Range	0x4E02	Charging Voltage High	I2	0	32767	4000	mV
Advanced Charge Algorithm	Voltage Range	0x4E04	Charging Voltage Hysteresis	U1	0	255	0	mV
Advanced Charge Algorithm	SoC Range	0x4E05	Charging SoC Med	U1	0	100	50	%
Advanced Charge Algorithm	SoC Range	0x4E06	Charging SoC High	U1	0	100	75	%
Advanced Charge Algorithm	SoC Range	0x4E07	Charging SoC Hysteresis	U1	0	100	1	%
Advanced Charge Algorithm	Degrade Mode 1	0x4E08	Cycle Threshold	U2	0	65535	50	—
Advanced Charge Algorithm	Degrade Mode 1	0x4E0A	SOH Threshold	U1	0	100	95	%
Advanced Charge Algorithm	Degrade Mode 1	0x4E0B	Runtime Threshold	U2	0	65535	8760	h
Advanced Charge Algorithm	Degrade Mode 1	0x4E0D	Voltage Degradation	I2	0	32767	10	mV
Advanced Charge Algorithm	Degrade Mode 1	0x4E0F	Current Degradation	U1	0	100	10	%
Advanced Charge Algorithm	Degrade Mode 2	0x4E10	Cycle Threshold	U2	0	65535	150	—
Advanced Charge Algorithm	Degrade Mode 2	0x4E12	SOH Threshold	U1	0	100	80	%
Advanced Charge Algorithm	Degrade Mode 2	0x4E13	Runtime Threshold	U2	0	65535	17520	h
Advanced Charge Algorithm	Degrade Mode 2	0x4E15	Voltage Degradation	I2	0	32767	40	mV
Advanced Charge Algorithm	Degrade Mode 2	0x4E17	Current Degradation	U1	0	100	20	%
Advanced Charge Algorithm	Degrade Mode 3	0x4E18	Cycle Threshold	U2	0	65535	350	—

Table 16-1. Data Flash Table (continued)

Class	Subclass	Address	Name	Type	Min Value	Max Value	Default	Units
Advanced Charge Algorithm	Degrade Mode 3	0x4E1A	SOH Threshold	U1	0	100	60	%
Advanced Charge Algorithm	Degrade Mode 3	0x4E1B	Runtime Threshold	U2	0	65535	26280	h
Advanced Charge Algorithm	Degrade Mode 3	0x4E1D	Voltage Degradation	I2	0	32767	70	mV
Advanced Charge Algorithm	Degrade Mode 3	0x4E1F	Current Degradation	U1	0	100	40	%
Advanced Charge Algorithm	Degrade Mode	0x4500	Runtime Degrade	U2	0	65535	0	hours
Advanced Charge Algorithm	Degrade Mode	0x4E20	Cycle Count Start Runtime	U1	0	255	1	—
Advanced Charge Algorithm	Degrade Mode	0x4E21	Runtime Update Interval	U1	0	18	10	h
Advanced Charge Algorithm	CS Degrade	0x4E22	Temperature Threshold	I2	0	32767	3232	0.1 K
Advanced Charge Algorithm	CS Degrade	0x4E24	Voltage Threshold	I2	0	32767	4200	mV
Advanced Charge Algorithm	CS Degrade	0x4E26	Time Interval	U2	0	14400	300	s
Advanced Charge Algorithm	CS Degrade	0x4E28	Delta Voltage	I2	0	32767	25	mV
Advanced Charge Algorithm	CS Degrade	0x4E2A	Min CV	I2	0	32767	3000	mV
Advanced Charge Algorithm	Termination Config	0x4E2C	Charge Term Taper Current	I2	0	32767	250	mA
Advanced Charge Algorithm	Termination Config	0x4E30	Charge Term Voltage Offset	I2	0	32767	75	mV
Advanced Charge Algorithm	Termination Config	0x4E32	Charge Term Charging Voltage	I2	0	32767	4200	mV
Advanced Charge Algorithm	Charging Rate of Change	0x4E35	Current Rate	U1	1	255	1	steps
Advanced Charge Algorithm	Charging Rate of Change	0x4E36	Voltage Rate	U1	1	255	1	steps
Advanced Charge Algorithm	Charge Loss Compensation	0x4E37	CCC Current Threshold	I2	0	32767	3520	mA
Advanced Charge Algorithm	Charge Loss Compensation	0x4E39	CCC Voltage Threshold	I2	0	32767	4200	mV
Advanced Charge Algorithm	IR Correction	0x4E3B	Averaging Interval	U1	1	255	12	s
Advanced Charge Algorithm	Cell Balancing Config	0x4C42	Bal Time/mAh Cell 1	U2	0	65535	367	s/mAh
Advanced Charge Algorithm	Cell Balancing Config	0x4C44	Bal Time/mAh Cell 2-4	U2	0	65535	514	s/mAh
Advanced Charge Algorithm	Cell Balancing Config	0x4C46	Min Start Balance Delta	U1	0	255	3	mV
Advanced Charge Algorithm	Cell Balancing Config	0x4C47	Relax Balance Interval	U4	0	4294967295	18000	s
Advanced Charge Algorithm	Cell Balancing Config	0x4C4B	Min Rsoc for Balancing	U1	0	100	80	%
Advanced Charge Algorithm	Cell Balancing Config	0x4C4C	Start Rsoc for Bal in Sleep	U1	0	100	95	%
Advanced Charge Algorithm	Cell Balancing Config	0x4C4D	End Rsoc for Bal in Sleep	U1	0	100	60	%
Advanced Charge Algorithm	Cell Balancing Config	0x4C4E	Start Time for Bal in Sleep	U2	0	65520	100	hrs
Advanced Charge Algorithm	Elevated Degrade	0x4540	Accumulated ERM Time	U2	0	65535	0	hours
Advanced Charge Algorithm	Elevated Degrade	0x4542	Accumulated ERETM Time	U2	0	65535	0	hours
Advanced Charge Algorithm	Elevated Degrade	0x4544	ERETM Status	H1	0x0	0xFF	0x0	—

Table 16-1. Data Flash Table (continued)

Class	Subclass	Address	Name	Type	Min Value	Max Value	Default	Units
Advanced Charge Algorithm	Elevated Degrade	0x4F01	ERM Reset RSoC Threshold	U1	0	100	85	%
Advanced Charge Algorithm	Elevated Degrade	0x4F02	ERM Reset Voltage Threshold	I2	0	32767	3700	mV
Advanced Charge Algorithm	Elevated Degrade	0x4F04	ERM RSoC Threshold	U1	0	100	90	%
Advanced Charge Algorithm	Elevated Degrade	0x4F05	ERM Voltage Threshold	I2	0	32767	4000	mV
Advanced Charge Algorithm	Elevated Degrade	0x4F07	ERM Time Threshold	U2	0	65535	10000	hours
Advanced Charge Algorithm	Elevated Degrade	0x4F09	ERETM RSoC Threshold	U1	0	100	90	%
Advanced Charge Algorithm	Elevated Degrade	0x4F0A	ERETM Voltage Threshold	I2	0	32767	4200	mV
Advanced Charge Algorithm	Elevated Degrade	0x4F0C	ERETM Temperature Threshold	I2	2332	3932	3123	0.1 K
Advanced Charge Algorithm	Elevated Degrade	0x4F0E	ERETM Temperature Max Threshold	I2	2332	3932	3223	0.1 K
Advanced Charge Algorithm	Elevated Degrade	0x4F10	ERETM Time Threshold	U2	0	65535	10000	hours
Advanced Charge Algorithm	Elevated Degrade	0x4F12	ERETM Charging Voltage	I2	0	32767	3900	mV
Power	Power	0x4AA4	Valid Update Voltage	I2	0	32767	3500	mV
Power	Shutdown	0x4AA6	Shutdown Voltage	I2	0	32767	1750	mV
Power	Shutdown	0x4AA8	Shutdown Time	U1	0	255	10	s
Power	Shutdown	0x4AA9	IO Shutdown Delay	U1	0	255	1	250 ms
Power	Shutdown	0x4AAA	IO Shutdown Timeout	U1	0	255	8	250 ms
Power	Shutdown	0x4AAB	PF Shutdown Voltage	I2	0	32767	1750	mV
Power	Shutdown	0x4AAD	PF Shutdown Time	U1	0	255	10	s
Power	Shutdown	0x4AAE	PS Shutdown Voltage	I2	0	32767	2500	mV
Power	Shutdown	0x4AB0	PS NoLoadResCap Threshold	I2	0	32767	0	mAh
Power	Shutdown	0x4AB2	Charger Present Threshold	I2	0	32767	3000	mV
Power	Sleep	0x4AB4	Sleep Current	I2	0	32767	10	mA
Power	Sleep	0x4AB6	Bus Timeout	U1	0	255	5	s
Power	Sleep	0x4ABB	Voltage Time	U1	1	20	5	s
Power	Sleep	0x4ABC	Current Time	U1	1	60	20	s
Power	Sleep	0x4ABD	Wake Comparator	H1	0x0	0xFF	0x0	Hex
Power	Ship	0x4ABE	FET Off Time	U1	0	127	10	s
Power	Ship	0x4ABF	Delay	U1	0	254	20	s
Power	Ship	0x4AC0	Auto Ship Time	U2	0	65535	1440	min
Power	Power Off	0x4AC2	Timeout	U2	0	65535	30	min
Power	Manual FET Control	0x4AC4	MFC Delay	U1	0	255	60	0.25 s
Power	IATA	0x4B80	IATA Config	H1	0x0	0xFF	0x03	—
Power	IATA	0x4B81	IATA Delay Time	U2	0	65535	10	s
Power	IATA	0x4B83	IATA RSOC Threshold	U1	0	100	30	%
Power	IATA	0x4B84	IATA DeltaV Threshold	U1	0	255	50	mV
Power	IATA	0x4B85	IATA Delta RSOC	U1	0	100	3	%
Power	IATA	0x4B86	IATA Wake AbsRsoc	U1	0	100	10	%
Power	IATA	0x4B87	IATA Min Temperature	I2	2332	3932	2832	0.1 K
Power	IATA	0x4B89	IATA Max Temperature	I2	2332	3932	3132	0.1 K
Power	IATA	0x4B8B	IATA Min Voltage	I2	0	32767	3000	mV
Power	IATA	0x4B8D	IATA Max Voltage	I2	0	32767	3600	mV
Power	IATA STORE	0x4680	IATA RM mAh	I2	0	32767	0	mAh
Power	IATA STORE	0x4682	IATA RM cWh	I2	0	32767	0	cWh

Table 16-1. Data Flash Table (continued)

Class	Subclass	Address	Name	Type	Min Value	Max Value	Default	Units
Power	IATA STORE	0x4684	IATA FCC mAh	I2	0	32767	0	mAh
Power	IATA STORE	0x4686	IATA FCC cWh	I2	0	32767	0	cWh
Power	IATA STORE	0x4688	IATA Flag	H1	0x0	0xFF	0x0	—
Power	Unintended Wakeup	0x4BC0	Delay	U1	0	240	2	s
Power	Unintended Wakeup	0x4BC1	Count	U1	0	255	3	—
LED Support	LED Config	0x4B02	LED Flash Period	U2	32	65535	512	488 µs
LED Support	LED Config	0x4B04	LED Blink Period	U2	32	65535	1024	488 µs
LED Support	LED Config	0x4B06	LED Delay	U2	16	65535	100	488 µs
LED Support	LED Config	0x4B08	LED Hold Time	U1	1	63	16	0.25 s
LED Support	LED Config	0x4B09	LED FC Time	U1	0	96	4	15 mins
LED Support	LED Config	0x4B0A	CHG Flash Alarm	I1	0	100	10	%
LED Support	LED Config	0x4B0B	CHG Thresh 1	I1	0	100	0	%
LED Support	LED Config	0x4B0C	CHG Thresh 2	I1	0	100	20	%
LED Support	LED Config	0x4B0D	CHG Thresh 3	I1	0	100	40	%
LED Support	LED Config	0x4B0E	CHG Thresh 4	I1	0	100	60	%
LED Support	LED Config	0x4B0F	CHG Thresh 5	I1	0	100	80	%
LED Support	LED Config	0x4B10	DSG Flash Alarm	I1	0	100	10	%
LED Support	LED Config	0x4B11	DSG Thresh 1	I1	0	100	0	%
LED Support	LED Config	0x4B12	DSG Thresh 2	I1	0	100	20	%
LED Support	LED Config	0x4B13	DSG Thresh 3	I1	0	100	40	%
LED Support	LED Config	0x4B14	DSG Thresh 4	I1	0	100	60	%
LED Support	LED Config	0x4B15	DSG Thresh 5	I1	0	100	80	%
System Data	Manufacturer Data	0x4040	Manufacturer Info A Length	U1	1	32	32	—
System Data	Manufacturer Data	0x4041	Manufacturer Info Block A01	H1	0x0	0xFF	0x61	Hex
System Data	Manufacturer Data	0x4042	Manufacturer Info Block A02	H1	0x0	0xFF	0x62	Hex
System Data	Manufacturer Data	0x4043	Manufacturer Info Block A03	H1	0x0	0xFF	0x63	Hex
System Data	Manufacturer Data	0x4044	Manufacturer Info Block A04	H1	0x0	0xFF	0x64	Hex
System Data	Manufacturer Data	0x4045	Manufacturer Info Block A05	H1	0x0	0xFF	0x65	Hex
System Data	Manufacturer Data	0x4046	Manufacturer Info Block A06	H1	0x0	0xFF	0x66	Hex
System Data	Manufacturer Data	0x4047	Manufacturer Info Block A07	H1	0x0	0xFF	0x67	Hex
System Data	Manufacturer Data	0x4048	Manufacturer Info Block A08	H1	0x0	0xFF	0x68	Hex
System Data	Manufacturer Data	0x4049	Manufacturer Info Block A09	H1	0x0	0xFF	0x69	Hex
System Data	Manufacturer Data	0x404A	Manufacturer Info Block A10	H1	0x0	0xFF	0x6A	Hex
System Data	Manufacturer Data	0x404B	Manufacturer Info Block A11	H1	0x0	0xFF	0x6B	Hex
System Data	Manufacturer Data	0x404C	Manufacturer Info Block A12	H1	0x0	0xFF	0x6C	Hex
System Data	Manufacturer Data	0x404D	Manufacturer Info Block A13	H1	0x0	0xFF	0x6D	Hex
System Data	Manufacturer Data	0x404E	Manufacturer Info Block A14	H1	0x0	0xFF	0x6E	Hex
System Data	Manufacturer Data	0x404F	Manufacturer Info Block A15	H1	0x0	0xFF	0x6F	Hex
System Data	Manufacturer Data	0x4050	Manufacturer Info Block A16	H1	0x0	0xFF	0x70	Hex
System Data	Manufacturer Data	0x4051	Manufacturer Info Block A17	H1	0x0	0xFF	0x71	Hex
System Data	Manufacturer Data	0x4052	Manufacturer Info Block A18	H1	0x0	0xFF	0x72	Hex
System Data	Manufacturer Data	0x4053	Manufacturer Info Block A19	H1	0x0	0xFF	0x73	Hex
System Data	Manufacturer Data	0x4054	Manufacturer Info Block A20	H1	0x0	0xFF	0x74	Hex
System Data	Manufacturer Data	0x4055	Manufacturer Info Block A21	H1	0x0	0xFF	0x75	Hex
System Data	Manufacturer Data	0x4056	Manufacturer Info Block A22	H1	0x0	0xFF	0x76	Hex
System Data	Manufacturer Data	0x4057	Manufacturer Info Block A23	H1	0x0	0xFF	0x77	Hex
System Data	Manufacturer Data	0x4058	Manufacturer Info Block A24	H1	0x0	0xFF	0x7A	Hex
System Data	Manufacturer Data	0x4059	Manufacturer Info Block A25	H1	0x0	0xFF	0x78	Hex
System Data	Manufacturer Data	0x405A	Manufacturer Info Block A26	H1	0x0	0xFF	0x79	Hex
System Data	Manufacturer Data	0x405B	Manufacturer Info Block A27	H1	0x0	0xFF	0x30	Hex

Table 16-1. Data Flash Table (continued)

Class	Subclass	Address	Name	Type	Min Value	Max Value	Default	Units
System Data	Manufacturer Data	0x405C	Manufacturer Info Block A28	H1	0x0	0xFF	0x31	Hex
System Data	Manufacturer Data	0x405D	Manufacturer Info Block A29	H1	0x0	0xFF	0x32	Hex
System Data	Manufacturer Data	0x405E	Manufacturer Info Block A30	H1	0x0	0xFF	0x33	Hex
System Data	Manufacturer Data	0x405F	Manufacturer Info Block A31	H1	0x0	0xFF	0x34	Hex
System Data	Manufacturer Data	0x4060	Manufacturer Info Block A32	H1	0x0	0xFF	0x35	Hex
System Data	Manufacturer Info B	0x4062	Manufacturer Info Block B01	H1	0x0	0xFF	0x01	Hex
System Data	Manufacturer Info B	0x4063	Manufacturer Info Block B02	H1	0x0	0xFF	0x23	Hex
System Data	Manufacturer Info B	0x4064	Manufacturer Info Block B03	H1	0x0	0xFF	0x45	Hex
System Data	Manufacturer Info B	0x4065	Manufacturer Info Block B04	H1	0x0	0xFF	0x67	Hex
System Data	Integrity	0x4066	Static DF Signature	H2	0x0	0x7FFF	0x0	Hex
System Data	Integrity	0x4068	Static Chem DF Signature	H2	0x0	0x7FFF	0x73B5	Hex
System Data	Integrity	0x406A	All DF Signature	H2	0x0	0x7FFF	0x0	Hex
SBS Configuration	Data	0x406C	Manufacture Date	U2	0	65535	0	date
SBS Configuration	Data	0x406E	Serial Number	H2	0x0	0xFFFF	0x0001	Hex
SBS Configuration	Data	0x4070	Manufacturer Name	S21	x	x	Texas Instruments	—
SBS Configuration	Data	0x4085	Device Name	S21	x	x	bq40z50-R3	—
SBS Configuration	Data	0x409A	Device Chemistry	S5	x	x	LION	—
SBS Configuration	Data	0x4B40	Remaining AH Cap. Alarm	I2	0	32767	300	mAh
SBS Configuration	Data	0x4B42	Remaining WH Cap. Alarm	I2	0	32767	432	cWh
SBS Configuration	Data	0x4B44	Remaining Time Alarm	U2	0	65535	10	min
SBS Configuration	Data	0x4B46	Initial Battery Mode	H2	0x0	0xFFFF	0x0081	Hex
SBS Configuration	Data	0x4B48	Specification Information	H2	0x0	0xFFFF	0x0031	Hex
Lifetimes	Voltage	0x4380	Cell 1 Max Voltage	I2	0	32767	0	mV
Lifetimes	Voltage	0x4382	Cell 2 Max Voltage	I2	0	32767	0	mV
Lifetimes	Voltage	0x4384	Cell 3 Max Voltage	I2	0	32767	0	mV
Lifetimes	Voltage	0x4386	Cell 4 Max Voltage	I2	0	32767	0	mV
Lifetimes	Voltage	0x4388	Cell 1 Min Voltage	I2	0	32767	32767	mV
Lifetimes	Voltage	0x438A	Cell 2 Min Voltage	I2	0	32767	32767	mV
Lifetimes	Voltage	0x438C	Cell 3 Min Voltage	I2	0	32767	32767	mV
Lifetimes	Voltage	0x438E	Cell 4 Min Voltage	I2	0	32767	32767	mV
Lifetimes	Voltage	0x4390	Max Delta Cell Voltage	I2	0	32767	0	mV
Lifetimes	Current	0x4392	Max Charge Current	I2	0	32767	0	mA
Lifetimes	Current	0x4394	Max Discharge Current	I2	–32768	0	0	mA
Lifetimes	Current	0x4396	Max Avg Dsg Current	I2	–32768	0	0	mA
Lifetimes	Current	0x4398	Max Avg Dsg Power	I2	–32768	0	0	cW
Lifetimes	Temperature	0x439A	Max Temp Cell	I1	–128	127	–128	°C
Lifetimes	Temperature	0x439B	Min Temp Cell	I1	–128	127	127	°C
Lifetimes	Temperature	0x439C	Max Delta Cell Temp	I1	–128	127	0	°C
Lifetimes	Temperature	0x439D	Max Temp Int Sensor	I1	–128	127	–128	°C
Lifetimes	Temperature	0x439E	Min Temp Int Sensor	I1	–128	127	127	°C
Lifetimes	Temperature	0x439F	Max Temp Fet	I1	–128	127	–128	°C
Lifetimes	Safety Events	0x43A0	No Of COV Events	U2	0	32767	0	events
Lifetimes	Safety Events	0x43A2	Last COV Event	U2	0	32767	0	cycles
Lifetimes	Safety Events	0x43A4	No Of CUV Events	U2	0	32767	0	events
Lifetimes	Safety Events	0x43A6	Last CUV Event	U2	0	32767	0	cycles
Lifetimes	Safety Events	0x43A8	No Of OCD1 Events	U2	0	32767	0	events
Lifetimes	Safety Events	0x43AA	Last OCD1 Event	U2	0	32767	0	cycles

Table 16-1. Data Flash Table (continued)

Class	Subclass	Address	Name	Type	Min Value	Max Value	Default	Units
Lifetimes	Safety Events	0x43AC	No Of OCD2 Events	U2	0	32767	0	events
Lifetimes	Safety Events	0x43AE	Last OCD2 Event	U2	0	32767	0	cycles
Lifetimes	Safety Events	0x43B0	No Of OCC1 Events	U2	0	32767	0	events
Lifetimes	Safety Events	0x43B2	Last OCC1 Event	U2	0	32767	0	cycles
Lifetimes	Safety Events	0x43B4	No Of OCC2 Events	U2	0	32767	0	events
Lifetimes	Safety Events	0x43B6	Last OCC2 Event	U2	0	32767	0	cycles
Lifetimes	Safety Events	0x43B8	No Of AOLD Events	U2	0	32767	0	events
Lifetimes	Safety Events	0x43BA	Last AOLD Event	U2	0	32767	0	cycles
Lifetimes	Safety Events	0x43BC	No Of ASCD Events	U2	0	32767	0	events
Lifetimes	Safety Events	0x43BE	Last ASCD Event	U2	0	32767	0	cycles
Lifetimes	Safety Events	0x43C0	No Of ASCC Events	U2	0	32767	0	events
Lifetimes	Safety Events	0x43C2	Last ASCC Event	U2	0	32767	0	cycles
Lifetimes	Safety Events	0x43C4	No Of OTC Events	U2	0	32767	0	events
Lifetimes	Safety Events	0x43C6	Last OTC Event	U2	0	32767	0	cycles
Lifetimes	Safety Events	0x43C8	No Of OTD Events	U2	0	32767	0	events
Lifetimes	Safety Events	0x43CA	Last OTD Event	U2	0	32767	0	cycles
Lifetimes	Safety Events	0x43CC	No Of OTF Events	U2	0	32767	0	events
Lifetimes	Safety Events	0x43CE	Last OTF Event	U2	0	32767	0	cycles
Lifetimes	Charging Events	0x43D0	No Valid Charge Term	U2	0	32767	0	events
Lifetimes	Charging Events	0x43D2	Last Valid Charge Term	U2	0	32767	0	cycles
Lifetimes	Gauging Events	0x43D4	No Of Qmax Updates	U2	0	32767	0	events
Lifetimes	Gauging Events	0x43D6	Last Qmax Update	U2	0	32767	0	cycles
Lifetimes	Gauging Events	0x43D8	No Of Ra Updates	U2	0	32767	0	events
Lifetimes	Gauging Events	0x43DA	Last Ra Update	U2	0	32767	0	cycles
Lifetimes	Gauging Events	0x43DC	No Of Ra Disable	U2	0	32767	0	events
Lifetimes	Gauging Events	0x43DE	Last Ra Disable	U2	0	32767	0	cycles
Lifetimes	Power Events	0x43E0	No Of Shutdowns	U1	0	255	0	events
Lifetimes	Cell Balancing	0x43E4	Cb Time Cell 1	U4	0	4294967295	0	s
Lifetimes	Cell Balancing	0x43E8	Cb Time Cell 2	U4	0	4294967295	0	s
Lifetimes	Cell Balancing	0x43EC	Cb Time Cell 3	U4	0	4294967295	0	s
Lifetimes	Cell Balancing	0x43F0	Cb Time Cell 4	U4	0	4294967295	0	s
Lifetimes	Time	0x43F4	Total Fw Runtime	U4	0	4294967295	0	s
Lifetimes	Time	0x43F8	Time Spent In UT RSOC A	U4	0	4294967295	0	s
Lifetimes	Time	0x43FC	Time Spent In UT RSOC B	U4	0	4294967295	0	s
Lifetimes	Time	0x4400	Time Spent In UT RSOC C	U4	0	4294967295	0	s
Lifetimes	Time	0x4404	Time Spent In UT RSOC D	U4	0	4294967295	0	s
Lifetimes	Time	0x4408	Time Spent In UT RSOC E	U4	0	4294967295	0	s
Lifetimes	Time	0x440C	Time Spent In UT RSOC F	U4	0	4294967295	0	s
Lifetimes	Time	0x4410	Time Spent In UT RSOC G	U4	0	4294967295	0	s
Lifetimes	Time	0x4414	Time Spent In UT RSOC H	U4	0	4294967295	0	s
Lifetimes	Time	0x4418	Time Spent In LT RSOC A	U4	0	4294967295	0	s

Table 16-1. Data Flash Table (continued)

Class	Subclass	Address	Name	Type	Min Value	Max Value	Default	Units
Lifetimes	Time	0x441C	Time Spent In LT RSOC B	U4	0	4294967295	0	s
Lifetimes	Time	0x4420	Time Spent In LT RSOC C	U4	0	4294967295	0	s
Lifetimes	Time	0x4424	Time Spent In LT RSOC D	U4	0	4294967295	0	s
Lifetimes	Time	0x4428	Time Spent In LT RSOC E	U4	0	4294967295	0	s
Lifetimes	Time	0x442C	Time Spent In LT RSOC F	U4	0	4294967295	0	s
Lifetimes	Time	0x4430	Time Spent In LT RSOC G	U4	0	4294967295	0	s
Lifetimes	Time	0x4434	Time Spent In LT RSOC H	U4	0	4294967295	0	s
Lifetimes	Time	0x4438	Time Spent In STL RSOC A	U4	0	4294967295	0	s
Lifetimes	Time	0x443C	Time Spent In STL RSOC B	U4	0	4294967295	0	s
Lifetimes	Time	0x4440	Time Spent In STL RSOC C	U4	0	4294967295	0	s
Lifetimes	Time	0x4444	Time Spent In STL RSOC D	U4	0	4294967295	0	s
Lifetimes	Time	0x4448	Time Spent In STL RSOC E	U4	0	4294967295	0	s
Lifetimes	Time	0x444C	Time Spent In STL RSOC F	U4	0	4294967295	0	s
Lifetimes	Time	0x4450	Time Spent In STL RSOC G	U4	0	4294967295	0	s
Lifetimes	Time	0x4454	Time Spent In STL RSOC H	U4	0	4294967295	0	s
Lifetimes	Time	0x4458	Time Spent In RT RSOC A	U4	0	4294967295	0	s
Lifetimes	Time	0x445C	Time Spent In RT RSOC B	U4	0	4294967295	0	s
Lifetimes	Time	0x4460	Time Spent In RT RSOC C	U4	0	4294967295	0	s
Lifetimes	Time	0x4464	Time Spent In RT RSOC D	U4	0	4294967295	0	s
Lifetimes	Time	0x4468	Time Spent In RT RSOC E	U4	0	4294967295	0	s
Lifetimes	Time	0x446C	Time Spent In RT RSOC F	U4	0	4294967295	0	s
Lifetimes	Time	0x4470	Time Spent In RT RSOC G	U4	0	4294967295	0	s
Lifetimes	Time	0x4474	Time Spent In RT RSOC H	U4	0	4294967295	0	s
Lifetimes	Time	0x4478	Time Spent In STH RSOC A	U4	0	4294967295	0	s
Lifetimes	Time	0x447C	Time Spent In STH RSOC B	U4	0	4294967295	0	s
Lifetimes	Time	0x4480	Time Spent In STH RSOC C	U4	0	4294967295	0	s
Lifetimes	Time	0x4484	Time Spent In STH RSOC D	U4	0	4294967295	0	s
Lifetimes	Time	0x4488	Time Spent In STH RSOC E	U4	0	4294967295	0	s
Lifetimes	Time	0x448C	Time Spent In STH RSOC F	U4	0	4294967295	0	s
Lifetimes	Time	0x4490	Time Spent In STH RSOC G	U4	0	4294967295	0	s
Lifetimes	Time	0x4494	Time Spent In STH RSOC H	U4	0	4294967295	0	s

Table 16-1. Data Flash Table (continued)

Class	Subclass	Address	Name	Type	Min Value	Max Value	Default	Units
Lifetimes	Time	0x4498	Time Spent In HT RSOC A	U4	0	4294967295	0	s
Lifetimes	Time	0x449C	Time Spent In HT RSOC B	U4	0	4294967295	0	s
Lifetimes	Time	0x44A0	Time Spent In HT RSOC C	U4	0	4294967295	0	s
Lifetimes	Time	0x44A4	Time Spent In HT RSOC D	U4	0	4294967295	0	s
Lifetimes	Time	0x44A8	Time Spent In HT RSOC E	U4	0	4294967295	0	s
Lifetimes	Time	0x44AC	Time Spent In HT RSOC F	U4	0	4294967295	0	s
Lifetimes	Time	0x44B0	Time Spent In HT RSOC G	U4	0	4294967295	0	s
Lifetimes	Time	0x44B4	Time Spent In HT RSOC H	U4	0	4294967295	0	s
Lifetimes	Time	0x44B8	Time Spent In OT RSOC A	U4	0	4294967295	0	s
Lifetimes	Time	0x44BC	Time Spent In OT RSOC B	U4	0	4294967295	0	s
Lifetimes	Time	0x44C0	Time Spent In OT RSOC C	U4	0	4294967295	0	s
Lifetimes	Time	0x44C4	Time Spent In OT RSOC D	U4	0	4294967295	0	s
Lifetimes	Time	0x44C8	Time Spent In OT RSOC E	U4	0	4294967295	0	s
Lifetimes	Time	0x44CC	Time Spent In OT RSOC F	U4	0	4294967295	0	s
Lifetimes	Time	0x44D0	Time Spent In OT RSOC G	U4	0	4294967295	0	s
Lifetimes	Time	0x44D4	Time Spent In OT RSOC H	U4	0	4294967295	0	s
Protections	CUV	0x4CC6	Threshold	I2	0	32767	2500	mV
Protections	CUV	0x4CC8	Delay	U1	0	255	2	s
Protections	CUV	0x4CC9	Recovery	I2	0	32767	3000	mV
Protections	CUVC	0x4CCB	Threshold	I2	0	32767	2400	mV
Protections	CUVC	0x4CCD	Delay	U1	0	255	2	s
Protections	CUVC	0x4CCE	Recovery	I2	0	32767	3000	mV
Protections	COV	0x4CD0	Threshold Low Temp	I2	0	32767	4300	mV
Protections	COV	0x4CD2	Threshold Standard Temp Low	I2	0	32767	4300	mV
Protections	COV	0x4CD4	Threshold Standard Temp High	I2	0	32767	4300	mV
Protections	COV	0x4CD6	Threshold High Temp	I2	0	32767	4300	mV
Protections	COV	0x4CD8	Threshold Rec Temp	I2	0	32767	4300	mV
Protections	COV	0x4CDA	Delay	U1	0	255	2	s
Protections	COV	0x4CDB	Recovery Low Temp	I2	0	32767	3900	mV
Protections	COV	0x4CDD	Recovery Standard Temp Low	I2	0	32767	3900	mV
Protections	COV	0x4CDF	Recovery Standard Temp High	I2	0	32767	3900	mV
Protections	COV	0x4CE1	Recovery High Temp	I2	0	32767	3900	mV
Protections	COV	0x4CE3	Recovery Rec Temp	I2	0	32767	3900	mV
Protections	COV	0x4CE5	Latch Limit	U1	0	255	0	—
Protections	COV	0x4CE6	Counter Dec Delay	U1	0	255	10	s
Protections	COV	0x4CE7	Reset	U1	0	255	15	s
Protections	OCC1	0x4CE8	Threshold	I2	–32768	32767	6000	mA
Protections	OCC1	0x4CEA	Delay	U1	0	255	6	s

Table 16-1. Data Flash Table (continued)

Class	Subclass	Address	Name	Type	Min Value	Max Value	Default	Units
Protections	OCC2	0x4CEB	Threshold	I2	–32768	32767	8000	mA
Protections	OCC2	0x4CED	Delay	U1	0	255	3	s
Protections	OCC	0x4CEE	Recovery Threshold	I2	–32768	32767	–200	mA
Protections	OCC	0x4CF0	Recovery Delay	U1	0	255	5	s
Protections	OCD1	0x4CF1	Threshold	I2	–32768	32767	–6000	mA
Protections	OCD1	0x4CF3	Delay	U1	0	255	6	s
Protections	OCD2	0x4CF4	Threshold	I2	–32768	32767	–8000	mA
Protections	OCD2	0x4CF6	Delay	U1	0	255	3	s
Protections	OCD	0x4CF7	Recovery Threshold	I2	–32768	32767	200	mA
Protections	OCD	0x4CF9	Recovery Delay	U1	0	255	5	s
Protections	OCD	0x4CFA	Latch Limit	U1	0	255	0	—
Protections	OCD	0x4CFB	Counter Dec Delay	U1	0	255	10	s
Protections	OCD	0x4CFC	Reset	U1	0	255	15	s
Protections	AOLD	0x4CFD	Latch Limit	U1	0	255	0	—
Protections	AOLD	0x4CFE	Counter Dec Delay	U1	0	255	10	s
Protections	AOLD	0x4CFF	Recovery	U1	0	255	5	s
Protections	AOLD	0x4D00	Reset	U1	0	255	15	s
Protections	AOLD	0x4E46	Threshold	H1	0x0	0xFF	0xF4	Hex
Protections	ASCC	0x4D01	Latch Limit	U1	0	255	0	—
Protections	ASCC	0x4D02	Counter Dec Delay	U1	0	255	10	s
Protections	ASCC	0x4D03	Recovery	U1	0	255	5	s
Protections	ASCC	0x4D04	Reset	U1	0	255	15	s
Protections	ASCC	0x4E47	Threshold	H1	0x0	0xFF	0x77	Hex
Protections	ASCD	0x4D05	Latch Limit	U1	0	255	0	—
Protections	ASCD	0x4D06	Counter Dec Delay	U1	0	255	10	s
Protections	ASCD	0x4D07	Recovery	U1	0	255	5	s
Protections	ASCD	0x4D08	Reset	U1	0	255	15	s
Protections	ASCD	0x4E48	Threshold 1	H1	0x0	0xFF	0x77	Hex
Protections	ASCD	0x4E49	Threshold 2	H1	0x0	0xFF	0xE7	Hex
Protections	OTC	0x4D09	Threshold	I2	2332	3932	3282	0.1 K
Protections	OTC	0x4D0B	Delay	U1	0	255	2	s
Protections	OTC	0x4D0C	Recovery	I2	2332	3932	3232	0.1 K
Protections	OTD	0x4D0E	Threshold	I2	2332	3932	3332	0.1 K
Protections	OTD	0x4D10	Delay	U1	0	255	2	s
Protections	OTD	0x4D11	Recovery	I2	2332	3932	3282	0.1 K
Protections	OTF	0x4D13	Threshold	I2	2332	3932	3532	0.1 K
Protections	OTF	0x4D15	Delay	U1	0	255	2	s
Protections	OTF	0x4D16	Recovery	I2	2332	3932	3382	0.1 K
Protections	UTC	0x4D18	Threshold	I2	2332	3932	2732	0.1 K
Protections	UTC	0x4D1A	Delay	U1	0	255	2	s
Protections	UTC	0x4D1B	Recovery	I2	2332	3932	2782	0.1 K
Protections	UTD	0x4D1D	Threshold	I2	2332	3932	2732	0.1 K
Protections	UTD	0x4D1F	Delay	U1	0	255	2	s
Protections	UTD	0x4D20	Recovery	I2	2332	3932	2782	0.1 K
Protections	HWD	0x4D22	Delay	U1	0	255	10	s
Protections	PTO	0x4D23	Charge Threshold	I2	–32768	32767	2000	mA
Protections	PTO	0x4D25	Suspend Threshold	I2	–32768	32767	1800	mA
Protections	PTO	0x4D27	Delay	U2	0	65535	1800	s
Protections	PTO	0x4D29	Reset	I2	0	32767	2	mAh
Protections	CTO	0x4D2B	Charge Threshold	I2	–32768	32767	2500	mA
Protections	CTO	0x4D2D	Suspend Threshold	I2	–32768	32767	2000	mA

Table 16-1. Data Flash Table (continued)

Class	Subclass	Address	Name	Type	Min Value	Max Value	Default	Units
Protections	CTO	0x4D2F	Delay	U2	0	65535	54000	s
Protections	CTO	0x4D31	Reset	I2	0	32767	2	mAh
Protections	OC	0x4D33	Threshold	I2	–32768	32767	300	mAh
Protections	OC	0x4D35	Recovery	I2	–32768	32767	2	mAh
Protections	OC	0x4D37	RSOC Recovery	U1	0	100	90	%
Protections	CHGV	0x4D38	Threshold	I2	–32768	32767	500	mV
Protections	CHGV	0x4D3A	Delay	U1	0	255	30	s
Protections	CHGV	0x4D3B	Recovery	I2	–32768	32767	–500	mV
Protections	CHGC	0x4D3D	Threshold	I2	–32768	32767	500	mA
Protections	CHGC	0x4D3F	Delay	U1	0	255	2	s
Protections	CHGC	0x4D40	Recovery Threshold	I2	–32768	32767	100	mA
Protections	CHGC	0x4D42	Recovery Delay	U1	0	255	2	s
Protections	PCHGC	0x4D43	Threshold	I2	–32768	32767	50	mA
Protections	PCHGC	0x4D45	Delay	U1	0	255	2	s
Protections	PCHGC	0x4D46	Recovery Threshold	I2	–32768	32767	10	mA
Protections	PCHGC	0x4D48	Recovery Delay	U1	0	255	2	s
Permanent Fail	SUV	0x4D4D	Threshold	I2	0	32767	2200	mV
Permanent Fail	SUV	0x4D4F	Delay	U1	0	255	5	s
Permanent Fail	SOV	0x4D50	Threshold	I2	0	32767	4500	mV
Permanent Fail	SOV	0x4D52	Delay	U1	0	255	5	s
Permanent Fail	SOCC	0x4D53	Threshold	I2	–32768	32767	10000	mA
Permanent Fail	SOCC	0x4D55	Delay	U1	0	255	5	s
Permanent Fail	SOCD	0x4D56	Threshold	I2	–32768	32767	–10000	mA
Permanent Fail	SOCD	0x4D58	Delay	U1	0	255	5	s
Permanent Fail	SOT	0x4D59	Threshold	I2	2332	3932	3382	0.1 K
Permanent Fail	SOT	0x4D5B	Delay	U1	0	255	5	s
Permanent Fail	SOTF	0x4D5C	Threshold	I2	2332	3932	3732	0.1 K
Permanent Fail	SOTF	0x4D5E	Delay	U1	0	255	5	s
Permanent Fail	Open Thermistor	0x4D5F	Threshold	I2	0	32767	2232	0.1 K
Permanent Fail	Open Thermistor	0x4D61	Delay	U1	0	255	5	s
Permanent Fail	Open Thermistor	0x4D62	Fet Delta	I2	0	1500	200	0.1 K
Permanent Fail	Open Thermistor	0x4D64	Cell Delta	I2	0	1500	200	0.1 K
Permanent Fail	QIM	0x4D66	Delta Threshold	I2	0	32767	150	0.1%
Permanent Fail	QIM	0x4D68	Delay	U1	0	255	2	updates
Permanent Fail	CB	0x4D69	Max Threshold	I2	0	32767	120	2 h
Permanent Fail	CB	0x4D6B	Delta Threshold	U1	0	255	20	2 h
Permanent Fail	CB	0x4D6C	Delay	U1	0	255	2	cycles
Permanent Fail	VIMR	0x4D6D	Check Voltage	I2	0	5000	3500	mV
Permanent Fail	VIMR	0x4D6F	Check Current	I2	0	32767	10	mA
Permanent Fail	VIMR	0x4D71	Delta Threshold	I2	0	5000	500	mV
Permanent Fail	VIMR	0x4D73	Delta Delay	U1	0	255	5	s
Permanent Fail	VIMR	0x4D74	Duration	U2	0	65535	100	s
Permanent Fail	VIMA	0x4D76	Check Voltage	I2	0	5000	3700	mV
Permanent Fail	VIMA	0x4D78	Check Current	I2	0	32767	50	mA
Permanent Fail	VIMA	0x4D7A	Delta Threshold	I2	0	5000	200	mV
Permanent Fail	VIMA	0x4D7C	Delay	U1	0	255	5	s
Permanent Fail	IMP	0x4D7D	Delta Threshold	I2	0	32767	300	%
Permanent Fail	IMP	0x4D7F	Max Threshold	I2	0	32767	400	%
Permanent Fail	IMP	0x4D81	Ra Update Counts	U1	0	255	2	Counts
Permanent Fail	CD	0x4D82	Threshold	I2	0	32767	0	mAh
Permanent Fail	CD	0x4D84	Delay	U1	0	255	2	cycles

Table 16-1. Data Flash Table (continued)

Class	Subclass	Address	Name	Type	Min Value	Max Value	Default	Units
Permanent Fail	CFET	0x4D85	OFF Threshold	I2	0	500	5	mA
Permanent Fail	CFET	0x4D87	OFF Delay	U1	0	255	5	s
Permanent Fail	DFET	0x4D88	OFF Threshold	I2	–500	0	–5	mA
Permanent Fail	DFET	0x4D8A	OFF Delay	U1	0	255	5	s
Permanent Fail	FUSE	0x4D8B	Threshold	I2	0	255	5	mA
Permanent Fail	FUSE	0x4D8D	Delay	U1	0	255	5	s
Permanent Fail	AFER	0x4D8E	Threshold	U1	0	255	100	—
Permanent Fail	AFER	0x4D8F	Delay Period	U1	0	255	2	s
Permanent Fail	AFER	0x4D90	Compare Period	U1	0	255	5	s
Permanent Fail	AFEC	0x4D91	Threshold	U1	0	255	100	—
Permanent Fail	AFEC	0x4D92	Delay Period	U1	0	255	5	s
Permanent Fail	2LVL	0x4D93	Delay	U1	0	255	5	s
PF Status	Device Status Data	0x45C0	Safety Alert A	H1	0x0	0xFF	0x0	Hex
PF Status	Device Status Data	0x45C1	Safety Status A	H1	0x0	0xFF	0x0	Hex
PF Status	Device Status Data	0x45C2	Safety Alert B	H1	0x0	0xFF	0x0	Hex
PF Status	Device Status Data	0x45C3	Safety Status B	H1	0x0	0xFF	0x0	Hex
PF Status	Device Status Data	0x45C4	Safety Alert C	H1	0x0	0xFF	0x0	Hex
PF Status	Device Status Data	0x45C5	Safety Status C	H1	0x0	0xFF	0x0	Hex
PF Status	Device Status Data	0x45C6	Safety Alert D	H1	0x0	0xFF	0x0	Hex
PF Status	Device Status Data	0x45C7	Safety Status D	H1	0x0	0xFF	0x0	Hex
PF Status	Device Status Data	0x45C8	PF Alert A	H1	0x0	0xFF	0x0	Hex
PF Status	Device Status Data	0x45C9	PF Status A	H1	0x0	0xFF	0x0	Hex
PF Status	Device Status Data	0x45CA	PF Alert B	H1	0x0	0xFF	0x0	Hex
PF Status	Device Status Data	0x45CB	PF Status B	H1	0x0	0xFF	0x0	Hex
PF Status	Device Status Data	0x45CC	PF Alert C	H1	0x0	0xFF	0x0	Hex
PF Status	Device Status Data	0x45CD	PF Status C	H1	0x0	0xFF	0x0	Hex
PF Status	Device Status Data	0x45CE	PF Alert D	H1	0x0	0xFF	0x0	Hex
PF Status	Device Status Data	0x45CF	PF Status D	H1	0x0	0xFF	0x0	Hex
PF Status	Device Status Data	0x45D0	Fuse Flag	H2	0x0	0xFFFF	0x0	Hex
PF Status	Device Status Data	0x45D2	Operation Status A	H2	0x0	0xFFFF	0x0	Hex
PF Status	Device Status Data	0x45D4	Operation Status B	H2	0x0	0xFFFF	0x0	Hex
PF Status	Device Status Data	0x45D6	Temp Range	H1	0x0	0xFF	0x0	Hex
PF Status	Device Status Data	0x45D7	Charging Status A	H1	0x0	0xFF	0x0	Hex
PF Status	Device Status Data	0x45D8	Charging Status B	H1	0x0	0xFF	0x0	Hex
PF Status	Device Status Data	0x45D9	Gauging Status	H1	0x0	0xFF	0x0	Hex

Table 16-1. Data Flash Table (continued)

Class	Subclass	Address	Name	Type	Min Value	Max Value	Default	Units
PF Status	Device Status Data	0x45DA	IT Status	H2	0x0	0xFFFF	0x0	Hex
PF Status	Device Voltage Data	0x45DC	Cell 1 Voltage	I2	–32768	32767	0	mV
PF Status	Device Voltage Data	0x45DE	Cell 2 Voltage	I2	–32768	32767	0	mV
PF Status	Device Voltage Data	0x45E0	Cell 3 Voltage	I2	–32768	32767	0	mV
PF Status	Device Voltage Data	0x45E2	Cell 4 Voltage	I2	–32768	32767	0	mV
PF Status	Device Voltage Data	0x45E4	Battery Direct Voltage	I2	–32768	32767	0	mV
PF Status	Device Voltage Data	0x45E6	Pack Voltage	I2	–32768	32767	0	mV
PF Status	Device Current Data	0x45E8	Current	I2	–32768	32767	0	mA
PF Status	Device Temperature Data	0x45EA	Internal Temperature	I2	–1	32767	0	0.1 K
PF Status	Device Temperature Data	0x45EC	External 1 Temperature	I2	–1	32767	0	0.1 K
PF Status	Device Temperature Data	0x45EE	External 2 Temperature	I2	–1	32767	0	0.1 K
PF Status	Device Temperature Data	0x45F0	External 3 Temperature	I2	–1	32767	0	0.1 K
PF Status	Device Temperature Data	0x45F2	External 4 Temperature	I2	–1	32767	0	0.1 K
PF Status	Device Gauging Data	0x45F4	Cell 1 Dod0	I2	–32768	32767	0	—
PF Status	Device Gauging Data	0x45F6	Cell 2 Dod0	I2	–32768	32767	0	—
PF Status	Device Gauging Data	0x45F8	Cell 3 Dod0	I2	–32768	32767	0	—
PF Status	Device Gauging Data	0x45FA	Cell 4 Dod0	I2	–32768	32767	0	—
PF Status	Device Gauging Data	0x45FC	Passed Charge	I2	–32768	32767	0	mAh
PF Status	AFE Regs	0x45FE	AFE Interrupt Status	H1	0x0	0xFF	0x0	Hex
PF Status	AFE Regs	0x45FF	AFE FET Status	H1	0x0	0xFF	0x0	Hex
PF Status	AFE Regs	0x4600	AFE RXIN	H1	0x0	0xFF	0x0	Hex
PF Status	AFE Regs	0x4601	AFE Latch Status	H1	0x0	0xFF	0x0	Hex
PF Status	AFE Regs	0x4602	AFE Interrupt Enable	H1	0x0	0xFF	0x0	Hex
PF Status	AFE Regs	0x4603	AFE FET Control	H1	0x0	0xFF	0x0	Hex
PF Status	AFE Regs	0x4604	AFE RXIEN	H1	0x0	0xFF	0x0	Hex
PF Status	AFE Regs	0x4605	AFE RLOUT	H1	0x0	0xFF	0x0	Hex
PF Status	AFE Regs	0x4606	AFE RHOUT	H1	0x0	0xFF	0x0	Hex
PF Status	AFE Regs	0x4607	AFE RHINT	H1	0x0	0xFF	0x0	Hex
PF Status	AFE Regs	0x4608	AFE Cell Balance	H1	0x0	0xFF	0x0	Hex
PF Status	AFE Regs	0x4609	AFE AD/CC Control	H1	0x0	0xFF	0x0	Hex
PF Status	AFE Regs	0x460A	AFE ADC Mux	H1	0x0	0xFF	0x0	Hex
PF Status	AFE Regs	0x460B	AFE LED Output	H1	0x0	0xFF	0x0	Hex
PF Status	AFE Regs	0x460C	AFE State Control	H1	0x0	0xFF	0x0	Hex
PF Status	AFE Regs	0x460D	AFE LED/Wake Control	H1	0x0	0xFF	0x0	Hex
PF Status	AFE Regs	0x460E	AFE Protection Control	H1	0x0	0xFF	0x0	Hex
PF Status	AFE Regs	0x460F	AFE OCD	H1	0x0	0xFF	0x0	Hex
PF Status	AFE Regs	0x4610	AFE SCC	H1	0x0	0xFF	0x0	Hex
PF Status	AFE Regs	0x4611	AFE SCD1	H1	0x0	0xFF	0x0	Hex
PF Status	AFE Regs	0x4612	AFE SCD2	H1	0x0	0xFF	0x0	Hex

Table 16-1. Data Flash Table (continued)

Class	Subclass	Address	Name	Type	Min Value	Max Value	Default	Units
Black Box	Safety Status	0x4580	1st Status Status A	H1	0x0	0xFF	0x0	Hex
Black Box	Safety Status	0x4581	1st Status Status B	H1	0x0	0xFF	0x0	Hex
Black Box	Safety Status	0x4582	1st Safety Status C	H1	0x0	0xFF	0x0	Hex
Black Box	Safety Status	0x4583	1st Safety Status D	H1	0x0	0xFF	0x0	Hex
Black Box	Safety Status	0x4584	1st Time to Next Event	U1	0	255	0	s
Black Box	Safety Status	0x4585	2nd Status Status A	H1	0x0	0xFF	0x0	Hex
Black Box	Safety Status	0x4586	2nd Status Status B	H1	0x0	0xFF	0x0	Hex
Black Box	Safety Status	0x4587	2nd Safety Status C	H1	0x0	0xFF	0x0	Hex
Black Box	Safety Status	0x4588	2nd Safety Status D	H1	0x0	0xFF	0x0	Hex
Black Box	Safety Status	0x4589	2nd Time to Next Event	U1	0	255	0	s
Black Box	Safety Status	0x458A	3rd Status Status A	H1	0x0	0xFF	0x0	Hex
Black Box	Safety Status	0x458B	3rd Status Status B	H1	0x0	0xFF	0x0	Hex
Black Box	Safety Status	0x458C	3rd Safety Status C	H1	0x0	0xFF	0x0	Hex
Black Box	Safety Status	0x458D	3rd Safety Status D	H1	0x0	0xFF	0x0	Hex
Black Box	Safety Status	0x458E	3rd Time to Next Event	U1	0	255	0	s
Black Box	PF Status	0x458F	1st PF Status A	H1	0x0	0xFF	0x0	Hex
Black Box	PF Status	0x4590	1st PF Status B	H1	0x0	0xFF	0x0	Hex
Black Box	PF Status	0x4591	1st PF Status C	H1	0x0	0xFF	0x0	Hex
Black Box	PF Status	0x4592	1st PF Status D	H1	0x0	0xFF	0x0	Hex
Black Box	PF Status	0x4593	1st Time to Next Event	U1	0	255	0	s
Black Box	PF Status	0x4594	2nd PF Status A	H1	0x0	0xFF	0x0	Hex
Black Box	PF Status	0x4595	2nd PF Status B	H1	0x0	0xFF	0x0	Hex
Black Box	PF Status	0x4596	2nd PF Status C	H1	0x0	0xFF	0x0	Hex
Black Box	PF Status	0x4597	2nd PF Status D	H1	0x0	0xFF	0x0	Hex
Black Box	PF Status	0x4598	2nd Time to Next Event	U1	0	255	0	s
Black Box	PF Status	0x4599	3rd PF Status A	H1	0x0	0xFF	0x0	Hex
Black Box	PF Status	0x459A	3rd PF Status B	H1	0x0	0xFF	0x0	Hex
Black Box	PF Status	0x459B	3rd PF Status C	H1	0x0	0xFF	0x0	Hex
Black Box	PF Status	0x459C	3rd PF Status D	H1	0x0	0xFF	0x0	Hex
Black Box	PF Status	0x459D	3rd Time to Next Event	U1	0	255	0	s
Gas Gauging	Current Thresholds	0x4E4F	Dsg Current Threshold	I2	–32768	32767	100	mA
Gas Gauging	Current Thresholds	0x4E51	Chg Current Threshold	I2	–32768	32767	50	mA
Gas Gauging	Current Thresholds	0x4E53	Quit Current	I2	0	32767	10	mA
Gas Gauging	Current Thresholds	0x4E55	Dsg Relax Time	U1	0	255	1	s
Gas Gauging	Current Thresholds	0x4E56	Chg Relax Time	U1	0	255	60	s
Gas Gauging	Design	0x4C00	Design Capacity mAh	I2	100	32767	4400	mAh
Gas Gauging	Design	0x4C02	Design Capacity cWh	I2	144	32767	6336	cWh
Gas Gauging	Design	0x4C04	Design Voltage	I2	0	32767	14400	mV
Gas Gauging	Cycle	0x4C06	Cycle Count Percentage	U1	0	100	90	%
Gas Gauging	FD	0x4C0C	Set Voltage Threshold	I2	0	5000	3000	mV
Gas Gauging	FD	0x4C0E	Clear Voltage Threshold	I2	0	5000	3100	mV
Gas Gauging	FD	0x4C10	Set % RSOC Threshold	U1	0	100	0	%
Gas Gauging	FD	0x4C11	Clear % RSOC Threshold	U1	0	100	5	%
Gas Gauging	FC	0x4C12	Set Voltage Threshold	I2	0	5000	4200	mV
Gas Gauging	FC	0x4C14	Clear Voltage Threshold	I2	0	5000	4100	mV
Gas Gauging	FC	0x4C16	Set % RSOC Threshold	U1	0	100	100	%
Gas Gauging	FC	0x4C17	Clear % RSOC Threshold	U1	0	100	95	%
Gas Gauging	TD	0x4C18	Set Voltage Threshold	I2	0	5000	3200	mV

Table 16-1. Data Flash Table (continued)

Class	Subclass	Address	Name	Type	Min Value	Max Value	Default	Units
Gas Gauging	TD	0x4C1A	Clear Voltage Threshold	I2	0	5000	3300	mV
Gas Gauging	TD	0x4C1C	Set % RSOC Threshold	U1	0	100	6	%
Gas Gauging	TD	0x4C1D	Clear % RSOC Threshold	U1	0	100	8	%
Gas Gauging	TC	0x4C1E	Set Voltage Threshold	I2	0	5000	4200	mV
Gas Gauging	TC	0x4C20	Clear Voltage Threshold	I2	0	5000	4100	mV
Gas Gauging	TC	0x4C22	Set % RSOC Threshold	U1	0	100	100	%
Gas Gauging	TC	0x4C23	Clear % RSOC Threshold	U1	0	100	95	%
Gas Gauging	State	0x4306	Qmax Cell 1	I2	0	32767	4400	mAh
Gas Gauging	State	0x4308	Qmax Cell 2	I2	0	32767	4400	mAh
Gas Gauging	State	0x430A	Qmax Cell 3	I2	0	32767	4400	mAh
Gas Gauging	State	0x430C	Qmax Cell 4	I2	0	32767	4400	mAh
Gas Gauging	State	0x430E	Qmax Pack	I2	0	32767	4400	mAh
Gas Gauging	State	0x4310	Qmax Cycle Count	U2	0	65535	0	—
Gas Gauging	State	0x4312	Update Status	H1	0x0	0x0E	0x0	—
Gas Gauging	State	0x4313	Cell 1 Chg Voltage at EoC	I2	0	32767	4200	mV
Gas Gauging	State	0x4315	Cell 2 Chg Voltage at EoC	I2	0	32767	4200	mV
Gas Gauging	State	0x4317	Cell 3 Chg Voltage at EoC	I2	0	32767	4200	mV
Gas Gauging	State	0x4319	Cell 4 Chg Voltage at EoC	I2	0	32767	4200	mV
Gas Gauging	State	0x431B	Current at EoC	I2	0	32767	250	mA
Gas Gauging	State	0x431D	Avg I Last Run	I2	–32768	32767	–2000	mA
Gas Gauging	State	0x431F	Avg P Last Run	I2	–32768	32767	–3022	cW
Gas Gauging	State	0x4321	Delta Voltage	I2	–32768	32767	0	mV
Gas Gauging	State	0x4323	Temp k	I2	0	32767	100	0.1°C/256 cW
Gas Gauging	State	0x4325	Temp a	I2	0	32767	1000	s
Gas Gauging	State	0x4327	Max Avg I Last Run	I2	–32768	32767	–2000	mA
Gas Gauging	State	0x4329	Max Avg P Last Run	I2	–32768	32767	–3022	cW
Gas Gauging	State	0x4340	Cycle Count	U2	0	65535	0	—
Gas Gauging	Turbo Cfg	0x4640	Min System Voltage	I2	0	32767	9000	mV
Gas Gauging	Turbo Cfg	0x4642	Ten Second Max C Rate	I1	–127	0	–20	0.1°C
Gas Gauging	Turbo Cfg	0x4643	Ten Millisecond Max C Rate	I1	–127	0	–40	0.1°C
Gas Gauging	Turbo Cfg	0x4644	High Frequency Resistance	I2	0	32767	36	mΩ
Gas Gauging	Turbo Cfg	0x4646	Reserve Energy %	U1	0	100	0	%
Gas Gauging	Turbo Cfg	0x4647	Turbo Adjustment Factor	U1	80	120	100	%
Gas Gauging	IT Cfg	0x4300	Design Resistance	I2	1	32767	96	mΩ
Gas Gauging	IT Cfg	0x4302	Pack Resistance	I2	0	32767	0	mΩ
Gas Gauging	IT Cfg	0x4304	System Resistance	I2	0	32767	0	mΩ
Gas Gauging	IT Cfg	0x49CE	Ra Filter	U2	0	999	800	0.1%
Gas Gauging	IT Cfg	0x49D1	Ra Max Delta	U1	0	255	15	%
Gas Gauging	IT Cfg	0x49D3	Reference Grid	U1	0	14	4	—
Gas Gauging	IT Cfg	0x49D4	Resistance Parameter Filter	U2	1	65535	65142	—
Gas Gauging	IT Cfg	0x49D6	Near EDV Ra Param Filter	U2	1	65535	59220	—
Gas Gauging	IT Cfg	0x49D8	Max Current Change %	U1	0	100	10	%
Gas Gauging	IT Cfg	0x49D9	Resistance Update Voltage	I2	0	32767	50	mV
Gas Gauging	IT Cfg	0x4A00	Qmax Delta	U1	3	100	5	%
Gas Gauging	IT Cfg	0x4A01	Qmax Upper Bound	U1	100	255	130	%
Gas Gauging	IT Cfg	0x4A02	Term Voltage	I2	0	32767	9000	mV
Gas Gauging	IT Cfg	0x4A04	Term V Hold Time	U1	0	255	1	s
Gas Gauging	IT Cfg	0x4A05	Term Voltage Delta	I2	0	32767	300	mV
Gas Gauging	IT Cfg	0x4A07	Term Min Cell V	I2	0	32767	2800	mV
Gas Gauging	IT Cfg	0x4A10	Max Simulation Iterations	U1	20	50	30	—
Gas Gauging	IT Cfg	0x4A13	Simulation Near Term Delta	I2	0	32767	250	mV

Table 16-1. Data Flash Table (continued)

Class	Subclass	Address	Name	Type	Min Value	Max Value	Default	Units
Gas Gauging	IT Cfg	0x4A25	Fast Scale Start SOC	U1	0	100	10	%
Gas Gauging	IT Cfg	0x4A2D	Min Delta Voltage	I2	–32768	32767	0	mV
Gas Gauging	IT Cfg	0x4A2F	Max Delta Voltage	I2	–32768	32767	200	mV
Gas Gauging	IT Cfg	0x4A31	DeltaV Max Voltage Delta	I2	–32768	32767	10	mV
Gas Gauging	IT Cfg	0x4C86	Load Select	U1	0	7	7	—
Gas Gauging	IT Cfg	0x4C87	Fast Scale Load Select	U1	0	7	3	—
Gas Gauging	IT Cfg	0x4C88	Load Mode	U1	0	1	0	—
Gas Gauging	IT Cfg	0x4C89	User Rate-mA	I2	–9000	0	0	mA
Gas Gauging	IT Cfg	0x4C8B	User Rate-cW	I2	–32768	0	0	cW
Gas Gauging	IT Cfg	0x4C8D	Reserve Cap-mAh	I2	0	9000	0	mAh
Gas Gauging	IT Cfg	0x4C8F	Reserve Cap-cWh	I2	0	32000	0	cWh
Gas Gauging	IT Cfg	0x4C9E	Predict Ambient Time	U2	0	65535	2000	s
Gas Gauging	Smoothing	0x4C91	Smooth Relax Time	U2	1	32767	1000	s
Gas Gauging	Smoothing	0x4C93	Term Smooth Start Cell V Delta	I2	0	32767	150	mV
Gas Gauging	Smoothing	0x4C95	Term Smooth Final Cell V Delta	I2	0	32767	100	mV
Gas Gauging	Smoothing	0x4C97	Term Smooth Time	U1	1	32767	20	s
Gas Gauging	Condition Flag	0x4C98	Max Error Limit	U1	0	100	100	%
Gas Gauging	Max Error	0x4C9C	Time Cycle Equivalent	U1	1	255	12	2 h
Gas Gauging	Max Error	0x4C9D	Cycle Delta	U1	0	255	5	0.01%
Gas Gauging	SoH	0x4A40	SoH Load Rate	U1	0	255	50	0.1 Hr rate
Ra Table	R_a0	0x4100	Cell0 R_a flag	H2	0x0	0xFFFF	0xFF55	—
Ra Table	R_a0	0x4102	Cell0 R_a 0	I2	0	32767	67	mΩ
Ra Table	R_a0	0x4104	Cell0 R_a 1	I2	0	32767	71	mΩ
Ra Table	R_a0	0x4106	Cell0 R_a 2	I2	0	32767	83	mΩ
Ra Table	R_a0	0x4108	Cell0 R_a 3	I2	0	32767	110	mΩ
Ra Table	R_a0	0x410A	Cell0 R_a 4	I2	0	32767	96	mΩ
Ra Table	R_a0	0x410C	Cell0 R_a 5	I2	0	32767	77	mΩ
Ra Table	R_a0	0x410E	Cell0 R_a 6	I2	0	32767	96	mΩ
Ra Table	R_a0	0x4110	Cell0 R_a 7	I2	0	32767	86	mΩ
Ra Table	R_a0	0x4112	Cell0 R_a 8	I2	0	32767	84	mΩ
Ra Table	R_a0	0x4114	Cell0 R_a 9	I2	0	32767	82	mΩ
Ra Table	R_a0	0x4116	Cell0 R_a 10	I2	0	32767	81	mΩ
Ra Table	R_a0	0x4118	Cell0 R_a 11	I2	0	32767	92	mΩ
Ra Table	R_a0	0x411A	Cell0 R_a 12	I2	0	32767	103	mΩ
Ra Table	R_a0	0x411C	Cell0 R_a 13	I2	0	32767	123	mΩ
Ra Table	R_a0	0x411E	Cell0 R_a 14	I2	0	32767	658	mΩ
Ra Table	R_a1	0x4140	Cell1 R_a flag	H2	0x0	0xFFFF	0xFF55	—
Ra Table	R_a1	0x4142	Cell1 R_a 0	I2	0	32767	67	mΩ
Ra Table	R_a1	0x4144	Cell1 R_a 1	I2	0	32767	71	mΩ
Ra Table	R_a1	0x4146	Cell1 R_a 2	I2	0	32767	83	mΩ
Ra Table	R_a1	0x4148	Cell1 R_a 3	I2	0	32767	110	mΩ
Ra Table	R_a1	0x414A	Cell1 R_a 4	I2	0	32767	96	mΩ
Ra Table	R_a1	0x414C	Cell1 R_a 5	I2	0	32767	77	mΩ
Ra Table	R_a1	0x414E	Cell1 R_a 6	I2	0	32767	96	mΩ
Ra Table	R_a1	0x4150	Cell1 R_a 7	I2	0	32767	86	mΩ
Ra Table	R_a1	0x4152	Cell1 R_a 8	I2	0	32767	84	mΩ
Ra Table	R_a1	0x4154	Cell1 R_a 9	I2	0	32767	82	mΩ
Ra Table	R_a1	0x4156	Cell1 R_a 10	I2	0	32767	81	mΩ
Ra Table	R_a1	0x4158	Cell1 R_a 11	I2	0	32767	92	mΩ

Table 16-1. Data Flash Table (continued)

Class	Subclass	Address	Name	Type	Min Value	Max Value	Default	Units
Ra Table	R_a1	0x415A	Cell1 R_a 12	I2	0	32767	103	mΩ
Ra Table	R_a1	0x415C	Cell1 R_a 13	I2	0	32767	123	mΩ
Ra Table	R_a1	0x415E	Cell1 R_a 14	I2	0	32767	658	mΩ
Ra Table	R_a2	0x4180	Cell2 R_a flag	H2	0x0	0xFFFF	0xFF55	—
Ra Table	R_a2	0x4182	Cell2 R_a 0	I2	0	32767	67	mΩ
Ra Table	R_a2	0x4184	Cell2 R_a 1	I2	0	32767	71	mΩ
Ra Table	R_a2	0x4186	Cell2 R_a 2	I2	0	32767	83	mΩ
Ra Table	R_a2	0x4188	Cell2 R_a 3	I2	0	32767	110	mΩ
Ra Table	R_a2	0x418A	Cell2 R_a 4	I2	0	32767	96	mΩ
Ra Table	R_a2	0x418C	Cell2 R_a 5	I2	0	32767	77	mΩ
Ra Table	R_a2	0x418E	Cell2 R_a 6	I2	0	32767	96	mΩ
Ra Table	R_a2	0x4190	Cell2 R_a 7	I2	0	32767	86	mΩ
Ra Table	R_a2	0x4192	Cell2 R_a 8	I2	0	32767	84	mΩ
Ra Table	R_a2	0x4194	Cell2 R_a 9	I2	0	32767	82	mΩ
Ra Table	R_a2	0x4196	Cell2 R_a 10	I2	0	32767	81	mΩ
Ra Table	R_a2	0x4198	Cell2 R_a 11	I2	0	32767	92	mΩ
Ra Table	R_a2	0x419A	Cell2 R_a 12	I2	0	32767	103	mΩ
Ra Table	R_a2	0x419C	Cell2 R_a 13	I2	0	32767	123	mΩ
Ra Table	R_a2	0x419E	Cell2 R_a 14	I2	0	32767	658	mΩ
Ra Table	R_a3	0x41C0	Cell3 R_a flag	H2	0x0	0xFFFF	0xFF55	—
Ra Table	R_a3	0x41C2	Cell3 R_a 0	I2	0	32767	67	mΩ
Ra Table	R_a3	0x41C4	Cell3 R_a 1	I2	0	32767	71	mΩ
Ra Table	R_a3	0x41C6	Cell3 R_a 2	I2	0	32767	83	mΩ
Ra Table	R_a3	0x41C8	Cell3 R_a 3	I2	0	32767	110	mΩ
Ra Table	R_a3	0x41CA	Cell3 R_a 4	I2	0	32767	96	mΩ
Ra Table	R_a3	0x41CC	Cell3 R_a 5	I2	0	32767	77	mΩ
Ra Table	R_a3	0x41CE	Cell3 R_a 6	I2	0	32767	96	mΩ
Ra Table	R_a3	0x41D0	Cell3 R_a 7	I2	0	32767	86	mΩ
Ra Table	R_a3	0x41D2	Cell3 R_a 8	I2	0	32767	84	mΩ
Ra Table	R_a3	0x41D4	Cell3 R_a 9	I2	0	32767	82	mΩ
Ra Table	R_a3	0x41D6	Cell3 R_a 10	I2	0	32767	81	mΩ
Ra Table	R_a3	0x41D8	Cell3 R_a 11	I2	0	32767	92	mΩ
Ra Table	R_a3	0x41DA	Cell3 R_a 12	I2	0	32767	103	mΩ
Ra Table	R_a3	0x41DC	Cell3 R_a 13	I2	0	32767	123	mΩ
Ra Table	R_a3	0x41DE	Cell3 R_a 14	I2	0	32767	658	mΩ
Ra Table	R_a0x	0x4200	xCell0 R_a flag	H2	0x0	0xFFFF	0xFFFF	—
Ra Table	R_a0x	0x4202	xCell0 R_a 0	I2	0	32767	67	mΩ
Ra Table	R_a0x	0x4204	xCell0 R_a 1	I2	0	32767	71	mΩ
Ra Table	R_a0x	0x4206	xCell0 R_a 2	I2	0	32767	83	mΩ
Ra Table	R_a0x	0x4208	xCell0 R_a 3	I2	0	32767	110	mΩ
Ra Table	R_a0x	0x420A	xCell0 R_a 4	I2	0	32767	96	mΩ
Ra Table	R_a0x	0x420C	xCell0 R_a 5	I2	0	32767	77	mΩ
Ra Table	R_a0x	0x420E	xCell0 R_a 6	I2	0	32767	96	mΩ
Ra Table	R_a0x	0x4210	xCell0 R_a 7	I2	0	32767	86	mΩ
Ra Table	R_a0x	0x4212	xCell0 R_a 8	I2	0	32767	84	mΩ
Ra Table	R_a0x	0x4214	xCell0 R_a 9	I2	0	32767	82	mΩ
Ra Table	R_a0x	0x4216	xCell0 R_a 10	I2	0	32767	81	mΩ
Ra Table	R_a0x	0x4218	xCell0 R_a 11	I2	0	32767	92	mΩ
Ra Table	R_a0x	0x421A	xCell0 R_a 12	I2	0	32767	103	mΩ
Ra Table	R_a0x	0x421C	xCell0 R_a 13	I2	0	32767	123	mΩ
Ra Table	R_a0x	0x421E	xCell0 R_a 14	I2	0	32767	658	mΩ

Table 16-1. Data Flash Table (continued)

Class	Subclass	Address	Name	Type	Min Value	Max Value	Default	Units
Ra Table	R_a1x	0x4240	xCell1 R_a flag	H2	0x0	0xFFFF	0xFFFF	—
Ra Table	R_a1x	0x4242	xCell1 R_a 0	I2	0	32767	67	mΩ
Ra Table	R_a1x	0x4244	xCell1 R_a 1	I2	0	32767	71	mΩ
Ra Table	R_a1x	0x4246	xCell1 R_a 2	I2	0	32767	83	mΩ
Ra Table	R_a1x	0x4248	xCell1 R_a 3	I2	0	32767	110	mΩ
Ra Table	R_a1x	0x424A	xCell1 R_a 4	I2	0	32767	96	mΩ
Ra Table	R_a1x	0x424C	xCell1 R_a 5	I2	0	32767	77	mΩ
Ra Table	R_a1x	0x424E	xCell1 R_a 6	I2	0	32767	96	mΩ
Ra Table	R_a1x	0x4250	xCell1 R_a 7	I2	0	32767	86	mΩ
Ra Table	R_a1x	0x4252	xCell1 R_a 8	I2	0	32767	84	mΩ
Ra Table	R_a1x	0x4254	xCell1 R_a 9	I2	0	32767	82	mΩ
Ra Table	R_a1x	0x4256	xCell1 R_a 10	I2	0	32767	81	mΩ
Ra Table	R_a1x	0x4258	xCell1 R_a 11	I2	0	32767	92	mΩ
Ra Table	R_a1x	0x425A	xCell1 R_a 12	I2	0	32767	103	mΩ
Ra Table	R_a1x	0x425C	xCell1 R_a 13	I2	0	32767	123	mΩ
Ra Table	R_a1x	0x425E	xCell1 R_a 14	I2	0	32767	658	mΩ
Ra Table	R_a2x	0x4280	xCell2 R_a flag	H2	0x0	0xFFFF	0xFFFF	—
Ra Table	R_a2x	0x4282	xCell2 R_a 0	I2	0	32767	67	mΩ
Ra Table	R_a2x	0x4284	xCell2 R_a 1	I2	0	32767	71	mΩ
Ra Table	R_a2x	0x4286	xCell2 R_a 2	I2	0	32767	83	mΩ
Ra Table	R_a2x	0x4288	xCell2 R_a 3	I2	0	32767	110	mΩ
Ra Table	R_a2x	0x428A	xCell2 R_a 4	I2	0	32767	96	mΩ
Ra Table	R_a2x	0x428C	xCell2 R_a 5	I2	0	32767	77	mΩ
Ra Table	R_a2x	0x428E	xCell2 R_a 6	I2	0	32767	96	mΩ
Ra Table	R_a2x	0x4290	xCell2 R_a 7	I2	0	32767	86	mΩ
Ra Table	R_a2x	0x4292	xCell2 R_a 8	I2	0	32767	84	mΩ
Ra Table	R_a2x	0x4294	xCell2 R_a 9	I2	0	32767	82	mΩ
Ra Table	R_a2x	0x4296	xCell2 R_a 10	I2	0	32767	81	mΩ
Ra Table	R_a2x	0x4298	xCell2 R_a 11	I2	0	32767	92	mΩ
Ra Table	R_a2x	0x429A	xCell2 R_a 12	I2	0	32767	103	mΩ
Ra Table	R_a2x	0x429C	xCell2 R_a 13	I2	0	32767	123	mΩ
Ra Table	R_a2x	0x429E	xCell2 R_a 14	I2	0	32767	658	mΩ
Ra Table	R_a3x	0x42C0	xCell3 R_a flag	H2	0x0	0xFFFF	0xFFFF	—
Ra Table	R_a3x	0x42C2	xCell3 R_a 0	I2	0	32767	67	mΩ
Ra Table	R_a3x	0x42C4	xCell3 R_a 1	I2	0	32767	71	mΩ
Ra Table	R_a3x	0x42C6	xCell3 R_a 2	I2	0	32767	83	mΩ
Ra Table	R_a3x	0x42C8	xCell3 R_a 3	I2	0	32767	110	mΩ
Ra Table	R_a3x	0x42CA	xCell3 R_a 4	I2	0	32767	96	mΩ
Ra Table	R_a3x	0x42CC	xCell3 R_a 5	I2	0	32767	77	mΩ
Ra Table	R_a3x	0x42CE	xCell3 R_a 6	I2	0	32767	96	mΩ
Ra Table	R_a3x	0x42D0	xCell3 R_a 7	I2	0	32767	86	mΩ
Ra Table	R_a3x	0x42D2	xCell3 R_a 8	I2	0	32767	84	mΩ
Ra Table	R_a3x	0x42D4	xCell3 R_a 9	I2	0	32767	82	mΩ
Ra Table	R_a3x	0x42D6	xCell3 R_a 10	I2	0	32767	81	mΩ
Ra Table	R_a3x	0x42D8	xCell3 R_a 11	I2	0	32767	92	mΩ
Ra Table	R_a3x	0x42DA	xCell3 R_a 12	I2	0	32767	103	mΩ
Ra Table	R_a3x	0x42DC	xCell3 R_a 13	I2	0	32767	123	mΩ
Ra Table	R_a3x	0x42DE	xCell3 R_a 14	I2	0	32767	658	mΩ

AFE Threshold and Delay Settings

A.1 Overload in Discharge Protection (AOLD)

Table A-1. Overload in Discharge Protection Threshold (Settings:AFE:AFE Protection Control [RSNS] = 0)[(1)]

OLD Threshold ([RSNS] = 0)			
Setting	Threshold	Setting	Threshold
0x00	–8.30 mV	0x08	–30.54 mV
0x01	–11.08 mV	0x09	–33.32 mV
0x02	–13.86 mV	0x0A	–36.10 mV
0x03	–16.64 mV	0x0B	–38.88 mV
0x04	–19.42 mV	0x0C	–41.66 mV
0x05	–22.20 mV	0x0D	–44.44 mV
0x06	–24.98 mV	0x0E	–47.22 mV
0x07	–27.76 mV	0x0F	–50.00 mV

(1) The data flash setting ***Protection:AFE Thresholds:OLD Threshold[3:0]*** sets the voltage threshold.

Table A-2. Overload in Discharge Protection Threshold (Settings:AFE:AFE Protection Control [RSNS] = 1)[(1)]

OLD Threshold ([RSNS] = 1)			
Setting	Threshold	Setting	Threshold
0x00	–16.60 mV	0x08	–61.08 mV
0x01	–22.16 mV	0x09	–66.64 mV
0x02	–27.72 mV	0x0A	–72.20 mV
0x03	–33.28 mV	0x0B	–77.76 mV
0x04	–38.84 mV	0x0C	–83.32 mV
0x05	–44.40 mV	0x0D	–88.88 mV
0x06	–49.96 mV	0x0E	–94.44 mV
0x07	–55.52 mV	0x0F	–100.00 mV

(1) The data flash setting ***Protection:AFE Thresholds:OLD Threshold[3:0]*** sets the voltage threshold.

Table A-3. Overload in Discharge Protection Delay[(1)]

Setting	Time	Setting	Time	Setting	Time	Setting	Time
0x00	1 ms	0x04	9 ms	0x08	17 ms	0x0C	25 ms
0x01	3 ms	0x05	11 ms	0x09	19 ms	0x0D	27 ms
0x02	5 ms	0x06	13 ms	0x0A	21 ms	0x0E	29 ms
0x03	7 ms	0x07	15 ms	0x0B	23 ms	0x0F	31 ms

(1) The data flash setting ***Protection:AFE Thresholds:OLD Threshold[7:4]*** sets the delay time.

A.2 Short Circuit in Charge (ASCC)

Table A-4. Short Circuit in Charge Threshold (Settings:AFE:AFE Protection Control [RSNS] = 0)[(1)]

Setting	Threshold	Setting	Threshold
0x00	22.2 mV	0x04	66.65 mV
0x01	33.3 mV	0x05	77.75 mV
0x02	44.4 mV	0x06	88.85 mV
0x03	55.5 mV	0x07	100 mV

(1) The data flash setting ***Protection:AFE Thresholds:SCC Threshold[2:0]*** sets the voltage threshold.

Table A-5. Short Circuit in Charge Threshold (Settings:AFE:AFE Protection Control [RSNS] = 1)[(1)]

Setting	Threshold	Setting	Threshold
0x00	44.4 mV	0x04	133.3 mV
0x01	66.6 mV	0x05	155.5 mV
0x02	88.8 mV	0x06	177.7 mV
0x03	111.1 mV	0x07	200 mV

(1) The data flash setting ***Protection:AFE Thresholds:SCC Threshold[2:0]*** sets the voltage threshold.

Table A-6. Short Circuit in Charge Delay[(1)]

Setting	Time	Setting	Time	Setting	Time	Setting	Time
0x00	0 µs	0x04	244 µs	0x08	488 µs	0x0C	732 µs
0x01	61 µs	0x05	305 µs	0x09	549 µs	0x0D	793 µs
0x02	122 µs	0x06	366 µs	0x0A	610 µs	0x0E	854 µs
0x03	183 µs	0x07	427 µs	0x0B	671 µs	0x0F	915 µs

(1) The data flash setting ***Protection:AFE Thresholds:SCC Threshold[7:4]*** sets the delay time.

A.3 Short Circuit in Discharge (ASCD1 and ASCD2)

Table A-7. Short Circuit in Discharge Threshold (Settings:AFE:AFE Protection Control [RSNS] = 0)[(1)]

Setting	Threshold	Setting	Threshold
0x00	–22.2 mV	0x04	–66.65 mV
0x01	–33.3 mV	0x05	–77.75 mV
0x02	–44.4 mV	0x06	–88.85 mV
0x03	–55.5 mV	0x07	–100 mV

(1) The data flash setting ***Protection:AFE Thresholds:SCD1 Threshold[2:0]*** and ***Protection:AFE Thresholds:SCD2 Threshold[2:0]*** sets the voltage thresholds.

Table A-8. Short Circuit in Discharge Threshold (Settings:AFE:AFE Protection Control [RSNS] = 1)[(1)]

Setting	Threshold	Setting	Threshold
0x00	–44.4 mV	0x04	–133.3 mV
0x01	–66.6 mV	0x05	–155.5 mV
0x02	–88.8 mV	0x06	–177.7 mV
0x03	–111.1 mV	0x07	–200 mV

(1) The data flash setting ***Protection:AFE Thresholds:SCD1 Threshold[2:0]*** and ***Protection:AFE Thresholds:SCD2 Threshold[2:0]*** sets the voltage thresholds.

Table A-9. Short Circuit in Discharge 1 Delay (Settings:AFE:AFE Protection Control [SCDDx2] = 0)[(1)]

Setting	Time	Setting	Time	Setting	Time	Setting	Time
0x00	0 µs	0x04	244 µs	0x08	488 µs	0x0C	732 µs
0x01	61 µs	0x05	305 µs	0x09	549 µs	0x0D	793 µs
0x02	122 µs	0x06	366 µs	0x0A	610 µs	0x0E	854 µs
0x03	183 µs	0x07	427 µs	0x0B	671 µs	0x0F	915 µs

(1) The data flash setting ***Protection:AFE Thresholds:SCD1Threshold[7:4]*** sets the delay time.

Table A-10. Short Circuit in Discharge 1 Delay (Settings:AFE:AFE Protection Control [SCDDx2] = 1)[(1)]

Setting	Time	Setting	Time	Setting	Time	Setting	Time
0x00	0 µs	0x04	488 µs	0x08	976 µs	0x0C	1464 µs
0x01	122 µs	0x05	610 µs	0x09	1098 µs	0x0D	1586 µs
0x02	244 µs	0x06	732 µs	0x0A	1220 µs	0x0E	1708 µs
0x03	366 µs	0x07	854 µs	0x0B	1342 µs	0x0F	1830 µs

(1) The data flash setting ***Protection:AFE Thresholds:SCD1 Threshold[7:4]*** sets the delay time.

Table A-11. Short Circuit in Discharge 2 Delay (Settings:AFE:AFE Protection Control [SCDDx2] = 0)[(1)]

Setting	Time	Setting	Time	Setting	Time	Setting	Time
0x00	0 µs	0x04	122 µs	0x08	244 µs	0x0C	366 µs
0x01	31 µs	0x05	153 µs	0x09	275 µs	0x0D	396 µs
0x02	61 µs	0x06	183 µs	0x0A	305 µs	0x0E	427 µs
0x03	92 µs	0x07	214 µs	0x0B	335 µs	0x0F	458 µs

(1) The data flash setting ***Protection:AFE Thresholds:SCD2 Threshold[7:4]*** sets the delay time.

Table A-12. Short Circuit in Discharge 2 Delay (Settings:AFE:AFE Protection Control [SCDDx2] = 1)[(1)]

Setting	Time	Setting	Time	Setting	Time	Setting	Time
0x00	0 µs	0x04	244 µs	0x08	488 µs	0x0C	732 µs
0x01	62 µs	0x05	306 µs	0x09	550 µs	0x0D	792 µs
0x02	122 µs	0x06	366 µs	0x0A	610 µs	0x0E	854 µs
0x03	184 µs	0x07	428 µs	0x0B	670 µs	0x0F	916 µs

(1) The data flash setting ***Protection:AFE Thresholds:SCD2 Threshold[7:4]*** sets the delay time.

Sample Filter Settings

Table B-1. Sample V/I/P Filter Settings and Associated Low-Pass Filter Time Constants (1)

Average V/I/P Filter	Effective Low-Pass Time Constant
10	0.25 seconds
50	0.5 seconds
145	1 second
200	3 seconds

(1) The data flash setting ***Calibration:Filter:Average V/I/P*** sets this threshold.

Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Original (January 2019) to A Revision	Page
• Added Figure 5-1	49

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